



US009170489B2

(12) **United States Patent**
Takizawa et al.(10) **Patent No.:** **US 9,170,489 B2**(45) **Date of Patent:** **Oct. 27, 2015**(54) **PATTERN-FORMING METHOD, ELECTRON BEAM-SENSITIVE OR EXTREME ULTRAVIOLET RADIATION-SENSITIVE RESIN COMPOSITION, RESIST FILM, MANUFACTURING METHOD OF ELECTRONIC DEVICE USING THEM AND ELECTRONIC DEVICE**(71) Applicant: **FUJIFILM Corporation**, Tokyo (JP)(72) Inventors: **Hiroo Takizawa**, Shizuoka (JP);
Hideaki Tsubaki, Shizuoka (JP); **Shuji Hirano**, Shizuoka (JP)(73) Assignee: **FUJIFILM Corporation**, Tokyo (JP)

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) Appl. No.: **14/207,867**(22) Filed: **Mar. 13, 2014**(65) **Prior Publication Data**

US 2014/0193749 A1 Jul. 10, 2014

Related U.S. Application Data

(63) Continuation of application No. PCT/JP2012/073765, filed on Sep. 11, 2012.

(60) Provisional application No. 61/535,024, filed on Sep. 15, 2011.

(30) **Foreign Application Priority Data**

Sep. 15, 2011 (JP) 2011-202044

(51) **Int. Cl.****G03F 7/004** (2006.01)
G03F 7/039 (2006.01)
G03F 7/20 (2006.01)
G03F 7/038 (2006.01)
C08F 212/14 (2006.01)
G03F 7/32 (2006.01)
H01J 37/317 (2006.01)
C08F 12/20 (2006.01)
C08F 12/24 (2006.01)
C08F 212/32 (2006.01)(52) **U.S. Cl.**CPC **G03F 7/0041** (2013.01); **C08F 212/14** (2013.01); **G03F 7/004** (2013.01); **G03F 7/038** (2013.01); **G03F 7/039** (2013.01); **G03F 7/0392** (2013.01); **G03F 7/0397** (2013.01); **G03F 7/20** (2013.01); **G03F 7/2037** (2013.01); **G03F 7/2059** (2013.01); **G03F 7/325** (2013.01); **H01J 37/3174** (2013.01); **C08F 12/20** (2013.01); **C08F 12/24** (2013.01); **C08F 212/32** (2013.01)(58) **Field of Classification Search**CPC **G03F 7/004**; **G03F 7/038**; **G03F 7/039**;
G03F 7/0392; **G03F 7/0397**; **G03F 7/20**;
G03F 7/2037; **G03F 7/2059**; **G03F 7/325**;
G03F 7/0041; **H01J 37/3174**; **C08F 12/20**;
C08F 12/24; **C08F 212/14**; **C08F 212/32**
USPC 430/296, 311, 942
See application file for complete search history.(56) **References Cited**

U.S. PATENT DOCUMENTS

2011/0300485 A1 12/2011 Tsubaki et al.
2012/0077131 A1 3/2012 Enomoto et al.

FOREIGN PATENT DOCUMENTS

JP 2002-299223 A 10/2002
JP 2008-170784 A 7/2008
JP 2010-217884 A 9/2010
JP 2011-123469 A 6/2011
WO 2010/095763 A1 8/2010
WO 2010/140709 A1 12/2010
WO 2011/108744 A1 9/2011

OTHER PUBLICATIONS

International Search Report (PCT/ISA/210), dated Oct. 23, 2012, issued by the International Searching Authority in counterpart International Patent Application No. PCT/JP2012/073765.

Written Opinion (PCT/ISA/237), dated Oct. 23, 2012, issued by the International Searching Authority in counterpart International Patent Application No. PCT/JP2012/073765.

Office Action dated Oct. 14, 2014 issued by Japanese Patent Office in counterpart Japanese Application No. 2012-196110.

Search Report dated Mar. 30, 2015, issued by the European Patent Office in counterpart European Application No. 12831380.6.

Primary Examiner — Christopher Young(74) *Attorney, Agent, or Firm* — Sughrue Mion, PLLC(57) **ABSTRACT**

A pattern-forming method includes in this order: step (1) of forming a film with an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition that contains (A) a resin having an acid-decomposable repeating unit and capable of decreasing a solubility of the resin (A) in a developer containing an organic solvent by an action of an acid, (B) a compound capable of generating an acid upon irradiation with an electron beam or extreme ultraviolet radiation and (C) a solvent; step (2) of exposing the film with an electron beam or extreme ultraviolet radiation; and step (4) of forming a negative pattern by development of the film with a developer containing an organic solvent after the exposing of the film, wherein a content of the compound (B) is 21% by mass to 70% by mass on the basis of all solids content of the composition.

54 Claims, No Drawings

1

**PATTERN-FORMING METHOD, ELECTRON
BEAM-SENSITIVE OR EXTREME
ULTRAVIOLET RADIATION-SENSITIVE
RESIN COMPOSITION, RESIST FILM,
MANUFACTURING METHOD OF
ELECTRONIC DEVICE USING THEM AND
ELECTRONIC DEVICE**

**CROSS REFERENCE TO RELATED
APPLICATION**

This is a continuation of International Application No. PCT/JP2012/073765 filed on Sep. 11, 2012, and claims priority from Japanese Patent Application No. 2011-202044 filed on Sep. 15, 2011 and U.S. Provisional Application No. 61/535,024 filed on Sep. 15, 2011, the entire disclosures of which are incorporated therein by reference.

TECHNICAL FIELD

The present invention relates to a pattern-forming method with a developer containing an organic solvent which is preferably used in super-micro-lithography process such as the manufacture of super LSI and high capacity microchips, and other photo-fabrication processes; an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition; a resist film; a manufacturing method of an electronic device by using them; and an electronic device. More specifically, the invention relates to a pattern-forming method with a developer containing an organic solvent capable of being preferably used in fine process of semiconductor devices using an electron beam or an EUV ray (wavelength: around 13 nm); an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition; a resist film; a manufacturing method of an electronic device by using them; and an electronic device.

BACKGROUND ART

In the manufacturing processes of semiconductor devices such as IC and LSI, fine process by lithography with a photoresist composition has been conventionally carried out. In recent years, ultrafine pattern formation of a sub-micron region and a quarter micron region has been required with higher integration of integrated circuits. In such a circumstance, exposure wavelength also shows a tendency to become shorter such as from g-rays to i-rays, and further to KrF excimer laser rays. Further, besides KrF excimer laser rays, development of lithography using electron beams, X-rays or EUV rays is also now progressing.

Lithography using electron beams, X-rays or EUV rays is positioned as a pattern-forming technique of the next generation or the next of the next generation, and resist compositions of high sensitivity and high resolution are desired.

In particular, for shortening the processing time of wafers, increase of sensitivity is a very important subject. However, pursuit of higher sensitization is accompanied by lowering of pattern form and resolution that is shown by limiting resolution line width, accordingly development of a resist composition satisfying these characteristics at the same time is strongly desired.

High sensitivity, high resolution and a good pattern form are in a relationship of trade-off, and it is very important how to meet these characteristics at the same time.

There are generally two types of actinic ray-sensitive or radiation-sensitive resin compositions, that is, one is a "positive" resin composition using a resin hardly soluble or

2

insoluble in an alkali developer and capable of forming a pattern by making an exposed part soluble in an alkali developer by exposure with radiation, and another is a "negative" resin composition using a resin soluble in an alkali developer and capable of forming a pattern by making an exposed part hardly soluble or insoluble in an alkali developer by exposure with radiation.

As such actinic ray-sensitive or radiation-sensitive resin compositions suitable for lithographic process using electron beams, X-rays or EUV rays, chemical amplification type positive resist compositions primarily utilizing acid catalytic reaction are examined from the viewpoint of the increase in sensitivity, and chemical amplification type positive resist composition comprising phenolic resin having a property insoluble or hardly soluble in an alkali developer and capable of being soluble in an alkali developer by the action of an acid (hereinafter abbreviated to a phenolic acid-decomposable resin), and an acid generator as the main components are effectively used.

On the other hand, in manufacturing semiconductor devices and the like, there are requirements to form patterns having various forms such as lines, trenches, holes, etc. For meeting the requirements for forming patterns having various forms, not only positive resin compositions but also negative actinic ray-sensitive or radiation-sensitive resin compositions have been developed (for example, refer to JP-A-2002-148806 (The term "JP-A" as used herein refers to an "unexamined published Japanese patent application".) and JP-A-2008-268935).

In forming super fine patterns, further improvements of the reductions of resolution and a pattern form are required.

For solving these problems, a method of developing an acid-decomposable resin with a developer other than an alkali developer is also proposed (for example, refer to JP-A-2010-217884 and JP-A-2011-123469).

However, it is demanded to satisfy high sensitivity, high resolution, and high line width roughness (LWR) performance in a super fine processing region at the same time on a higher order.

SUMMARY OF INVENTION

The objects of the invention are to solve the problems in the techniques for improving performance in fine processing of semiconductor devices using electron beams or extreme ultraviolet radiation (EUV rays), and provide a pattern-forming method capable of satisfying high sensitivity, high resolution (high resolving power, etc.) and high line width roughness (LWR) performance on an extremely higher order at the same time; an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition; a resist film; a manufacturing method of an electronic device using them; and an electronic device.

That is, the invention is as follows.

[1] A pattern-forming method, comprising in this order:

step (1) of forming a film with an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition that contains (A) a resin having an acid-decomposable repeating unit and capable of decreasing a solubility of the resin (A) in a developer containing an organic solvent by an action of an acid, (B) a compound capable of generating an acid upon irradiation with an electron beam or extreme ultraviolet radiation and (C) a solvent;

step (2) of exposing the film with an electron beam or extreme ultraviolet radiation; and

step (4) of forming a negative pattern by development of the film with a developer containing an organic solvent after the exposing of the film,

wherein a content of the compound (B) is 21% by mass to 70% by mass on the basis of all solids content of the composition.

[2] The pattern-forming method as described in [1] above, wherein the content of the compound (B) is 31% by mass to 60% by mass on the basis of all solids content of the composition.

[3] The pattern-forming method as described in [1] or [2] above, wherein the resin (A) further has a repeating unit having a polar group.

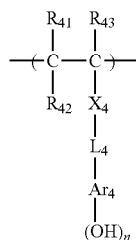
[4] The pattern-forming method as described in [3] above, wherein the polar group is selected from the group consisting of a hydroxyl group, a cyano group, a lactone group, a carboxylic acid group, a sulfonic acid group, an amido group, a sulfonamido group, an ammonium group, a sulfonium group and a group obtained by combining two or more of the above groups.

[5] The pattern-forming method as described in [1] or [2] above, wherein the resin (A) further has a repeating unit having an acid group.

[6] The pattern-forming method as described in [5] above, wherein the acid group is a phenolic hydroxyl group, a carboxylic acid group, a sulfonic acid group, a fluorinated alcohol group, a sulfonamido group, a sulfonylimido group, an (alkylsulfonyl)(alkylcarbonyl)methylene group, an (alkylsulfonyl)(alkylcarbonyl)imido group, a bis(alkylcarbonyl)methylene group, a bis(alkylcarbonyl)imido group, a bis(alkylsulfonyl)methylene group, a bis(alkylsulfonyl)imido group, a tris-(alkylcarbonyl)methylene group or a tris(alkylsulfonyl)methylene group.

[7] The pattern-forming method as described in any one of [1] to [6] above,

wherein a content of a repeating unit represented by the following formula (I) to all repeating units in the resin (A) is 4 mol % or less:



wherein each of R_{41} , R_{42} and R_{43} independently represents a hydrogen atom, an alkyl group, a halogen atom, a cyano group or an alkoxycarbonyl group, and R_{42} may be bonded to Ar_4 to form a ring, and in this case, R_{42} represents a single bond or an alkylene group;

X_4 represents a single bond, ---COO--- or $\text{---CONR}_{64}\text{---}$, and R_{64} represents a hydrogen atom or an alkyl group;

L_4 represents a single bond or an alkylene group;

Ar_4 represents an $(n+1)$ -valent aromatic ring group, and when Ar_4 forms a ring together with R_{42} , Ar_4 represents an $(n+2)$ -valent aromatic ring group; and

n represents an integer of 1 to 4.

[8] The pattern-forming method as described in any one of [1] to [7] above, which is a method for forming a semiconductor fine circuit.

[9] An electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition, which is used for the pattern-forming method as described in any one of [1] to [8] above.

[10] A resist film, which is formed with the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition as described in [9] above.

[11] A manufacturing method of an electronic device, comprising: the pattern-forming method as described in any one of [1] to [8] above.

[12] An electronic device, which is manufactured by the manufacturing method of an electronic device as described in [11] above.

DESCRIPTION OF EMBODIMENTS

The embodiments of the invention will be described in detail below.

In the description of a group (an atomic group) in the specification of the invention, the description not referring to substitution or unsubstitution includes both a group not having a substituent and a group having a substituent. For example, "an alkyl group" includes not only an alkyl group having no substituent (an unsubstituted alkyl group) but also an alkyl group having a substituent (a substituted alkyl group).

In the specification of the invention, light includes not only extreme ultraviolet rays (EUV rays) but also electron beams.

Further, "exposure" in the specification includes not only exposure with extreme ultraviolet rays (EUV rays) but also imaging by electron beams unless otherwise indicated.

[Pattern-Forming Method]

A pattern-forming method in the invention is described in the first place.

A pattern-forming method in the invention comprises in order of step (1) of forming a film with an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition containing (A) a resin having an acid-decomposable repeating unit and capable of decreasing the solubility in a developer containing an organic solvent by the action of an acid, (B) a compound capable of generating an acid upon irradiation with an electron beam or extreme ultraviolet radiation and (C) a solvent; step (2) of exposing the film with an electron beam or extreme ultraviolet radiation; and step (4) of developing the film with a developer containing an organic solvent after exposure. In the pattern-forming method in the invention, the content of compound (B) is 21% by mass to 70% by mass on the basis of all the solid contents of the composition. (In this specification, mass ratio is equal to weight ratio.)

According to the invention, the pattern-forming method capable of satisfying high sensitivity, high resolution and high line width roughness (LWR) performance on an extremely higher order at the same time; an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition; a resist film; a manufacturing method of an electronic device using them; and an electronic device can be provided. The reasons for these facts are not clear but are presumed as follows.

In the first place, in the pattern-forming method of performing exposure of a resist film containing a resin having an acid-decomposable repeating unit with an electron beam or extreme ultraviolet radiation, a site capable of generating

secondary electrons (typically, a site having a degree of polarity or acidity higher than other sites) present in the resist film is irradiated with light (i.e., an electron beam or extreme ultraviolet radiation). In the next place, secondary electron generated from the above site decomposes the acid generator to thereby generate an acid, by which reaction of the acid and the resin is carried out at the exposed part.

Here, in the case where a positive pattern is formed with an alkali developer after exposure of the resist film, when a site capable of generating secondary electrons (typically, a site having a high degree of polarity or acidity as described above) is present in a high content in the resist film, the degree of polarity or acidity of the resist film from the first becomes high even if the reaction efficiency of the acid and the resin at the exposed part is high, and so even the unexposed part is readily soluble in the alkali developer, which is liable to adversely affect the resolution and the like of the pattern. Accordingly, in a case where a positive pattern is formed with an alkali developer, it is thought to be necessary to take the prescription to control the content of the site capable of generating secondary electrons in the resist composition.

However, the present inventors have found that a system, which is exposed with an electron beam or extreme ultraviolet radiation to form a negative pattern with a developer containing an organic solvent (hereinafter also referred to as "an organic developer"), is a system showing sufficiently high dissolution speed of the unexposed part in an organic developer even when the content of the site capable of generating secondary electrons in the resist film is raised for improving the sensitivity and is a system capable of obtaining good resolution. This is perhaps for the reason that the original resist film mainly comprises a resin and has high affinity with an organic developer, and great and small of the content of the site capable of generating secondary electrons do not largely affect solubility of the unexposed part in the organic developer.

Further, the pattern-forming method of performing exposure with an electron beam or extreme ultraviolet radiation is expected to be a method which is capable of well forming an extremely fine pattern (e.g., a pattern having a line width of 50 nm or less).

However, in the case where a line and space pattern having, for example, a line width of 50 nm or less and the ratio of the line width and the space width of 1/1 is formed, a stronger capillary force is liable to occur in the fine space formed at development time, and the capillary force is applied to the side wall of the pattern having a fine line width when the developer is discharged out of the space. And when a positive pattern is formed with an alkali developer, since the affinity of the pattern mainly comprising a resin with the alkali developer has a tendency to be low, the capillary force applied to the side wall of the pattern is great and collapse of the pattern is liable to occur.

On the other hand, when a negative pattern is formed with an organic developer as in the invention, the affinity of the pattern mainly comprising a resin with the organic developer has a tendency to be high, and so the capillary force applied to the side wall of the pattern is small and collapse of the pattern difficulty occurs. It is thought from these facts that high resolution can be achieved (excellent in limit resolution) according to the invention. Further, the fact that the capillary force is small presumably contributes to the improvement of the line width roughness (LWR) performance.

Further, in the pattern-forming method in the invention, the content of compound (B) (an acid generator) is 21% by mass to 70% by mass on the basis of all the solid contents of the composition, which means that the concentration of the acid

generator is very high. It is thought that the reaction efficiency of the acid generator with the secondary electron is high due to high concentration of the acid generator, and so high sensitivity can be obtained. Sufficient acid is generated by high concentration of the acid generator at the exposed part and reaction unevenness and the like of the acid with the resin is inhibited, which presumably contributes to the improvement of LWR performance.

On the one hand, the concentration of the acid generator in the composition is high, but on the other hand the concentrations of other components may be low, and so there is a possibility that other performances are affected. For example, when the concentration of the resin lowers for the part that the concentration of the acid rises, the strength of the pattern decreases and the influence of capillary force is actualized, and the resist may be accompanied by reduction of resolution and lowering of LWR performance.

However, as described above, since the method of the invention is a method to form a negative pattern with an organic developer which is little in the influence of capillary force, disadvantage due to increase of the concentration of acid generator is difficult to occur, as a result it is presumed that high sensitivity, high resolution and high LWR performance are satisfied on an extremely high order at the same time.

(1) Film Forming

The resist film in the invention is a film formed from the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition.

More specifically, the resist film is formed by dissolving each of the components of the later-described electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition in a solvent and, if necessary, filtering through a filter and applying the resulting solution on a support (a substrate). As the filter, a filter made of polytetrafluoroethylene, polyethylene, or nylon having a pore size of 0.1 μm or less, more preferably 0.05 μm or less, and still more preferably 0.03 μm or less is preferably used.

The composition is applied on a substrate such as the one used in the manufacture of an integrated circuit device (e.g., silicon, silicon dioxide coating) by a proper coating method, e.g., with a spin coater or the like. The coated substrate is then dried to form a photosensitive film. In the drying step, to perform heating (prebaking) is preferred.

The film thickness is not especially restricted, but it is preferably adjusted to the range of 10 nm to 500 nm, more preferably to the range of 10 nm to 200 nm, and still more preferably to the range of 10 nm to 80 nm. When the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition is applied with a spinner, the revolution speed is generally 500 rpm to 3,000 rpm, preferably 800 rpm to 2,000 rpm, and more preferably 1,000 rpm to 1,500 rpm.

The temperature of heating (prebaking) is preferably 60° C. to 200° C., more preferably 80° C. to 150° C., and still more preferably 90° C. to 140° C.

The time of heating (prebaking) is not especially restricted, but the time is preferably 30 seconds to 300 seconds, more preferably 30 seconds to 180 seconds, and still more preferably 30 seconds to 90 seconds.

Heating can be performed with a unit attached to ordinary exposing and developing apparatus, and a hot plate and the like may also be used.

If necessary, a commercially available inorganic or organic antireflection film can be used. Further, an antireflection film may be applied on the under layer of an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition. As the antireflection films, either an inorganic film,

e.g., titanium, titanium dioxide, titanium nitride, chromium oxide, carbon, or amorphous silicon, or an organic film comprising a light absorber and a polymer material may be used. As organic antireflection films, commercially available organic antireflection films, such as DUV 30 series and DUV 40 series (manufactured by Brewer Science) and AR-2, AR-3 and AR-5 (manufactured by Shipley Company L.L.C.) may also be used.

(2) Exposure

Exposure is carried out with extreme ultraviolet radiation (EUV ray) or an electron beam (EB). When extreme ultraviolet radiation (EUV ray) is used as the exposure light source, it is preferred for the formed film to be irradiated with EUV ray (in the vicinity of 13 nm) through a prescribed mask. In irradiation with electron beams (EB), imaging (direct drawing) not via a mask is generally carried out. Exposure with extreme ultraviolet radiation is preferred.

(3) Baking

After exposure and before development, it is preferred to perform baking (heating).

Heating temperature is preferably 60° C. to 150° C., more preferably 80° C. to 150° C., and still more preferably 90° C. to 140° C.

Heating time is not especially restricted but is preferably 30 seconds to 300 seconds, more preferably 30 seconds to 180 seconds, and still more preferably 30 seconds to 90 seconds.

Heating can be performed with a unit attached to ordinary exposing and developing apparatus, and a hot plate and the like may also be used.

The reaction at the exposed part is expedited by baking and sensitivity and a pattern profile are improved. It is also preferred to have a heating step (post baking) after rinsing step. The heating temperature and heating time are as described above. The developer and rinsing solution remained between and within patterns are removed by baking.

(4) Development

In the invention, development is performed with a developer containing an organic solvent.

Developer

The vapor pressure of a developer (in the case of a mixed solvent, the vapor pressure as a whole) at 20° C. is preferably 5 kPa or less, more preferably 3 kPa or less, and especially preferably 2 kPa or less. By making the vapor pressure of an organic solvent 5 kPa or less, evaporation of the developer on a substrate or in a developing cup is inhibited and evenness of temperature in a wafer surface is improved, as a result dimensional evenness in the wafer surface is bettered.

As organic solvents for use as the developer, various organic solvents are widely used. For example, solvents such as ester solvents, ketone solvents, alcohol solvents, amide solvents, ether solvents and hydrocarbon solvents can be used.

In the invention, the ester solvents are solvents having an ester group in the molecule, the ketone solvents are solvents having a ketone group in the molecule, the alcohol solvents are solvents having an alcoholic hydroxyl group in the molecule, the amide solvents are solvents having an amido group in the molecule, and the ether solvents are solvents having an ether bond in the molecule. Of the above solvents, those having a plurality of functional groups in one molecule are also present. In such a case, these solvents are to come within the purview of all the kinds of solvents containing the functional groups that the solvents have. For example, diethylene glycol monomethyl ether is applicable to both of the alcohol solvents and the ether solvents of the above classification. Further, the hydrocarbon solvents are hydrocarbon solvents not having a substituent.

In particular, a developer containing at least one solvent selected from the ketone solvents, ester solvents, alcohol solvents and ether solvents is preferred as the developer in the invention.

As the examples of the ester solvents, e.g., methyl acetate, ethyl acetate, butyl acetate, pentyl acetate, isopropyl acetate, amyl acetate, isoamyl acetate, ethyl methoxyacetate, ethyl ethoxyacetate, propylene glycol monomethyl ether acetate (also known as PGMEA, 1-methoxy-2-acetoxypentane), ethylene glycol monoethyl ether acetate, ethylene glycol monopropyl ether acetate, ethylene glycol monobutyl ether acetate, ethylene glycol monophenyl ether acetate, diethylene glycol monomethyl ether acetate, diethylene glycol monopropyl ether acetate, diethylene glycol monoethyl ether acetate, diethylene glycol monophenyl ether acetate, diethylene glycol monobutyl ether acetate, diethylene glycol monoethyl ether acetate, 2-methoxybutyl acetate, 3-methoxybutyl acetate, 4-methoxybutyl acetate, 3-methyl-3-methoxybutyl acetate, 3-ethyl-3-methoxybutyl acetate, propylene glycol monoethyl ether acetate, propylene glycol monopropyl ether acetate, 2-ethoxybutyl acetate, 4-ethoxybutyl acetate, 4-propoxybutyl acetate, 2-methoxypentyl acetate, 3-methoxypentyl acetate, 4-methoxypentyl acetate, 2-methyl-3-methoxypentyl acetate, 3-methyl-3-methoxypentyl acetate, 3-methyl-4-methoxypentyl acetate, 4-methyl-4-methoxypentyl acetate, propylene glycol diacetate, methyl formate, ethyl formate, butyl formate, propyl formate, ethyl lactate, butyl lactate, propyl lactate, ethyl carbonate, propyl carbonate, butyl carbonate, methyl pyruvate, ethyl pyruvate, propyl pyruvate, butyl pyruvate, methyl acetoacetate, ethyl acetoacetate, methyl propionate, ethyl propionate, propyl propionate, isopropyl propionate, methyl-2-hydroxy propionate, ethyl-2-hydroxy propionate, methyl-3-methoxy propionate, ethyl-3-methoxy propionate, ethyl-3-ethoxy propionate, and propyl-3-methoxy propionate are exemplified.

As the examples of the ketone solvents, e.g., 1-octanone, 2-octanone, 1-nonanone, 2-nonanone, acetone, 2-heptanone, 4-heptanone, 1-hexanone, 2-hexanone, diisobutyl ketone, cyclohexanone, methylcyclohexanone, phenylacetone, methyl ethyl ketone, methyl isobutyl ketone, acetylacetone, acetonylacetone, ionone, diacetonyl alcohol, acetylcarbinol, acetophenone, methyl naphthyl ketone, isophorone, propylene carbonate, and γ -butyrolactone are exemplified.

As the examples of the alcohol solvents, alcohols, e.g., methyl alcohol, ethyl alcohol, n-propyl alcohol, isopropyl alcohol, n-butyl alcohol, sec-butyl alcohol, tert-butyl alcohol, isobutyl alcohol, n-hexyl alcohol, n-heptyl alcohol, n-octyl alcohol, n-decanol, 3-methoxy-1-butanol, etc., glycol solvents, e.g., ethylene glycol, diethylene glycol, triethylene glycol, etc., and glycol ether solvents having a hydroxyl group, e.g., ethylene glycol monomethyl ether, propylene glycol monomethyl ether (also known as PGME, 1-methoxy-2-propane), diethylene glycol monomethyl ether, triethylene glycol monoethyl ether, methoxymethylbutanol, ethylene glycol monoethyl ether, ethylene glycol monopropyl ether, ethylene glycol monobutyl ether, propylene glycol monoethyl ether, propylene glycol monopropyl ether, propylene glycol monobutyl ether, propylene glycol monophenyl ether, etc., are exemplified. Of these alcohol solvents, the glycol ether solvents are preferably used.

As the examples of the ether solvents, besides the glycol ether solvents having a hydroxyl group as described above, glycol ether solvents not having a hydroxyl group, e.g., propylene glycol dimethyl ether, propylene glycol diethyl ether, diethylene glycol dimethyl ether, diethylene glycol diethyl ether, etc., aromatic ether solvents, e.g., anisole, phenetole, etc., and dioxane, tetrahydrofuran, tetrahydropyran, per-

fluoro-2-butyltetrahydrofuran, perfluorotetrahydrofuran, 1,4-dioxane, etc., are exemplified. Glycol ether solvents and aromatic ether solvents such as anisole are preferably used.

As the examples of the amide solvents, e.g., N-methyl-2-pyrrolidone, N,N-dimethylacetamide, N,N-dimethylformamide, hexamethyl phosphoric triamide, 1,3-dimethyl-2-imidazolidinone, etc., can be used.

As the examples of the hydrocarbon solvents, aliphatic hydrocarbon solvents, e.g., pentane, hexane, octane, decane, 2,2,4-trimethylpentane, 2,2,3-trimethylhexane, perfluorohexane, perfluoroheptane, etc., and aromatic hydrocarbon solvents e.g., toluene, xylene, ethylbenzene, propylbenzene, 1-methylpropylbenzene, 2-methylpropylbenzene, dimethylbenzene, diethylbenzene, ethylmethylbenzene, trimethylbenzene, ethyldimethylbenzene, dipropylbenzene, etc., are exemplified. Of these hydrocarbon solvents, aromatic hydrocarbon solvents are preferably used.

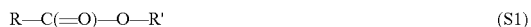
Two or more of these solvents may be blended, or these solvents may be used as mixture with solvents other than the above solvents and water. However, for sufficiently exhibiting the advantage of the invention, the water content as the developer at large is preferably less than 10% by mass, and it is more preferred not to substantially contain water.

The concentration of the organic solvent (when two or more solvents are blended, as total) in a developer is preferably 50% by mass or more, more preferably 70% by mass or more, and still more preferably 90% by mass or more. Especially preferred is the case consisting of organic solvents alone. Incidentally, the case consisting of organic solvents alone includes the case containing a trace amount of a surfactant, an antioxidant, a stabilizer, a defoaming agent, and the like.

Of the above solvents, it is more preferred to contain one or more solvents selected from the group consisting of butyl acetate, pentyl acetate, isopentyl acetate, propylene glycol monomethyl ether acetate, and anisole.

An organic solvent for use as the developer is preferably an ester solvent.

As the ester solvent, it is more preferred to use the later-described solvent represented by formula (S1) or the later-described solvent represented by formula (S2), it is still more preferred to use the solvent represented by formula (S1), it is especially preferred to use alkyl acetate, and it is most preferred to use butyl acetate, pentyl acetate or isopentyl acetate.



In formula (S1), each of R and R' independently represents a hydrogen atom, an alkyl group, a cycloalkyl group, an alkoxy group, an alkoxycarbonyl group, a carboxyl group, a hydroxyl group, a cyano group, or a halogen atom, and R and R' may be bonded to each other to form a ring.

The carbon atom number of the alkyl group, alkoxy group and alkoxycarbonyl group represented by R and R' is preferably in the range of 1 to 15, and the carbon atom number of the cycloalkyl group is preferably in the range of 3 to 15.

Each of R and R' preferably represents a hydrogen atom or an alkyl group, and the alkyl group, cycloalkyl group, alkoxy group, alkoxycarbonyl group, and the ring formed by bonding of R and R' to each other may be substituted with a hydroxyl group, a group containing a carbonyl group (e.g., an acyl group, an aldehyde group, an alkoxycarbonyl group or the like), or a cyano group.

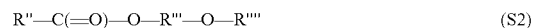
As the examples of the solvents represented by formula (S1), e.g., methyl acetate, butyl acetate, ethyl acetate, isopropyl acetate, amyl acetate, isoamyl acetate, methyl formate, ethyl formate, butyl formate, propyl formate, ethyl lactate, butyl lactate, propyl lactate, ethyl carbonate, propyl carbon-

ate, butyl carbonate, methyl pyruvate, ethyl pyruvate, propyl pyruvate, butyl pyruvate, methyl acetoacetate, ethyl acetoacetate, methyl propionate, ethyl propionate, propyl propionate, isopropyl propionate, methyl-2-hydroxy propionate, ethyl-2-hydroxy propionate, and the like are exemplified.

Of the above, each of R and R' is preferably an unsubstituted alkyl group.

The solvent represented by formula (S1) is preferably alkyl acetate, and more preferably butyl acetate, pentyl acetate or isopentyl acetate.

The solvent represented by formula (S1) may be used in combination with one or more other organic solvents. The solvents for use in combination in this case are not especially restricted so long as they can be blended with the solvent represented by formula (S1) without separation. The solvents represented by formula (S1) may be blended with each other. The solvent represented by formula (S1) may be used as mixture with the solvent selected from other ester solvents, ketone solvents, alcohol solvents, amide solvents, ether solvents and hydrocarbon solvents. One or more solvents may be used in combination, but for obtaining stable performance, the solvent to be used in combination is preferably one kind. When one kind of a solvent is used in combination as mixture, the blending ratio of the solvent represented by formula (S1) and the solvent to be used in combination is generally 20/80 to 99/1 as mass ratio, preferably 50/50 to 97/3, more preferably 60/40 to 95/5, and most preferably 60/40 to 90/10.



In formula (S2), each of R'' and R''' independently represents a hydrogen atom, an alkyl group, a cycloalkyl group, an alkoxy group, an alkoxycarbonyl group, a carboxyl group, a hydroxyl group, a cyano group, or a halogen atom, and R'' and R''' may be bonded to each other to form a ring.

Each of R'' and R''' preferably represents a hydrogen atom or an alkyl group. The carbon atom number of the alkyl group, alkoxy group and alkoxycarbonyl group represented by R'' and R''' is preferably in the range of 1 to 15, and the carbon atom number of the cycloalkyl group is preferably in the range of 3 to 15.

R''' represents an alkylene group or a cycloalkylene group. R''' preferably represents an alkylene group. The carbon atom number of the alkylene group represented by R''' is preferably in the range of 1 to 10. The carbon atom number of the cycloalkylene group represented by R''' is preferably in the range of 3 to 10.

The alkyl group, cycloalkyl group, alkoxy group, and alkoxycarbonyl group represented by each of R'' and R''', the alkylene group and cycloalkylene group represented by R''', and the ring formed by bonding of R'' and R''' to each other may be substituted with a hydroxyl group, a group containing a carbonyl group (e.g., an acyl group, an aldehyde group, an alkoxycarbonyl group or the like), or a cyano group.

The alkylene group represented by R''' in formula (S2) may have an ether bond in the alkylene chain.

The examples of the solvents represented by formula (S2) include, for example, propylene glycol monomethyl ether acetate, ethylene glycol monoethyl ether acetate, ethylene glycol monopropyl ether acetate, ethylene glycol monobutyl ether acetate, ethylene glycol monophenyl ether acetate, diethylene glycol monomethyl ether acetate, diethylene glycol monopropyl ether acetate, diethylene glycol monophenyl ether acetate, diethylene glycol monobutyl ether acetate, diethylene glycol monoethyl ether acetate, propylene glycol monoethyl ether acetate, propylene glycol monopropyl ether acetate, methyl-3-methoxy propionate, ethyl-3-methoxy propionate, ethyl-3-ethoxy propionate, propyl-3-methoxy propi-

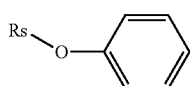
onate, ethyl methoxyacetate, ethyl ethoxyacetate, 2-methoxybutyl acetate, 3-methoxybutyl acetate, 4-methoxybutyl acetate, 3-methyl-3-methoxybutyl acetate, 3-ethyl-3-methoxybutyl acetate, 2-ethoxybutyl acetate, 4-ethoxybutyl acetate, 4-propoxybutyl acetate, 2-methoxypentyl acetate, 3-methoxypentyl acetate, 4-methoxypentyl acetate, 2-methyl-3-methoxypentyl acetate, 3-methyl-3-methoxypentyl acetate, 3-methyl-4-methoxypentyl acetate, 4-methyl-4-methoxypentyl acetate, etc., and propylene glycol monomethyl ether acetate is preferred.

Of the above, each of R" and R' preferably represents an unsubstituted alkyl group. R''' preferably represents an unsubstituted alkylene group. Each of R" and R' more preferably represents either a methyl group or an ethyl group. Still more preferably, each of R" and R''' represents a methyl group.

The solvent represented by formula (S2) may be used in combination with one or more other organic solvents. The solvents for use in combination in this case are not especially restricted so long as they can be blended with the solvent represented by formula (S2) without separation. The solvents represented by formula (S2) may be blended with each other. The solvent represented by formula (S2) may be used as mixture with the solvent selected from other ester solvents, ketone solvents, alcohol solvents, amide solvents, ether solvents and hydrocarbon solvents. One or more solvents may be used in combination, but for obtaining stable performance, the solvent to be used in combination is preferably one kind. When one kind of a solvent is used in combination as mixture, the blending ratio of the solvent represented by formula (S2) and the solvent to be used in combination is generally 20/80 to 99/1 as mass ratio, preferably 50/50 to 97/3, more preferably 60/40 to 95/5, and most preferably 60/40 to 90/10.

As organic solvents for use as the developer, ether solvents can also be preferably exemplified.

As ether solvents that can be used, the above-described ether solvents are exemplified. Of the above ether solvents, ether solvents having one or more aromatic rings are preferred, more preferably a solvent represented by the following formula (S3), and most preferably anisole.



In formula (S3), Rs represents an alkyl group. The alkyl group preferably has 1 to 4 carbon atoms, and is more preferably a methyl group or an ethyl group, and most preferably a methyl group.

In the invention, the water content of the developer is generally 10% by mass or less, preferably 5% by mass or less, more preferably 1% by mass or less, and it is most preferred not to substantially contain water.

Surfactant

To the developer containing an organic solvent may be added an appropriate amount of a surfactant according to necessity.

As the surfactant, the same surfactants as those for use in the later-described electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition can be used.

The amount of the surfactant to be used is generally 0.001% by mass to 5% by mass of the entire amount of the developer, preferably 0.005% by mass to 2% by mass, and more preferably 0.01% by mass to 0.5% by mass.

Developing Method

As a developing method, for example, a method of dipping a substrate in a tank filled with a developer for a prescribed time (a dipping method), a developing method by swelling a developer by surface tension to slightly above the surface of a substrate and standing still for a prescribed time (a puddling method), a method of spraying a developer on the surface of a substrate (a spraying method), and a method of continuously ejecting a developer by scanning a developer ejection nozzle at a constant speed on a substrate revolving at a constant speed (a dynamic dispensing method) can be applied.

After a development step, a step of stopping development while replacing the developer with other solvent may be performed.

The developing time is not especially restricted so long as it is sufficient for the resin in an unexposed part to be dissolved thoroughly, and is generally 10 seconds to 300 seconds, and preferably 20 seconds to 120 seconds.

The temperature of the developer is preferably 0° C. to 50° C., and more preferably 15° C. to 35° C.

(5) Rinsing

In the pattern-forming method of the invention, rinsing step (5) of rinsing the substrate with a rinsing solution containing an organic solvent may be included after development step (4).

Rinsing Solution

The vapor pressure of a rinsing solution to be used after development (in the case of a mixed solvent, the vapor pressure as a whole) at 20° C. is preferably 0.05 kPa or more and 5 kPa or less, more preferably 0.1 kPa or more and 5 kPa or less, and most preferably 0.12 kPa or more and 3 kPa or less. By making the vapor pressure of a rinsing solution 0.05 kPa or more and 5 kPa or less, evenness of in-plane temperature of the wafer is improved, swelling attributable to the osmosis of a rinsing solution is restrained, and evenness of in-plane dimension of a wafer is bettered.

Various organic solvents are used as the rinsing solution, and it is preferred to use a rinsing solution containing at least one organic solvent selected from hydrocarbon solvents, ketone solvents, ester solvents, alcohol solvents, amide solvents and ether solvents, or water.

It is more preferred to perform a step of rinsing with a rinsing solution containing at least one organic solvent selected from ketone solvents, ester solvents, alcohol solvents, amide solvents and hydrocarbon solvents after development. Still more preferred is to perform a step of rinsing with a rinsing solution containing an alcohol solvent or a hydrocarbon solvent after development.

Especially preferred is to use a rinsing solution containing one or more solvents selected from monohydric alcohols and hydrocarbon solvents.

As the monohydric alcohols for use in the rinsing step after development, straight chain, branched, or cyclic monohydric alcohols are exemplified. Specifically, 1-butanol, 2-butanol, 3-methyl-1-butanol, tert-butyl alcohol, 1-pentanol, 2-pentanol, 1-hexanol, 1-heptanol, 1-octanol, 2-hexanol, 2-heptanol, 2-octanol, 3-hexanol, 3-heptanol, 3-octanol, 4-octanol, 3-methyl-3-pentanol, cyclopentanol, 2,3-dimethyl-2-butanol, 3,3-dimethyl-2-butanol, 2-methyl-2-pentanol, 2-methyl-3-pentanol, 3-methyl-2-pentanol, 3-methyl-3-pentanol, 4-methyl-2-pentanol, 4-methyl-3-pentanol, cyclohexanol, 5-methyl-2-hexanol, 4-methyl-2-hexanol, 4,5-dimethyl-2-hexanol, 6-methyl-2-heptanol, 7-methyl-2-octanol, 8-methyl-2-nonanol, 9-methyl-2-decanol, etc., can be used. Of these alcohols, 1-hexanol, 2-hexanol, 1-pentanol, 3-methyl-1-butanol, 3-methyl-2-pentanol, 3-methyl-3-pentanol, 4-methyl-

13

2-pentanol, and 4-methyl-3-pentanol are preferred, and 1-hexanol and 4-methyl-2-pentanol are most preferred.

As the hydrocarbon solvents, aromatic hydrocarbon solvents such as toluene and xylene, and aliphatic hydrocarbon solvents such as octane and decane are exemplified.

The rinsing solution more preferably contains one or more selected from the group consisting of 1-hexanol, 4-methyl-2-pentanol and decane.

Two or more of the above components may be blended, or may be blended with organic solvents other than the above. The above solvents may be mixed with water but the water content in a rinsing solution is generally 60% by mass or less, preferably 30% by mass or less, more preferably 10% by mass or less, and most preferably 5% by mass or less. By making the water content 60% by mass or less, good rinsing characteristics can be obtained.

A proper amount of a surfactant may be added to a rinsing solution.

As the surfactant, the same surfactants as those for use in the later-described electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition can be used. The amount of the surfactant to be used is generally 0.001% by mass to 5% by mass of the entire amount of the rinsing solution, preferably 0.005% by mass to 2% by mass, and more preferably 0.01% by mass to 0.5% by mass.

Rinsing Method

In the rinsing step, a developed wafer is subjected to rinsing treatment with a rinsing solution containing the above organic solvent.

The method of rinsing treatment is not especially restricted, and, for example, a method of continuously ejecting a rinsing solution on a substrate rotating at a constant speed (a rotary ejecting method), a method of dipping a substrate in a tank filled with a rinsing solution for a prescribed time (a dipping method), and a method of spraying a rinsing solution on the surface of a substrate (a spraying method) can be applied. Of these methods, it is preferred to perform rinsing treatment by the rotary ejecting method and, after rinsing, remove the rinsing solution from the substrate by revolving the substrate by revolution of 2,000 rpm to 4,000 rpm.

The time of rinsing is not particularly limited, and it is generally 10 seconds to 300 seconds, preferably 10 seconds to 180 seconds, and most preferably 20 seconds to 120 seconds.

The temperature of the rinsing solution is preferably 0° C. to 50° C., and more preferably 15° C. to 35° C.

After developing treatment or rinsing treatment, the developer or the rinsing solution adhered on the pattern can be removed by supercritical fluid.

Further, after the developing treatment or rinsing treatment or the treatment by supercritical fluid, heating treatment can be carried out for taking clear away the solvent remaining in the pattern. The temperature of heating is not especially restricted so long as a good resist pattern can be obtained, and is generally 40° C. to 160° C., preferably 50° C. or more and 150° C. or less, and most preferably 50° C. or more and 110° C. or less. The heating time is not especially restricted so long as a good resist pattern can be obtained, and is generally 15 seconds to 300 seconds, and preferably 15 seconds to 180 seconds.

Alkali Development

The pattern-forming method in the invention can further include a step of development with an alkali aqueous solution to form a resist pattern (an alkali development step), by which a further finer pattern can be formed.

In the invention, a part where exposure strength is weak is removed by organic solvent development step (4), and a part

14

where exposure strength is strong is also removed by further performing the alkali development step. By multiple development step of performing a plurality of development steps like this, a pattern can be formed without dissolving an area of intermediate exposure strength alone, so that a pattern that is finer than a usual pattern can be formed (the same mechanism as disclosed in JP-A-2008-292975 [0077]).

The alkali development may be performed either before or after development step (4) with a developer containing an organic solvent, but it is more preferred to be performed before organic solvent development step (4).

As the alkali aqueous solution for use in the alkali development, for example, alkaline aqueous solutions such as inorganic alkalis, e.g., sodium hydroxide, potassium hydroxide, sodium carbonate, sodium silicate, sodium metasilicate, aqueous ammonia, etc., primary amines, e.g., ethylamine, n-propylamine, etc., secondary amines, e.g., diethylamine, di-n-butylamine, etc., tertiary amines, e.g., triethylamine, methyldiethylamine, etc., alcohol amines, e.g., dimethylethanolamine, triethanolamine, etc., quaternary ammonium salts, e.g., tetramethylammonium hydroxide, tetraethylammonium hydroxide, etc., and cyclic amines, e.g., pyrrole, piperidine, etc., are exemplified.

Further, appropriate amounts of alcohols and surfactants can be added to the above alkaline aqueous solutions.

The alkali concentration of the alkali developer is generally 0.1% by mass to 20% by mass.

The pH of the alkali developer is generally 10.0 to 15.0.

An aqueous solution of 2.38% by mass of tetramethylammonium hydroxide is especially preferred.

The time of alkali development is not especially restricted and the time is generally 10 seconds to 300 seconds and preferably 20 seconds to 120 seconds.

The temperature of the alkali developer is preferably 0° C. to 50° C. and more preferably 15° C. to 35° C.

After development with an alkali aqueous solution, rinsing treatment can be carried out. Pure water is preferred as a rinsing solution in the rinsing treatment, and a proper amount of a surfactant can also be added.

Further, after the developing treatment or the rinsing treatment, heating treatment can be carried out for removing the water content remaining in the pattern.

Further, treatment for removing the residual developer or rinsing solution can be performed by heating. The heating temperature is not especially restricted so long as a good resist pattern can be obtained, and it is generally 40° C. to 160° C., preferably 50° C. or more and 150° C. or less, and most preferably 50° C. or more and 110° C. or less. The heating time is not especially restricted so long as a good resist pattern can be obtained, and it is generally 15 seconds to 300 seconds and preferably 15 seconds to 180 seconds.

The film formed from the resist composition according to the invention may be subjected to immersion exposure by filling a liquid having a refractive index higher than that of air (an immersion medium) between the film and lens at the time of irradiation with an actinic ray or radiation. Resolution can be further improved by this immersion exposure. As the immersion medium to be used, any liquid can be used so long as it has a refractive index higher than that of air, but purer water is preferred.

Immersion liquids for use at the time of immersion exposure are described below.

A liquid which is transparent to the exposure wavelength and having the temperature coefficient of refractive index as small as possible is preferred as the immersion liquid so as to confine distortion of the optical image projected on a resist film to the minimum level. Water is preferably used for this

15

purpose from the points of easy availability and handling easiness, in addition to the above viewpoint.

Further, a medium having a refractive index of 1.5 or more can also be used from the point of capable of improvement of refractive index. The medium may be an aqueous solution or may be an organic solvent.

When water is used as the immersion liquid, a trace amount of additive (a liquid) which does not dissolve the resist film on the wafer and the influence of which on the optical coat of the lower surface of the lens is negligible may be added for the purpose of decreasing the surface tension of water and increasing surface activating property. As such additives, aliphatic alcohols having a refractive index almost equal to that of water are preferred, and specifically methyl alcohol, ethyl alcohol and isopropyl alcohol are exemplified. By the addition of an alcohol having a refractive index almost equal to that of water, an advantage such that the change of refractive index as the liquid at large can be made extremely small can be obtained even when the alcohol component in water evaporates and concentration of the content varies. On the other hand, when an impurity whose refractive index is greatly different from that of water is mixed, distortion of the optical image projected on the resist film is caused, and so the water to be used is preferably distilled water. Further, pure water having been filtered through an ion exchange filter may also be used.

Electrical resistance of water is preferably 18.3 MQ cm or more, TOC (concentration of organic substance) is preferably 20 ppb or less, and water has been preferably subjected to deaeration treatment.

Further, it is also possible to improve lithographic performance by increasing the refractive index of an immersion liquid. From such a point of view, an additive capable of heightening refractive index may be added to water or deuterium oxide (D_2O) may be used in place of water.

A hardly soluble film in an immersion liquid (hereinafter also referred to as "topcoat") may be provided between the film formed out of the composition of the invention and an immersion liquid to prevent the film from coming into directly contact with the immersion liquid. Functions necessary to the topcoat are coating aptitude to the upper layer of the film of the composition and slight solubility in the immersion liquid. It is preferred that the topcoat is not mixed with the film of the composition and can be uniformly applied on the upper layer of the composition film.

As the topcoat, a hydrocarbon polymer, an acrylic ester polymer, polymethacrylic acid, polyacrylic acid, polyvinyl ether, a silicon-containing polymer, and a fluorine-containing polymer are specifically exemplified. From the viewpoint of prevention of elution of impurities from a topcoat into an immersion liquid to cause pollution of the optical lens, the residual monomer component of the polymer contained in the topcoat is the smaller the better.

When a topcoat is peeled off, a developer may be used, or a peeling agent may be separately used. As the peeling agent, a solvent little in osmosis into a film is preferred. From the point that a peeling step can be carried out at the same time with a developing treatment step of a film, peeling with a developer containing an organic solvent is preferred.

Resolution is improved when there is no difference in refractive index between the topcoat and the immersion liquid. When water is used as the immersion liquid, the refractive index of the topcoat is preferably near to the refractive index of the immersion liquid. From the viewpoint of making the refractive index of the topcoat near to that of the immersion liquid, it is preferred to contain a fluorine atom in the

16

topcoat. Also from the aspect of transparency and refractive index, the topcoat is preferably a thin film.

It is preferred that the topcoat is not mixed with the film formed of the composition of the invention and also not mixed with the immersion liquid. From this point of view, when water is used as the immersion liquid, the solvent to be used in the topcoat is preferably hardly soluble in the solvent used in the composition of the invention, and is preferably a non-water-soluble medium. Further, when the immersion liquid is an organic solvent, the topcoat may be water-soluble or non-water-soluble.

[1] Electron Beam-Sensitive or Extreme Ultraviolet Radiation-Sensitive Resin Composition

The electron beam-sensitive or extreme ultraviolet radiation-sensitive resin compositions usable in the invention are described below.

The electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition in the invention is used for negative type development (development of a type in which the solubility in a developer of a resin composition decreases by exposure and the exposed part remains as a pattern, and the unexposed part is removed). That is, the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition according to the invention can be made an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition for organic solvent development for use in development using a developer containing an organic solvent. Here, "for organic solvent development" means the use offered to a development step with a developer containing at least an organic solvent.

Thus, the invention also relates to an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition for use in the pattern-forming method according to the invention.

The electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition according to the invention is typically a resist composition, and especially preferably a negative resist composition (that is, a resist composition for organic solvent development) for the reason of capable of obtaining high effect. The composition according to the invention is also typically a chemical amplification type resist composition.

The composition for use in the invention contains resin (A) having an acid-decomposable repeating unit and capable of decreasing the solubility in an organic solvent by the action of an acid, compound (B) capable of generating an acid upon irradiation with an electron beam or extreme ultraviolet radiation, and solvent (C). Resin (A) is explained below.

[1] Resin (A)

(a) Repeating Unit Having an Acid-Decomposable Group

Resin (A) is a resin capable of decreasing the solubility in a developer containing an organic solvent by the action of an acid and has an acid-decomposable repeating unit. The acid-decomposable repeating unit is a repeating unit having a group capable of decomposing by the action of an acid (hereinafter also referred to as "acid-decomposable group") on the main chain or side chain or both main chain and side chain of the resin. A group generated by decomposition is preferably a polar group for the reason that the affinity with the developer containing an organic solvent becomes low, which is preferred to progress insolubilization or slight solubilization (negativation). The polar group is more preferably an acid group. The definition of the polar group has the same meaning with the definition explained in the item of repeating unit (b) described later. The examples of the polar groups generated by decomposition of acid-decomposable groups include an alcoholic hydroxyl group, an amino group and an acid group.

17

The polar group generated by decomposition of an acid-decomposable group is preferably an acid group.

The acid group is not especially restricted so long as it is a group capable of being insolubilized in a developer containing an organic solvent. As preferred acid groups, a phenolic hydroxyl group, a carboxylic acid group, a sulfonic acid group, a fluorinated alcohol group, a sulfonamido group, a sulfonylimido group, an (alkylsulfonyl)(alkylcarbonyl)methylene group, an (alkylsulfonyl)(alkylcarbonyl)-imido group, a bis(alkylcarbonyl)methylene group, a bis(alkylcarbonyl)imido group, a bis(alkylsulfonyl)methylene group, a bis(alkylsulfonyl)imido group, a tris-(alkylcarbonyl)methylene group and a tris(alkylsulfonyl)methylene group are exemplified, and more preferably a carboxylic acid group, a fluorinated alcohol group (preferably hexafluoroisopropanol), a phenolic hydroxyl group and a sulfonic acid group (a group dissociable in a 2.38% by mass tetramethylammonium hydroxide aqueous solution used as conventional resist developer) are exemplified.

Preferred groups as acid-decomposable groups are groups obtained by substituting the hydrogen atoms of these groups with a group capable of leaving by the action of an acid.

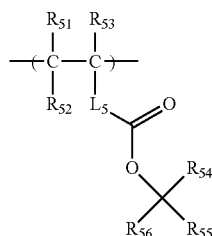
As groups capable of leaving by the action of an acid, e.g., $-\text{C}(\text{R}_{36})(\text{R}_{37})(\text{R}_{38})$, $-\text{C}(\text{R}_{36})(\text{R}_{37})(\text{OR}_{39})$ and $-\text{C}(\text{R}_{01})(\text{R}_{02})(\text{OR}_{39})$ are exemplified.

In the above formulae, each of R_{36} to R_{39} independently represents an alkyl group, a cycloalkyl group, a monovalent aromatic ring group, a group obtained by combining an alkylene group and a monovalent aromatic ring group, or an alkenyl group. R_{36} and R_{37} may be bonded to each other to form a ring.

Each of R_{01} and R_{02} independently represents a hydrogen atom, an alkyl group, a cycloalkyl group, a monovalent aromatic ring group, a group obtained by combining an alkylene group and a monovalent aromatic ring group, or an alkenyl group.

As acid-decomposable groups, preferably a cumyl ester group, an enol ester group, an acetal ester group, and a tertiary alkyl ester group are exemplified, and more preferably a tertiary alkyl ester group is exemplified.

As repeating unit (a), a repeating unit represented by the following formula (V) is more preferred.



In formula (V), each of R_{51} , R_{52} and R_{53} independently represents a hydrogen atom, an alkyl group, a cycloalkyl group, a halogen atom, a cyano group or an alkoxycarbonyl group, and R_{52} may be bonded to L_5 to form a ring, and R_{52} represents an alkylene group in that case.

L_5 represents a single bond or a divalent linking group, and when L_5 forms a ring with R_{52} , L_5 represents a trivalent linking group.

R_{54} represents an alkyl group; each of R_{55} and R_{56} independently represents a hydrogen atom, an alkyl group, a cycloalkyl group, a monovalent aromatic ring group or an aralkyl group, and R_{55} and R_{56} may be bonded to each other

18

to form a ring, provided that R_{55} and R_{56} do not represent a hydrogen atom at the same time.

Formula (V) will be described in further detail below.

As the examples of the alkyl groups represented by each of R_{51} to R_{53} in formula (V), alkyl groups having 20 or less carbon atoms, e.g., a methyl group, an ethyl group, a propyl group, an isopropyl group, an n-butyl group, a sec-butyl group, a hexyl group, a 2-ethylhexyl group, an octyl group and a dodecyl group, each of which groups may have a substituent, are preferably exemplified, more preferably an alkyl group having 8 or less carbon atoms, and especially preferably an alkyl group having 3 or less carbon atoms.

As the alkyl group contained in the alkoxycarbonyl group, the same groups as in the above alkyl groups represented by each of R_{51} to R_{53} are preferred.

The cycloalkyl group may be monocyclic or polycyclic, and a monocyclic cycloalkyl group having 3 to 8 carbon atoms, e.g., a cyclopropyl group, a cyclopentyl group and a cyclohexyl group, each of which groups may have a substituent, are preferably exemplified.

As the halogen atom, a fluorine atom, a chlorine atom, a bromine atom and an iodine atom are exemplified, and a fluorine atom is especially preferred.

As preferred substituents in each of the above groups, e.g., an alkyl group, a cycloalkyl group, an aryl group, an amino group, an amido group, a ureido group, a urethane group, a hydroxyl group, a carboxyl group, a halogen atom, an alkoxy group, a thioether group, an acyl group, an acyloxy group, an alkoxycarbonyl group, a cyano group and a nitro group can be exemplified. The carbon atom number of each substituent is preferably 8 or less.

When R_{52} represents an alkylene group and forms a ring with L_5 , the alkylene group is preferably an alkylene group having 1 to 8 carbon atoms, and as the examples of preferred alkylene groups, for example, a methylene group, an ethylene group, a propylene group, a butylenes group, a hexylene group and an octylene group are exemplified. An alkylene group having 1 to 4 carbon atoms is more preferred, and an alkylene group having 1 or 2 carbon atoms is especially preferred. The ring formed by bonding of R_{52} and L_5 is especially preferably a 5- or 6-membered ring.

As each of R_{51} and R_{53} in formula (V), a hydrogen atom, an alkyl group, or a halogen atom is more preferred, and a hydrogen atom, a methyl group, an ethyl group, a trifluoromethyl group ($-\text{CF}_3$), a hydroxymethyl group ($-\text{CH}_2-\text{OH}$), a chloromethyl group ($-\text{CH}_2-\text{Cl}$) or a fluorine atom ($-\text{F}$) is especially preferred. As R_{52} , a hydrogen atom, an alkyl group, a halogen atom or an alkylene group (forming a ring with L_5) is more preferred, and a hydrogen atom, a methyl group, an ethyl group, a trifluoromethyl group ($-\text{CF}_3$), a hydroxymethyl group ($-\text{CH}_2-\text{OH}$), a chloromethyl group ($-\text{CH}_2-\text{Cl}$), a fluorine atom ($-\text{F}$), a methylene group (forming a ring with L_5), or an ethylene group (forming a ring with L_5) is especially preferred.

As the divalent linking group represented by L_5 , an alkylene group, a divalent aromatic ring group, $-\text{COO}-\text{L}_1-$, $-\text{O}-\text{L}_1-$, and a group formed by combining two or more of these groups are exemplified. Here, L_1 represents an alkylene group, a cycloalkylene group, a divalent aromatic ring group or a group obtained by combining an alkylene group and a divalent aromatic ring group.

L_5 preferably represents a single bond, a group represented by $-\text{COO}-\text{L}_1-$, or a divalent aromatic ring group. L_1 preferably represents an alkylene group having 1 to 5 carbon atoms, and more preferably a methylene group or a propylene group. As the divalent aromatic ring group, a 1,4-phenylene group,

1,3-phenylene group, 1,2-phenylene group, or a 1,4-naphthylene group is preferred, and a 1,4-phenylene group is more preferred.

As the trivalent linking group represented by L_5 in the case where L_5 is bonded to R_{52} and forms a ring, a group obtained by removing one arbitrary hydrogen atom from any of the above-described specific examples of divalent linking groups represented by L_5 can be preferably exemplified.

As the alkyl group represented by each of R_{54} to R_{56} , an alkyl group having 1 to 20 carbon atoms is preferred, more preferably an alkyl group having 1 to 10 carbon atoms, and especially preferably an alkyl group having 1 to 4 carbon atoms, such as a methyl group, an ethyl group, an n-propyl group, an isopropyl group, an n-butyl group, an isobutyl group, or a t-butyl group.

As the cycloalkyl group represented by each of R_{55} and R_{56} , a cycloalkyl group having 3 to 20 carbon atoms is preferred. The cycloalkyl group may be a monocyclic group such as a cyclopentyl group or a cyclohexyl group, or may be a polycyclic group such as a norbornyl group, an adamantyl group, a tetracyclodecanyl group, or a tetracyclododecanyl group.

As the ring formed by bonding of R_{55} to R_{56} to each other, a group having 3 to 20 carbon atoms is preferred, and the group may be a monocyclic group such as a cyclopentyl group or a cyclohexyl group, or may be a polycyclic group such as a norbornyl group, an adamantyl group, a tetracyclodecanyl group, or a tetracyclododecanyl group. When R_{55} and R_{56} are bonded to each other to form a ring, R_{54} preferably represents an alkyl group having 1 to 3 carbon atoms, and a methyl group or an ethyl group is more preferred.

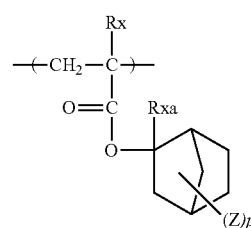
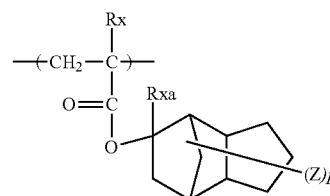
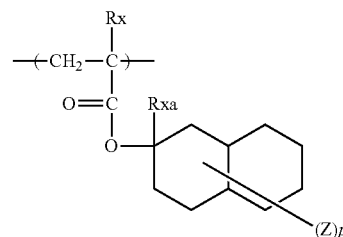
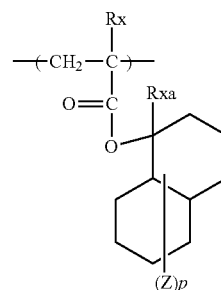
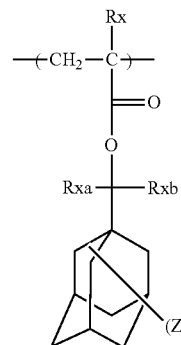
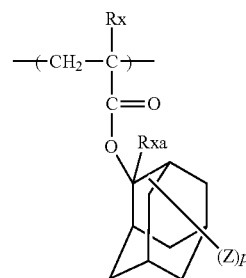
The monovalent aromatic ring group represented by each of R_{55} and R_{56} is preferably an aromatic ring group having 6 to 20 carbon atoms, which group may be monocyclic or polycyclic, and may have a substituent and, for example, a phenyl group, a 1-naphthyl group, a 2-naphthyl group, a 4-methylphenyl group and a 4-methoxyphenyl group are exemplified. When either one of R_{55} and R_{56} represents a hydrogen atom, the other preferably represents a monovalent aromatic ring group.

The aralkyl group represented by each of R_{55} and R_{56} may be monocyclic or polycyclic, and may have a substituent. Preferred is a group having 7 to 21 carbon atoms and, e.g., a benzyl group and a 1-naphthylmethyl group are exemplified.

A monomer corresponding to the repeating unit represented by formula (V) can be synthesized according to ordinary synthesizing methods of polymeric group-containing esters with no particular restriction.

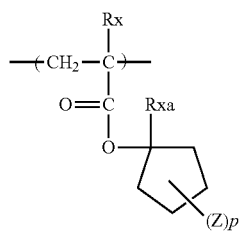
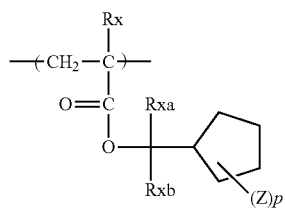
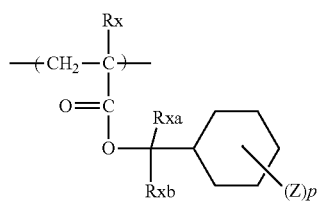
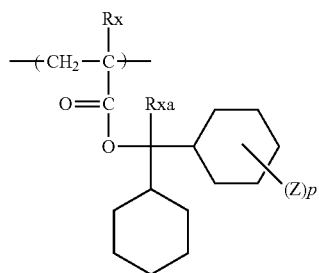
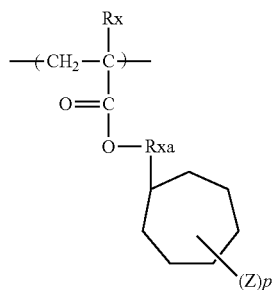
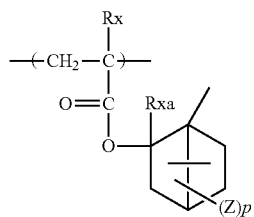
The specific examples of the repeating units (a) represented by formula (V) are shown below, but the invention is not restricted thereto.

In the specific examples, each of R_x and X_{a1} represents a hydrogen atom, CH_3 , CF_3 or CH_2OH . Each of R_{xa} and R_{xb} independently represents an alkyl group having 1 to 4 carbon atoms, an aryl group having 6 to 18 carbon atoms, or an aralkyl group having 7 to 19 carbon atoms. Z represents a substituent. p represents 0 or a positive integer, preferably 0 to 2, and more preferably 0 or 1. When two or more Z are present, they may be the same with or different from each other. As Z , from the point of increasing contrast of dissolution in a developer containing an organic solvent before and after acid-decomposition, groups consisting of hydrogen atoms or carbon atoms alone are preferably exemplified, for example, a straight chain or branched alkyl group and cycloalkyl group are preferred.

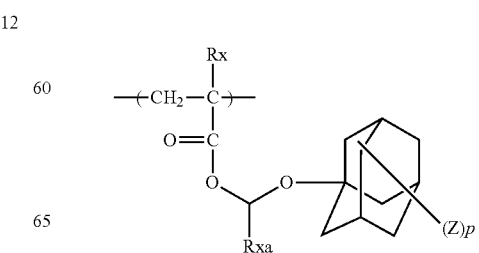
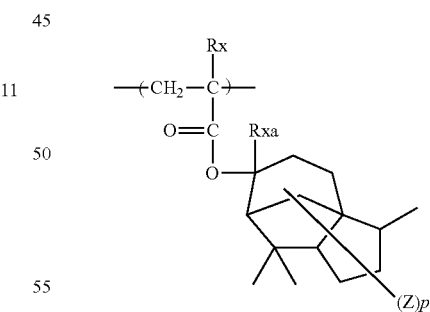
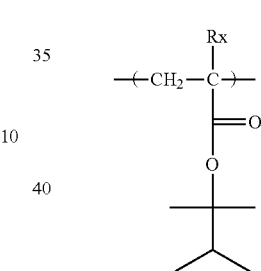
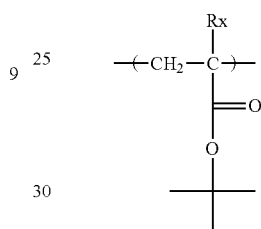
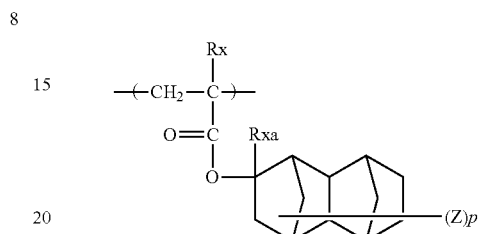
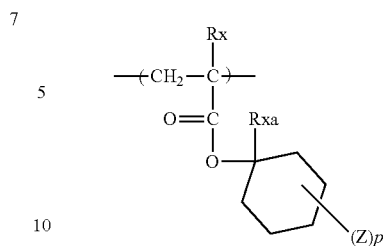


21

-continued

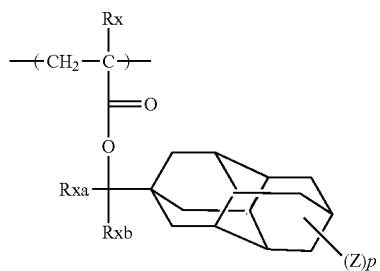
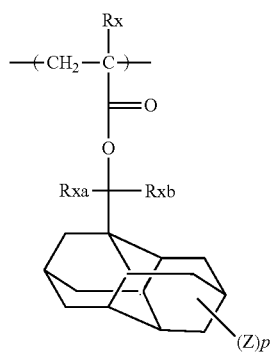
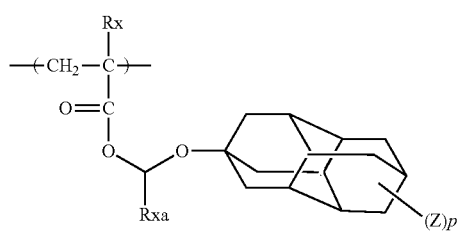
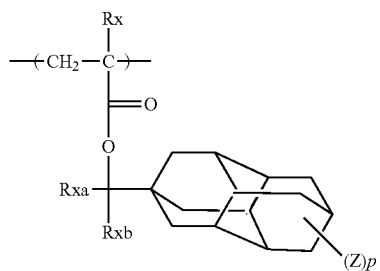
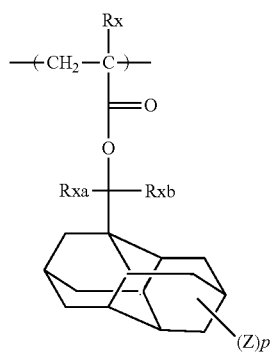
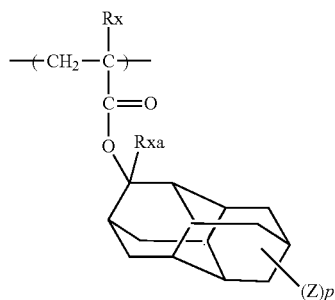
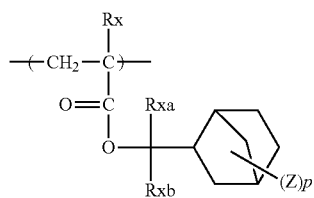
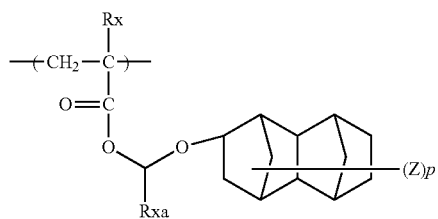
**22**

-continued

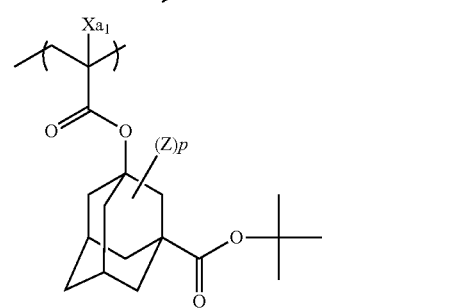
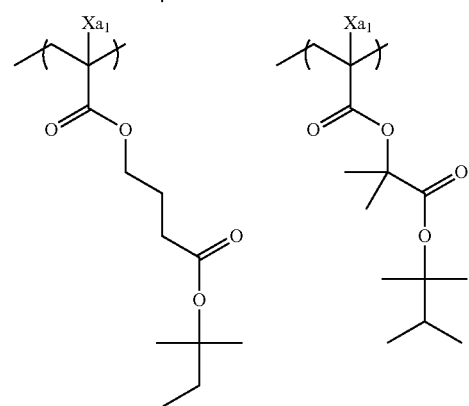
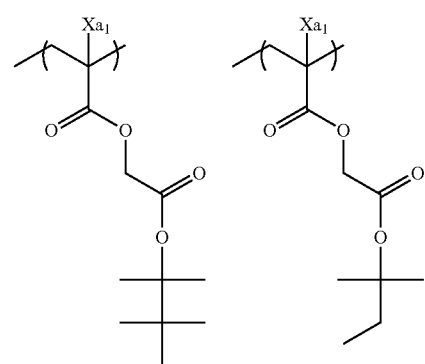
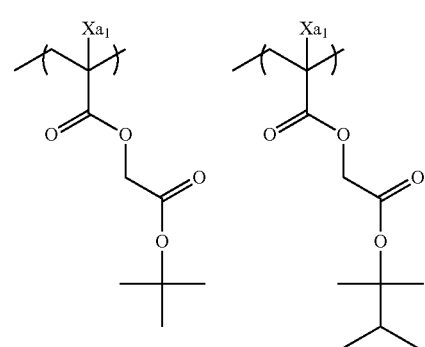
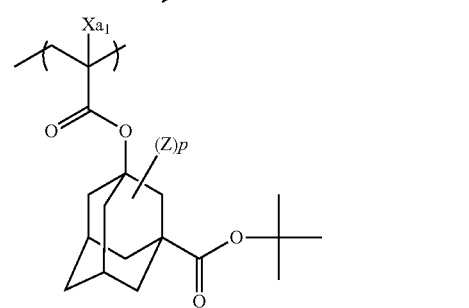
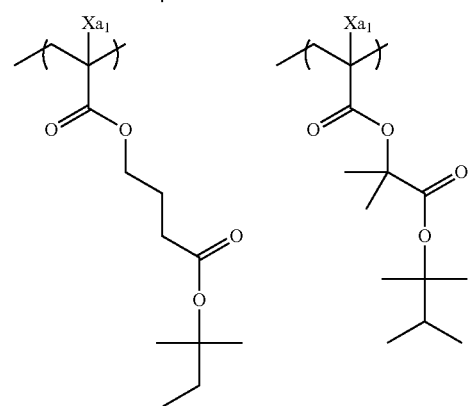
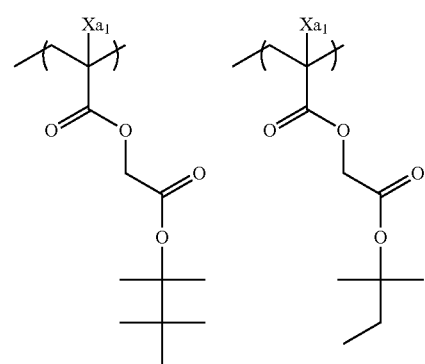
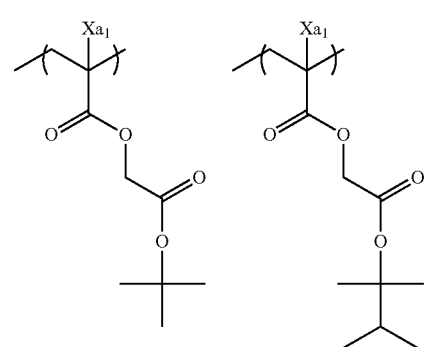
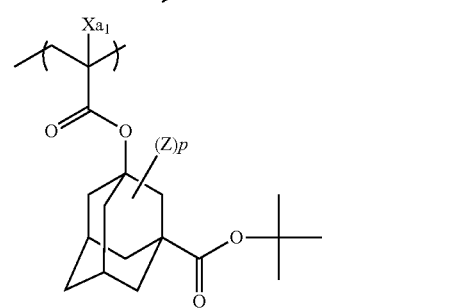
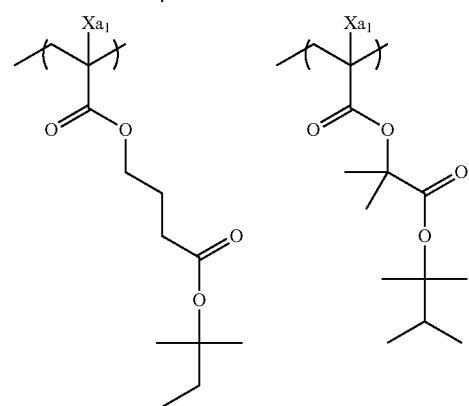
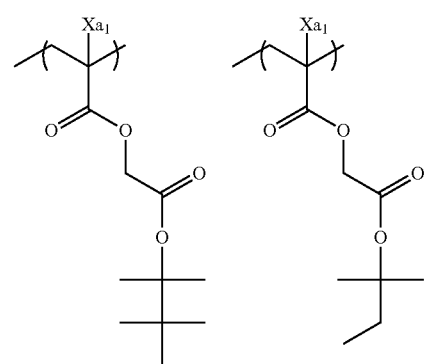
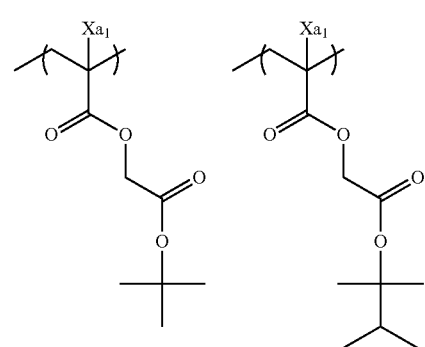
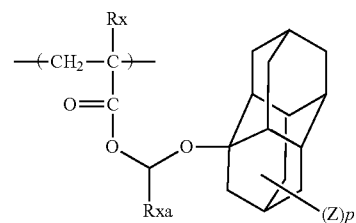


23

-continued

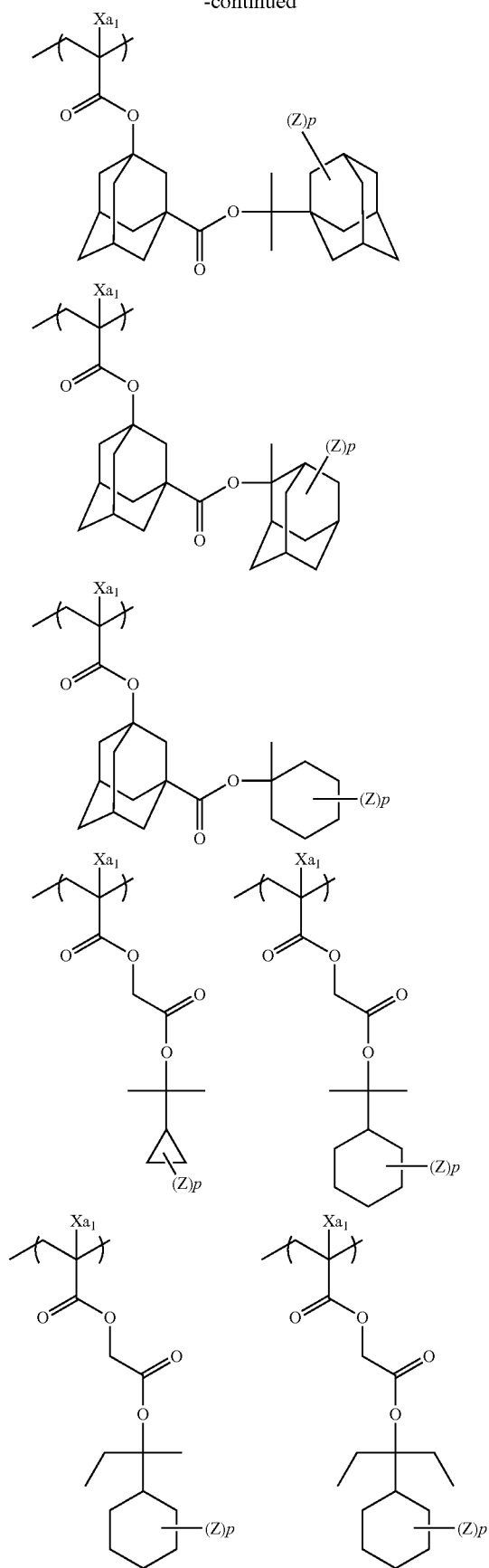
**24**

-continued

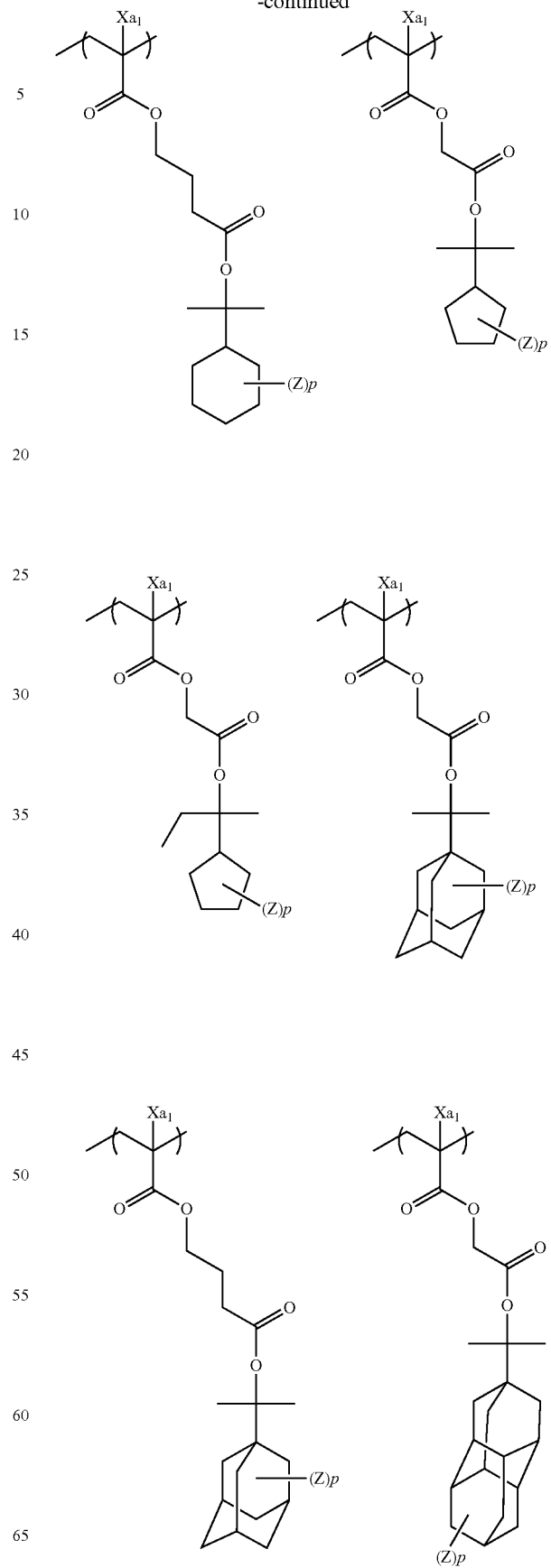


25

-continued

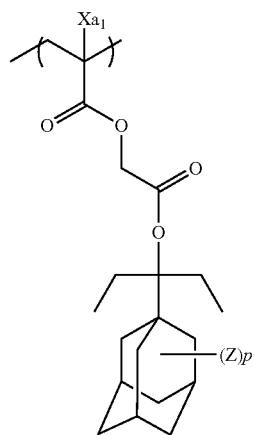
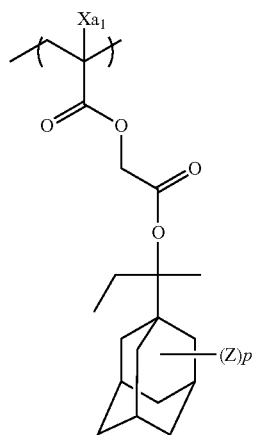
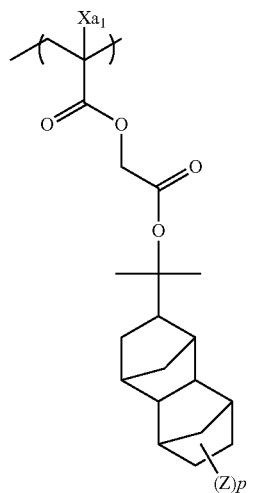
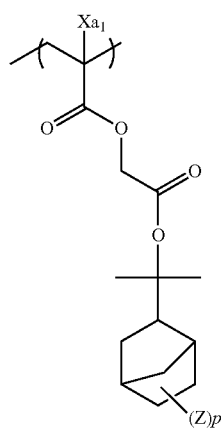
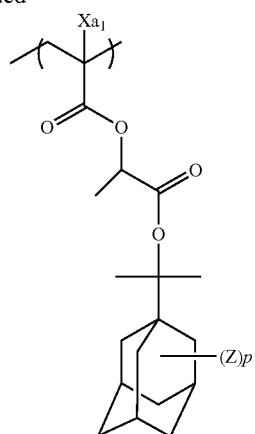
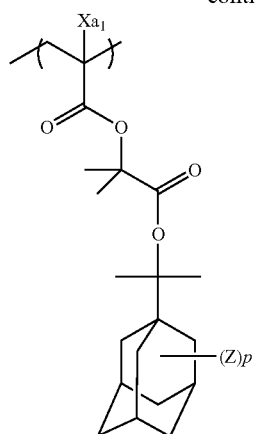
**26**

-continued



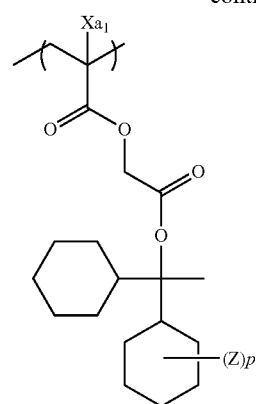
27

-continued

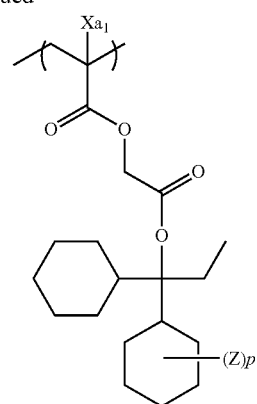
**28**

-continued

5

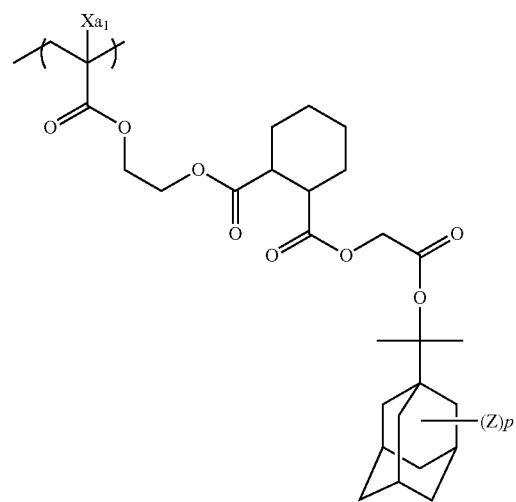


10



15

20

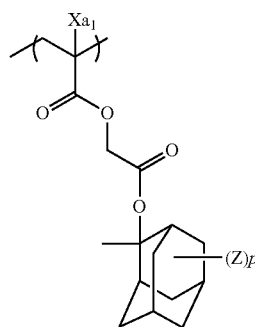


25

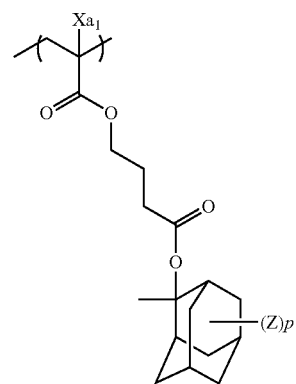
30

35

40

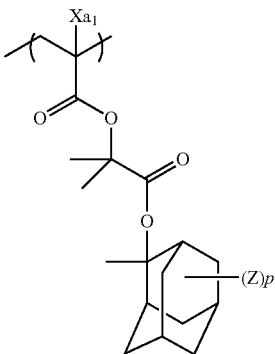


45



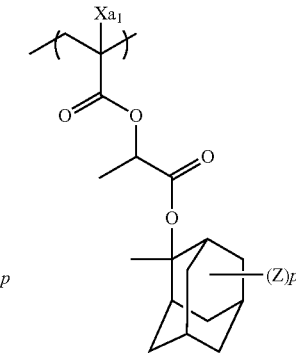
50

55



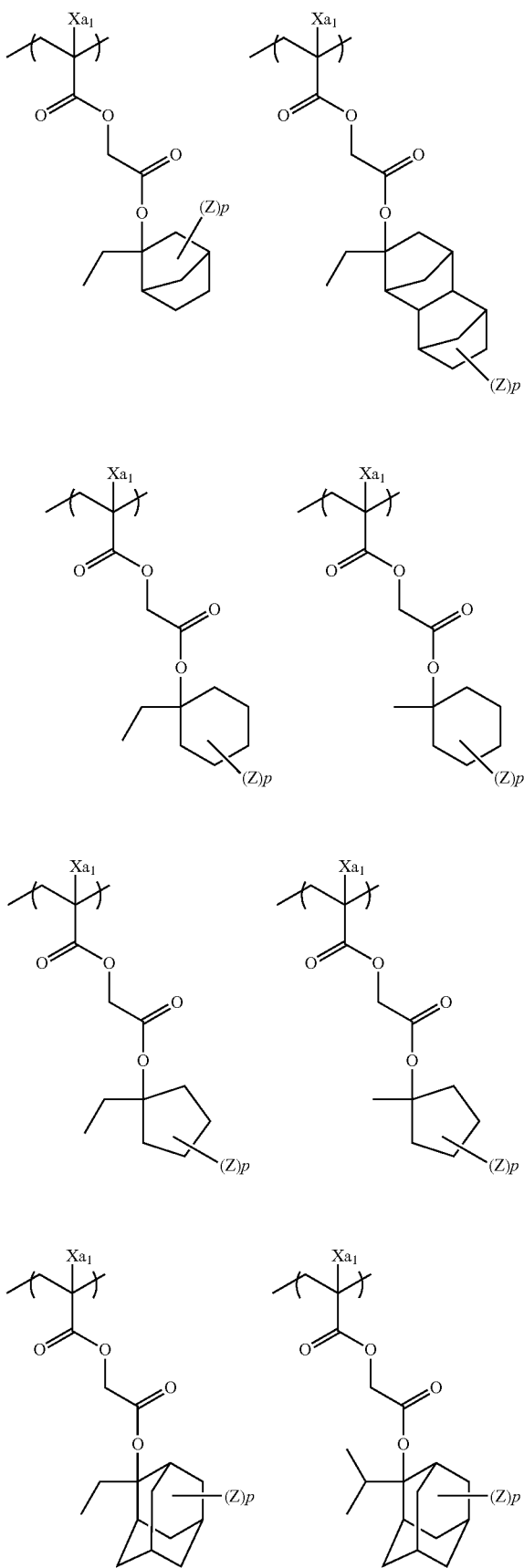
60

65

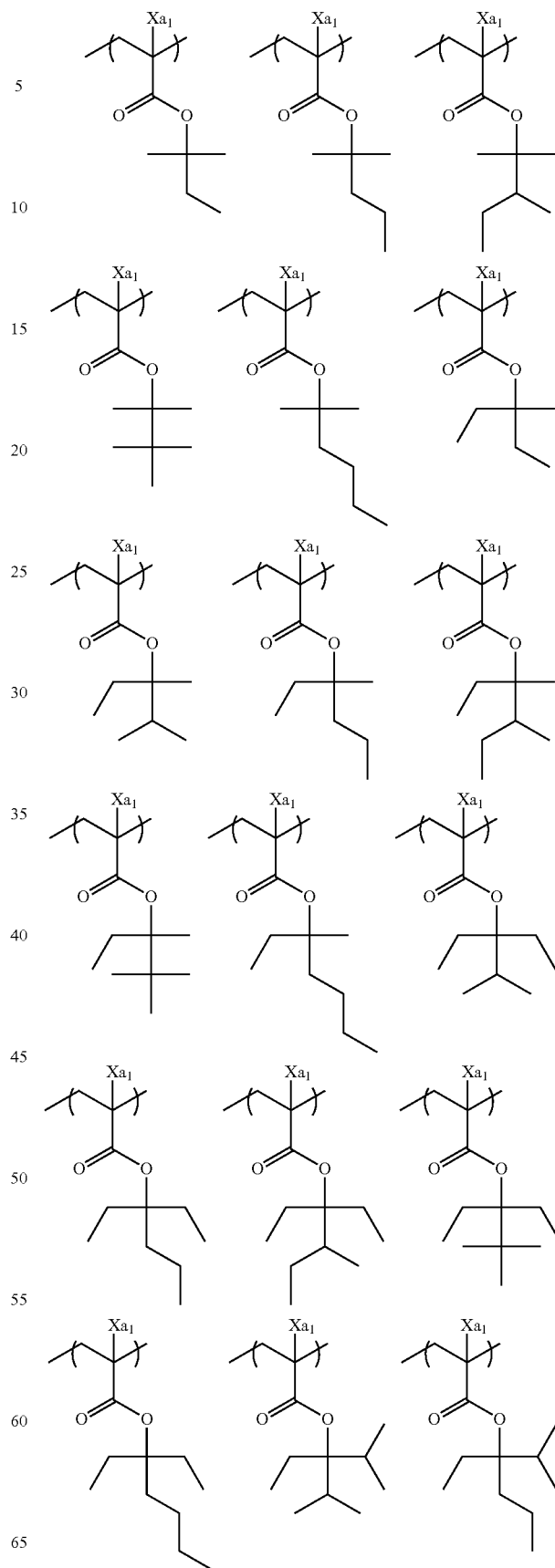


29

-continued

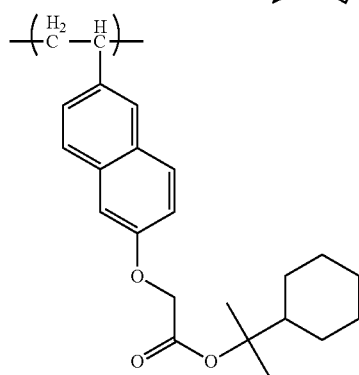
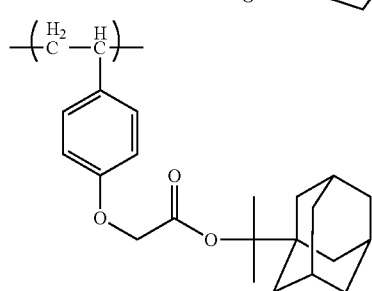
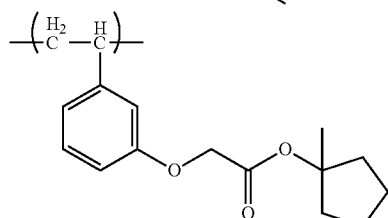
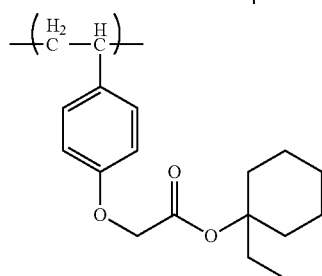
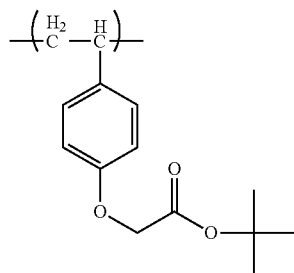
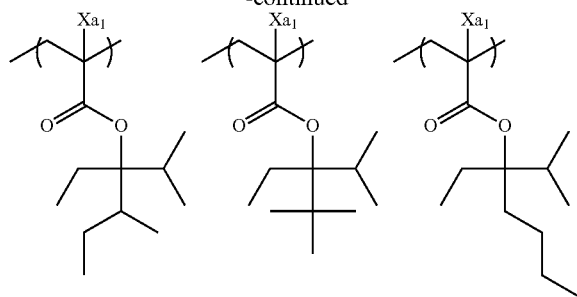
**30**

-continued

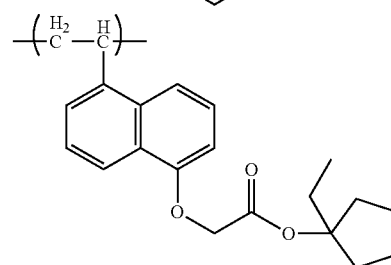
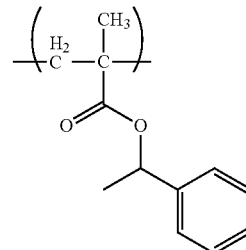
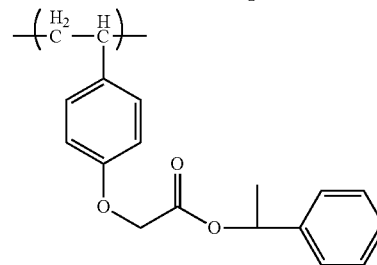
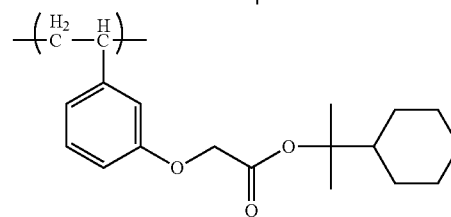
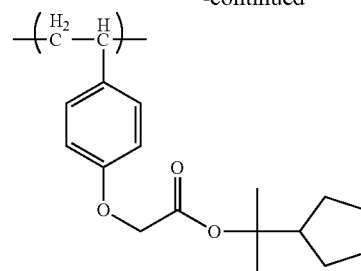


31

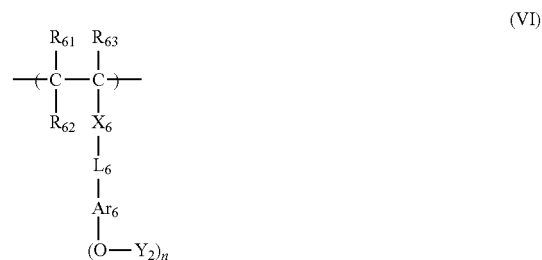
-continued

**32**

-continued



Resin (A) may have a repeating unit represented by the following formula (VI) as repeating unit (a).



In formula (VI), each of R_{61} , R_{62} and R_{63} independently represents a hydrogen atom, an alkyl group, a cycloalkyl

33

group, a halogen atom, a cyano group or an alkoxycarbonyl group. R_{62} may be bonded to Ar_6 to form a ring, and R_{62} in such a case represents a single bond or an alkylene group.

X_6 represents a single bond, $-COO-$ or $-CONR_{64}-$. R_{64} represents a hydrogen atom or an alkyl group.

L_6 represents a single bond or an alkylene group.

Ar_6 represents an (n+1)-valent aromatic ring group, and when Ar_6 is bonded to R_{62} to form a ring, Ar_6 represents an (n+2)-valent aromatic ring group.

Each of Y_2 independently represents a hydrogen atom or a group capable of leaving by the action of an acid in the case where n is equal to or larger than 2, provided that at least one of Y_2 represents a group capable of leaving by the action of an acid.

n represents an integer of 1 to 4.

Formula (VI) will be described in further detail.

As the alkyl group represented by each of R_{61} to R_{63} in formula (VI), an alkyl group having 20 or less carbon atoms, e.g., a methyl group, an ethyl group, a propyl group, an isopropyl group, an n-butyl group, a sec-butyl group, a hexyl group, a 2-ethylhexyl group, an octyl group and a dodecyl group can be preferably exemplified, each of which may have a substituent, and more preferably an alkyl group having 8 or less carbon atoms can be exemplified.

As the alkyl group contained in the alkoxycarbonyl group, the same alkyl groups as in the above R_{61} to R_{63} are preferred.

The cycloalkyl group may be monocyclic or polycyclic, and a monocyclic cycloalkyl group having 3 to 8 carbon atoms, and a cyclopropyl group, a cyclopentyl group and a cyclohexyl group are preferably exemplified, each of which group may have a substituent.

As the halogen atom, a fluorine atom, a chlorine atom, a bromine atom and an iodine atom are exemplified, and more preferably a fluorine atom.

When R_{62} represents an alkylene group, an alkylene group having 1 to 8 carbon atoms, e.g., a methylene group, an ethylene group, a propylene group, a butylenes group, a hexylene group and an octylene group are preferably exemplified, each of which may have a substituent.

As the alkyl group of R_{64} in $-CONR_{64}-$ (wherein R_{64} represents a hydrogen atom or an alkyl group) represented by X_6 , the same alkyl groups as in the alkyls group represented by each of R_{61} to R_{63} are exemplified.

X_6 preferably represents a single bond, $-COO-$ or $-CONH-$, and more preferably a single bond or $-COO-$.

As the alkylene group represented by L_6 , preferably an alkylene group having 1 to 8 carbon atoms, e.g., a methylene group, an ethylene group, a propylene group, a butylenes group, a hexylene group, and an octylene group are exemplified, each of which group may have a substituent. The ring formed by bonding of R_{62} and L_6 is especially preferably a 5- or 6-membered ring.

Ar_6 represents an (n+1)-valent aromatic ring group. The divalent aromatic ring group in the case where n is 1 may have a substituent. For example, an arylene group having 6 to 18 carbon atoms, e.g., a phenylene group, a tolylene group and a naphthylene group, and a divalent aromatic ring group containing a heterocyclic ring such as thiophene, furan, pyrrole, benzothiophene, benzofuran, benzopyrrole, triazine, imidazole, benzimidazole, triazole, thiadiazole or thiazole are preferably exemplified.

As the specific example of the (n+1)-valent aromatic ring group in the case where n represents an integer of 2 or more, a group obtained by removing arbitrary (n-1)-number of hydrogen atom(s) from any of the above-described specific examples of the divalent aromatic ring groups can be preferably exemplified.

34

The (n+1)-valent aromatic ring group may further have a substituent.

As the substituents that the above alkyl group, cycloalkyl group, alkoxycarbonyl group, alkylene group, and (n+1)-valent aromatic ring group may have, the same examples with the substituents that each group represented by R_{51} , R_{52} or R_{53} in formula (V) above may have are exemplified as specific examples.

n is preferably 1 or 2, and more preferably 1.

Each of n-number of Y_2 independently represents a hydrogen atom or a group capable of leaving by the action of an acid, but at least one of n-number of Y_2 represents a group capable of leaving by the action of an acid.

As group Y_2 capable of leaving by the action of an acid, e.g., $-C(R_{36})(R_{37})(R_{38})$, $-C(=O)-O-C(R_{36})(R_{37})(R_{38})$, $-C(R_{01})(R_{02})(OR_{39})$, $-C(R_{01})(R_{02})-C(=O)-O-C(R_{36})(R_{37})(R_{38})$, and $-CH(R_{36})(Ar)$ are exemplified.

In the above formulae, each of R_{36} to R_{39} independently represents an alkyl group, a cycloalkyl group, a monovalent aromatic ring group, a group obtained by combining an alkylene group and a monovalent aromatic ring group, or an alkenyl group. R_{36} and R_{37} may be bonded to each other to form a ring.

Each of R_{01} and R_{02} independently represents a hydrogen atom, an alkyl group, a cycloalkyl group, a monovalent aromatic ring group, a group obtained by combining an alkylene group and a monovalent aromatic ring group, or an alkenyl group.

Ar represents a monovalent aromatic ring group.

The alkyl group represented by each of R_{36} to R_{39} , R_{01} and R_{02} is preferably an alkyl group having 1 to 8 carbon atoms, e.g., a methyl group, an ethyl group, a propyl group, an n-butyl group, a sec-butyl group, a hexyl group, and an octyl group are exemplified.

The cycloalkyl group represented by each of R_{36} to R_{39} , R_{01} and R_{02} may be monocyclic or polycyclic. As the monocyclic cycloalkyl group, a cycloalkyl group having 3 to 8 carbon atoms is preferred and, e.g., a cyclopropyl group, a cyclobutyl group, a cyclopentyl group, a cyclohexyl group, and a cyclooctyl group can be exemplified. As the polycyclic cycloalkyl group, a cycloalkyl group having 6 to 20 carbon atoms is preferred and, e.g., an adamantyl group, a norbornyl group, an isoboronyl group, a camphanlyl group, a dicyclopentyl group, an α -pinyl group, a tricyclodecanyl group, a tetracyclododecyl group, and an androstanyl group can be exemplified. The carbon atoms in the cycloalkyl group may be partially replaced by a hetero atom such as an oxygen atom.

The monovalent aromatic ring group represented by each of R_{36} to R_{39} , R_{01} , R_{02} and Ar is preferably a monovalent aromatic ring group having 6 to 10 carbon atoms. For example, an aryl group, e.g., a phenyl group, a naphthyl group, and an anthryl group, and a divalent aromatic ring group containing a heterocyclic ring such as thiophene, furan, pyrrole, benzothiophene, benzofuran, benzopyrrole, triazine, imidazole, benzimidazole, triazole, thiadiazole, or thiazole can be exemplified.

As the group obtained by combining an alkylene group and a monovalent aromatic ring group represented by each of R_{36} to R_{39} , R_{01} and R_{02} is preferably an aralkyl group having 7 to 12 carbon atoms and, for example, a benzyl group, a phenethyl group, and a naphthylmethyl group are exemplified.

The alkenyl group represented by each of R_{36} to R_{39} , R_{01} and R_{02} is preferably an alkenyl group having 2 to 8 carbon atoms and, for example, a vinyl group, an allyl group, a butenyl group and a cyclohexenyl group can be exemplified.

35

The ring formed by bonding of R_{36} and R_{37} to each other may be monocyclic or polycyclic. As the monocyclic type, a cycloalkyl structure having 3 to 8 carbon atoms is preferred and, e.g., a cyclopropane structure, a cyclobutane structure, a cyclopentane structure, a cyclohexane structure, a cycloheptane structure, and a cyclooctane structure can be exemplified. As the polycyclic type, a cycloalkyl structure having 6 to 20 carbon atoms is preferred and, e.g., an adamantane structure, a norbornane structure, a dicyclopentane structure, a tricyclodecane structure, and a tetracyclododecane structure can be exemplified. The carbon atoms in the cycloalkyl structure may be partially substituted with a hetero atom such as an oxygen atom.

Each group represented by each of R_{36} to R_{39} , R_{01} , R_{02} and Ar may have a substituent. As the substituents, e.g., an alkyl group, a cycloalkyl group, an aryl group, an amino group, an amido group, a ureido group, a urethane group, a hydroxyl group, a carboxyl group, a halogen atom, an alkoxy group, a thioether group, an acyl group, an acyloxy group, an alkoxy-carbonyl group, a cyano group, and a nitro group can be exemplified. The carbon atom number of each substituent is preferably 8 or less.

It is more preferred for group Y_2 capable of leaving by the action of an acid to have a structure represented by the following formula (VI-A).



In formula (VI-A), each of L_1 and L_2 independently represents a hydrogen atom, an alkyl group, a cycloalkyl group, a monovalent aromatic ring group, or a group obtained by combining an alkylene group and a monovalent aromatic ring group.

M represents a single bond or a divalent linking group.

Q represents an alkyl group, a cycloalkyl group which may contain a hetero atom, a monovalent aromatic ring group which may contain a hetero atom, an amino group, an ammonium group, a mercapto group, a cyano group or an aldehyde group.

At least two of Q, M and L_1 may be bonded to form a ring (preferably a 5- or 6-membered ring).

The alkyl group represented by each of L_1 and L_2 is, for example, an alkyl group having 1 to 8 carbon atoms, and specifically a methyl group, an ethyl group, a propyl group, an n-butyl group, a sec-butyl group, a hexyl group, and an octyl group can be preferably exemplified.

The cycloalkyl group represented by each of L_1 and L_2 is, for example, a cycloalkyl group having 3 to 15 carbon atoms, and specifically a cyclopentyl group, a cyclohexyl group, a norbornyl group and an adamantyl group can be preferably exemplified.

The monovalent aromatic ring group represented by each of L_1 and L_2 is, for example, an aryl group having 6 to 15 carbon atoms, and specifically a phenyl group, a tolyl group, a naphthyl group, and an anthryl group can be preferably exemplified.

The group obtained by combining an alkylene group and a monovalent aromatic ring group represented by each of L_1 and L_2 is, for example, a group having 6 to 20 carbon atoms, and an aralkyl group such as a benzyl group and a phenethyl group can be exemplified.

36

As the divalent linking group represented by M, for example, an alkylene group (e.g., a methylene group, an ethylene group, a propylene group, a butylene group, a hexylene group, and an octylene group), a cycloalkylene group (e.g., a cyclopentylene group, a cyclohexylene group, and an adamantylene group), an alkenylene group (e.g., an ethylene group, a propenylene group, and a butenylene group), a divalent aromatic ring group (e.g., a phenylene group, a tolylene group, and a naphthylene group), $-S-$, $-O-$, $-CO-$, $-SO_2-$, $-N(R_0)-$, and divalent linking groups obtained by combining a plurality of these groups are exemplified. R_0 represents a hydrogen atom or an alkyl group (e.g., an alkyl group having 1 to 8 carbon atoms, specifically a methyl group, an ethyl group, a propyl group, an n-butyl group, a sec-butyl group, a hexyl group, and an octyl group).

The alkyl group represented by Q is the same with each group represented by L_1 and L_2 .

As the alicyclic hydrocarbon group not containing a hetero atom and the monovalent aromatic ring group not containing a hetero atom in the cycloalkyl group which may contain a hetero atom and the monovalent aromatic ring group which may contain a hetero atom represented by Q, the cycloalkyl group and the monovalent aromatic ring group represented by L_1 and L_2 are exemplified, and preferably the carbon atom number is 3 to 15.

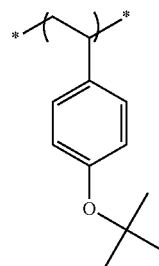
As the cycloalkyl group containing a hetero atom and the monovalent aromatic ring group containing a hetero atom, groups having a heterocyclic structure, e.g., thiirane, cyclothioran, thiophene, furan, pyrrole, benzothiophene, benzofuran, benzopyrrole, triazine, imidazole, benzimidazole, triazole, thiadiazole, thiazole, and pyrrolidone are exemplified, but they are not restricted thereto so long as they have a structure generally called a heterocyclic structure (a ring formed by carbon atoms and hetero atoms, or a ring formed by hetero atoms).

As the ring which may be formed by bonding of at least two of Q, M and L_1 , a case where at least two of Q, M and L_1 are bonded to form, e.g., a propylene group or a butylenes group to form a 5- or 6-membered ring containing oxygen atoms is exemplified.

Each group represented by L_1 , L_2 , M and Q in formula (VI-A) may have a substituent and, for example, the substituents exemplified above as the examples of the substituents that each of R_{36} to R_{39} , R_{01} , R_{02} and Ar may have are exemplified. The carbon atom number of the substituents is preferably 8 or less.

As the group represented by $-M-Q$, a group comprised of 1 to 30 carbon atoms is preferred, and a group comprised of 5 to 20 carbon atoms is more preferred.

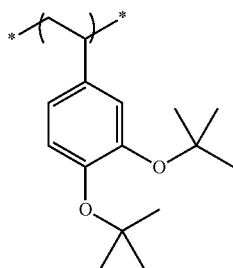
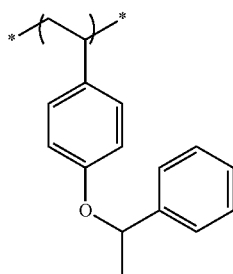
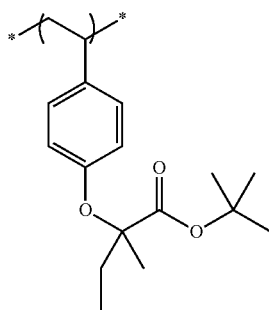
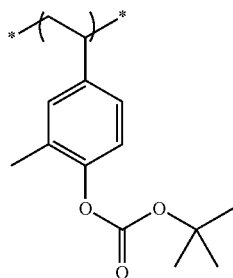
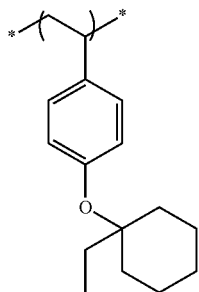
As the preferred specific examples of repeating unit (a), the specific examples of the repeating unit represented by formula (VI) are shown below, but the invention is not restricted thereto.



(VI-1)

37

-continued

**38**

-continued

(VI-2)

5

10

(VI-3)

20

25

(VI-4)

30

35

40

(VI-5)

45

50

55

(VI-6)

60

65

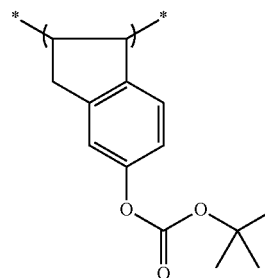
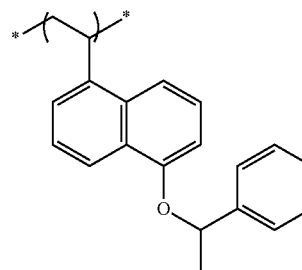
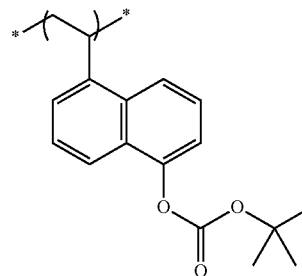
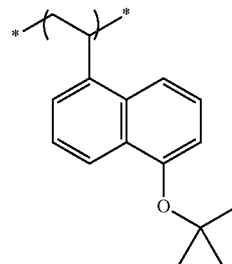
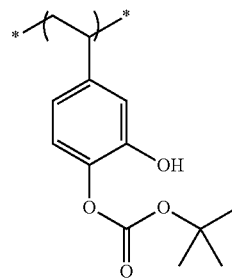
(VI-7)

(VI-8)

(VI-9)

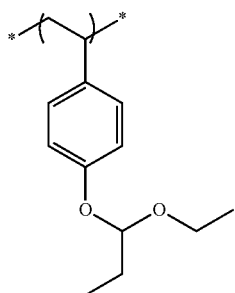
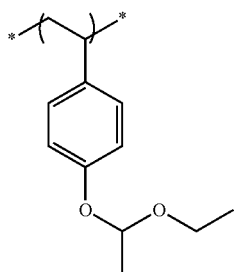
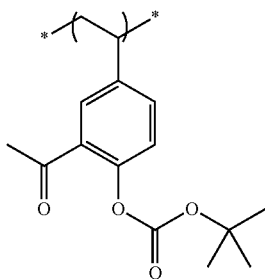
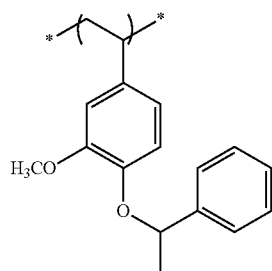
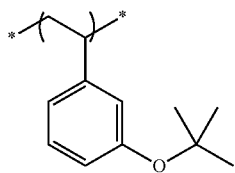
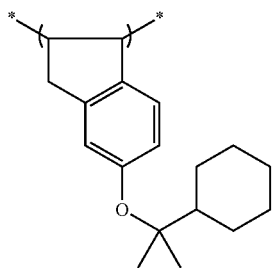
(VI-10)

(VI-11)



39

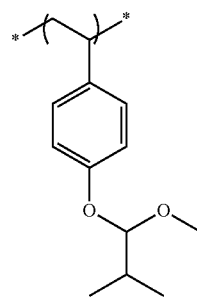
-continued

**40**

-continued

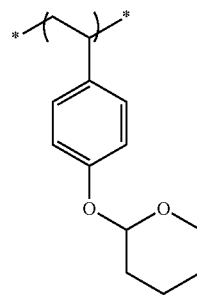
(VI-12)

5



(VI-13)

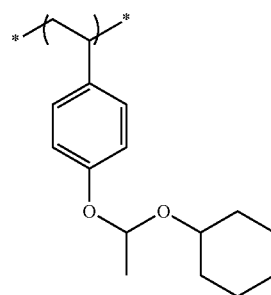
15



(VI-14)

20

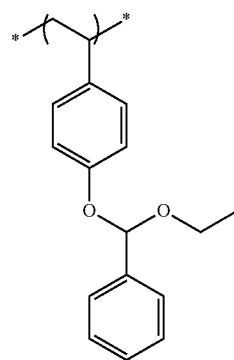
25



(VI-15)

35

40



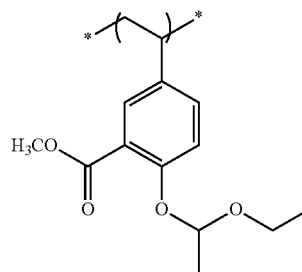
(VI-16)

45

50

(VI-17)

55



60

65

(VI-18)

(VI-19)

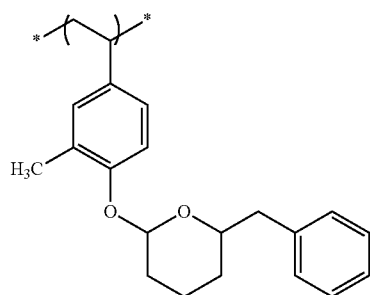
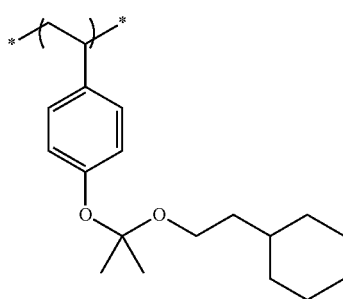
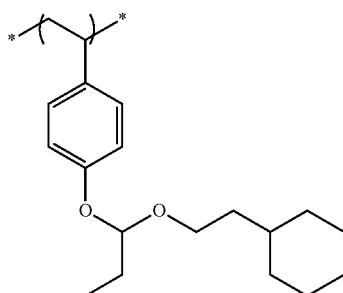
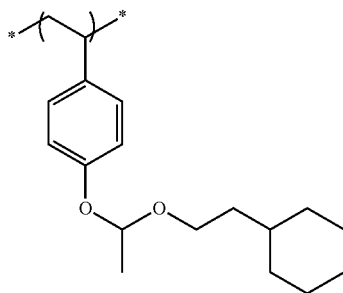
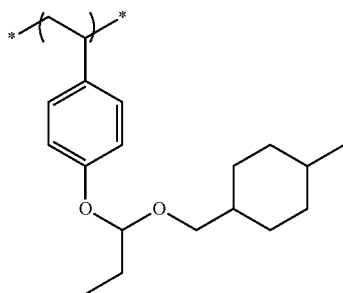
(VI-20)

(VI-21)

(VI-22)

41

-continued

**42**

-continued

(VI-23)

5

10

(VI-24)

15

20

25

(VI-25)

30

35

40

(VI-26)

45

50

(VI-27)

55

60

65

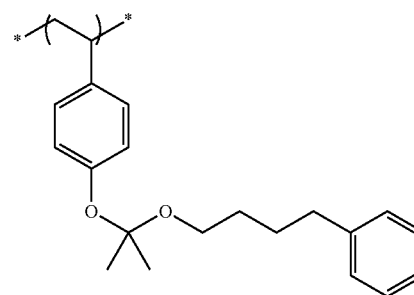
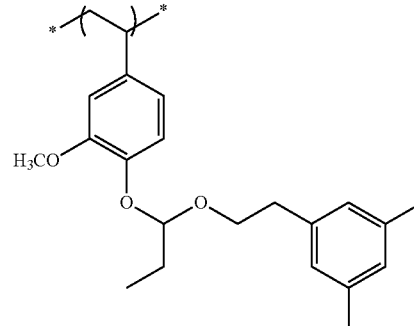
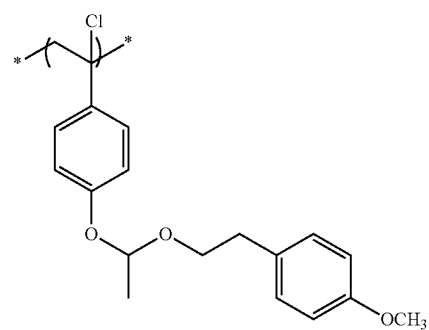
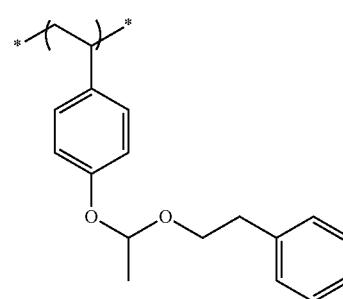
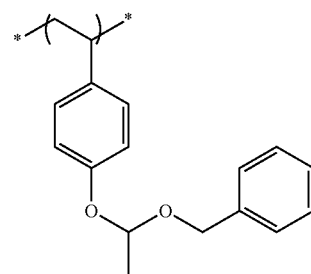
(VI-28)

(VI-29)

(VI-30)

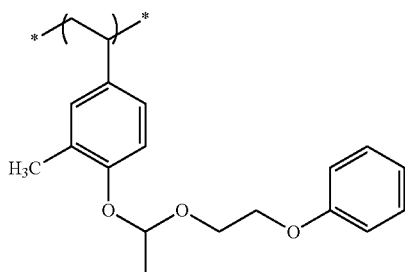
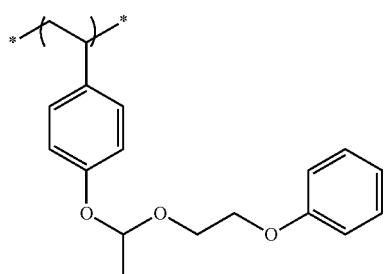
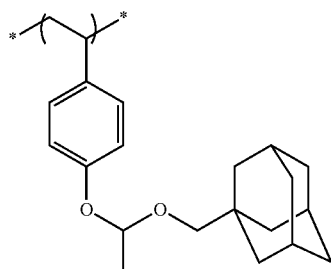
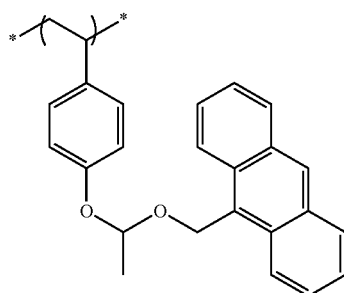
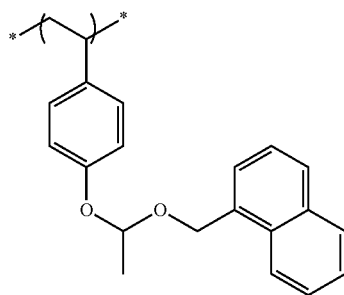
(VI-31)

(VI-32)



43

-continued

**44**

-continued

(VI-33)

(VI-38)

5

10

15

(VI-34)

(VI-39)

20

25

(VI-35)

(VI-40)

35

40

(VI-36)

(VI-41)

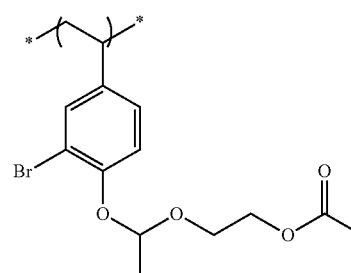
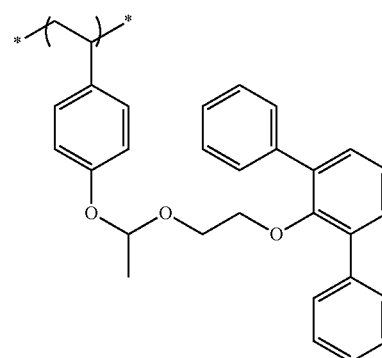
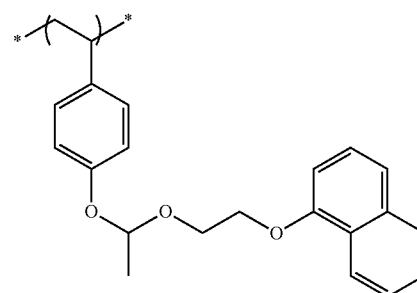
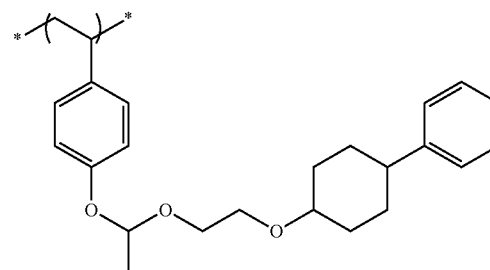
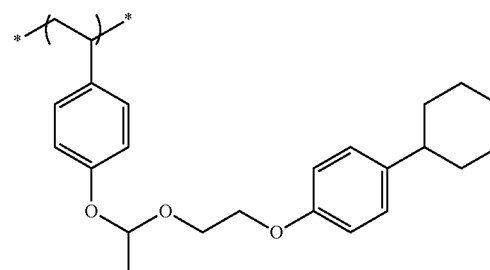
50

(VI-37)

(VI-42)

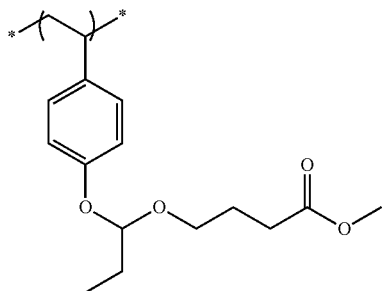
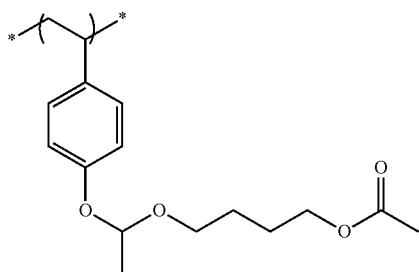
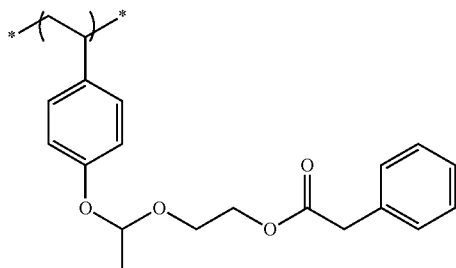
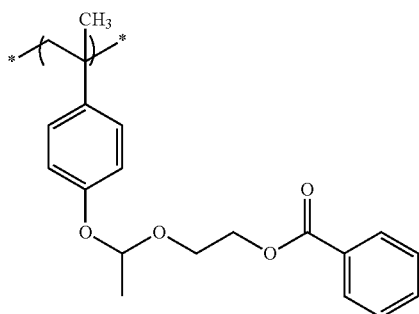
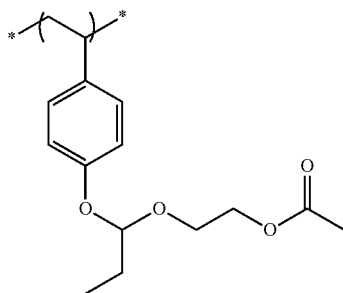
60

65

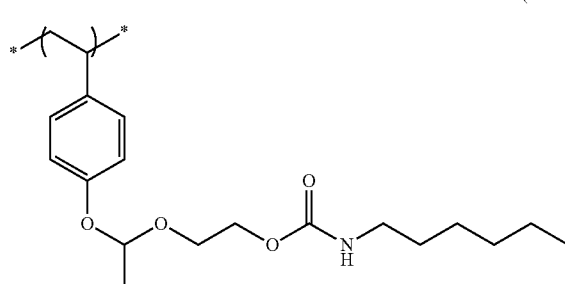
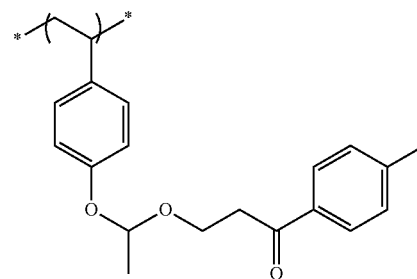
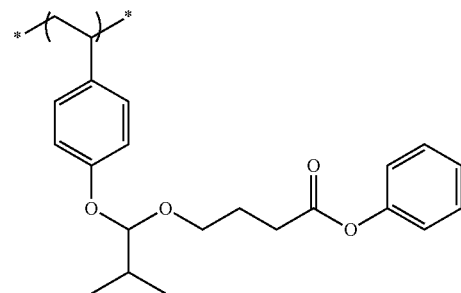
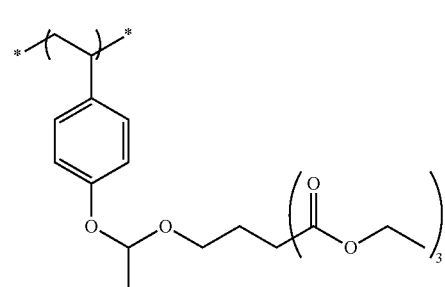
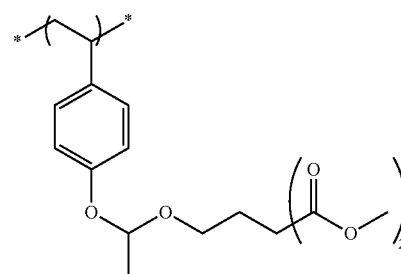


45

-continued

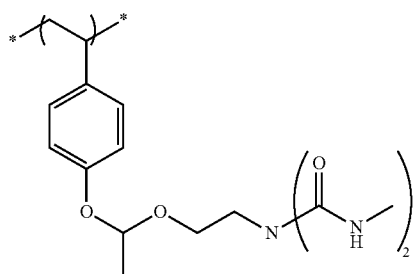
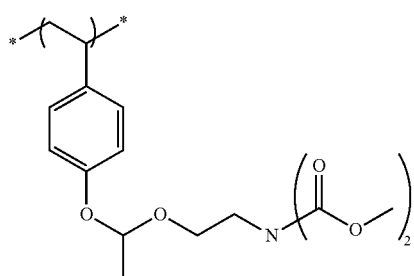
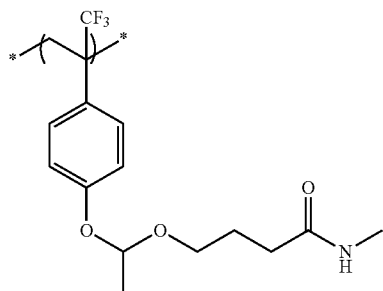
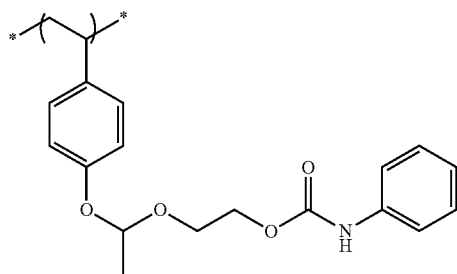
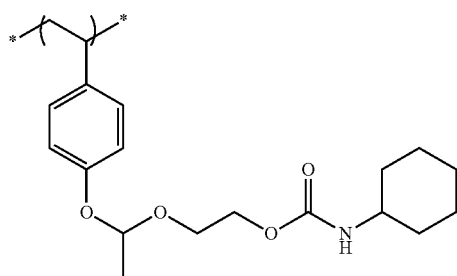
**46**

-continued



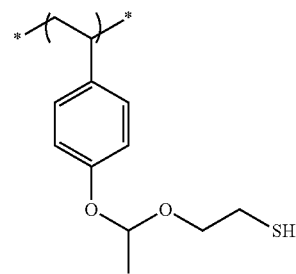
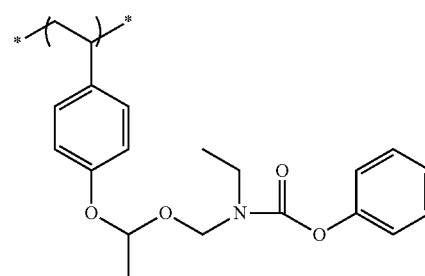
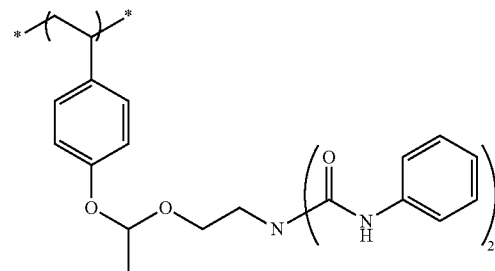
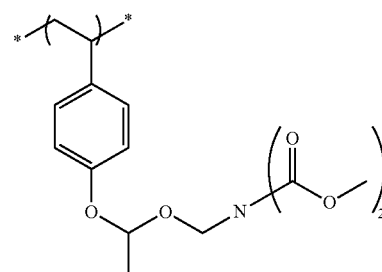
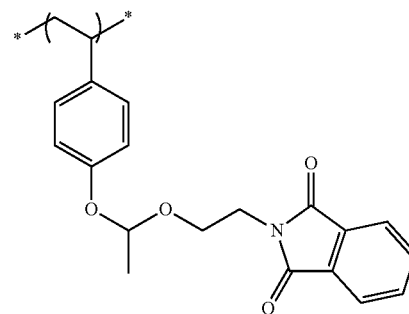
47

-continued



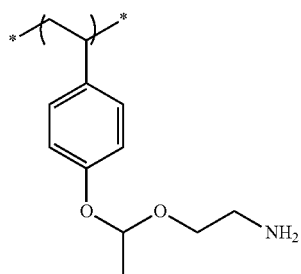
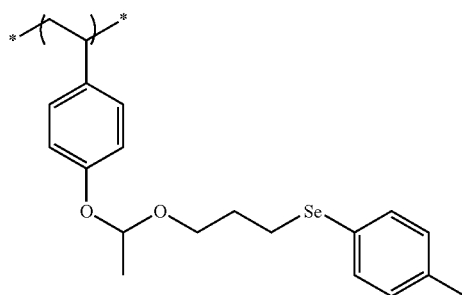
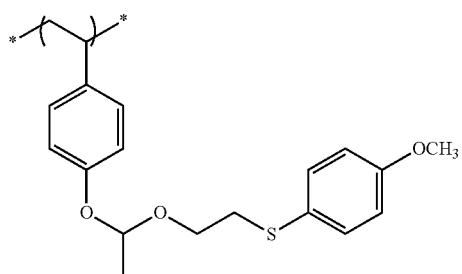
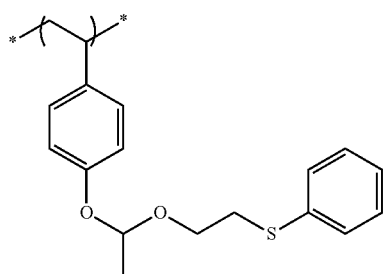
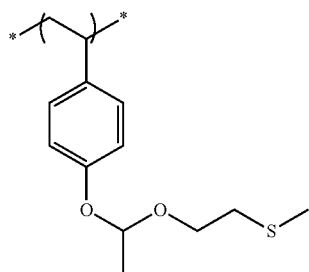
48

-continued

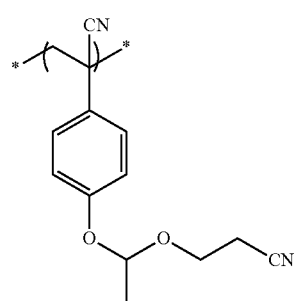
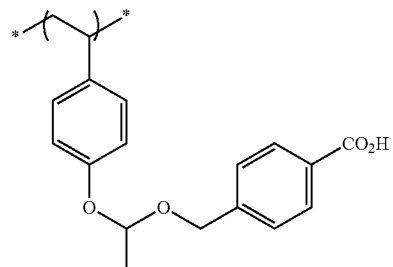
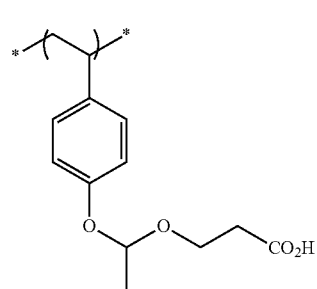
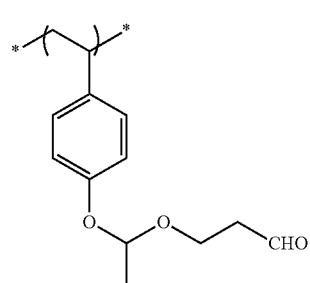
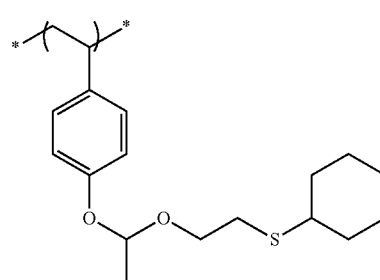


49

-continued

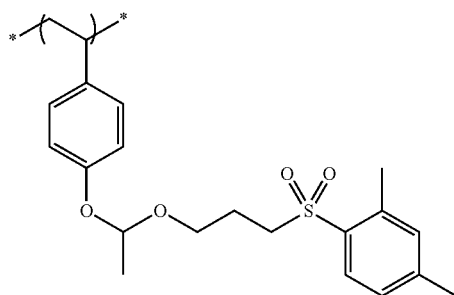
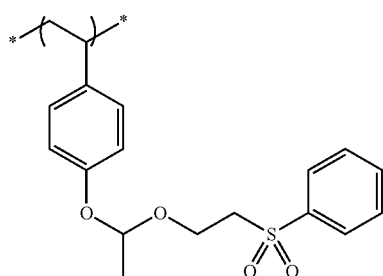
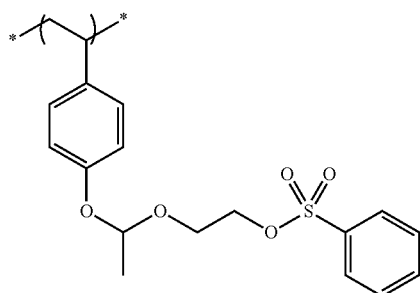
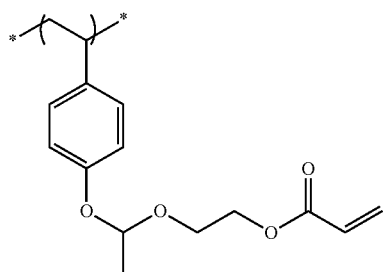
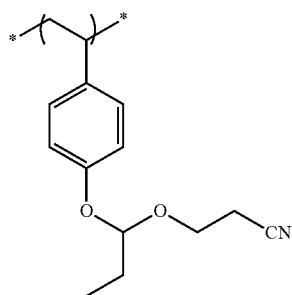
**50**

-continued

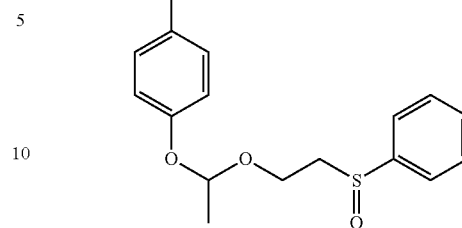


51

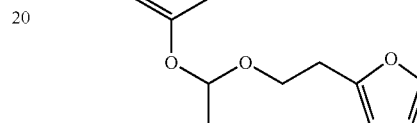
-continued

**52**

-continued

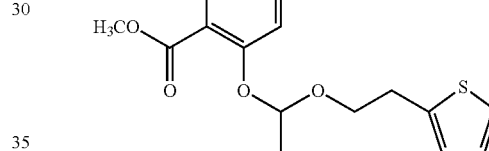


(VI-79)



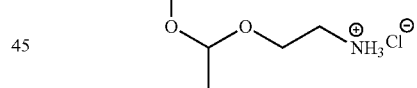
(VI-80)

(VI-81)

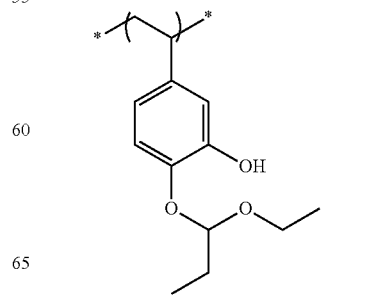


(VI-82)

(VI-83)

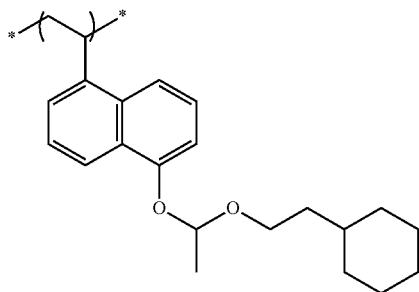
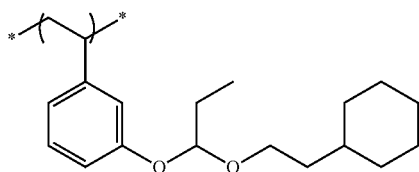
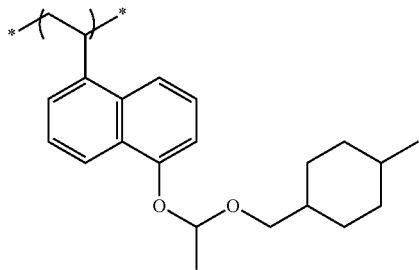
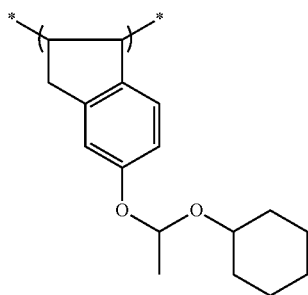
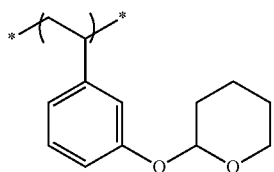
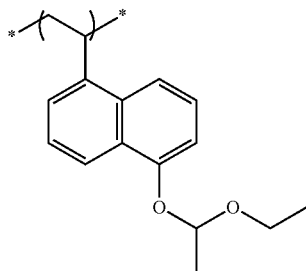


(VI-83)

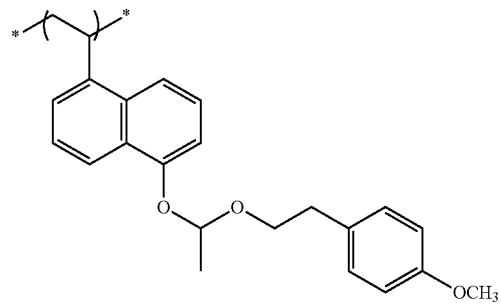
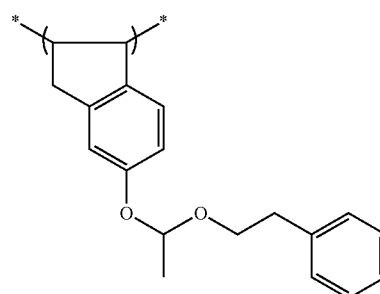
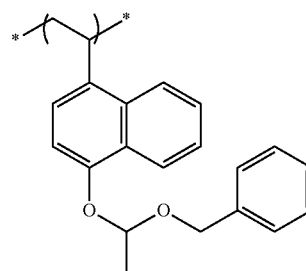
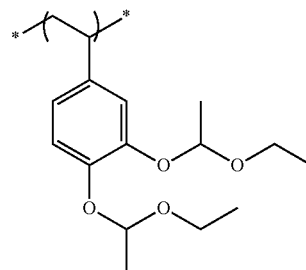
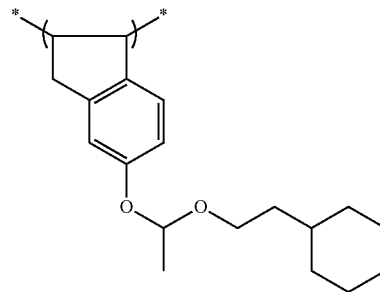


53

-continued

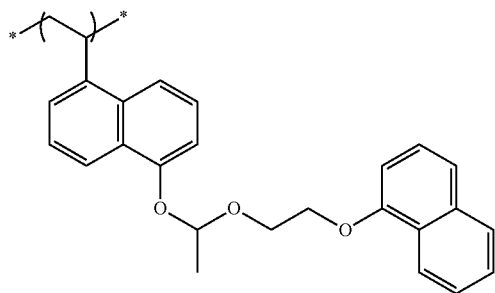
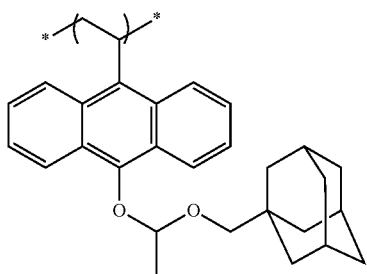
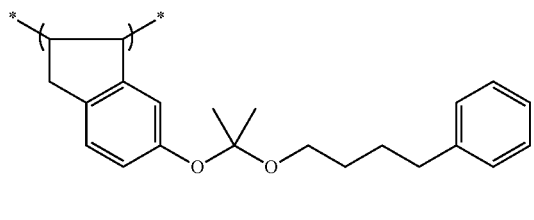
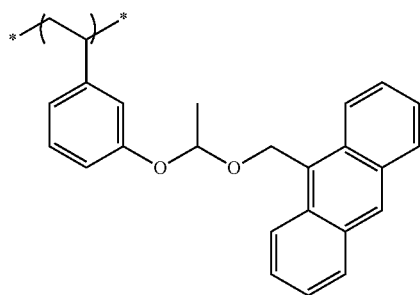
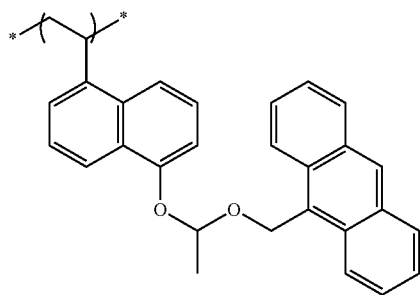
**54**

-continued

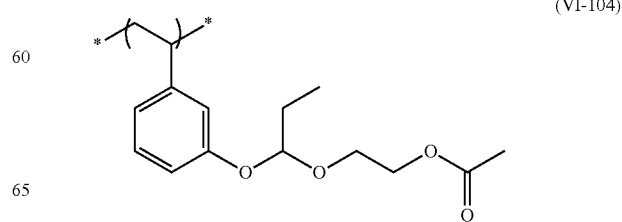
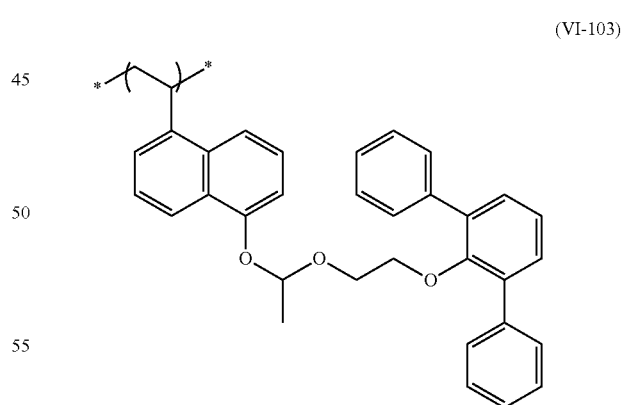
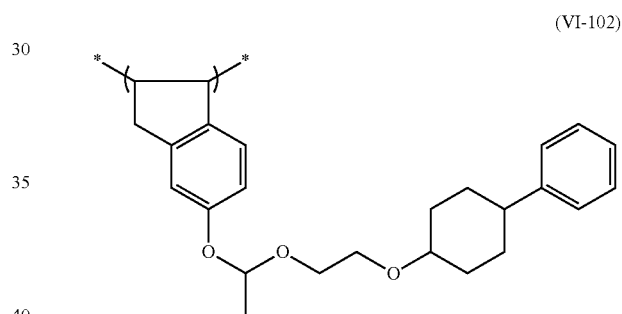
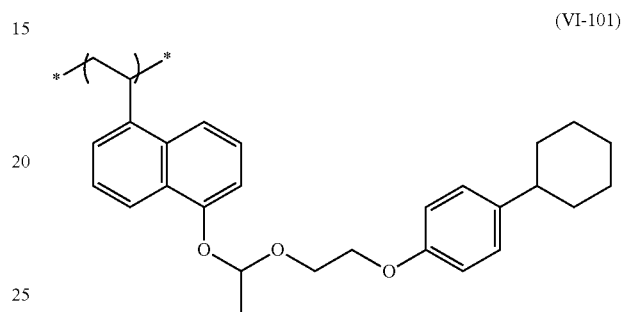
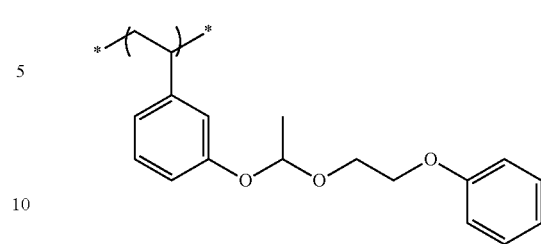


55

-continued

**56**

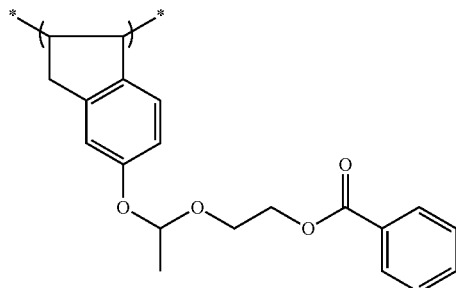
-continued



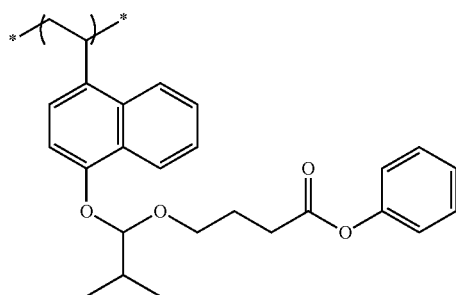
57

-continued

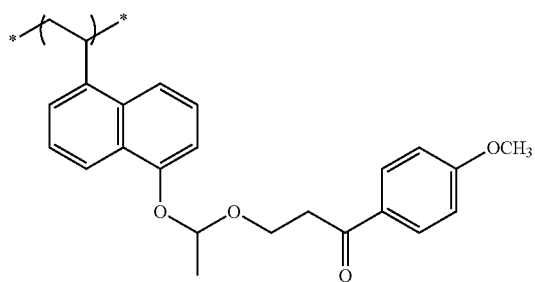
(VI-105)



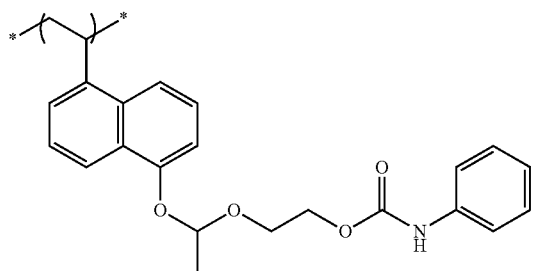
(VI-106)



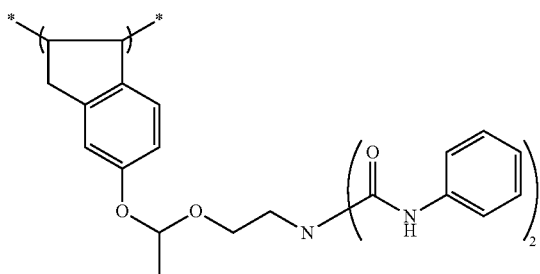
(VI-107)



(VI-108)

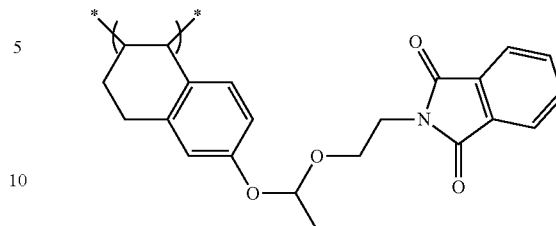


(VI-109)

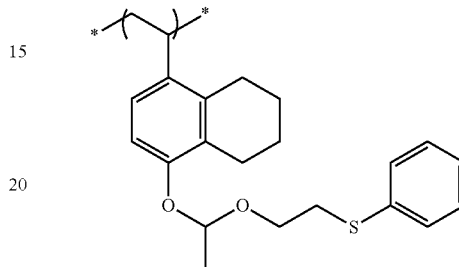
**58**

-continued

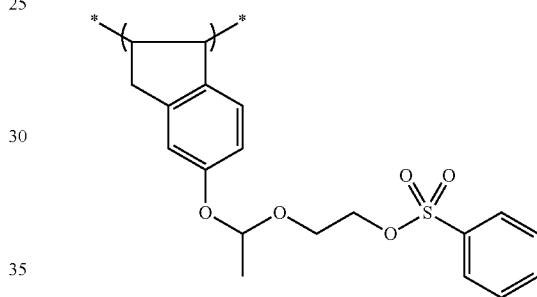
(VI-110)



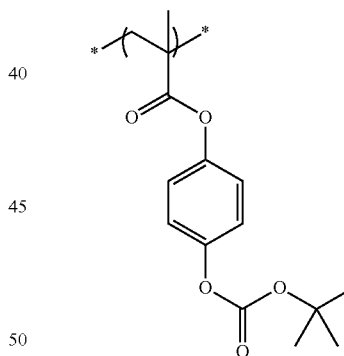
(VI-111)



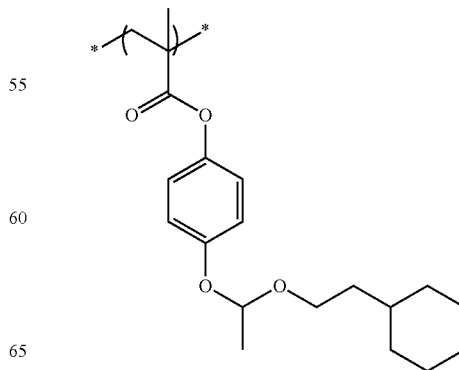
(VI-112)



(VI-113)



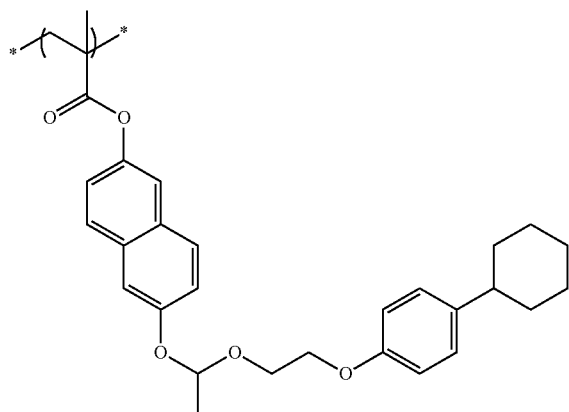
(VI-114)



59

-continued

(VI-115)

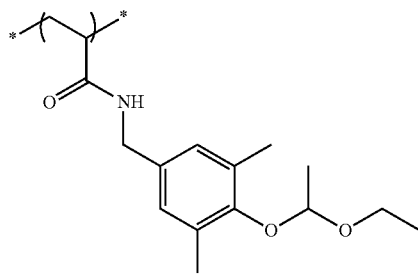


5

10

15

(VI-116)

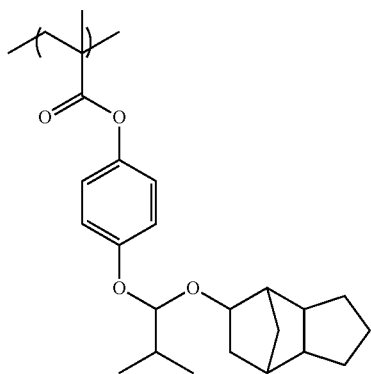


20

25

30

(VI-117)

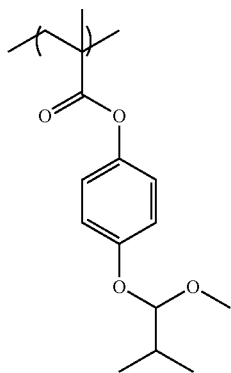


40

45

50

(VI-118)



55

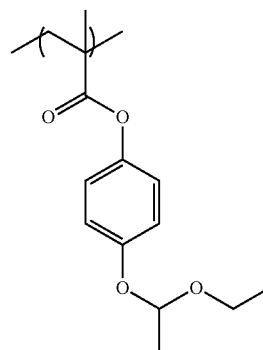
60

65

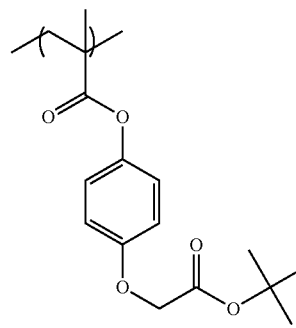
60

-continued

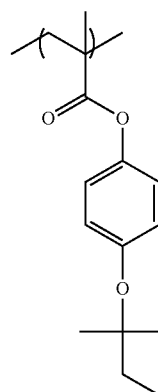
(VI-119)



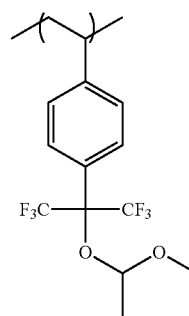
(VI-120)



(VI-121)

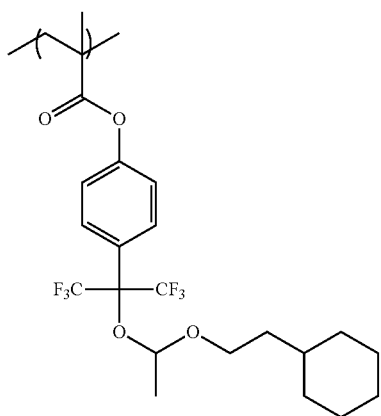
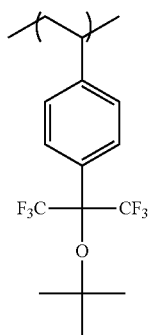
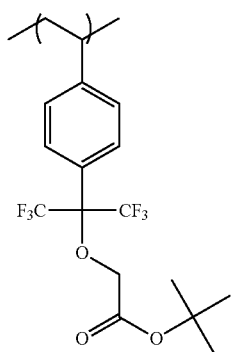
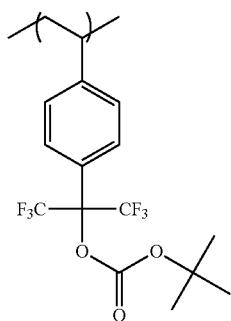


(VI-122)



61

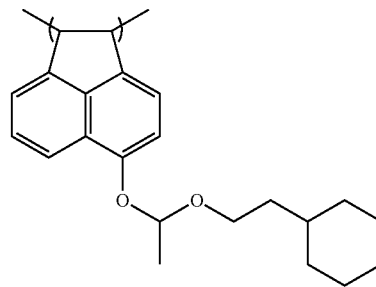
-continued

**62**

-continued

(VI-123)

5

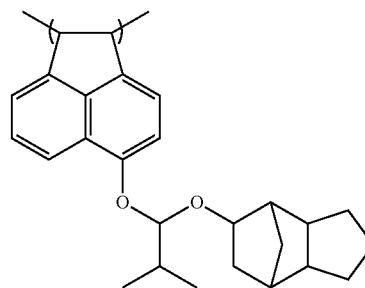


10

15

(VI-124)

20

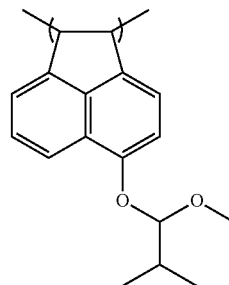


25

30

(VI-125)

35

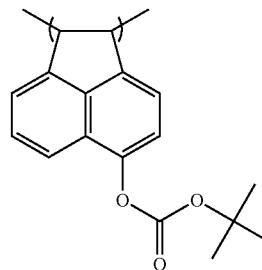


40

45

(VI-126)

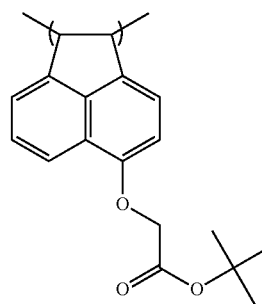
50



55

60

65



(VI-127)

(VI-128)

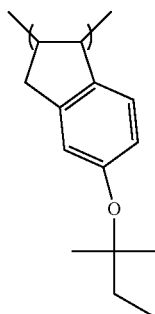
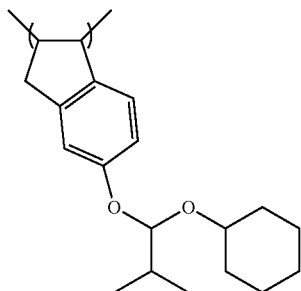
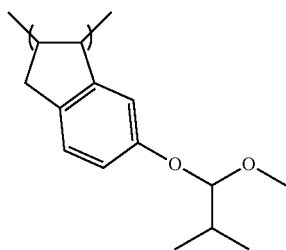
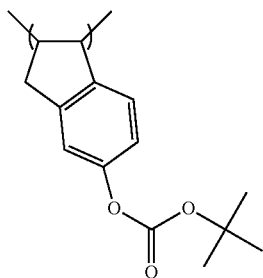
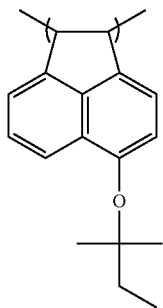
(VI-129)

(VI-130)

(VI-131)

63

-continued



64

-continued

(VI-132)

5

10

15

(VI-133)

20

25

(VI-134)

30

35

(VI-135)

45

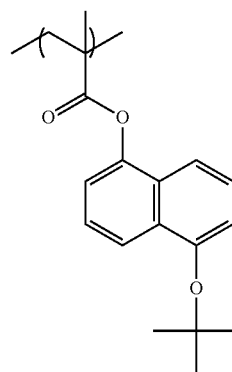
50

(VI-136)

55

60

65

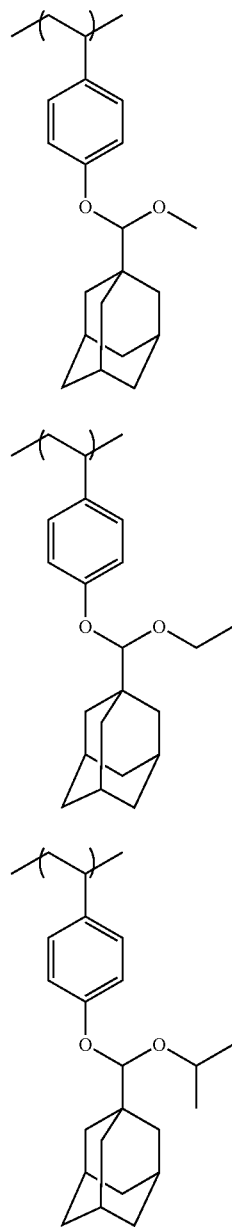


(VI-137)

(VI-138)

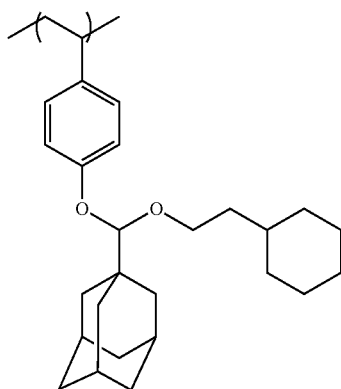
(VI-139)

(VI-140)



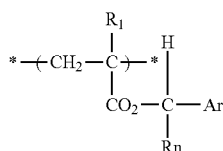
65

-continued



The repeating unit represented by formula (VI) is a repeating unit capable of generating a phenolic hydroxyl group by decomposition of an acid-decomposable group. In this case, the solubility in an organic solvent of the resin at the exposed part shows a tendency to be difficult to become sufficiently low, and so there are cases where the repeating unit is preferably not added in a large amount in the point of resolution. This tendency reveals more strongly in repeating units deriving from hydroxystyrenes (that is, the case where both X_6 and L_6 represent a single bond in formula (VI)), and the cause is not clear but it is presumed for the reason that the phenolic hydroxyl group is present in the vicinity of the main chain. Thus, in the invention, the content of the repeating unit generating a phenolic hydroxyl group by decomposition of an acid-decomposable group (for example, the repeating unit represented by formula (VI), preferably the repeating unit represented by formula (VI) in which both X_6 and L_6 represent a single bond) is preferably 4 mol % or less on the basis of all the repeating units in resin (A), more preferably 2 mol % or less, and most preferably 0 mol % (that is, the repeating unit is not contained).

Resin (A) may also contain a repeating unit represented by the following formula (BZ) as repeating unit (a).



In formula (BZ), AR represents an aryl group. Rn represents an alkyl group, a cycloalkyl group or an aryl group. Rn and AR may be bonded to each other to form a non-aromatic ring.

R_1 represents a hydrogen atom, an alkyl group, a cycloalkyl group, a halogen atom, a cyano group or an alkyloxycarbonyl group.

As the aryl group of AR, an aryl group having 6 to 20 carbon atoms such as a phenyl group, a naphthyl group, an anthryl group or a fluorene group is preferred, and an aryl group having 6 to 15 carbon atoms is more preferred.

When AR represents a naphthyl group, an anthryl group or a fluorene group, the bonding position of AR and the carbon atom to which Rn is bonded is not especially restricted. For example, when AR is a naphthyl group, the carbon atom may be bonded to the α -position of the naphthyl group, or may be

66

bonded to the β -position. Alternatively, when AR is an anthryl group, the carbon atom may be bonded to the 1-position of the anthryl group, or may be bonded to the 2-position, or may be bonded to the 9-position.

The aryl group as AR may have one or more substituents. As the specific examples of such substituents, straight chain or branched chain alkyl groups having 1 to 20 carbon atoms, e.g., a methyl group, an ethyl group, a propyl group, an isopropyl group, an n-butyl group, an isobutyl group, a t-butyl group, a pentyl group, a hexyl group, an octyl group, and a dodecyl group, alkoxy groups containing these alkyl group moieties, cycloalkyl groups, e.g., a cyclopentyl group and a cyclohexyl group, cycloalkoxy groups containing these cycloalkyl group moieties, a hydroxyl group, a halogen atom, an aryl group, a cyano group, a nitro group, an acyl group, an acyloxy group, an acylamino group, a sulfonylamino group, an alkylthio group, an arylthio group, an aralkylthio group, a thiophenecarbonyloxy group, a thiophenemethyl-carbonyloxy group, and heterocyclic residues, e.g., a pyrrolidone residue are exemplified. As these substituents, straight chain or branched chain alkyl groups having 1 to 5 carbon atoms and alkoxy groups containing these alkyl group moieties are preferred, and para-methyl groups and para-methoxy groups are more preferred.

When the aryl group as AR has two or more substituents, at least two of the plurality of substituents may be bonded to each other to form a ring. The ring is preferably any of 5- to 8-membered rings, and more preferably a 5- or 6-membered ring. The ring may be a heterocyclic ring containing a hetero atom such as an oxygen atom, a nitrogen atom or a sulfur atom in the ring member.

Further, the ring may have a substituent. As the examples of substituents, the same substituents as described later concerning further substituents that Rn may have are exemplified.

From the aspect of roughness performance, it is preferred for repeating unit (a) represented by formula (BZ) to contain 2 or more aromatic rings. The number of the aromatic rings that the repeating unit has is generally preferably 5 or less, and more preferably 3 or less.

Further, in repeating unit (a) represented by formula (BZ), from the viewpoint of roughness performance, it is more preferred for AR to have 2 or more aromatic rings, and it is still more preferred that AR is a naphthyl group or a biphenyl group. The number of the aromatic rings that AR has is generally preferably 5 or less, and more preferably 3 or less.

As described above, Rn represents an alkyl group, a cycloalkyl group or an aryl group.

The alkyl group represented by Rn may be a straight chain alkyl group or may be a branched chain alkyl group. As the alkyl group, preferably an alkyl group having 1 to 20 carbon atoms, e.g., a methyl group, an ethyl group, a propyl group, an isopropyl group, an n-butyl group, an isobutyl group, a t-butyl group, a pentyl group, a hexyl group, a cyclohexyl group, an octyl group, and a dodecyl group are exemplified. The alkyl group of Rn is preferably an alkyl group having 1 to 5 carbon atoms, and more preferably 1 to 3 carbon atoms.

As the cycloalkyl group of Rn, those having 3 to 15 carbon atoms, e.g., a cyclopentyl group and a cyclohexyl group are exemplified.

As the aryl group of Rn, aryl groups having 6 to 14 carbon atoms, e.g., a phenyl group, a xylyl group, a toluoyl group, a cumenyl group, a naphthyl group and an anthryl group are preferred.

Each of the alkyl group, cycloalkyl group and aryl group as Rn may further have a substituent. As the substituents, an alkoxy group, a hydroxyl group, a halogen atom, a nitro group, an acyl group, an acyloxy group, an acylamino group,

67

a sulfonylamino group, a dialkylamino group, an alkylthio group, an arylthio group, an aralkylthio group, a thiophenecarbonyloxy group, a thiophenemethylcarbonyloxy group, and heterocyclic residues, e.g., a pyrrolidone residue are exemplified. Of these groups, an alkoxy group, a hydroxyl group, a halogen atom, a nitro group, an acyl group, an acyloxy group, an acylamino group, and a sulfonylamino group are especially preferred.

R₁ represents a hydrogen atom, an alkyl group, a cycloalkyl group, a halogen atom, a cyano group, or an alkoxy carbonyl group as described above.

As the alkyl group and cycloalkyl group of R₁, the same groups as described above concerning R_n are exemplified. Each of these alkyl group and cycloalkyl group may have a substituent. As the substituents, the same groups as described above in R_n are exemplified.

When R₁ represents an alkyl group or a cycloalkyl group having a substituent, a trifluoromethyl group, an alkoxy carbonylmethyl group, an alkylcarbonyloxymethyl group, a hydroxymethyl group, and an alkoxy methyl group are exemplified as especially preferred R₁.

As the halogen atom of R₁, a fluorine atom, a chlorine atom, a bromine atom and an iodine atom are exemplified, and a fluorine atom is especially preferred.

As the alkyl group moieties contained in the alkoxy carbonyl group of R₁, structures described above as the alkyl groups of R₁ can be adopted.

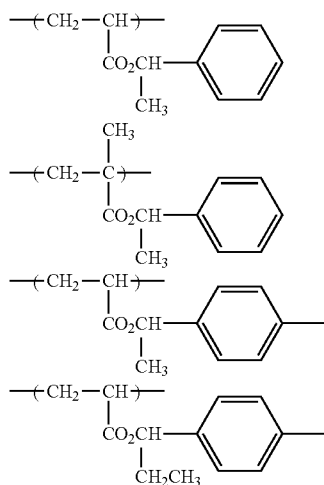
It is preferred that R_n and AR are bonded to each other to form a ring, by which roughness performance can be improved furthermore.

The non-aromatic ring formed by bonding of R_n and AR is preferably any of 5- to 8-membered rings, and more preferably a 5- or 6-membered ring.

The non-aromatic ring may be an aliphatic ring or may be a heterocyclic ring containing a hetero atom such as an oxygen atom, a nitrogen atom or a sulfur atom as the ring member.

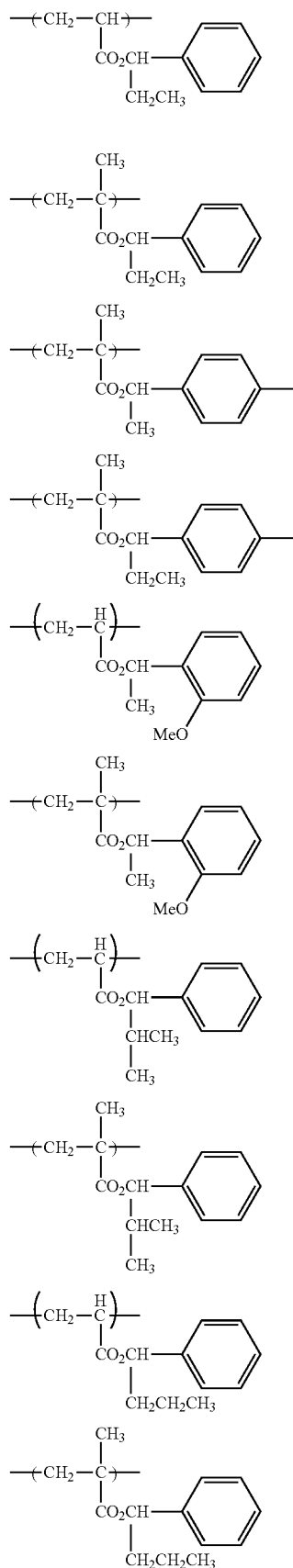
The non-aromatic ring may have a substituent. As the substituents, the same groups as described above in R_n as further substituents that R_n may have are exemplified.

The specific examples of repeating units (a) represented by formula (BZ) are shown below, but the invention is not restricted thereto.



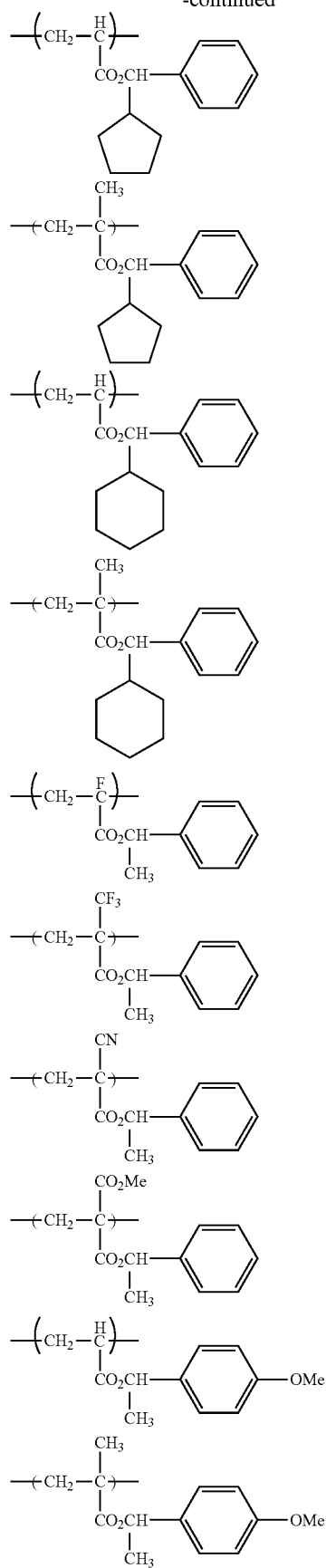
68

-continued

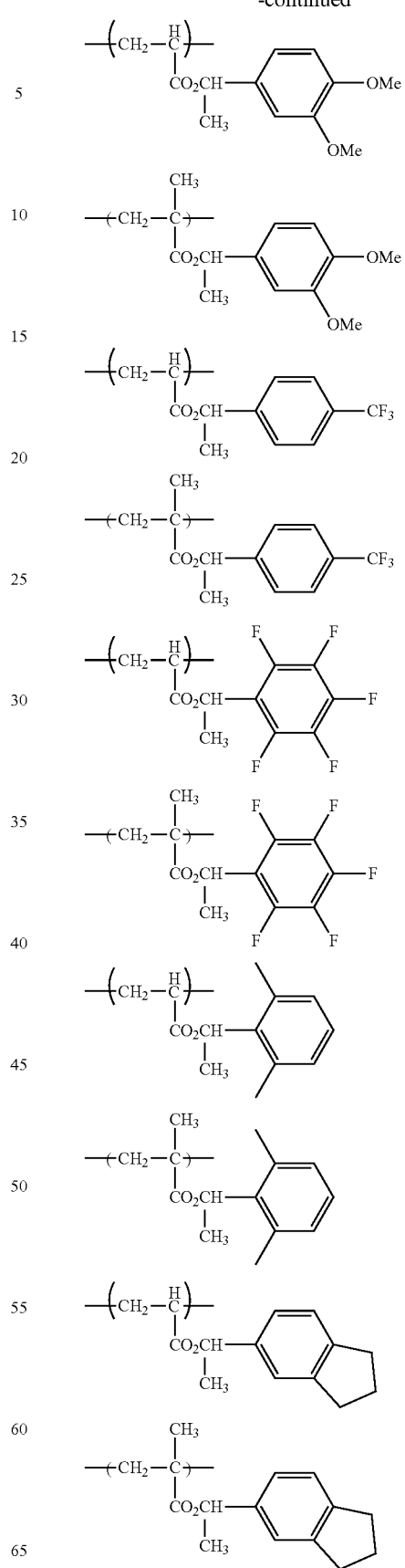


69

-continued

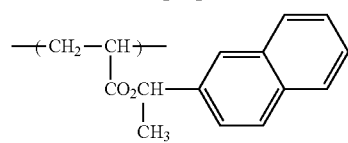
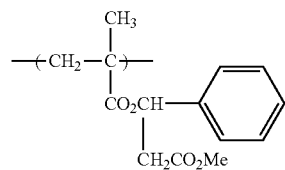
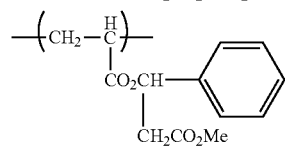
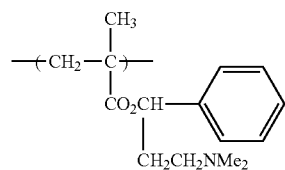
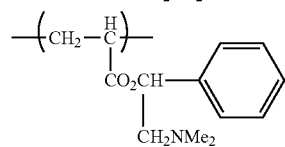
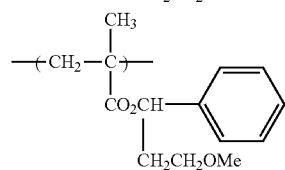
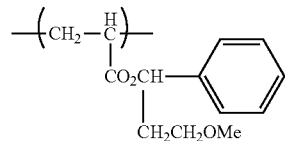
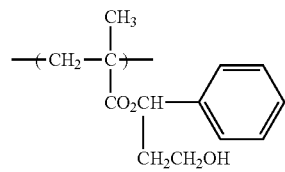
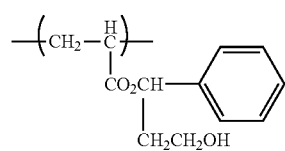
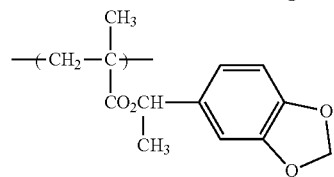
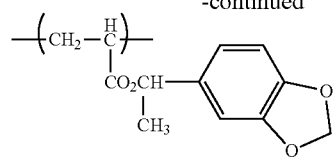
**70**

-continued



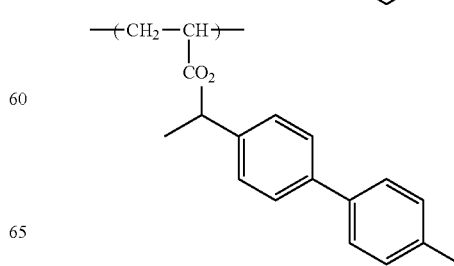
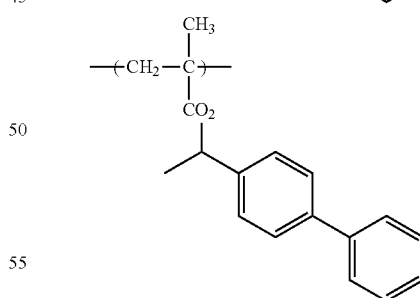
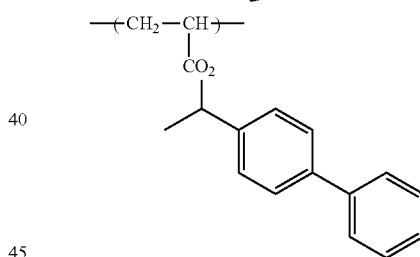
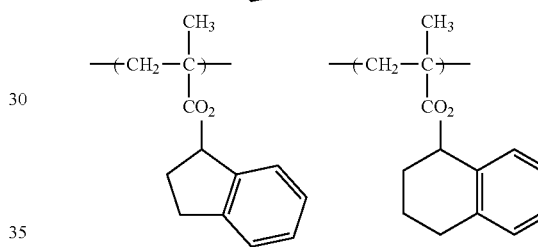
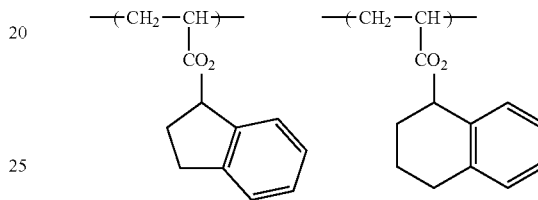
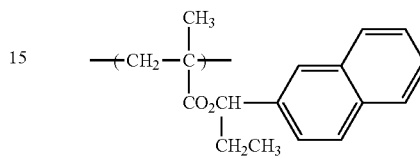
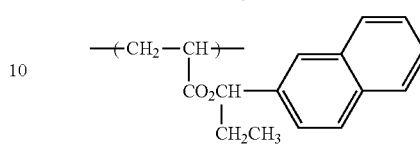
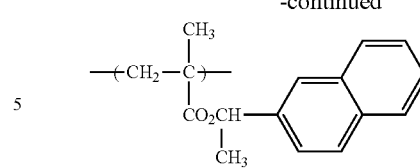
71

-continued



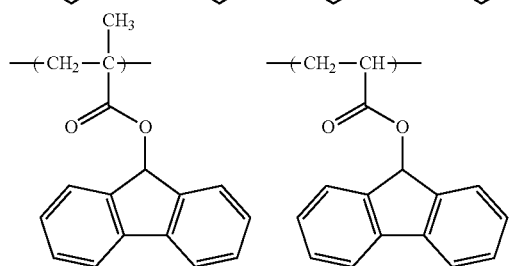
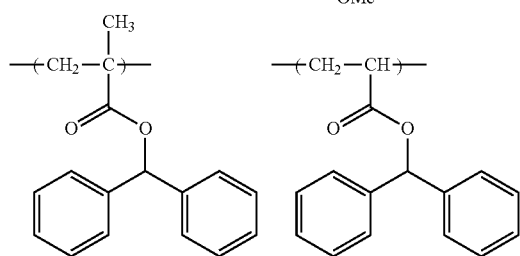
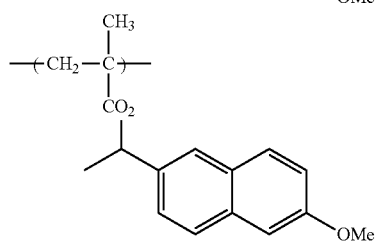
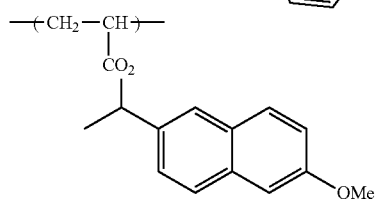
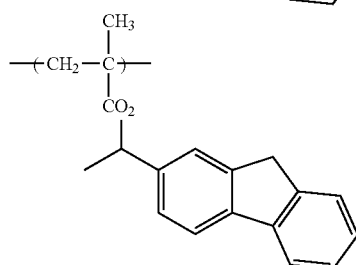
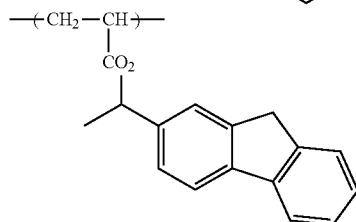
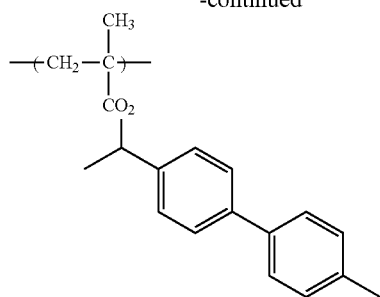
72

-continued

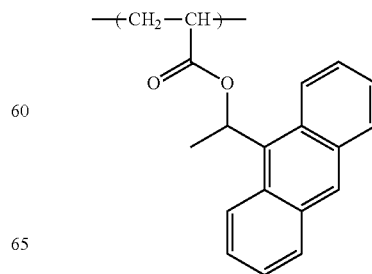
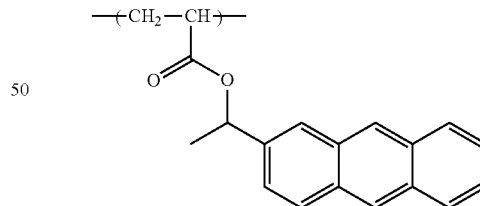
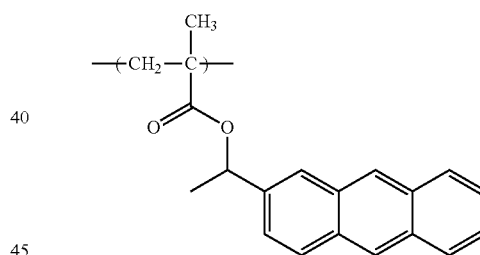
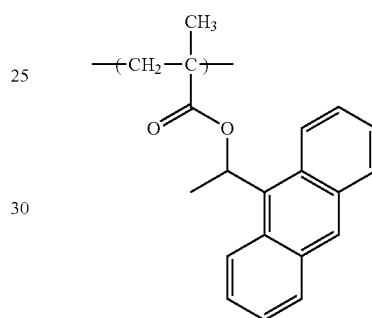
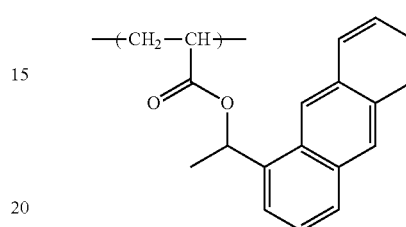
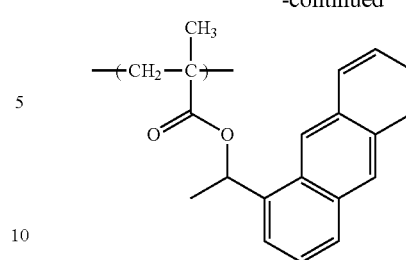


73

-continued

**74**

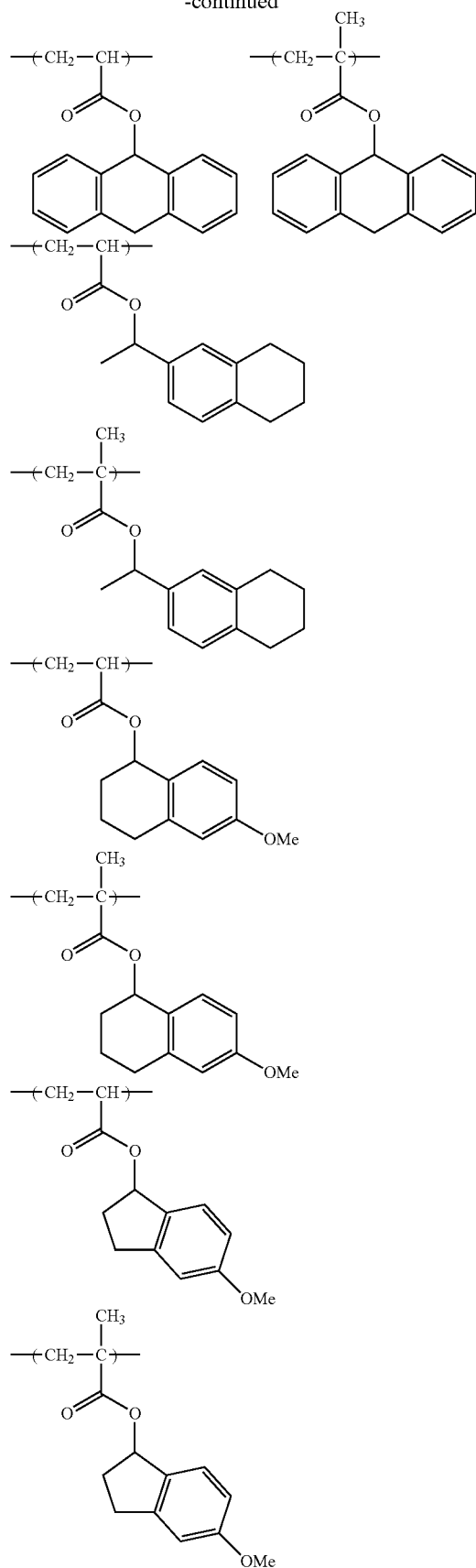
-continued



65

75

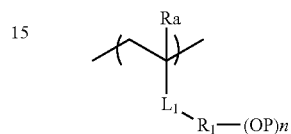
-continued



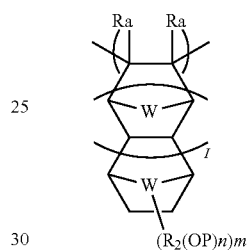
76

As an embodiment of a repeating unit having an acid-decomposable group different from the repeating units described above, an embodiment of a repeating unit generating an alcoholic hydroxyl group may be taken. In this case, such a repeating unit is preferably represented by at least one selected from the group consisting of the following formulae (I-1) to (I-10), more preferably represented by at least one selected from the group consisting of the following formulae (I-1) to (I-3), and still more preferably represented by the following formula (I-1).

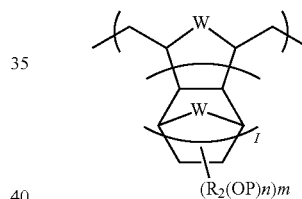
(I-1)



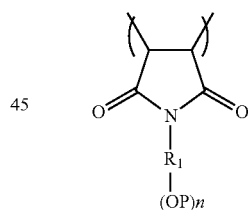
(I-2)



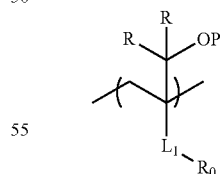
(I-3)



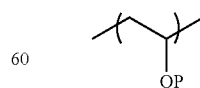
(I-4)



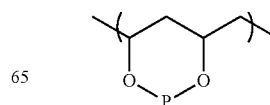
(I-5)



(I-6)

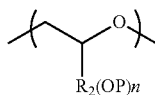
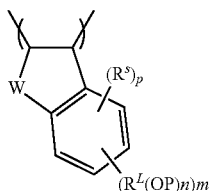
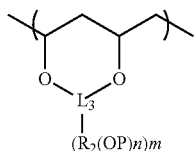


(I-7)



77

-continued



In the above formulae, each of R_a independently represents a hydrogen atom, an alkyl group, or a group represented by $-\text{CH}_2-\text{O}-\text{Ra}_2$, wherein Ra_2 represents a hydrogen atom, an alkyl group or an acyl group.

R_1 represents an $(n+1)$ -valent organic group.

In the case where m is equal to or greater than 2, each R_2 independently represents a single bond or an $(n+1)$ -valent organic group.

Each OP independently represents the above-described group of decomposing by the action of an acid to generate an alcoholic hydroxyl group. In the case of n being equal to or greater than 2 and/or m being equal to or greater than 2, two or more OP's may be bonded to each other and form a ring.

W represents a methylene group, an oxygen atom or a sulfur atom.

Each of n and m represents an integer of 1 or more. When R_2 represents a single bond in formula (I-2), (I-3) or (I-8), n is 1.

l represents an integer of 0 or more.

L_1 represents a linking group represented by $-\text{COO}-$, $-\text{OCO}-$, $-\text{CONH}-$, $-\text{O}-$, $-\text{Ar}-$, $-\text{SO}_3-$, or $-\text{SO}_2\text{NH}-$, wherein Ar represents a divalent aromatic ring group.

Each R independently represents a hydrogen atom or an alkyl group.

R_0 represents a hydrogen atom or an organic group.

L_3 represents an $(m+2)$ -valent linking group.

Each R^L represents an $(n+1)$ -valent linking group in the case where m is equal to or greater than 2.

Each R^S independently represents a substituent in the case where p is equal to or greater than 2. In the case where p is equal to or greater than 2, a plurality of R^S 's may be bonded to each other to form a ring.

p represents an integer of 0 to 3.

R_a represents a hydrogen atom, an alkyl group, or a group represented by $-\text{CH}_2-\text{O}-\text{Ra}_2$. Ra_2 preferably represents a hydrogen atom or an alkyl group having 1 to 10 carbon atoms, and more preferably a hydrogen atom or a methyl group.

W represents a methylene group, an oxygen atom or a sulfur atom, and preferably a methylene group or an oxygen atom.

R_1 represents an $(n+1)$ -valent organic group, and preferably a non-aromatic hydrocarbon group. In this case, R_1 may be a chain-like hydrocarbon group or may be an alicyclic hydrocarbon group, and more preferably represents an alicyclic hydrocarbon group.

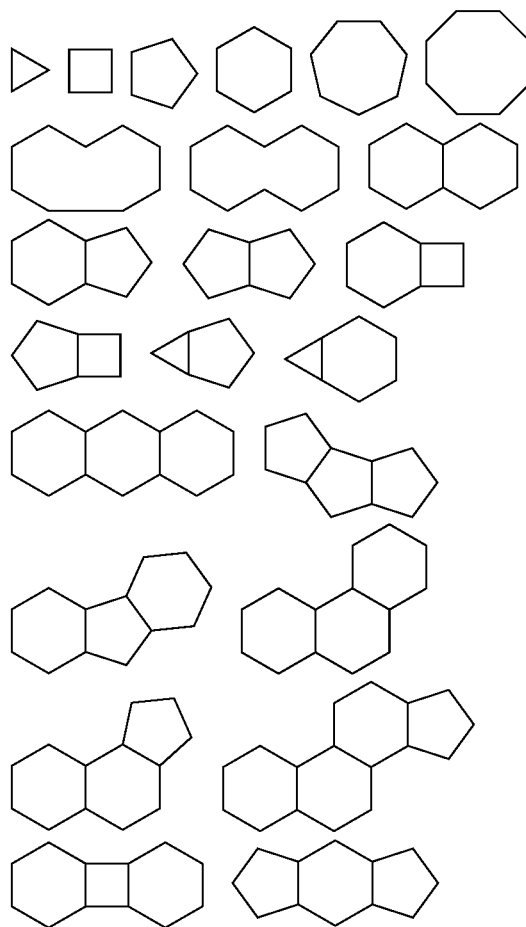
78

R_2 represents a single bond or an $(n+1)$ -valent organic group. R_2 preferably represents a single bond or a non-aromatic hydrocarbon group. In this case, R_2 may be a chain-like hydrocarbon group or may be an alicyclic hydrocarbon group.

When R_1 and/or R_2 are a chain-like hydrocarbon group, the chain-like hydrocarbon group may be a straight chain or a branched chain. The carbon atom number of the chain-like hydrocarbon group is preferably 1 to 8. For example, when R_1 and/or R_2 represent an alkylene group, R_1 and/or R_2 are preferably a methylene group, an ethylene group, an n -propylene group, an isopropylene group, an n -butylene group, an isobutylene group or a sec-butylene group.

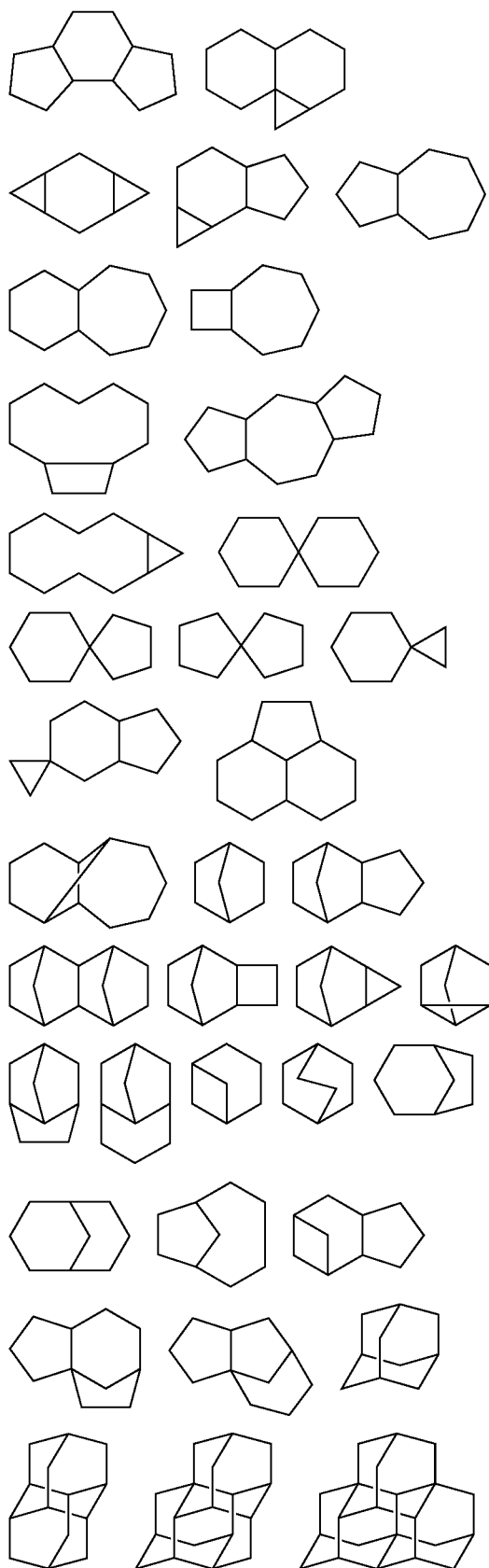
When R_1 and/or R_2 are an alicyclic hydrocarbon group, the alicyclic hydrocarbon group may be monocyclic or polycyclic. The alicyclic hydrocarbon group takes a monocyclic, bicyclic, tricyclic or tetracyclic structure. The carbon atom number of the alicyclic hydrocarbon group is generally 5 or more, preferably 6 to 30, and more preferably 7 to 25.

As the alicyclic hydrocarbon group, for example, those having the following partial structures are exemplified. Each of these partial structures may have a substituent. Further, in each of the partial structures, the methylene group ($-\text{CH}_2-$) may be substituted with an oxygen atom ($-\text{O}-$), a sulfur atom ($-\text{S}-$), a carbonyl group [$-\text{C}(=\text{O})-$], a sulfonyl group [$-\text{S}(=\text{O})_2-$], a sulfinyl group [$-\text{S}(=\text{O})-$], or an imino group [$-\text{N}(\text{R})-$] (wherein R represents a hydrogen atom or an alkyl group).



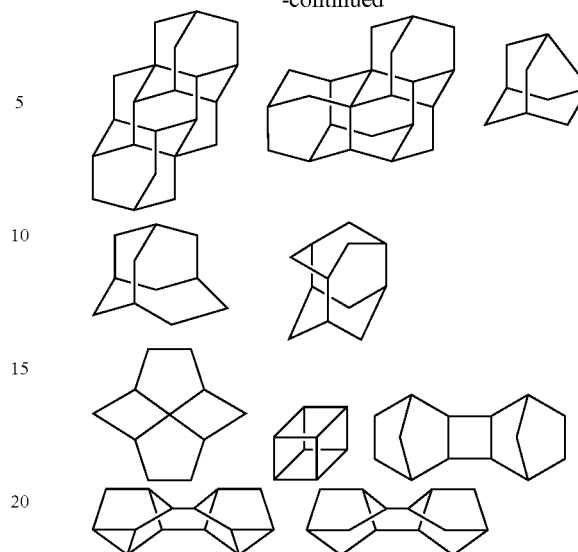
79

-continued



80

-continued



For example, in the case where R_1 and/or R_2 are a cycloalkylene group, R_1 and/or R_2 are preferably an adamantylene group, a noradamantylene group, a decahydronaphthylene group, a tricyclodecanylene group, a tetracyclododecanylene group, a norbornylene group, a cyclopentylene group, a cyclohexylene group, a cycloheptylene group, a cyclooctylene group, a cyclodecanylene group, or a cyclododecanylene group, and more preferably an adamantylene group, a norbornylene group, a cyclohexylene group, a cyclopentylene group, a tetracyclododecanylene group, or a tricyclodecanylene group.

The non-aromatic hydrocarbon group represented by R_1 and/or R_2 may have a substituent. As the substituent, an alkyl group having 1 to 4 carbon atoms, a halogen atom, a hydroxyl group, an alkoxy group having 1 to 4 carbon atoms, a carboxyl group, and an alkoxycarbonyl group having 2 to 6 carbon atoms are exemplified. Each of these alkyl group, alkoxy group and alkoxycarbonyl group may further have a substituent. As such further substituent, e.g., a hydroxyl group, a halogen atom and an alkoxy group are exemplified.

L_1 represents a linking group represented by formula $-\text{COO}-$, $-\text{OCO}-$, $-\text{CONH}-$, $-\text{O}-$, $-\text{Ar}-$, $-\text{SO}_3-$, or $-\text{SO}_2\text{NH}-$, wherein Ar represents a divalent aromatic ring group. L_1 preferably represents a linking group represented by $-\text{COO}-$, $-\text{CONH}-$ or $-\text{Ar}-$, and more preferably a linking group represented by $-\text{COO}-$ or $-\text{CONH}-$.

R represents a hydrogen atom or an alkyl group. The alkyl group may be a straight chain or a branched chain. The carbon atom number of the alkyl group is preferably 1 to 6, and more preferably 1 to 3. R preferably represents a hydrogen atom or a methyl group, and more preferably a hydrogen atom.

R_0 represents a hydrogen atom or an organic group. As the organic group, e.g., an alkyl group, a cycloalkyl group, an aryl group, an alkynyl group and an alkenyl group are exemplified. R_0 preferably represents a hydrogen atom or an alkyl group, and more preferably a hydrogen atom or a methyl group.

L_3 represents an $(m+2)$ -valent linking group. That is, L_3 represents a trivalent or higher linking group. As such linking groups, for example, corresponding groups in the later-described specific examples are exemplified.

R^L represents an $(n+1)$ -valent linking group. That is, R^L represents a divalent or higher linking group. As such linking

81

groups, for example, an alkylene group, a cycloalkylene group, and corresponding groups in the later-described specific examples are exemplified. R^L may be bonded to each other or bonded to R^S to form a cyclic structure.

R^S represents a substituent. As the substituents, e.g., an alkyl group, an alkenyl group, an alkynyl group, an aryl group, an alkoxy group, an acyloxy group, an alkoxycarbonyl group and a halogen atom are exemplified.

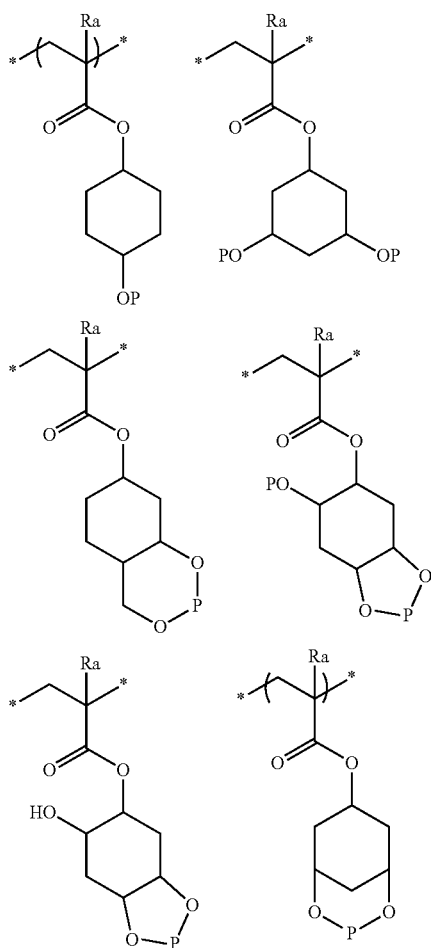
n represents an integer of 1 or more, preferably an integer of 1 to 3, and more preferably 1 or 2. When n is 2 or higher, it becomes possible to further improve contrast of dissolution in a developer containing an organic solvent. Accordingly, limiting resolution and roughness characteristics can further be improved by the above constitution.

m represents an integer of 1 or more, preferably 1 to 3, and more preferably 1 or 2.

l represents an integer of 0 or more, and preferably 0 or 1.

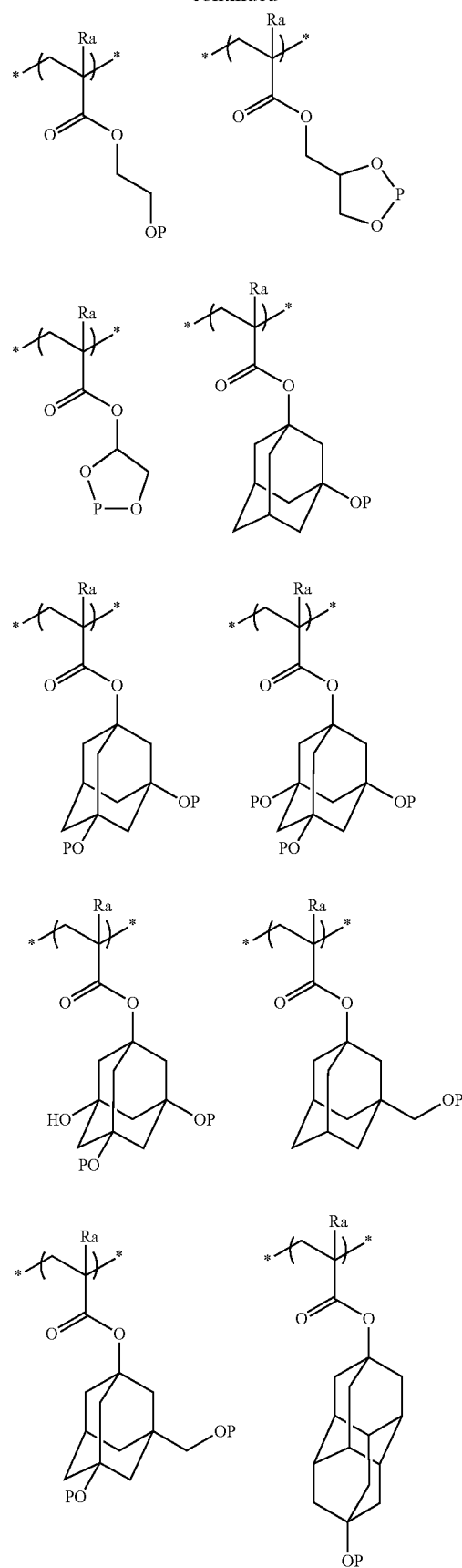
p represents an integer of 0 to 3.

The specific examples of the repeating units having a group capable of decomposing by the action of an acid to generate an alcoholic hydroxyl group are shown below. In the specific examples, R_a and OP are respectively the same with those in formulae (I-1) to (I-3). When two or more OP's are bonded to each other to form a ring, the corresponding cyclic structure is inscribed as "O—P—O" for conveniences' sake.



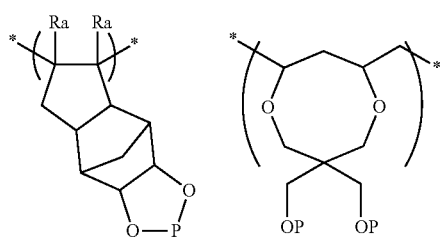
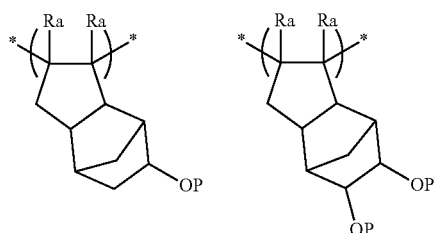
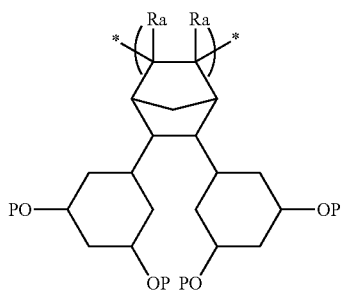
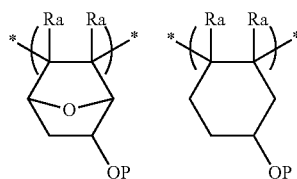
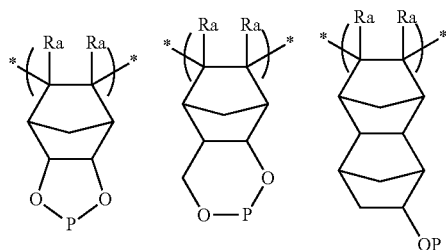
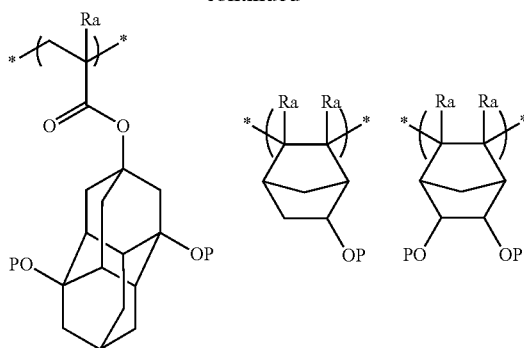
82

-continued

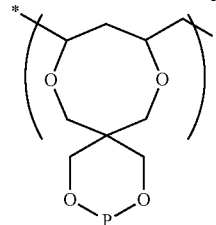


83

-continued

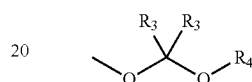
**84**

-continued

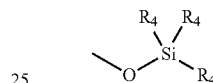


The group capable of decomposing by the action of an acid to generate an alcoholic hydroxyl group is preferably represented by at least one formula selected from the group consisting of the following formulae (II-1) to (II-4).

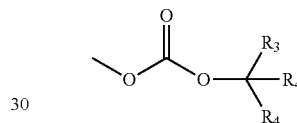
(II-1)



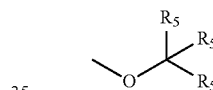
(II-2)



(II-3)



(II-4)



(II-5)

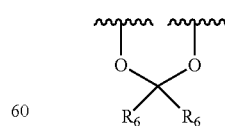
In the above formulae, each of R₃'s independently represents a hydrogen atom or a monovalent organic group. R₃'s may be bonded to each other to form a ring.

Each of R₄'s independently represents a monovalent organic group. R₄'s may be bonded to each other to form a ring. R₃ and R₄ may be bonded to each other to form a ring.

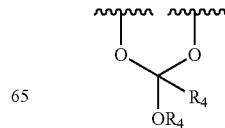
Each of R₅'s independently represents a hydrogen atom, an alkyl group, a cycloalkyl group, an aryl group, an alkenyl group or an alkynyl group. At least two R₅'s may be bonded to each other to form a ring, provided that when at least one or two of three R₅'s represent a hydrogen atom, at least one of the remaining R₅'s represents an aryl group, an alkenyl group or an alkynyl group.

The group capable of decomposing by the action of an acid to generate an alcoholic hydroxyl group is also preferably represented by at least one formula selected from the group consisting of the following formulae (II-5) to (II-9).

(II-5)

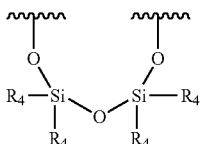
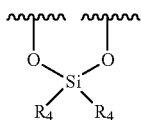
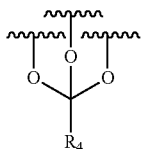


(II-6)



85

-continued



In the above formulae, R_4 has the same meaning as in formulae (II-1) to (II-3).

Each of R_6 's independently represents a hydrogen atom or a monovalent organic group. R_6 's may be bonded to each other to form a ring.

The group capable of decomposing by the action of an acid to generate an alcoholic hydroxyl group is preferably represented by at least one formula selected from the group consisting of formulae (II-1) to (II-3), more preferably represented by formula (II-1) or (II-3), and especially preferably represented by formula (II-1).

R_3 represents a hydrogen atom or a monovalent organic group as described above. R_3 preferably represents a hydrogen atom, an alkyl group, or a cycloalkyl group, and more preferably a hydrogen atom or an alkyl group.

The alkyl group represented by R_3 may be a straight chain or a branched chain. The number of carbon atoms of the alkyl group of R_3 is preferably 1 to 10, and more preferably 1 to 3. As the alkyl group of R_3 , e.g., a methyl group, an ethyl group, an n-propyl group, an isopropyl group, and an n-butyl group are exemplified.

The cycloalkyl group represented by R_3 may be monocyclic or polycyclic. The number of carbon atoms of the cycloalkyl group of R_3 is preferably 3 to 10, and more preferably 4 to 8. As the cycloalkyl group of R_3 , e.g., a cyclopropyl group, a cyclobutyl group, a cyclopentyl group, a cyclohexyl group, a norbornyl group and an adamantyl group are exemplified.

In formula (II-1), at least one of R_3 's preferably represents a monovalent organic group. Especially high sensitivity can be attained by taking such constitution.

R_4 represents a monovalent organic group. R_4 preferably represents an alkyl group or a cycloalkyl group, and more preferably an alkyl group. These alkyl group and cycloalkyl group may have a substituent.

It is preferred that the alkyl group represented by R_4 does not have a substituent, or R_4 has one or more aryl groups and/or one or more silyl groups as the substituents. The number of carbon atoms of the unsubstituted alkyl group is preferably 1 to 20. The number of carbon atoms of the alkyl group moieties in the alkyl group substituted with one or more aryl groups is preferably 1 to 25. The number of carbon atoms of the alkyl group moieties in the alkyl group substituted with one or more silyl groups is preferably 1 to 30. In the case where the cycloalkyl group of R_4 does not have a substituent, the number of carbon atoms is preferably 3 to 20.

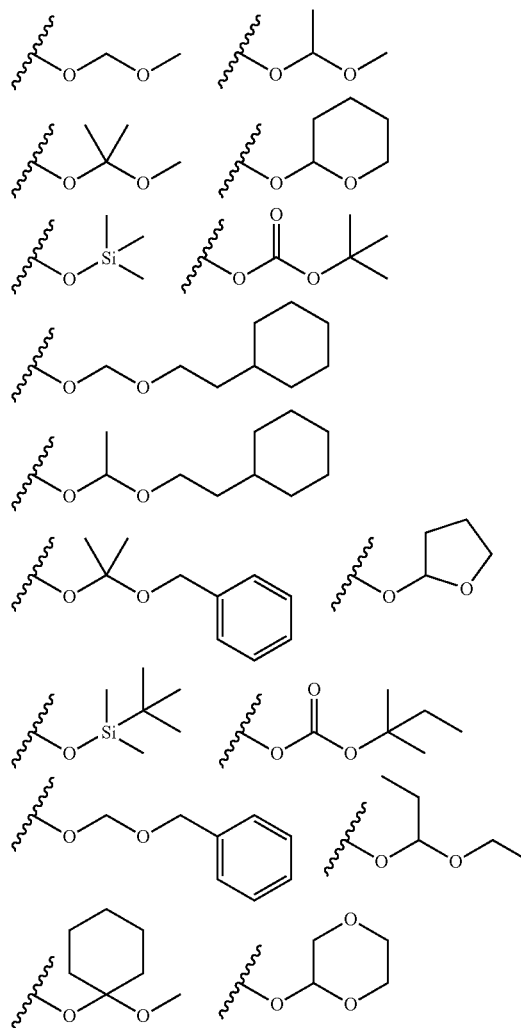
86

R_5 represents a hydrogen atom, an alkyl group, a cycloalkyl group, an aryl group, an alkenyl group or an alkynyl group, provided that when at least one or two of three R_5 's represent a hydrogen atom, at least one of the remaining R_5 's represents an aryl group, an alkenyl group or an alkynyl group. R_5 preferably represents a hydrogen atom or an alkyl group. The alkyl group may have a substituent or may not have a substituent. When the alkyl group does have a substituent, the number of carbon atoms is preferably 1 to 6, and more preferably 1 to 3.

As described above, R_6 represents a hydrogen atom or a monovalent organic group. R_6 preferably represents a hydrogen atom, an alkyl group or a cycloalkyl group, more preferably a hydrogen atom or an alkyl group, and still more preferably a hydrogen atom or an alkyl group not having a substituent. R_6 preferably represents a hydrogen atom or an alkyl group having 1 to 10 carbon atoms, and more preferably a hydrogen atom or an alkyl group having 1 to 10 carbon atoms and not having a substituent.

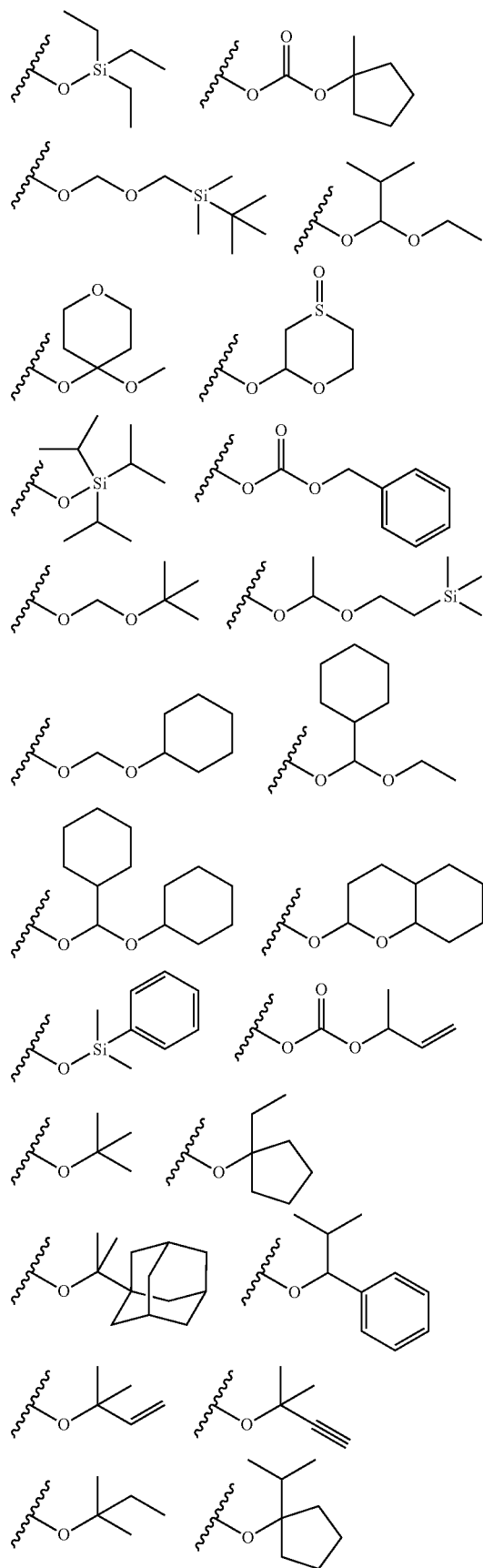
As the alkyl group and cycloalkyl group of R_4 , R_5 and R_6 , the same groups as described above in R_3 are exemplified.

The specific examples of the groups capable of decomposing by the action of an acid to generate an alcoholic hydroxyl group are shown below.

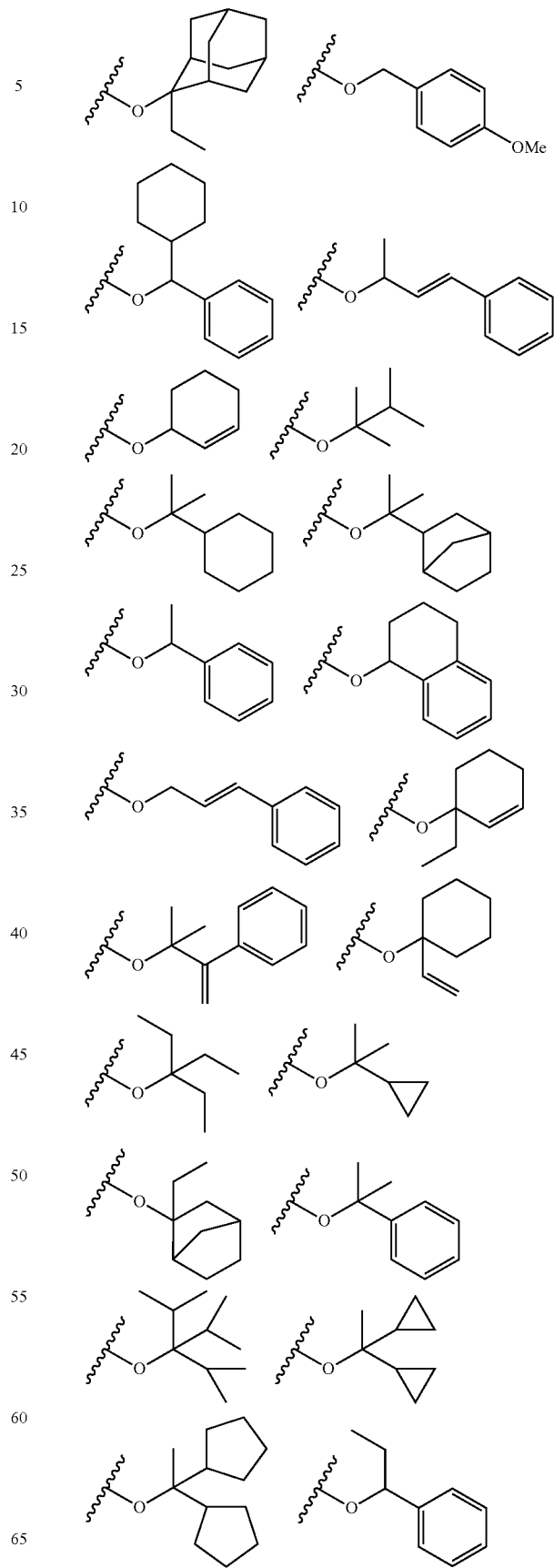


87

-continued

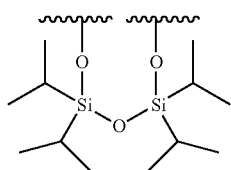
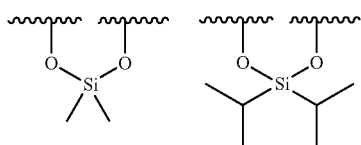
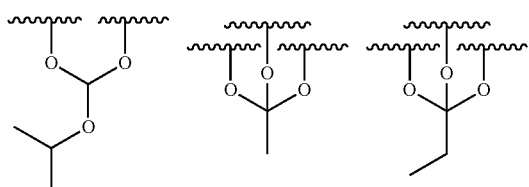
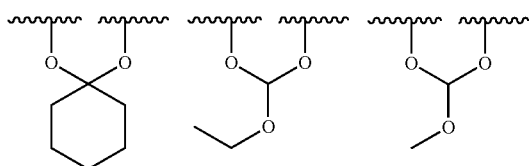
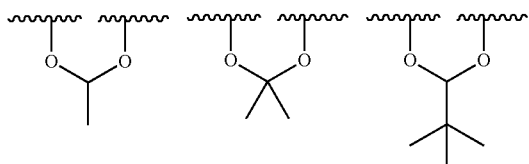
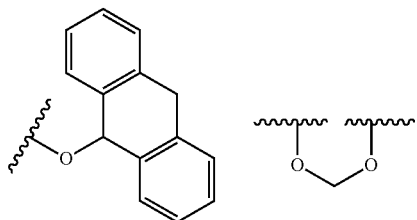
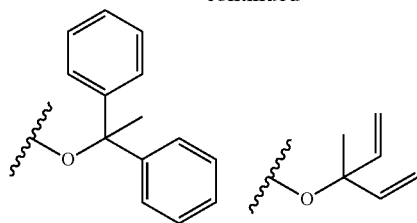
**88**

-continued

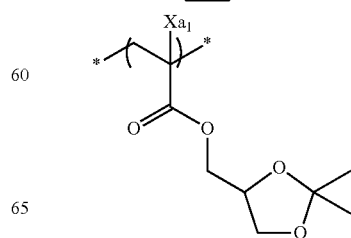
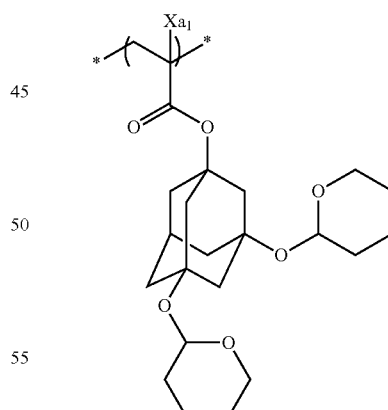
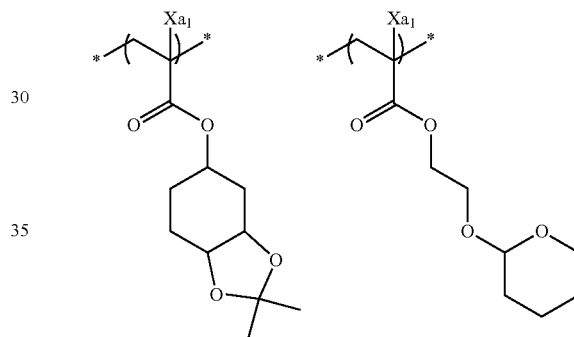
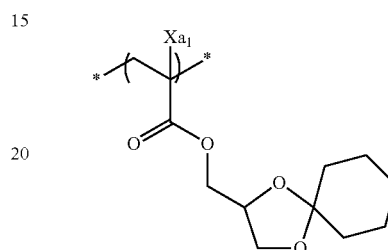
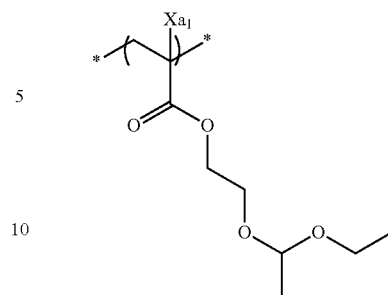


89

-continued



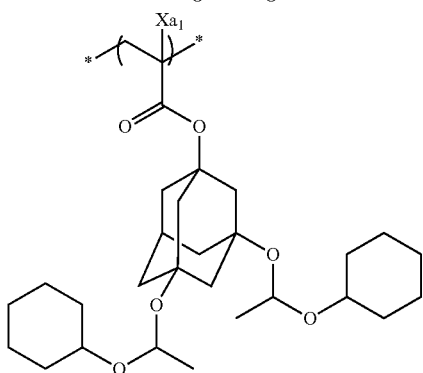
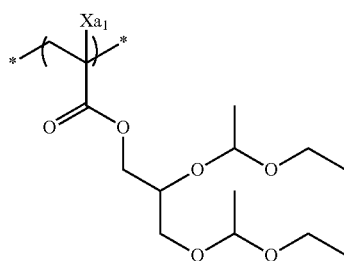
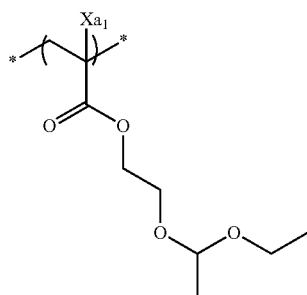
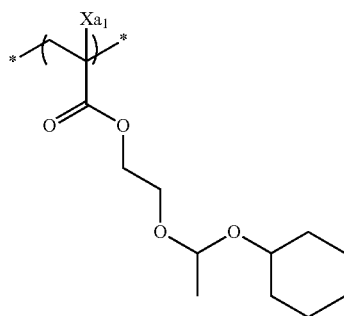
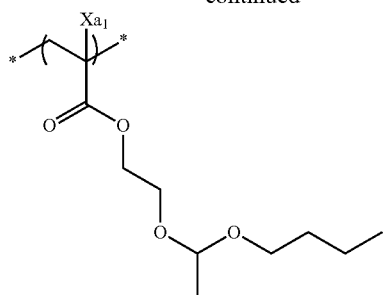
90



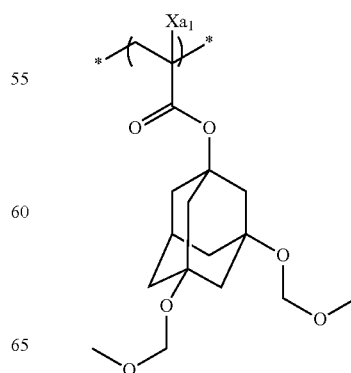
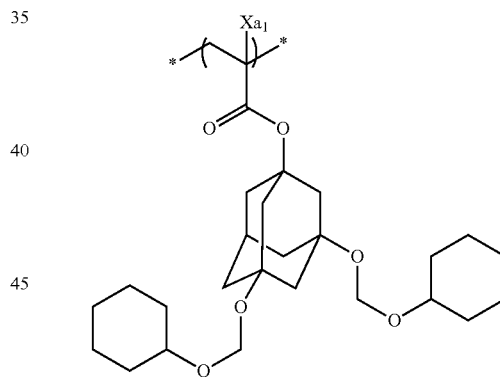
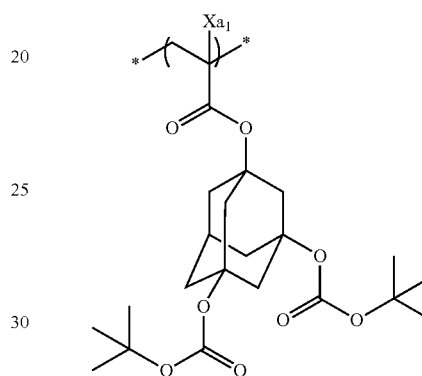
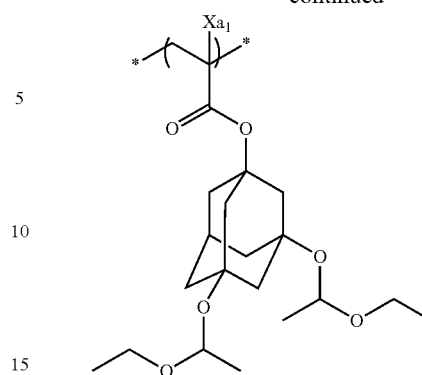
The specific examples of the repeating units having a group capable of decomposing by the action of an acid to generate an alcoholic hydroxyl group are shown below. In the formulae, X_{a1} represents a hydrogen atom, CH_3 , CF_3 or CH_2OH .

91

-continued

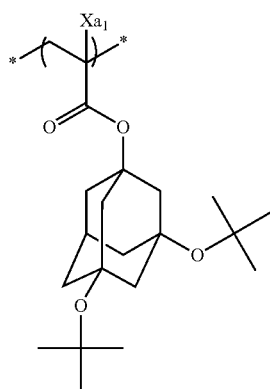
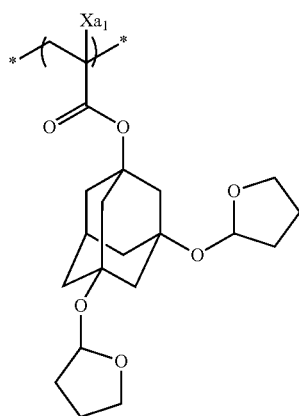
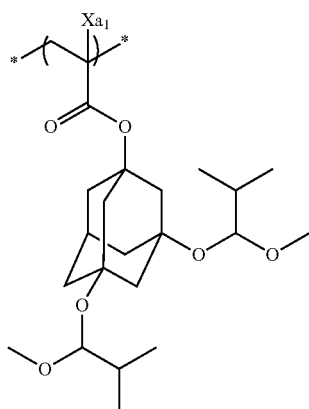
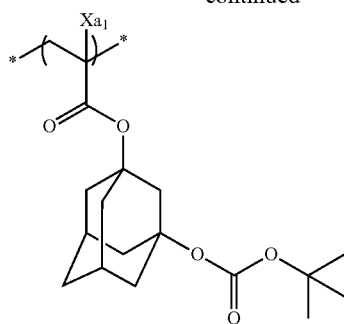
**92**

-continued



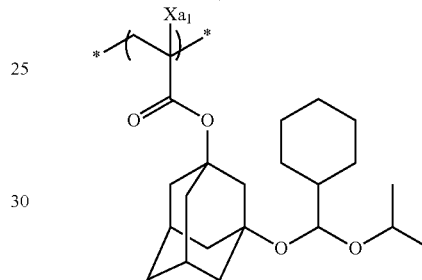
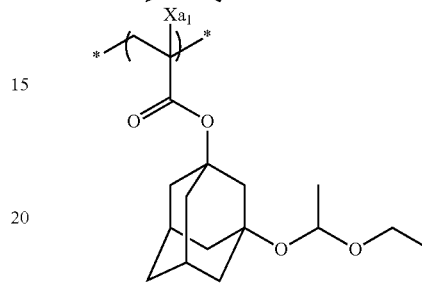
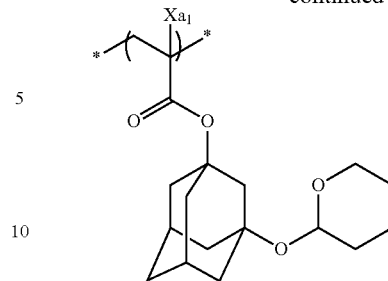
93

-continued



94

-continued



35 As for the repeating unit having an acid-decomposable group, one kind may be used, or two or more kinds may be used in combination.

The content of the acid-decomposable group-containing repeating unit (in the case of containing a plurality of kinds of repeating units, the total thereof) in the resin (A) is preferably from 5 to 80 mol %, more preferably from 5 to 75 mol %, still more preferably from 10 to 65 mol %, based on all repeating units in the resin (A).

(b) Repeating Units Having a Polar Group

45 It is preferred for resin (A) to contain repeating unit (b) having a polar group. By containing repeating unit (b), sensitivity of the composition containing the resin can be increased. Repeating unit (b) is preferably a non-acid-decomposable repeating unit (that is, the repeating unit does not have an acid-decomposable group).

50 As "polar groups" which can be contained in repeating unit (b), for example, the following (1) to (4) can be exemplified. Incidentally, in the following, "electronegativity" means the value by Pauling.

(1) A Functional Group Containing the Structure in which an Oxygen Atom and an Atom Having the Difference in Electronegativity Between the Oxygen Atom being 1.1 or More are Bonded by a Single Bond

55 As such a polar group, a group containing the structure represented, for example, by O—H such as a hydroxyl group is exemplified.

(2) A Functional Group Containing the Structure in which a Nitrogen Atom and an Atom Having the Difference in Electronegativity Between the Nitrogen Atom being 0.6 or More are Bonded by a Single Bond

65 As such a polar group, a group containing the structure represented, for example, by N—H such as an amino group is exemplified.

95

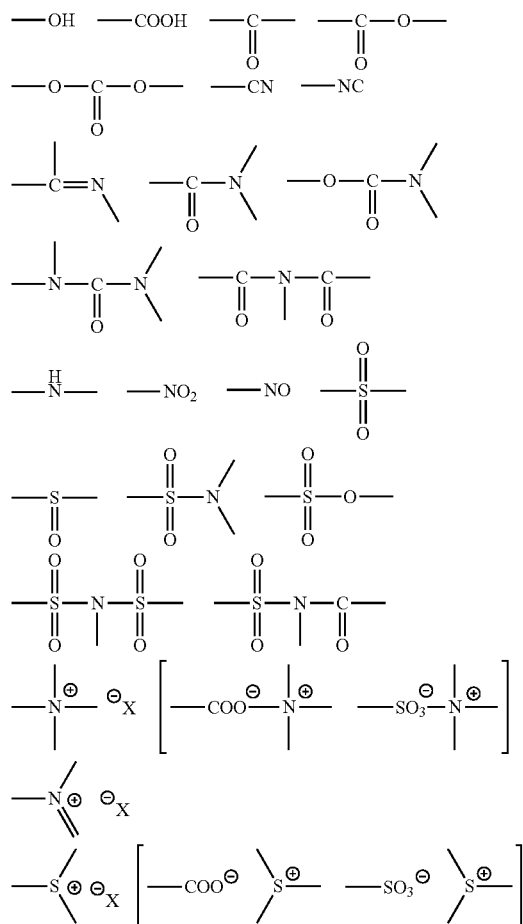
(3) A Functional Group Containing the Structure in which Two Atoms Different in Electronegativity by 0.5 or More are Bonded by a Double Bond or a Triple Bond

As such a polar group, a group containing the structure represented, for example, by $C\equiv N$, $C=O$, $N=O$, $S=O$ or $C=N$ is exemplified.

(4) A Functional Group Having an Ionic Site

As such a polar group, a group having the site represented, for example, by N^+ or S^+ is exemplified.

The specific examples of partial structures that "polar group" can contain are shown below.



"Polar group" that repeating unit (b) can contain is preferably at least one selected from the group consisting of (I) a hydroxyl group, (II) a cyano group, (III) a lactone group, (IV) a carboxylic acid group or a sulfonic acid group, (V) an amido group, a sulfonamide group, or a group corresponding to the derivative thereof, (VI) an ammonium group or a sulfonium group, and a group obtained by combining two or more of these groups.

The polar group is preferably selected from a hydroxyl group, a cyano group, a lactone group, a carboxylic acid group, a sulfonic acid group, an amido group, a sulfonamide group, an ammonium group, a sulfonium group, and a group obtained by combining two or more of these groups, and especially preferably an alcoholic hydroxyl group, a cyano group, a lactone group, or a group containing a cyanolactone structure.

When a repeating unit having an alcoholic hydroxyl group is further added to the resin, the exposure latitude (EL) of a composition containing the resin can be further improved.

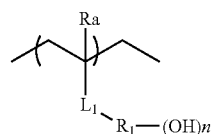
96

When a repeating unit having a cyano group is further added to the resin, the sensitivity of a composition containing the resin can be further improved.

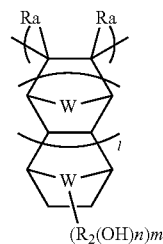
When a repeating unit having a lactone group is further added to the resin, dissolution contrast in a developer containing an organic solvent can be further improved, by which it also becomes possible to further improve the dry etching resistance, coating stability and adhering property to substrate of the composition containing the resin.

When a repeating unit having a group containing a lactone structure having a cyano group is further added to the resin, dissolution contrast in a developer containing an organic solvent can be further improved, by which it also becomes possible to further improve the sensitivity, dry etching resistance, coating stability and adhering property to substrate of the composition containing the resin. In addition to the above, it is possible for a single repeating unit to bear functions resulting from each of the cyano group and the lactone group, thus the degree of freedom of design of the resin can further be increased.

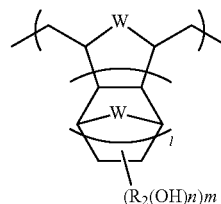
When the polar group that repeating unit (b) has is an alcoholic hydroxyl group, repeating unit (b) is preferably represented by at least one formula selected from the group consisting of the following formulae (I-1H) to (I-10H), more preferably represented by at least one formula selected from the group consisting of formulae (I-1H) to (I-3H), and still more preferably represented by formulae (I-1H).



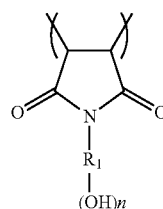
(I-1H)



(I-2H)



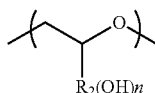
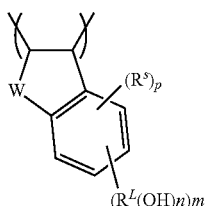
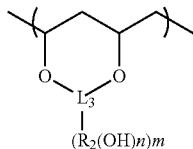
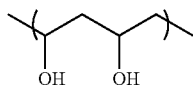
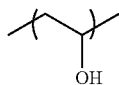
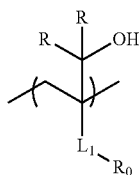
(I-3H)



(I-4H)

97

-continued



In the above formulae, Ra, R₁, R₂, W, n, m, l, L₁, R, R₀, L₃, R^L, R^S and p are respectively the same as in formulae (I-1) to (I-10).

When a repeating unit having a group capable of decomposing by the action of an acid to generate an alcoholic hydroxyl group is used in combination with a repeating unit represented by at least one formula selected from the group consisting of the following formulae (I-1H) to (I-10H), it becomes possible to improve exposure latitude (EL) by control of distribution of acid by the alcoholic hydroxyl group and increase of sensitivity by the group capable of decomposing by the action of an acid to generate an alcoholic hydroxyl group without deteriorating other performances.

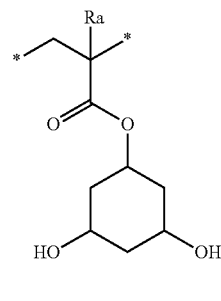
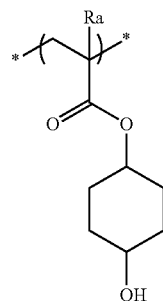
The content of the repeating unit having the alcoholic hydroxyl group is preferably 1 mol % to 60 mol % to all the repeating units in resin (A), more preferably 3 mol % to 50 mol %, and still more preferably 5 mol % to 40 mol %.

The specific examples of the repeating units represented by any of formulae (I-1H) to (I-10H) are shown below. In the formulae, Ra is the same meaning with those in formulae (I-1H) to (I-10H).

98

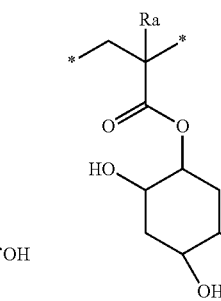
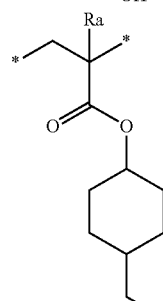
(I-5H)

5



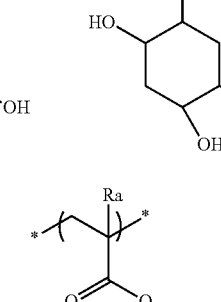
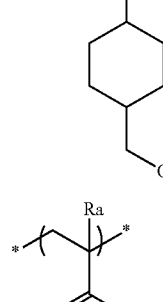
(I-6H)

15



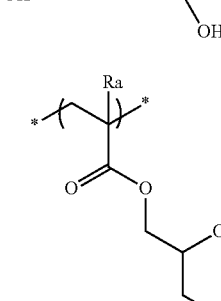
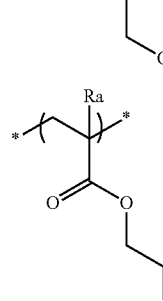
(I-7H)

20



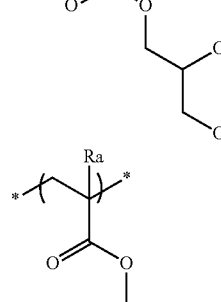
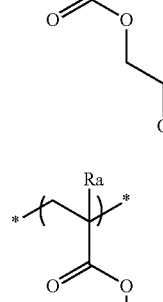
(I-8H)

25



(I-9H)

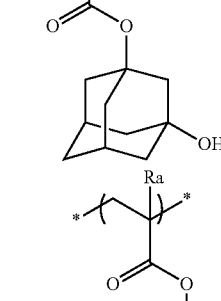
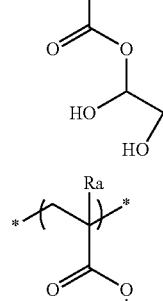
30



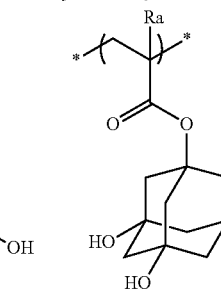
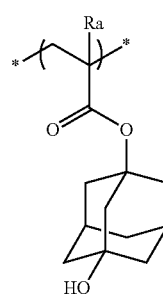
35

(I-10H)

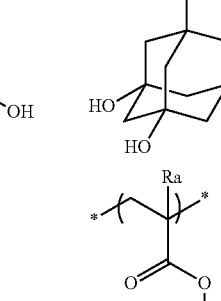
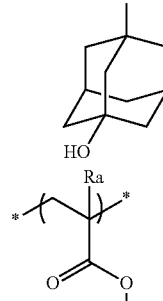
40



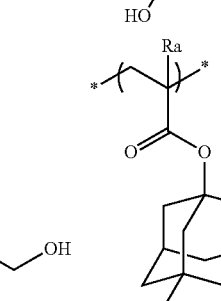
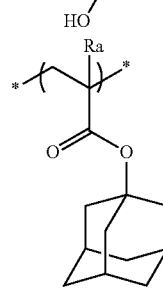
45



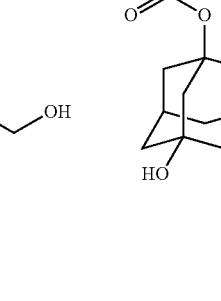
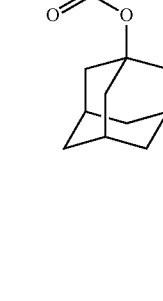
50



55



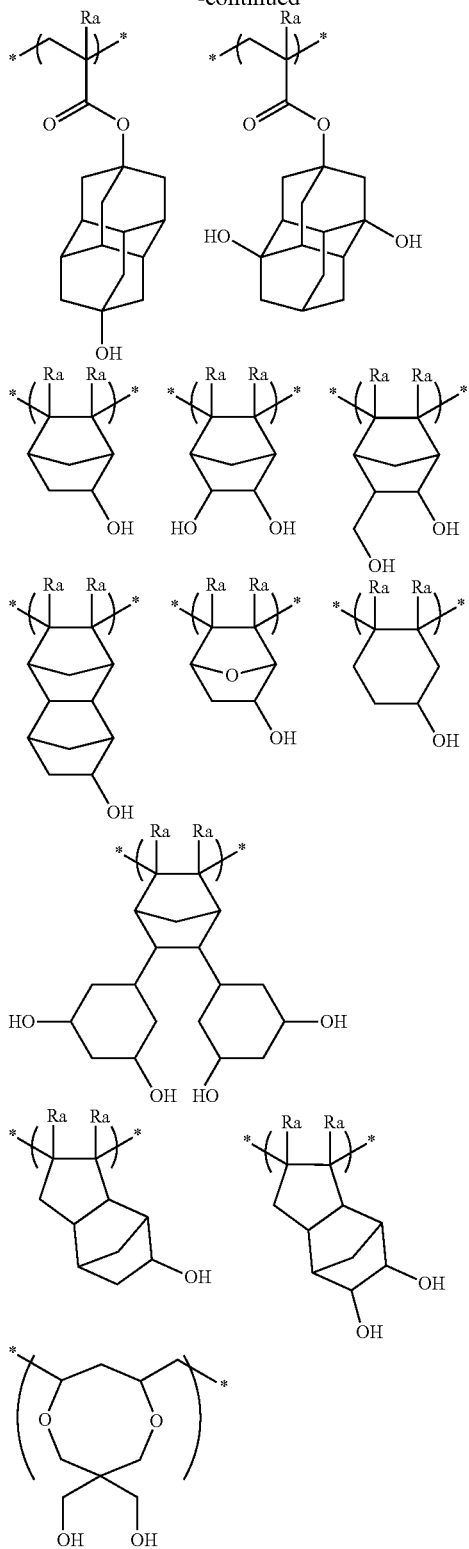
60



65

99

-continued

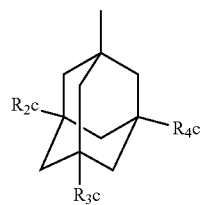


When the polar group that repeating unit (b) has is an alcoholic hydroxyl group or a cyano group, as one embodiment of preferred repeating unit, a repeating unit having an alicyclic hydrocarbon structure substituted with a hydroxyl group or a cyano group is exemplified. At this time, it is preferred not to have an acid-decomposable group. As the

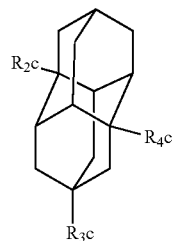
100

alicyclic hydrocarbon structure in the alicyclic hydrocarbon structure substituted with a hydroxyl group or a cyano group, an adamantyl group, a diamantyl group and a norbornane group are preferred. As preferred alicyclic hydrocarbon structure substituted with a hydroxyl group or a cyano group, a partial structure represented by any of the following formulae (VIIa) to (VIIc) is preferred. Adhering property to substrate and affinity with developer are improved by this constitution.

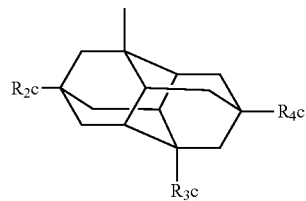
(VIIa)



(VIIb)



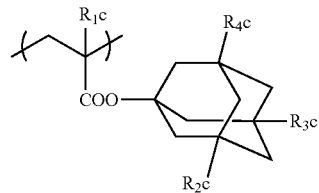
(VIIc)



In formulae (VIIa) to (VIIc), each of R₂c to R₄c independently represents a hydrogen atom, a hydroxyl group or a cyano group, provided that at least one of R₂c to R₄c represents a hydroxyl group, preferably one or two of R₂c to R₄c are a hydroxyl group and the remaining is a hydrogen atom. In formula (VIIa), more preferably two of R₂c to R₄c represent a hydroxyl group and the remaining is a hydrogen atom.

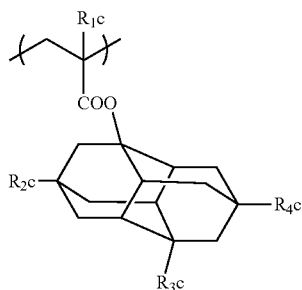
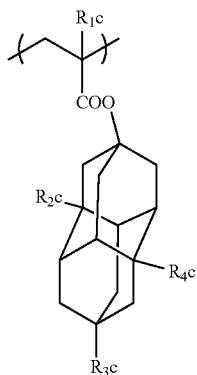
As the repeating unit having the partial structure represented by formula (VIIa), (VIIb) or (VIIc), a repeating unit represented by the following formula (AIIa), (AIIb) or (AIIc) can be exemplified.

(AIIa)



101

-continued

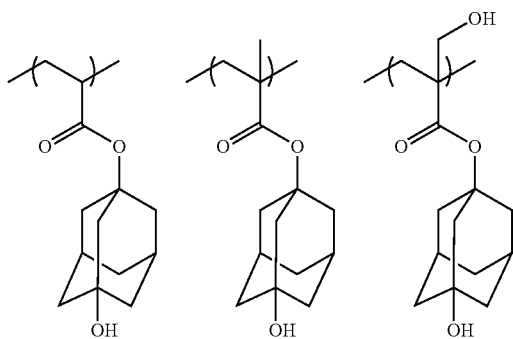


In formulae (AIIa) to (AIIc), R_{1c} represents a hydrogen atom, a methyl group, a trifluoromethyl group or a hydroxymethyl group.

R_{2c} , R_{3c} and R_{4c} respectively have the same meaning with R_2 , R_3 and R_4 in formulae (VIIa) to (VIIc).

Resin (A) may contain or may not contain a repeating unit having a hydroxyl group or a cyano group, but when resin (A) contain the repeating unit, the content of the repeating unit having a hydroxyl group or a cyano group is preferably 1 mol % to 60 mol % to all the repeating units in resin (A), more preferably 3 mol % to 50 mol %, and still preferably 5 mol % to 40 mol %.

The specific examples of repeating units having a hydroxyl group or a cyano group are shown below but the invention is not restricted thereto.

**102**

-continued

(AIIb)

5

10

15

20

(AIIc)

25

30

35

40

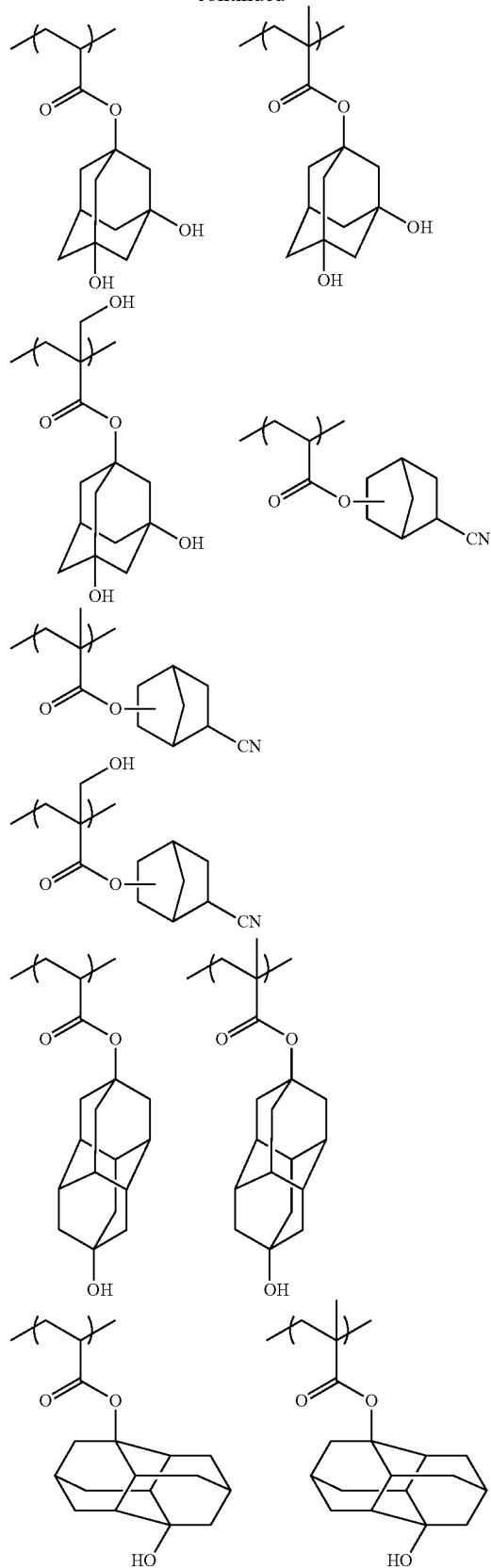
45

50

55

60

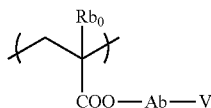
65



Repeating unit (b) may be a repeating unit having a lactone structure as the polar group.

103

As the repeating unit having a lactone structure, a repeating unit represented by the following formula (AII) is more preferred.



In formula (AII), Rb_0 represents a hydrogen atom, a halogen atom or an alkyl group (preferably having a carbon number of 1 to 4) which may have a substituent.

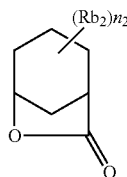
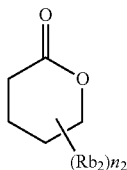
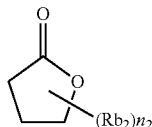
Preferred examples of the substituent which may be substituted on the alkyl group of Rb_0 include a hydroxyl group and a halogen atom. The halogen atom of Rb_0 includes a fluorine atom, a chlorine atom, a bromine atom and an iodine atom. Rb_0 is preferably a hydrogen atom, a methyl group, a hydroxymethyl group or a trifluoromethyl group, more preferably a hydrogen atom or a methyl group.

Ab represents a single bond, an alkylene group, a divalent linking group having a monocyclic or polycyclic cycloalkyl structure, an ether bond, an ester bond, a carbonyl group, or a divalent linking group formed by combining these members. Ab is preferably a single bond or a divalent linking group represented by $-Ab_1-CO_2-$.

Ab_1 is a linear or branched alkylene group or a monocyclic or polycyclic cycloalkylene group and is preferably a methylene group, an ethylene group, a cyclohexylene group, an adamantylene group or a norbornylene group.

V represents a group having a lactone structure.

As the group having a lactone structure, any group may be used as long as it has a lactone structure, but a 5- to 7-membered ring lactone structure is preferred, and a 5- to 7-membered ring lactone structure to which another ring structure is fused to form a bicyclo or Spiro structure is preferred. It is more preferred to contain a repeating unit having a lactone structure represented by any one of the following formulae (LC1-1) to (LC1-17). The lactone structure may be bonded directly to the main chain. Preferred lactone structures are (LC1-1), (LC1-4), (LC1-5), (LC1-6), (LC1-8), (LC1-13) and (LC1-14).



(AII)

5

10

15

20

25

30

35

40

45

LC1-1

50

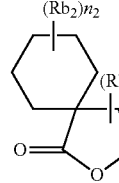
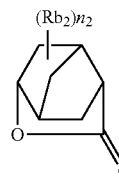
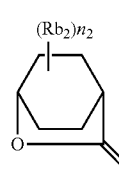
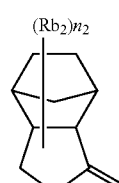
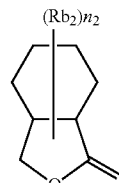
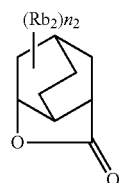
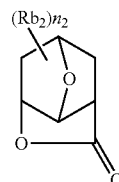
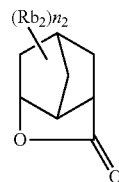
LC1-2

55

LC1-3

60

65



104

-continued

LC1-4

LC1-5

LC1-6

LC1-7

LC1-8

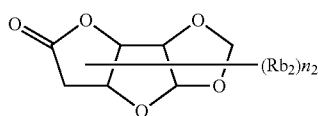
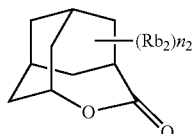
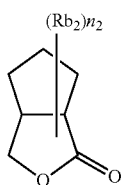
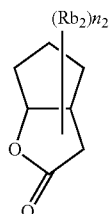
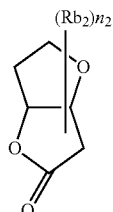
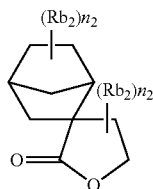
LC1-9

LC1-10

LC1-11

105

-continued



The lactone structure moiety may or may not have a substituent (Rb_2). Preferred examples of the substituent (Rb_2) include an alkyl group having a carbon number of 1 to 8, a monovalent cycloalkyl group having a carbon number of 4 to 7, an alkoxy group having a carbon number of 1 to 8, an alkoxycarbonyl group having a carbon number of 2 to 8, a carboxyl group, a halogen atom, a hydroxyl group, a cyano group and an acid-decomposable group. Among these, an alkyl group having a carbon number of 1 to 4, a cyano group and an acid-decomposable group are more preferred. n_2 represents an integer of 0 to 4. When n_2 is 2 or more, each substituent (Rb_2) may be the same as or different from every other substituents (Rb_2) and also, the plurality of substituents (Rb_2) may combine together to form a ring.

The repeating unit having a lactone group usually has an optical isomer, but any optical isomer may be used. One optical isomer may be used alone or a mixture of a plurality of optical isomers may be used. In the case of mainly using one optical isomer, the optical purity (ee) thereof is preferably 90% or more, more preferably 95% or more.

106

LC1-12

The resin (A) may or may not contain the repeating unit having a lactone structure, but in the case of containing the repeating unit having a lactone structure, the content of the repeating unit in the resin (A) is preferably from 1 to 70 mol %, more preferably from 3 to 65 mol %, still more preferably from 5 to 60 mol %, based on all repeating units.

LC1-13

Specific examples of the lactone structure-containing repeating unit in the resin (A) are illustrated below, but the present invention is not limited thereto. In the formulae, Rx represents H, CH_3 , CH_2OH or CF_3 .

15

LC1-14

20

25

LC1-15

30

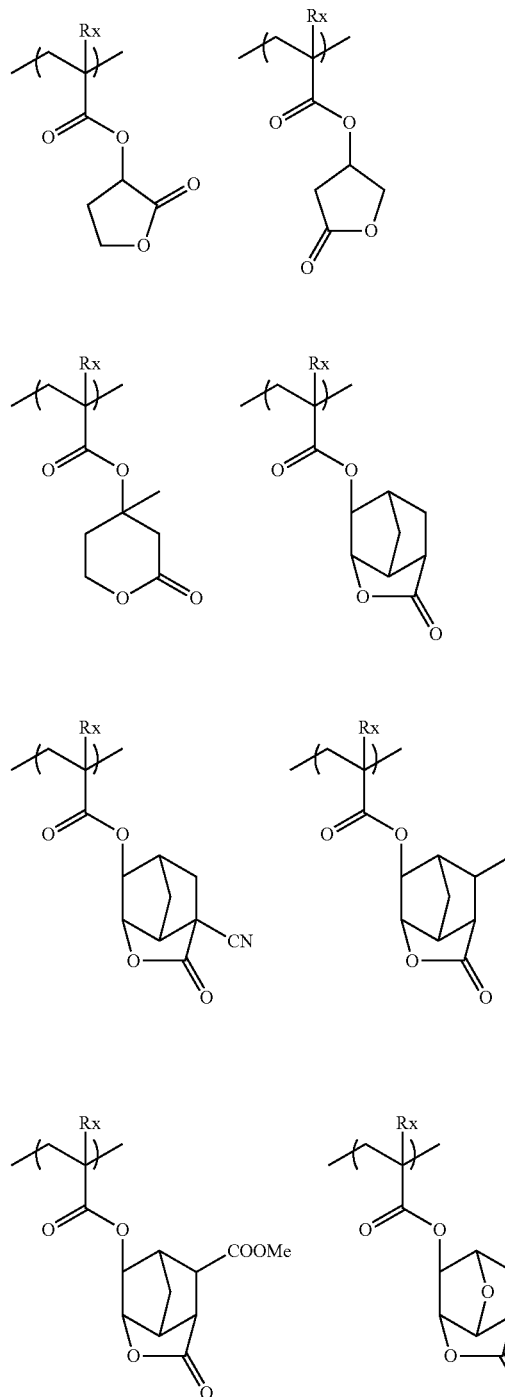
LC1-16

35

40

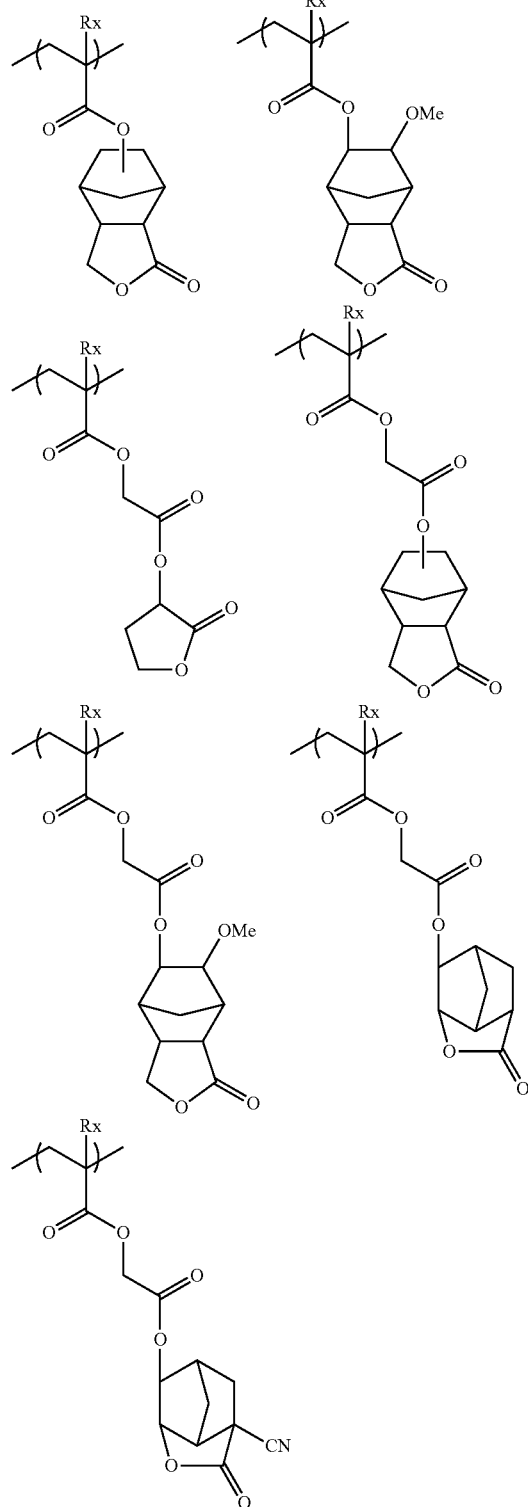
LC1-17

45



107

-continued



The polar group that repeating unit (b) may have is an acid group is also one especially preferred embodiment. As preferred acid groups, a phenolic hydroxyl group, a carboxylic acid group, a sulfonic acid group, a fluorinated alcohol group (e.g., a hexafluoroisopropanol group), a sulfonamide group, a sulfonylimido group, an (alkylsulfonyl)(alkylcarbonyl)methylene group, an (alkylsulfonyl)(alkylcarbonyl)-imido group,

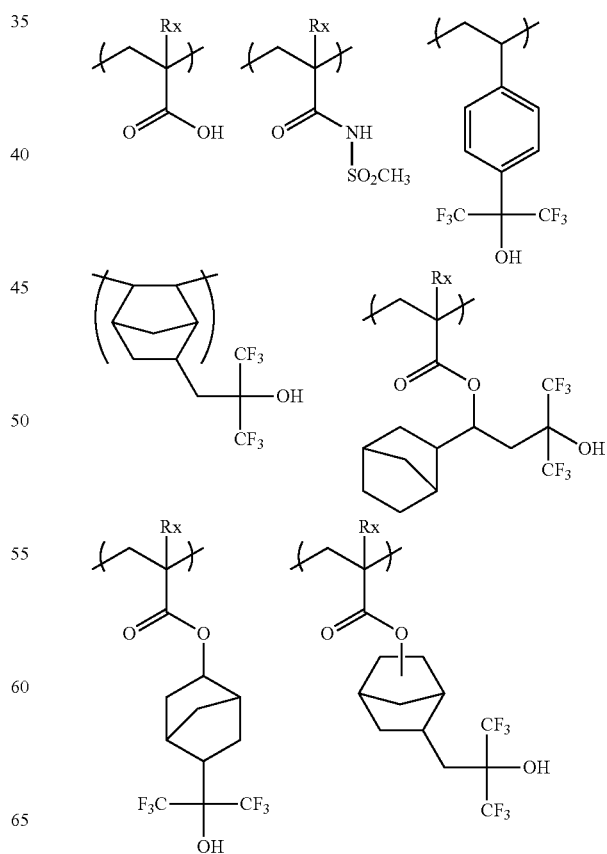
108

a bis(alkylcarbonyl)methylene group, a bis(alkylcarbonyl)imido group, a bis(alkylsulfonyl)methylene group, a bis(alkylsulfonyl)imido group, a tris-(alkylcarbonyl)methylene group, and a tris(alkylsulfonyl)methylene group are exemplified. It is more preferred that repeating unit (b) is a repeating unit having a carboxyl group. By containing a repeating unit having an acid group, resolution in a use for contact hole increases. As repeating units having an acid group, a repeating unit having an acid group directly bonded to the main chain of the resin such as a repeating unit by an acrylic acid or a methacrylic acid, a repeating unit having an acid group bonded to the main chain of the resin via a linking group, and a repeating unit having an acid group introduced to the terminal of the polymer chain by using a polymerization initiator or a chain transfer agent at the time of polymerization are known and all of them are preferred. Especially preferred is a repeating unit by an acrylic acid or a methacrylic acid.

An acid group that repeating unit (b) can have may contain or may not contain an aromatic ring, but when an aromatic ring is contained, the aromatic ring is preferably selected from acid groups other than a phenolic hydroxyl group. When repeating unit (b) has an acid group, the content of the repeating unit having an acid group is preferably 30 mol % or less to all the repeating units in resin (A), and more preferably 20 mol % or less. When resin (A) contains a repeating unit having an acid group, the content of the repeating unit having an acid group in resin (A) is generally 1 mol % or more.

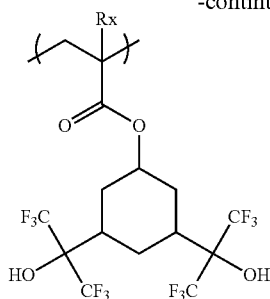
The specific examples of repeating units having an acid group are shown below but the invention is not restricted thereto.

In the specific examples, Rx represents H, CH₃, CH₂OH or CF₃.

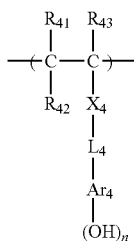


109

-continued



Resin (A) according to the invention can contain non-acid-decomposable repeating unit (b) having a phenolic hydroxyl group. As repeating unit (b) in this case, a structure represented by the following formula (I) is more preferred.



In formula (I), each of R_{41} , R_{42} and R_{43} independently represents a hydrogen atom, an alkyl group, a halogen atom, a cyano group or an alkoxy carbonyl group, provided that R_{42} may be bonded to Ar_4 to form a ring, and R_{42} represents a single bond or an alkylene group in that case.

X_4 represents a single bond, $-COO-$ or $-CONR_{64}-$, and R_{64} represents a hydrogen atom or an alkyl group.

L_4 represents a single bond or an alkylene group.

Ar_4 represents an $(n+1)$ -valent aromatic ring group, and when Ar_4 is bonded to R_{42} to form a ring, Ar_4 represents an $(n+2)$ -valent aromatic ring group.

n represents an integer of 1 to 4.

The specific examples of the alkyl group, cycloalkyl group, halogen atom, alkoxy carbonyl group of R_{41} , R_{42} and R_{43} in formula (I) and the substituents that these groups can have are the same with the specific examples as described in each group of R_{51} , R_{52} and R_{53} in formula (V).

Ar_4 represents an $(n+1)$ -valent aromatic ring group. The divalent aromatic ring group in the case where n is 1 may have a substituent. For example, an arylene group having 6 to 18 carbon atoms, e.g., a phenylene group, a tolylene group, a naphthylene group, and an anthracenylene, and an aromatic ring group containing a heterocyclic ring such as thiophene, furan, pyrrole, benzothiophene, benzofuran, benzopyrrole, triazine, imidazole, benzimidazole, triazole, thiazole or thiazole are preferably exemplified.

As the specific example of the $(n+1)$ -valent aromatic ring group in the case where n represents an integer of 2 or more, a group obtained by removing arbitrary $(n-1)$ -number of hydrogen atom(s) from any of the above-described specific examples of the divalent aromatic ring groups can be preferably exemplified.

The $(n+1)$ -valent aromatic ring group may further have a substituent.

As the substituents that the above alkyl group, cycloalkyl group, alkoxy carbonyl group, alkylene group, and $(n+1)$ -

110

valent aromatic ring group may have, the alkyl group, methoxy group, ethoxy group, hydroxyethoxy group, propoxy group, hydroxypropoxy group, alkoxy group such as a butoxy, and aryl group such as a phenyl group enumerated in R_{51} , R_{52} or R_{53} in formula (V) are exemplified.

As the alkyl group of R_{64} in $-CONR_{64}-$ (wherein R_{64} represents a hydrogen atom or an alkyl group) represented by X_4 , the same alkyl groups as in the alkyls group represented by each of R_{61} to R_{63} are exemplified.

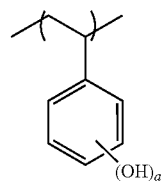
X_4 preferably represents a single bond, $-COO-$ or $-CONH-$, and more preferably a single bond or $-COO-$.

As the alkylene group represented by L_4 , preferably an alkylene group having 1 to 8 carbon atoms, e.g., a methylene group, an ethylene group, a propylene group, a butylenes group, a hexylene group, and an octylene group are exemplified, each of which group may have a substituent.

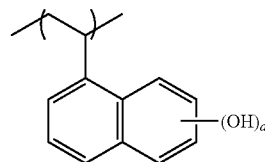
As Ar_4 , an aromatic ring group having 6 to 18 carbon atoms which may have a substituent is more preferred, and a benzene ring group, a naphthalene ring group and a biphenylene ring group are especially preferred.

It is preferred for repeating unit (b) to have a hydroxystyrene structure. That is, Ar_4 is preferably a benzene ring group.

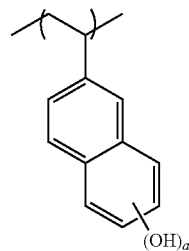
The specific examples of repeating unit (b) represented by formula (I) are shown below, but the invention is not restricted thereto. In the following formulae, a represents an integer of 1 or 2.



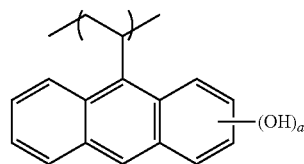
(B-1)



(B-2)



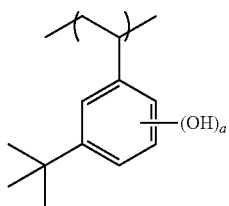
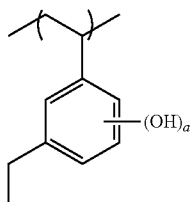
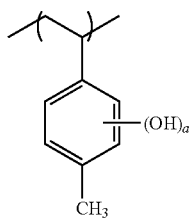
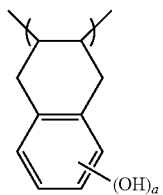
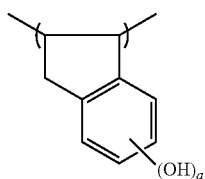
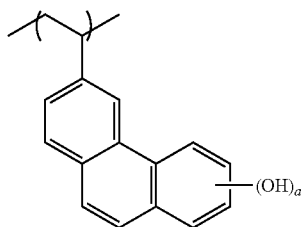
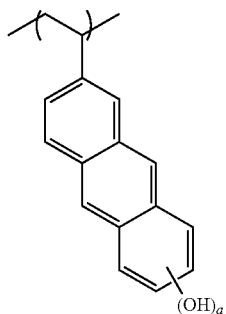
(B-3)



(B-4)

111

-continued

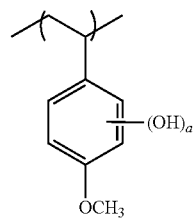
**112**

-continued

(B-5)

5

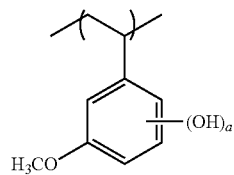
10



(B-12)

(B-6) 15

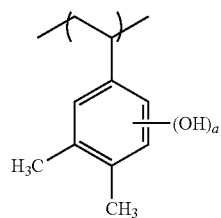
20



(B-13)

(B-7) 25

30

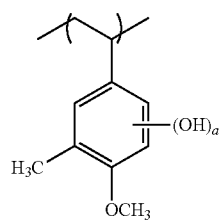


(B-14)

(B-8)

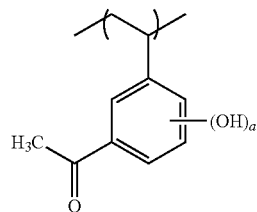
35

(B-9) 40



(B-15)

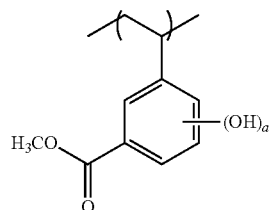
45



(B-16)

(B-10) 50

55

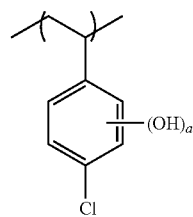


(B-17)

(B-11)

60

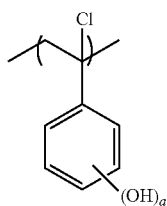
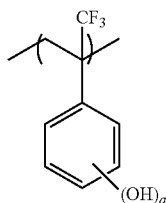
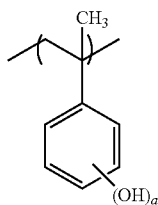
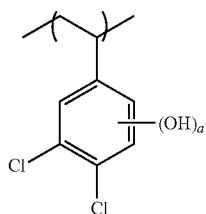
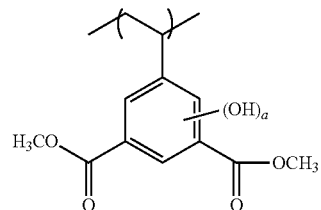
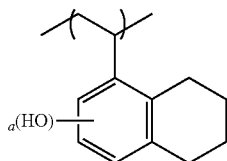
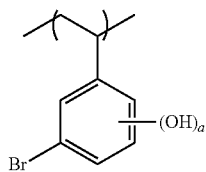
65



(B-18)

113

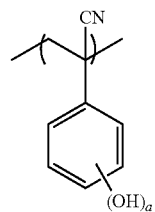
-continued

**114**

-continued

(B-19)

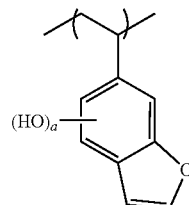
5



(B-26)

(B-20)

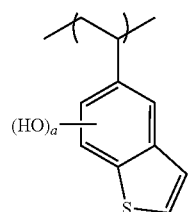
10



(B-27)

(B-21)

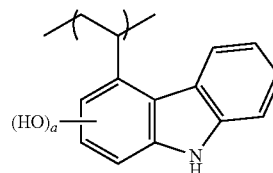
20



(B-28)

(B-22)

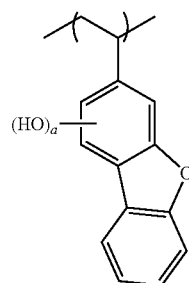
30



(B-29)

(B-23)

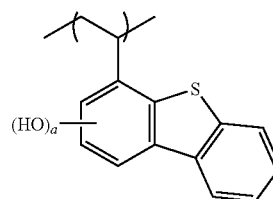
40



(B-30)

(B-24)

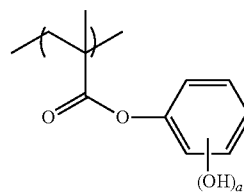
50



(B-31)

(B-25)

60

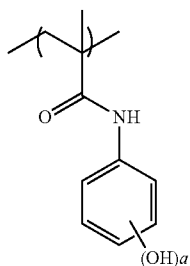
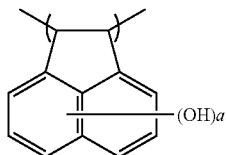
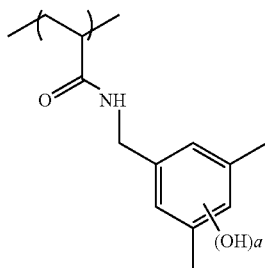
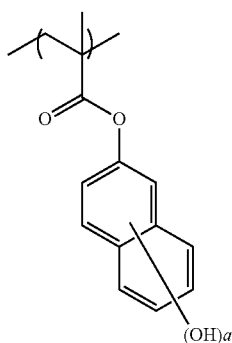
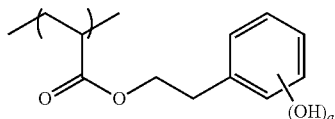
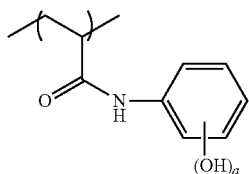


(B-32)

65

115

-continued



Resin (A) may contain two or more kinds of repeating units represented by formula (I).

A repeating unit having a phenolic hydroxyl group such as repeating unit (b) represented by formula (I) has a tendency to heighten the solubility of resin (A) in an organic solvent, and so there are cases where the repeating unit is preferably not added in a large amount in the point of resolution. This ten-

116

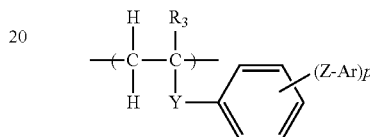
dency reveals more strongly in repeating units deriving from hydroxystyrenes (that is, the case where both X_4 and L_4 represent a single bond in formula (I)), and the cause is not clear but it is presumed for the reason that the phenolic hydroxyl group is present in the vicinity of the main chain. Thus, in the invention, the content of the repeating unit represented by formula (I) (for example, the repeating unit represented by formula (I), in which both X_4 and L_4 represent a single bond) is preferably 4 mol % or less on the basis of all the repeating units in resin (A), more preferably 2 mol % or less, and most preferably 0 mol % (that is, the repeating unit is not contained).

(c) Repeating Unit Having a Plurality of Aromatic Rings

Resin (A) may have repeating unit (c) having a plurality of aromatic rings represented by the following formula (c1).

(B-35)

(c1)



In formula (c1), R_3 represents a hydrogen atom, an alkyl group, a halogen atom, a cyano group or a nitro group; Y represents a single bond or a divalent linking group; Z represents a single bond or a divalent linking group; Ar represents an aromatic ring group; and p represents an integer of 1 or more.

The alkyl group represented by R_3 may be straight chain or branched, and, for example, a methyl group, an ethyl group, an n-propyl group, an i-propyl group, an n-butyl group, a sec-butyl group, a t-butyl group, an n-pentyl group, an n-hexyl group, an n-heptyl group, an n-octyl group, an n-nonyl group, an n-decanyl group, and an i-butyl group are exemplified. Each of these groups may further have a substituent, and as preferred substituents, an alkoxy group, a hydroxyl group, a halogen atom and a nitro group are exemplified. As the alkyl group having a substituent, a CF_3 group, an alkyloxycarbonylmethyl group, an alkylcarbonyloxymethyl group, a hydroxymethyl group, and an alkoxyethyl group are preferred.

As the halogen atom represented by R_3 , a fluorine atom, a chlorine atom, a bromine atom and an iodine atom are exemplified, and a fluorine atom is especially preferred.

Y represents a single bond or a divalent linking group. The examples of the divalent linking groups include, e.g., an ether group (an oxygen atom), a thioether group (a sulfur atom), an alkylene group, an arylene group, a carbonyl group, a sulfide group, a sulfone group, $-COO-$, $-CONH-$, $-SO_2NH-$, $-CF_2-$, $-CF_2CF_2-$, $-OCF_2O-$, $-CF_2OCF_2-$, $-SS-$, $-CH_2SO_2CH_2-$, $-CH_2COCH_2-$, $-COCF_2CO-$, $-COCO-$, $-OCOO-$, $-OSO_2O-$, an amino group (a nitrogen atom), an acyl group, an alkylsulfonyl group, $-CH=CH-$, $-C\equiv C-$, an aminocarbonylamino group, an aminosulfonylamino group, and a group obtained by combining these groups. The number of carbon atoms of Y is preferably 15 or less, and more preferably 10 or less.

Y preferably represents a single, a $-COO-$ group, a $-COS-$ group, or a $-CONH-$ group, more preferably a $-COO-$ group or a $-CONH-$ group, and especially preferably a $-COO-$ group.

117

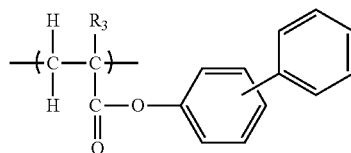
Z represents a single bond or a divalent linking group. The examples of the divalent linking groups include, e.g., an ether group (an oxygen atom), a thioether group (a sulfur atom), an alkylene group, an arylene group, a carbonyl group, a sulfide group, a sulfone group, $-\text{COO}-$, $-\text{CONH}-$, $-\text{SO}_2\text{NH}-$, an amino group (a nitrogen atom), an acyl group, an alkylsulfonyl group, $-\text{CH}=\text{CH}-$, an aminocarbonylamino group, an aminosulfonylamino group, and a group obtained by combining these groups.

Z preferably represents a single bond, an ether group, a carbonyl group or $-\text{COO}-$, more preferably a single bond or an ether group, and especially preferably a single bond.

Ar represents an aromatic ring group, specifically a phenyl group, a naphthyl group, an anthracenyl group, a phenanthrenyl group, a quinolinyl group, a furanyl group, a thiophenyl group, a fluorenyl-9-on-yl group, an anthraquinonyl group, a phenanthraquinonyl group, and a pyrrole group are exemplified, and a phenyl group is preferred. These aromatic ring groups may further have a substituent. As preferred substituents, an alkyl group, an alkoxy group, a hydroxyl group, a halogen atom, a nitro group, an acyl group, an acyloxy group, an acylamino group, a sulfonylamino group, aryl group, e.g., a phenyl group, an aryloxy group, an arylcarbonyl group, and a heterocyclic residue are exemplified. Of these groups, a phenyl group is preferred from the viewpoint of capable of controlling deterioration of exposure latitude attributable to out-of-band light beam and deterioration of the pattern shape.

p is an integer of 1 or more, and preferably an integer of 1 to 3.

Repeating unit (c) is more preferably a repeating unit represented by the following formula (c2).



In formula (c2), R_3 represents a hydrogen atom or an alkyl group. The preferred alkyl groups represented by R_3 are the same with those in formula (c1).

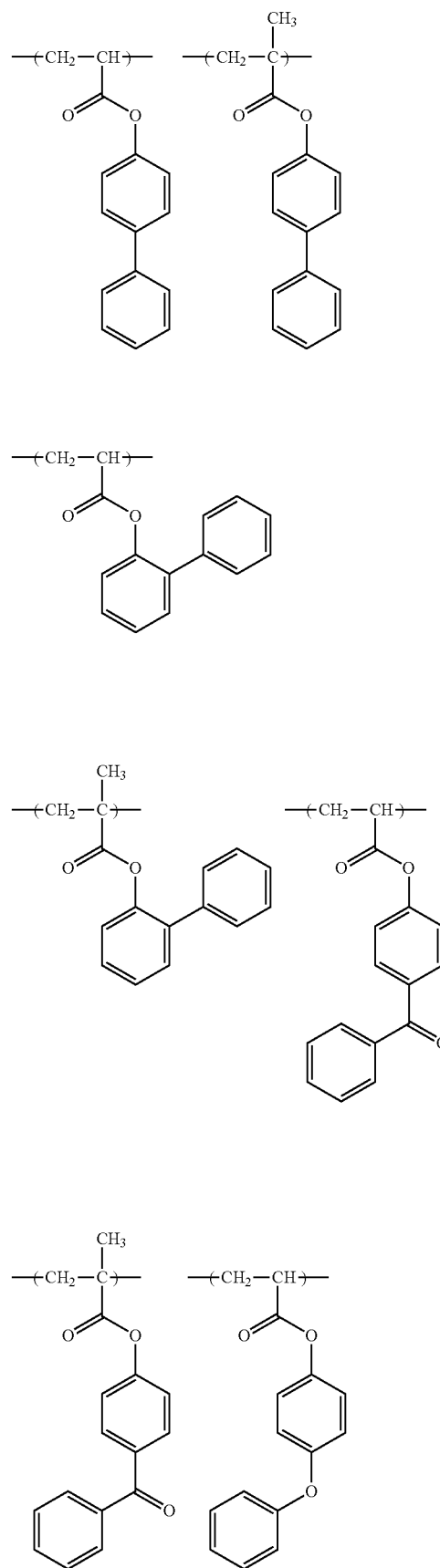
Concerning extreme ultraviolet radiation (EUV ray) exposure, leaking light (out-of-band light) occurring in ultraviolet region of wavelength of 100 nm to 400 nm deteriorates surface roughness, and as a result resolution and LWR performance are liable to lower due to bridge between patterns and breakage of the pattern.

However, the aromatic ring in repeating unit (c) functions as the inside filter capable of absorbing the above-described out-of-band light. Accordingly, from the aspects of high resolution and low LWR, it is preferred for resin (A) to contain repeating unit (c).

Here, for obtaining high resolution, it is preferred that repeating unit (c) does not contain a phenolic hydroxyl group (a hydroxyl group directly bonded onto the aromatic ring).

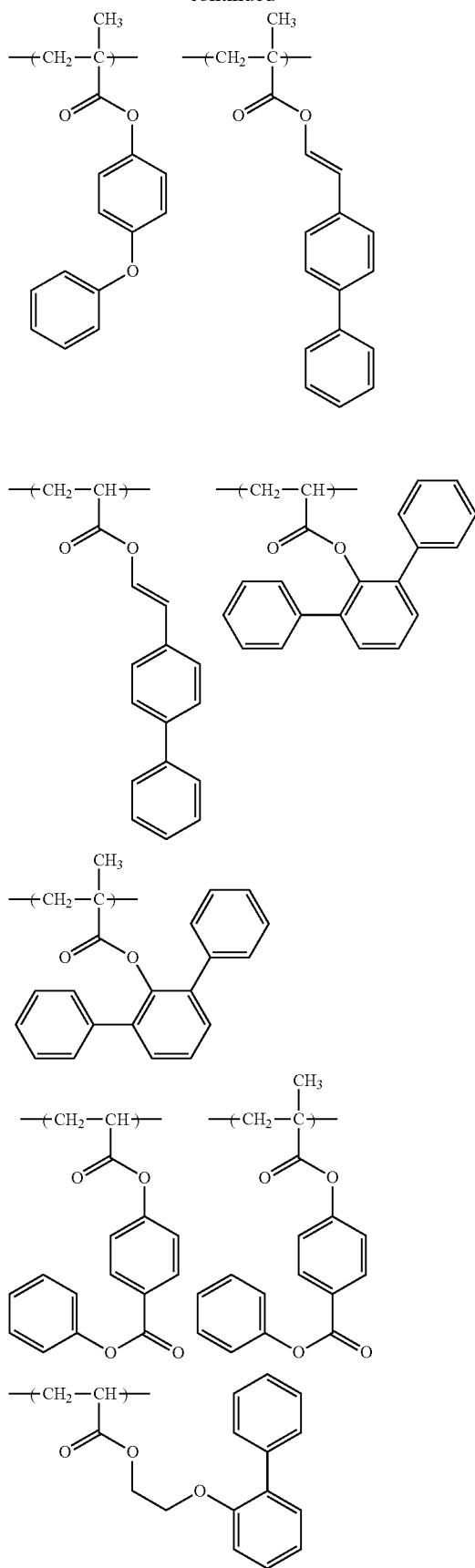
The specific examples of repeating unit (c) are shown below, but the invention is not restricted thereto.

118

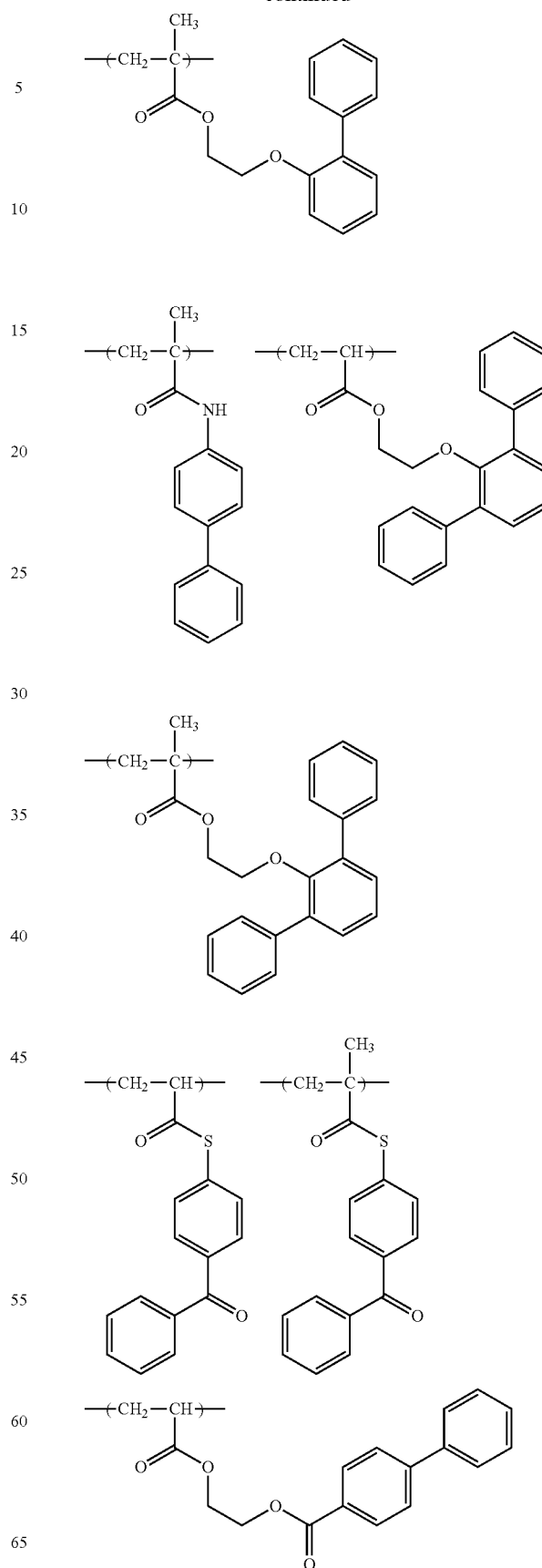


119

-continued

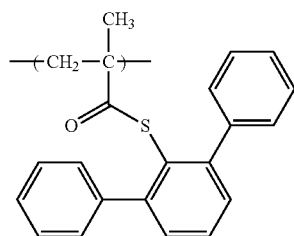
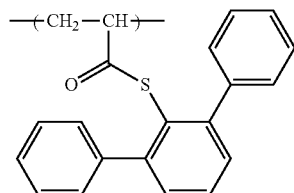
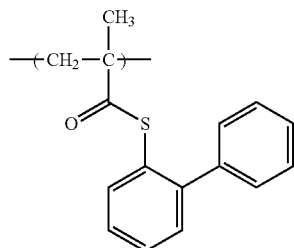
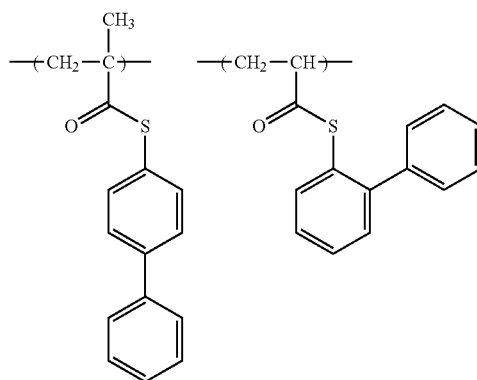
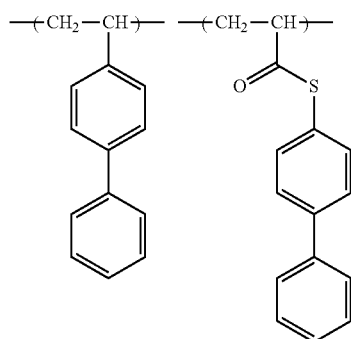
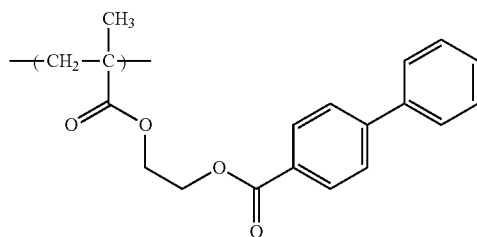
**120**

-continued

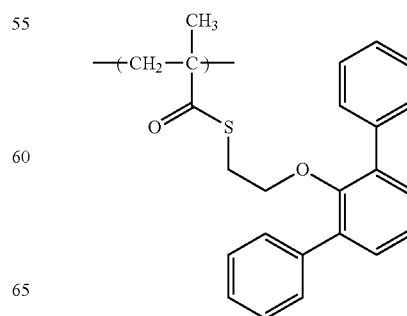
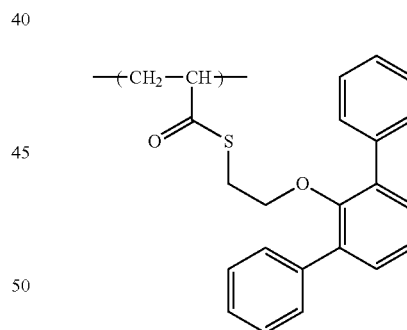
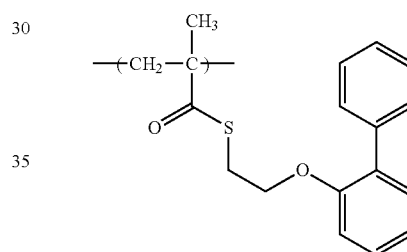
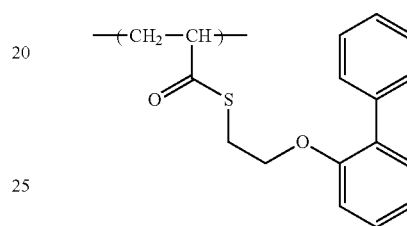
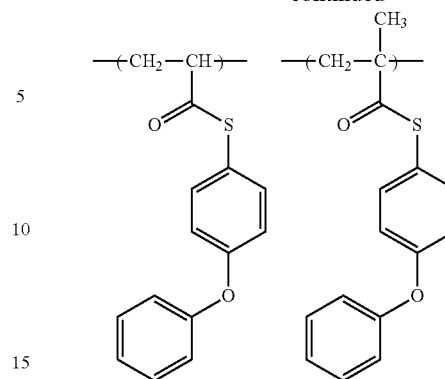


121

-continued

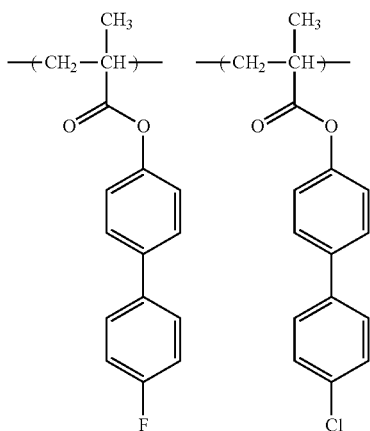
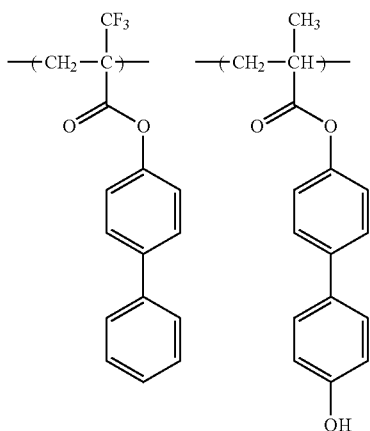
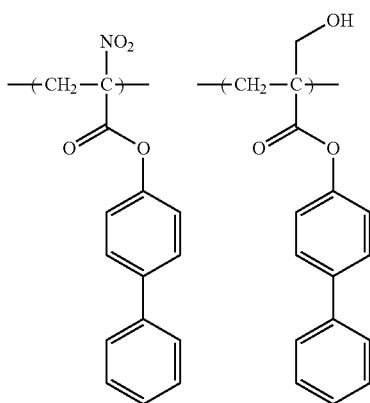
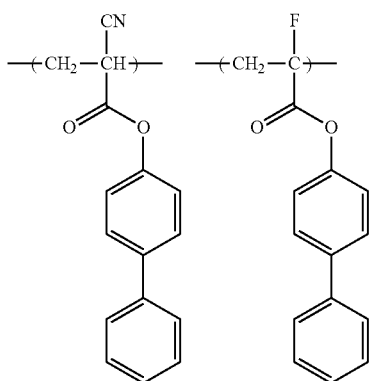
**122**

-continued



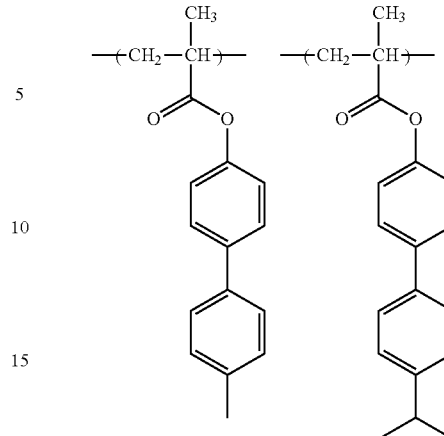
123

-continued



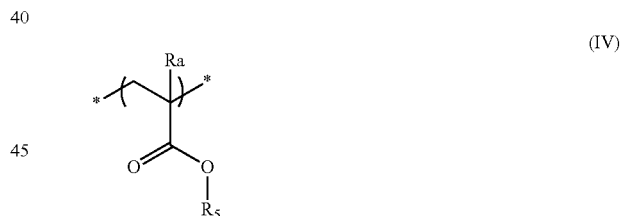
124

-continued



20 Resin (A) may contain or may not contain repeating unit (c), but when resin (A) contains repeating unit (c), the content of repeating unit (c) is preferably in the range of 1 mol % to 30 mol % to all the repeating units in resin (A), more preferably in the range of 1 mol % to 20 mol %, and still preferably in the range of 1 mol % to 15 mol %.

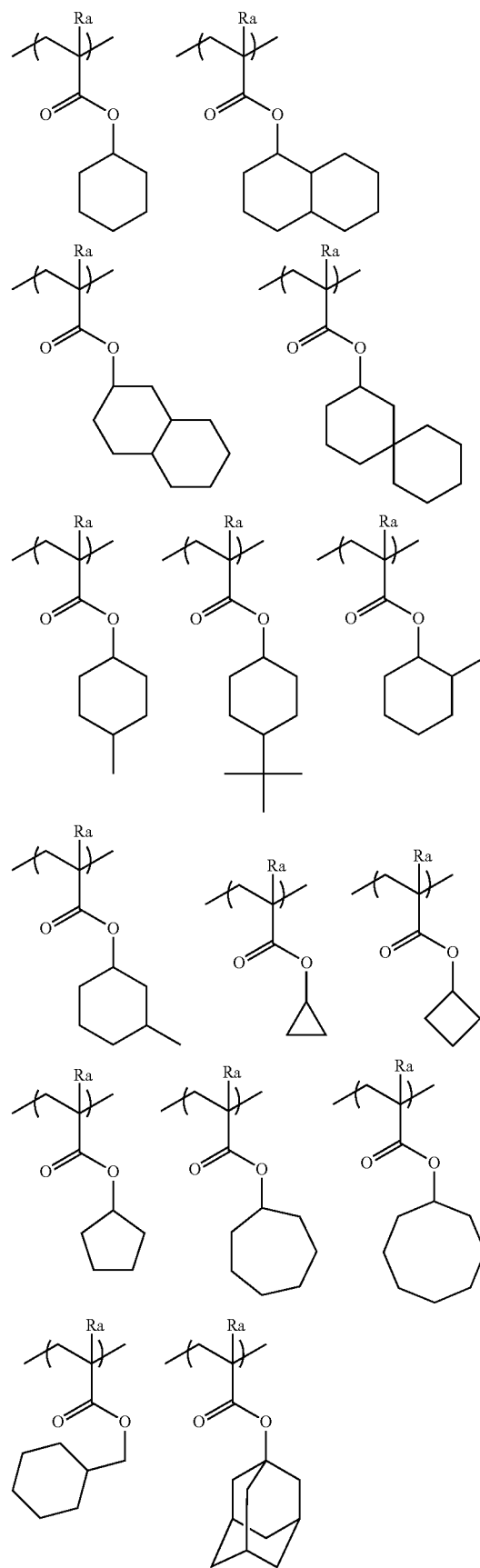
25 Resin (A) may contain two or more kinds of repeating units (c) in combination. Resin (A) in the invention may arbitrarily contain repeating units other than repeating units (a) to (c). As an example of such other repeating unit, resin (A) can contain a repeating unit having an alicyclic hydrocarbon structure not having further polar groups (for example, the above shown acid group, hydroxyl group and cyano group) and not showing acid decomposition property, by which the solubility of the resin can be properly adjusted at the time of development using a developer containing an organic solvent. As such a repeating unit, a repeating unit represented by the following formula (IV) can be exemplified.



50 In formula (IV), R₅ represents a hydrocarbon group having at least one cyclic structure and having no polar group.

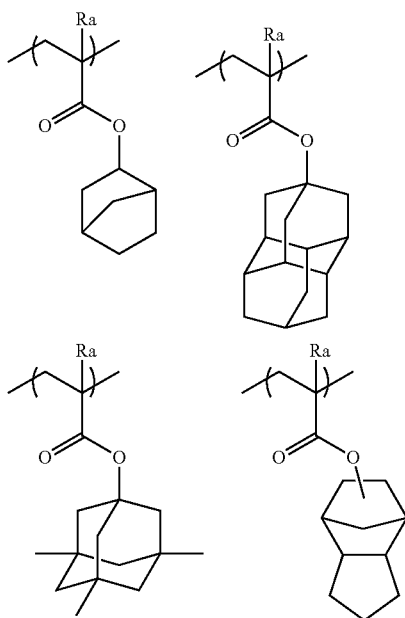
R_a represents a hydrogen atom, an alkyl group or a —CH₂—O—R_{a2} group, wherein R_{a2} represents a hydrogen atom, an alkyl group or an acyl group. R_a is preferably a hydrogen atom, a methyl group, a hydroxymethyl group or a trifluoromethyl group, more preferably a hydrogen atom or a methyl group.

The cyclic structure contained in R₅ includes a monocyclic hydrocarbon group and a polycyclic hydrocarbon group. Examples of the monocyclic hydrocarbon group include a cycloalkyl group having a carbon number of 3 to 12, such as cyclopentyl group, cyclohexyl group, cycloheptyl group and cyclooctyl group, and a cycloalkenyl group having a carbon number of 3 to 12, such as cyclohexenyl group. The monocyclic hydrocarbon group is preferably a monocyclic hydrocarbon group having a carbon number of 3 to 7, more preferably a cyclopentyl group or a cyclohexyl group.

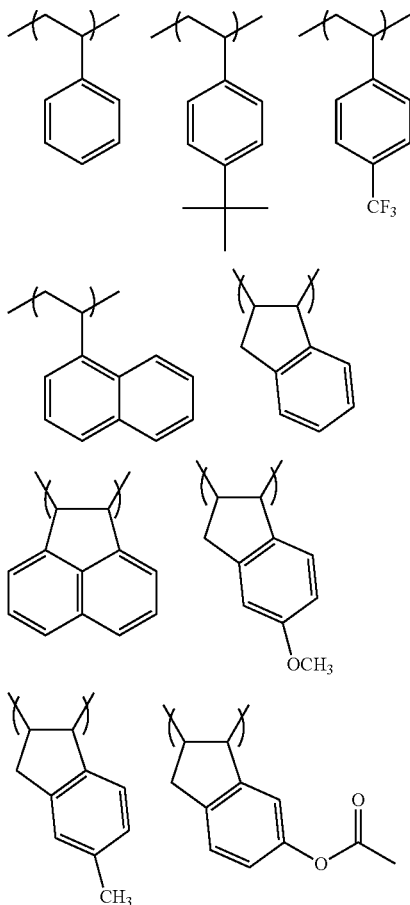


127

-continued

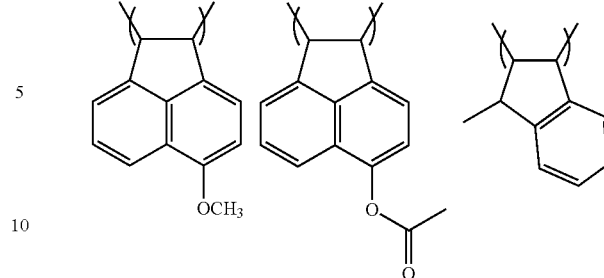


Resin (A) may also contain the following monomer components in view of the improvements of Tg and dry etching resistance, and effect of inside filter for out-of-band light.



128

-continued



In resin (A) for use in the composition of the invention, the content molar ratio of each repeating structural unit is properly set for regulating the dry etching resistance, standard developer aptitude, adhesion to the substrate, resist profile, and generally required performances of the resist such as resolution, heat resistance and sensitivity.

The form of resin (A) may be any of random, block, comb and star types.

Resin (A) can be synthesized by, for example, radical polymerization, cationic polymerization, or anionic polymerization of unsaturated monomer corresponding to each structure. It is also possible to obtain an objective resin by polymerization with an unsaturated monomer corresponding to the precursor of each structure, and then by performing polymeric reaction.

For example, as general synthesizing methods, batch polymerization of performing polymerization by dissolving an unsaturated monomer and a polymerization initiator in a solvent and heating, and drop polymerization of adding a solution of an unsaturated monomer and a polymerization initiator to a heated solvent by dropping over 1 to 10 hours are given, and drop polymerization is preferred.

As the solvents for use in polymerization, for example, solvents which can be used in manufacturing the later-described electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition can be exemplified, and more preferably it is preferred to perform polymerization by using the same solvents with the solvents used in the composition of the invention. By using the same solvents, generation of particles during preservation can be inhibited.

Polymerization reaction is preferably carried out in the atmosphere of inert gases such as nitrogen and argon gas. Polymerization is initiated with commercially available radical initiators as polymerization initiators (azo initiators, peroxides and the like). Azo initiators are preferred as radical initiators and, for example, azo initiators having an ester group, a cyano group, or a carboxyl group are preferably used. As preferred initiators, azobisisobutyronitrile, azobisisobutyronitrile, and dimethyl-2,2'-azobis(2-methylpropionate) are exemplified. If necessary, polymerization may be performed in the presence of a chain transfer agent (e.g., alkyl mercaptan and the like).

The reaction concentration is 5% by mass to 70% by mass, and preferably 10% by mass to 50% by mass. The reaction temperature is generally 10° C. to 150° C., preferably 30° C. to 120° C., and more preferably 40° C. to 100° C.

The reaction temperature is generally 1 hour to 48 hours, preferably 1 hour to 24 hours, and more preferably 1 hour to 12 hours.

After termination of the reaction, the temperature is allowed to be cooled to room temperature, and followed by purification. Various ordinary methods can be applied to the purification. For example, purification methods in the state of

a solution such as washing, liquid-liquid extraction of combining proper solvents to remove residual monomer and oligomer components, and ultrafiltration of extractive removal of only the monomer components of a molecular weight lower than the prescribed molecular weight, and purification in a solid state such as reprecipitation of removing residual monomers and the like by dropping a resin solution into a poor solvent to coagulate the resin in the poor solvent, and washing the filtered resin slurry with a poor solvent can be used. For example, the resin is precipitated as a solid by bringing the solvent in which the resin is hardly soluble or insoluble (poor solvent) into contact with the reaction solution in a volume amount of the solvent of 10 times or less of the reaction solution, and preferably in a volume amount of 10 to 5 times.

Poor solvents are sufficient as the solvents for use in the process of precipitation or reprecipitation from the polymer solution (precipitation or reprecipitation solvents), and such solvents can be arbitrarily selected from among hydrocarbon, hydrocarbon halide, a nitro compound, ether, ketone, ester, carbonate, alcohol, carboxylic acid, water, and mixed solvents containing these solvents according to the kinds of polymers. Of these solvents, solvents containing at least alcohol (in particular, methanol) or water are preferred as precipitation or reprecipitation solvents.

The use amount of the precipitation or reprecipitation solvent can be arbitrarily selected by considering efficiency and yield, but is generally 100 parts by mass to 10,000 parts by mass to 100 parts by mass of the polymer solution, preferably 200 parts by mass to 2,000 parts by mass, and more preferably 300 parts by mass to 1,000 parts by mass.

The temperature at the time of precipitation or reprecipitation can be arbitrarily selected by considering efficiency and operating conditions, but is generally 0° C. to 50° C. or so, and preferably around room temperature (e.g., about 20° C. to 35° C.). Precipitation or reprecipitation can be performed by known methods such as a batch system or continuous system with conventional mixers such as a stirring tank.

A precipitated or reprecipitated polymer is generally subjected to filtration, conventional solid-liquid separation such as centrifugation, drying, and then used. Filtration is preferably performed under pressure with a solvent-resisting filter material. Drying is carried out under normal pressure or reduced pressure (preferably under reduced pressure) at temperature of about 30° C. to 100° C., and preferably 30° C. to 50° C. or so.

Once precipitated and separated resin may be again dissolved in a solvent and brought into contact with the solvent in which the resin is hardly soluble or insoluble. That is, after termination of the above radical polymerization reaction, the reaction solution may be purified by a purification method containing steps of bringing the reaction solution into contact with the solvent in which the resin is hardly soluble or insoluble to precipitate the resin (step a), separating the resin from the solution (step b), dissolving the resin again in a solvent to prepare resin solution A (step c), bringing the solvent in which the resin is hardly soluble or insoluble into contact with resin solution A in a volume amount of the solvent less than 10 times of the resin solution A (preferably in a volume amount of 5 times or less) to precipitate the solid of the resin (step d), and separating the precipitated (step e).

Polymerization reaction is preferably carried out in the atmosphere of inert gases such as nitrogen and argon gas. Polymerization is initiated with commercially available radical initiators as polymerization initiators (azo initiators, peroxides and the like). Azo initiators are preferred as radical initiators and, for example, azo initiators having an ester

group, a cyano group, or a carboxyl group are preferably used. As preferred initiators, azobisisobutyronitrile, azobisdimethylvaleronitrile, and dimethyl-2,2'-azobis(2-methylpropionate) are exemplified. The initiator is added according to necessity or added in parts, and after the reaction, the reaction solution is put into a solvent and a desired polymer is recovered by a method of powder recovery or solid recovery. The reaction concentration is 5% by mass to 50% by mass, and preferably 10% by mass to 30% by mass. The reaction temperature is generally 10° C. to 150° C., preferably 30° C. to 120° C., and more preferably 60° C. to 100° C.

The molecular weight of resin (A) in the invention is not especially restricted, but the weight average molecular weight is preferably in the range of 1,000 to 100,000, more preferably in the range of 1,500 to 60,000, and especially preferably in the range of 2,000 to 30,000. By bringing the weight average molecular weight into the range of 1,000 to 100,000, deterioration of heat resistance and dry etching resistance can be prevented, and degradation of developing property and film-forming property due to high viscosity can also be prevented. The weight average molecular weight of the resin here shows the polystyrene equivalent molecular weight measured by GPC (carrier: THF or N-methyl-2-pyrrolidone (NMP)).

Polydispersity (Mw/Mn) is preferably 1.00 to 5.00, more preferably 1.03 to 3.50, and still more preferably 1.05 to 2.50. The smaller the molecular weight, the more excellent are resolution and resist form. Further, the side wall of the resist pattern is smooth and excellent in roughness performance.

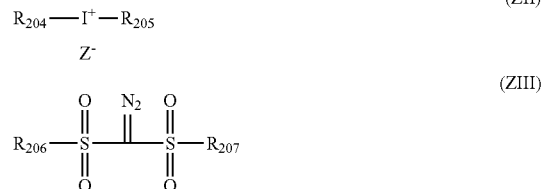
Resin (A) of the invention may be used by one kind alone, or two or more in combination. The content of resin (A) is preferably 20% by mass to 99% by mass based on all the solid contents in the actinic ray-sensitive or radiation-sensitive resin compositions in the invention, more preferably 30% by mass to 89% by mass, and especially preferably 40% by mass to 79% by mass.

[2] Compound Capable of Generating Acid Upon Irradiation with Actinic Ray or Radiation (B)

The composition of the invention contains a compound capable of generating an acid upon irradiation with actinic ray or radiation (hereinafter also referred to as "an acid generator").

Known acid generators can be used with no particular limitation, but compounds capable of generating organic acids, e.g., at least any of a sulfonic acid, bis(alkylsulfonyl) imide and tris(alkylsulfonyl)methide by irradiation with actinic ray or radiation are preferably used.

More preferably, the compound represented by the following formula (ZI), (ZII) or (ZIII) can be exemplified.



In formula (ZI), each of R₂₀₁, R₂₀₂ and R₂₀₃ independently represents an organic group.

131

The number of carbon atoms of the organic groups of R_{201} , R_{202} and R_{203} is generally 1 to 30, and preferably 1 to 20.

Two of R_{201} , R_{202} and R_{203} may be bonded to form a cyclic structure, and an oxygen atom, a sulfur atom, an ester bond, an amido bond, or a carbonyl group may be contained in the ring. As the group to be formed by bonding of two of R_{201} , R_{202} and R_{203} , an alkylene group (e.g., a butylene group and a pentylene group) can be given.

Z^- represents a non-nucleophilic anion (an anion which is extremely low in capability of causing nucleophilic reaction).

The examples of the non-nucleophilic anions include, e.g., a sulfonic acid anion (an aliphatic sulfonic acid anion, an aromatic sulfonic acid anion, a camphor sulfonic acid anion), a carboxylic acid anion (an aliphatic carboxylic acid anion, an aromatic carboxylic acid anion, an aralkylcarboxylic acid anion), a sulfonylimide anion, a bis(alkylsulfonyl)imide anion, and a tris(alkylsulfonyl)methide anion.

The aliphatic sites in the aliphatic sulfonic acid anion and the aliphatic carboxylic acid anion may be an alkyl group or a cycloalkyl group, and preferably a straight chain or branched alkyl group having 1 to 30 carbon atoms and cycloalkyl group having 3 to 30 carbon atoms are exemplified.

The aromatic group in the aromatic sulfonic acid anion and the aromatic carboxylic acid anion is preferably an aryl group having 6 to 14 carbon atoms, e.g., a phenyl group, a tolyl group, and a naphthyl group are exemplified.

The alkyl group, cycloalkyl group and aryl group described above may have a substituent. As the specific examples of the substituents, a nitro group, a halogen atom, e.g., a fluorine atom, a carboxyl group, a hydroxyl group, an amino group, a cyano group, an alkoxy group (preferably having 1 to 15 carbon atoms), a cycloalkyl group (preferably having 3 to 15 carbon atoms), an aryl group (preferably having 6 to 14 carbon atoms), an alkoxycarbonyl group (preferably having 2 to 7 carbon atoms), an acyl group (preferably having 2 to 12 carbon atoms), an alkoxycarbonyloxy group (preferably having 2 to 7 carbon atoms), an alkylthio group (preferably having 1 to 15 carbon atoms), an alkylsulfonyl group (preferably having 1 to 15 carbon atoms), an alkyliminosulfonyl group (preferably having 2 to 15 carbon atoms), an aryloxysulfonyl group (preferably having 6 to 20 carbon atoms), an alkylaryloxysulfonyl group (preferably having 7 to 20 carbon atoms), a cycloalkylaryloxysulfonyl group (preferably having 10 to 20 carbon atoms), an alkylalkoxyalkoxy group (preferably having 5 to 20 carbon atoms), and a cycloalkylalkoxyalkoxy group (preferably having 8 to 20 carbon atoms) are exemplified. In connection with the aryl group and the cyclic structure of each group, an alkyl group (preferably having 1 to 15 carbon atoms) can further be exemplified as the substituent.

As the aralkyl group in the aralkylcarboxylic acid anion, preferably an aralkyl group having 6 to 12 carbon atoms, e.g., a benzyl group, a phenethyl group, a naphthylmethyl group, a naphthylethyl group, and a naphthylbutyl group can be exemplified.

As the sulfonylimide anion, e.g., a saccharin anion can be exemplified.

The alkyl group in the bis(alkylsulfonyl)imide anion and tris(alkylsulfonyl)-methide anion is preferably an alkyl group having 1 to 5 carbon atoms. As the substituents of these alkyl groups, a halogen atom, an alkyl group substituted with a halogen atom, an alkoxy group, an alkylthio group, an alkoxysulfonyl group, an aryloxysulfonyl group, and a cycloalkylaryloxysulfonyl group can be exemplified, and a fluorine atom and an alkyl group substituted with a fluorine atom are preferred.

132

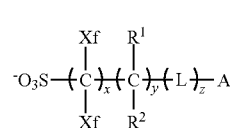
The alkyl groups in the bis(alkylsulfonyl)imide anion may be bonded to each other to form a cyclic structure, by which acid strength is heightened.

As other non-nucleophilic anions, e.g., fluorinated phosphorus (e.g., PF_6^-), fluorinated boron (e.g., BF_4^-) and fluorinated antimony (e.g., SbF_6^-) can be exemplified.

As the non-nucleophilic anions, an aliphatic sulfonic acid anion in which at least the α -position of the sulfonic acid is substituted with a fluorine atom, an aromatic sulfonic acid anion substituted with a fluorine atom or a group having a fluorine atom, a bis(alkylsulfonyl)imide anion in which the alkyl group is substituted with a fluorine atom, and a tris(alkylsulfonyl)methide anion in which the alkyl group is substituted with a fluorine atom are preferred. More preferred non-nucleophilic anions are an aliphatic perfluorosulfonic acid anion (still more preferably having 4 to 8 carbon atoms), and a benzenesulfonic acid anion having a fluorine atom, and still more preferred non-nucleophilic anions are a nonafluorobutanesulfonic acid anion, a perfluorooctanesulfonic acid anion, a pentafluorobenzenesulfonic acid anion, and a 3,5-bis(trifluoromethyl)benzenesulfonic acid anion.

From the viewpoint of acid strength, pK_a of a generated acid is preferably -1 or less in view of the improvement of sensitivity.

As non-nucleophilic anion, an anion represented by the following formula (AN1) is also exemplified as preferred embodiment.



(AN1)

In formula (AN1), each of Xf independently represents a fluorine atom, or an alkyl group substituted with at least one fluorine atom.

Each of R^1 and R^2 independently represents a hydrogen atom, a fluorine atom or an alkyl group, and each R^1 and R^2 , when a plurality of R^1 and R^2 are present, may be the same with or different from every other R^1 and R^2 .

L represents a divalent linking group, and each L, when a plurality of L are present, may be the same with or different from every other L.

A represents a cyclic organic group.

x represents an integer of 1 to 20, y represents an integer of 0 to 10, and z represents an integer of 0 to 10.

Formula (AN1) will be described in further detail.

The alkyl group in the alkyl group substituted with a fluorine atom represented by Xf is preferably an alkyl group having 1 to 10 carbon atoms, and more preferably 1 to 4 carbon atoms. The alkyl group substituted with a fluorine atom represented by Xf is preferably a perfluoroalkyl group.

Xf preferably represents a fluorine atom or a perfluoroalkyl group having 1 to 4 carbon atoms. Specifically, a fluorine atom, CF_3 , C_2F_5 , C_3F_7 , C_4F_9 , CH_2CF_3 , $CH_2CH_2CF_3$, $CH_2C_2F_5$, $CH_2CH_2C_2F_5$, $CH_2C_3F_7$, $CH_2CH_2C_3F_7$, $CH_2C_4F_9$ and $CH_2CH_2C_4F_9$ are exemplified, and a fluorine atom and CF_3 are preferred of all. It is especially preferred that both Xf represent a fluorine atom.

The alkyl group represented by R^1 and R^2 may have a substituent (preferably a fluorine atom), preferably a substituent having 1 to 4 carbon atoms, and more preferably a perfluoroalkyl group having 1 to 4 carbon atoms. As the specific examples of the alkyl group of R^1 and R^2 having a substituent,

133

CF₃, C₂F₅, C₃F₇, C₄F₉, C₅F₁₁, C₆F₁₃, C₇F₁₅, C₈F₁₇, CH₂CF₃, CH₂CH₂CF₃, CH₂C₂F₅, CH₂CH₂C₂F₅, CH₂C₃F₇, CH₂CH₂C₃F₇, CH₂C₄F₉, and CH₂CH₂C₄F₉ are exemplified, and CF₃ is especially preferred.

Each of R¹ and R² preferably represents a fluorine atom or CF₃.

x is preferably 1 to 10, and more preferably 1 to 5.

y is preferably 0 to 4, and more preferably 0.

z is preferably 0 to 5, and more preferably 0 to 3.

The divalent linking group represented by L is not especially restricted, and —COO—, —OCO—, —CO—, —O—, —S—, —SO—, —SO₂—, an alkylene group, a cycloalkylene group, an alkenylene group, and a linking group obtained by linking two or more of these groups are exemplified, and linking groups having total carbon atoms of 12 or less are preferred. Of these, —COO—, —OCO—, —CO— and —O— are preferred, and —COO— and —OCO— are more preferred.

The cyclic organic group represented by A is not especially limited so long as it has a cyclic structure, and an alicyclic group, an aryl group, and a heterocyclic group (including not only those having an aromatic property but also those not having an aromatic property) are exemplified.

The alicyclic group may be monocyclic or polycyclic, and monocyclic cycloalkyl groups, e.g., a cyclopentyl group, a cyclohexyl group, and a cyclooctyl group, and polycyclic cycloalkyl groups, e.g., a norbornyl group, a tricyclodecanyl group, a tetracyclodecanyl group, a tetracyclododecanyl group, and an adamantyl group are preferably exemplified. Of these groups, alicyclic groups having 7 or more carbon atoms and a bulky structure such as a norbornyl group, a tricyclodecanyl group, a tetracyclodecanyl group, a tetracyclododecanyl group, and an adamantyl group are preferred for capable of controlling diffusibility in a film in the heating step after exposure and from the viewpoint of the improvement of MEEF.

As the aryl group, a benzene ring, a naphthalene ring, a phenanthrene ring, and an anthracene ring are exemplified.

As the heterocyclic group, groups deriving from a furan ring, a thiophene ring, a benzofuran ring, a benzothiophene ring, a dibenzofuran ring, a dibenzothiophene ring, or a pyridine ring are exemplified, and groups deriving from a furan ring, a thiophene ring, or a pyridine ring are preferred of all.

As the cyclic organic group, lactone structures can also be exemplified, and as the specific examples, the lactone structures represented by any of the above formulae (LC1-1) to (LC1-17) that resin (A) may have can be given.

The above cyclic organic groups may have a substituent. As the substituents, an alkyl group (which may be straight chain, branched or cyclic, and preferably having 1 to 12 carbon atoms), a cycloalkyl group (which may be monocyclic, polycyclic or spirocyclic, and preferably having 3 to 20 carbon atoms), an aryl group (preferably having 6 to 14 carbon atoms), a hydroxyl group, an alkoxy group, an ester group, an amido group, a urethane group, a ureido group, a thioether group, a sulfonamide group, and a sulfonic ester group are exemplified. Carbon atoms for constituting the cyclic organic group (carbon atoms contributing to ring formation) may be carbonyl carbon atoms.

As the organic groups represented by R₂₀₁, R₂₀₂ and R₂₀₃, an aryl group, an alkyl group and a cycloalkyl group are exemplified.

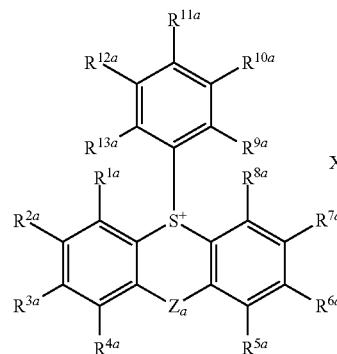
It is preferred that at least one of R₂₀₁, R₂₀₂ and R₂₀₃ represents an aryl group, and more preferably all of three represent an aryl group. As the aryl group, besides a phenyl group and a naphthyl group, hetero aryl group such as an indole residue and a pyrrole residue are also included. As the

134

alkyl group and cycloalkyl group represented by R₂₀₁, R₂₀₂ and R₂₀₃, a straight chain or branched alkyl group having 1 to 10 carbon atoms, and a cycloalkyl group having 3 to 10 carbon atoms are preferably exemplified. As the alkyl group, more preferably a methyl group, an ethyl group, an n-propyl group, an i-propyl group, and an n-butyl group can be exemplified. As the cycloalkyl group, more preferably a cyclopropyl group, a cyclobutyl group, a cyclopentyl group, a cyclohexyl group, and a cycloheptyl group can be exemplified. These groups may further have a substituent. As the substituents, a nitro group, a halogen atom such as a fluorine atom, a carboxyl group, a hydroxyl group, an amino group, a cyano group, an alkoxy group (preferably having 1 to 15 carbon atoms), a cycloalkyl group (preferably having 3 to 15 carbon atoms), an aryl group (preferably having 6 to 14 carbon atoms), an alkoxycarbonyl group (preferably having 2 to 7 carbon atoms), an acyl group (preferably having 2 to 12 carbon atoms), and an alkoxycarbonyloxy group (preferably having 2 to 7 carbon atoms) are exemplified, but the substituents are not restricted thereto.

When two of R₂₀₁, R₂₀₂ and R₂₀₃ are bonded to each other to form a cyclic structure, the structure is preferably the structure represented by the following formula (A1).

(A1)



In formula (A1), each of R^{1a} to R^{13a} independently represents a hydrogen atom or a substituent.

Preferably one to three of R^{1a} to R^{13a} do not represent a hydrogen atom, and more preferably any one of R^{9a} to R^{13a} does not represent a hydrogen atom.

Z_a represents a single bond or a divalent linking group.

X⁻ is the same with Z⁻ in formula (ZI).

When each of R^{1a} to R^{13a} does not represent a hydrogen atom, the specific examples include a halogen atom, a straight chain, branched or cyclic alkyl group, an alkenyl group, an alkynyl group, an aryl group, a heterocyclic group, a cyano group, a nitro group, a carboxyl group, an alkoxy group, an acyloxy group, a silyloxy group, a heterocyclic oxy group, an acyloxy group, a carbamoyloxy group, an alkoxycarbonyloxy group, an aryloxycarbonyloxy group, an amino group (including an anilino group), an ammonio group, an acylamino group, an aminocarbonylamino group, an alkoxycarbonylamino group, an aryloxycarbonylamino group, a sulfamoylamino group, an alkylsulfonylamino group, an arylsulfonylamino group, a mercapto group, an alkylthio group, an arylthio group, a heterocyclic thio group, a sulfamoyl group, a sulfo group, an alkylsulfinyl group, an arylsulfinyl group, an alkylsulfonyl group, an arylsulfonyl group, an acyl group, an aryloxycarbonyl group, an alkoxycarbonyl group, a carbamoyl group, an arylazo group, a heterocyclic azo group, an imido group, a phosphino group, a phosphinyl

135

group, a phosphinyloxy group, a phosphinylamino group, a phosphono group, a silyl group, a hydrazino group, a ureido group, a boronic acid group ($-\text{B}(\text{OH})_2$), a phosphato group ($-\text{OPO}(\text{OH})_2$), a sulfato group ($-\text{OSO}_3\text{H}$), and other known substituents.

When each of R^{1a} to R^{13a} does not represent a hydrogen atom, a straight chain, branched or cyclic alkyl group substituted with a hydroxyl group is preferably exemplified.

As the divalent linking group represented by Za , an alkylene group, an arylene group, a carbonyl group, a sulfonyl group, a carbonyloxy group, a carbonylamino group, a sulfonylamido group, an ether bond, a thioether bond, an amino group, a disulfide group, $-(\text{CH}_2)_n-\text{CO}-$, $-(\text{CH}_2)_n-\text{SO}_2-$, $-\text{CH}=\text{CH}-$, an aminocarbonylamino group, and an aminosulfonylamino group are exemplified (n is an integer of 1 to 3).

Preferred structures in the case where at least one of R_{201} , R_{202} and R_{203} is not an aryl group may take cationic structures, such as the compounds disclosed in JP-A-2004-233661, paragraphs 0047 and 0048, JP-A-2003-35948, paragraphs 0040 to 0046, U.S. Patent Application 2003/0224288A1, compounds (1-1) to (1-70), and U.S. Patent Application 2003/0077540A1, compounds (IA-1) to (IA-54), (IB-1) to (IB-24).

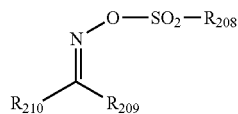
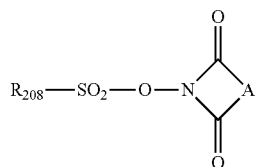
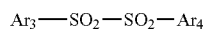
In formulae (ZII) and (ZIII), each of R_{204} to R_{207} independently represents an aryl group, an alkyl group or a cycloalkyl group.

The aryl group, alkyl group and cycloalkyl group represented by each of R_{204} to R_{207} are the same with the aryl group, alkyl group and cycloalkyl group represented by each of R_{201} to R_{203} in formula (ZI).

The aryl group, alkyl group and cycloalkyl group represented by each of R_{204} to R_{207} may have a substituent. As the examples of the substituents, the same substituents with those that the aryl group, alkyl group and cycloalkyl group represented by each of R_{201} to R_{203} in formula (ZI) may have are exemplified.

Z^- represents a non-nucleophilic anion, and the same non-nucleophilic anions as represented by Z^- in formula (ZI) can be exemplified.

As acid generators, the compounds represented by the following formula (ZIV), (ZV) or (ZVI) are also exemplified.



In formulae (ZIV) to (ZVI), each of Ar_3 and Ar_4 independently represents an aryl group.

Each of R_{208} , R_{209} and R_{210} independently represents an alkyl group, a cycloalkyl group or an aryl group.

A represents an alkylene group, an alkenylene group or an arylene group.

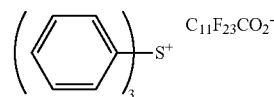
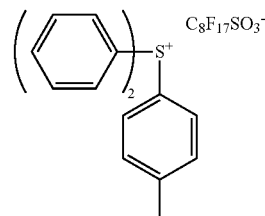
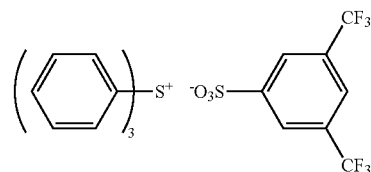
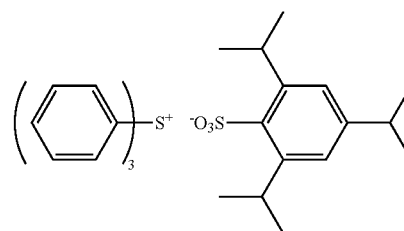
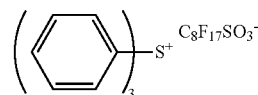
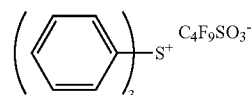
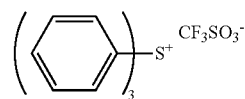
136

Specific examples of the aryl group of Ar_3 , Ar_4 , R_{208} , R_{209} and R_{210} are the same as specific examples of the aryl group as R_{201} , R_{202} and R_{203} in formula (ZI).

Specific examples of the alkyl group and cycloalkyl group of R_{208} , R_{209} and R_{210} are the same as specific examples of the alkyl group and cycloalkyl group of R_{201} , R_{202} and R_{203} in formula (ZI).

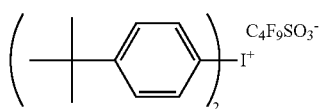
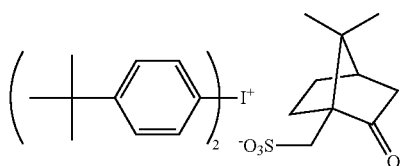
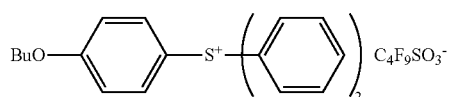
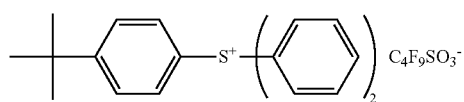
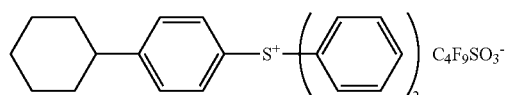
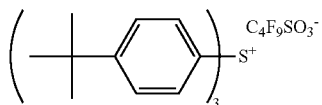
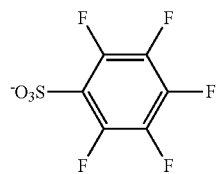
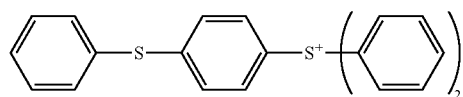
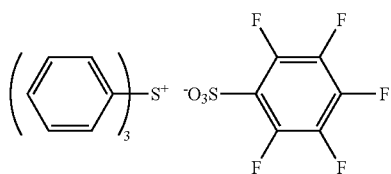
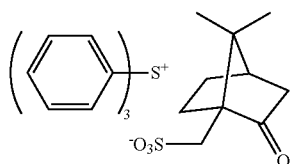
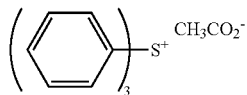
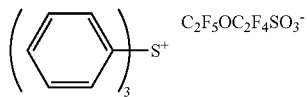
The alkylene group of A includes an alkylene group having a carbon number of 1 to 12 (e.g., methylene group, ethylene group, propylene group, isopropylene group, butylene group, isobutylene group); the alkenylene group of A includes an alkenylene group having a carbon number of 2 to 12 (e.g., ethynylene group, propenylene group, butenylene group); and the arylene group of A includes an arylene group having a carbon number of 6 to 10 (e.g., phenylene group, tolylene group, naphthylene group).

Among the acid generators, particularly preferred examples are illustrated below.



137

-continued



138

-continued

(z8)

(z19)

(z9)

(z10)

(z11)

(z12)

(z13)

(z14)

(z15)

(z16)

(z17)

(z18)

(z19)

(z20)

(z21)

(z22)

(z23)

(z24)

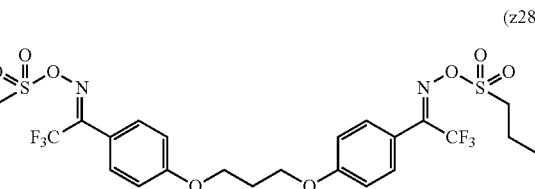
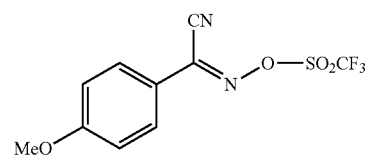
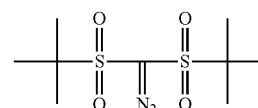
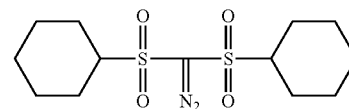
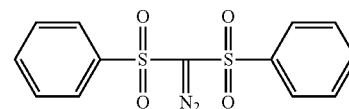
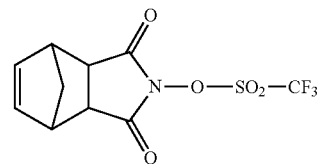
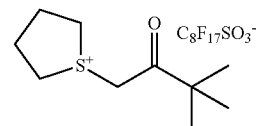
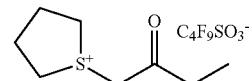
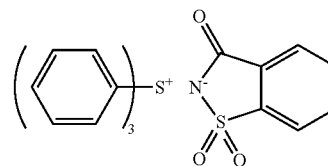
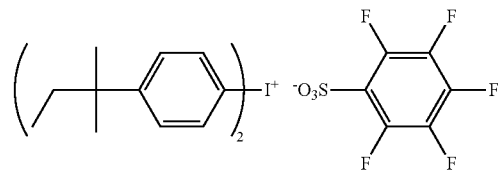
(z25)

(z26)

(z27)

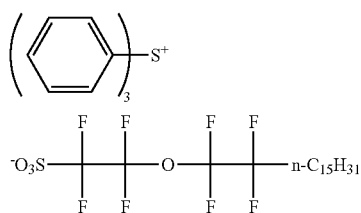
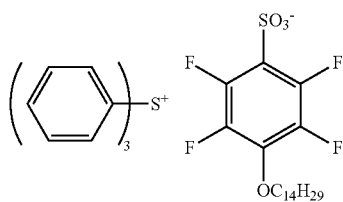
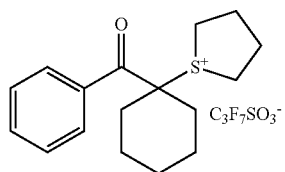
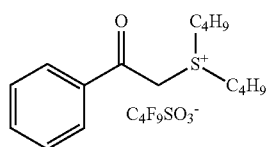
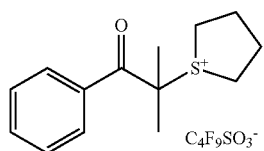
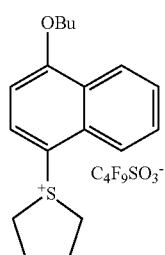
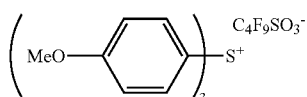
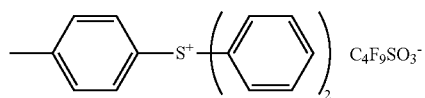
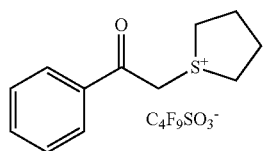
(z28)

(z29)

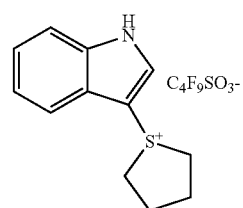
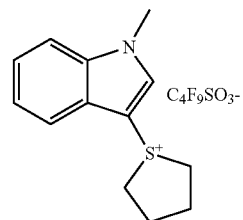
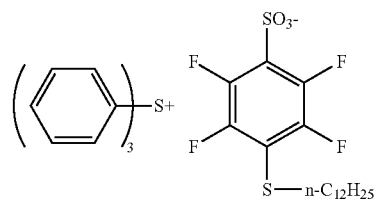
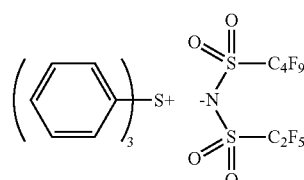
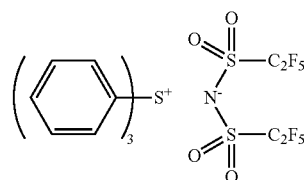
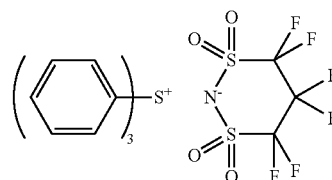
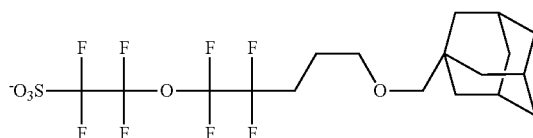
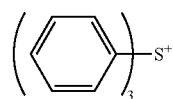


139

-continued

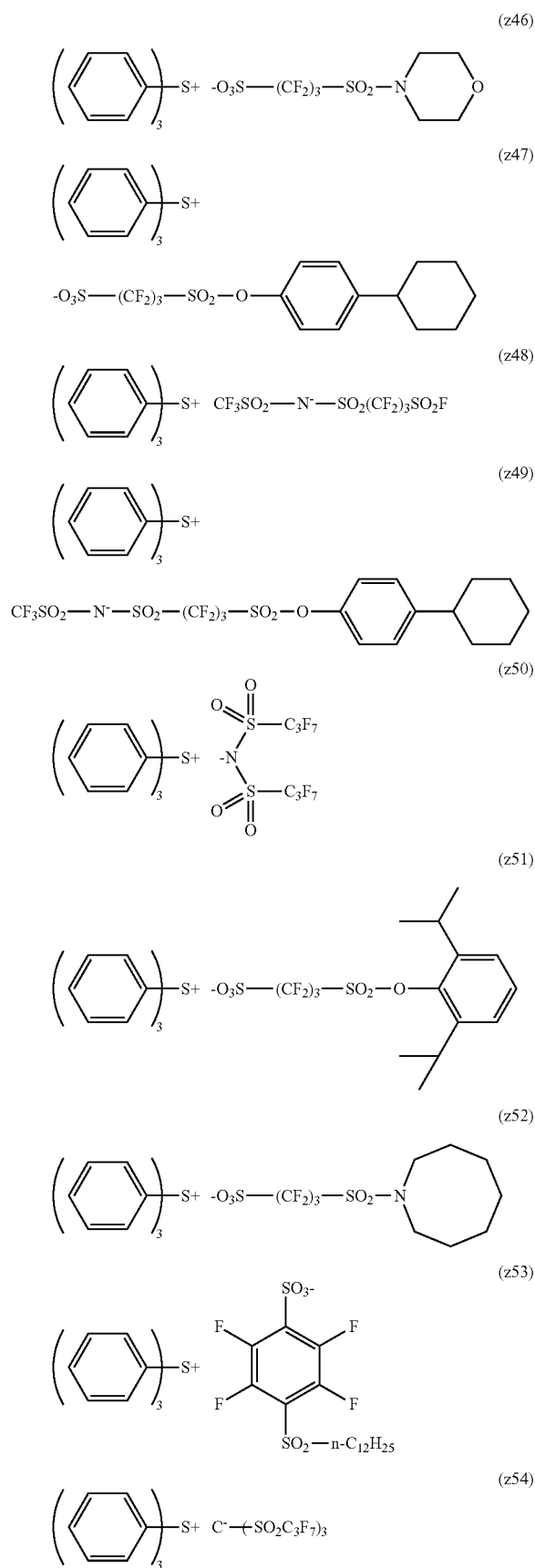
**140**

-continued

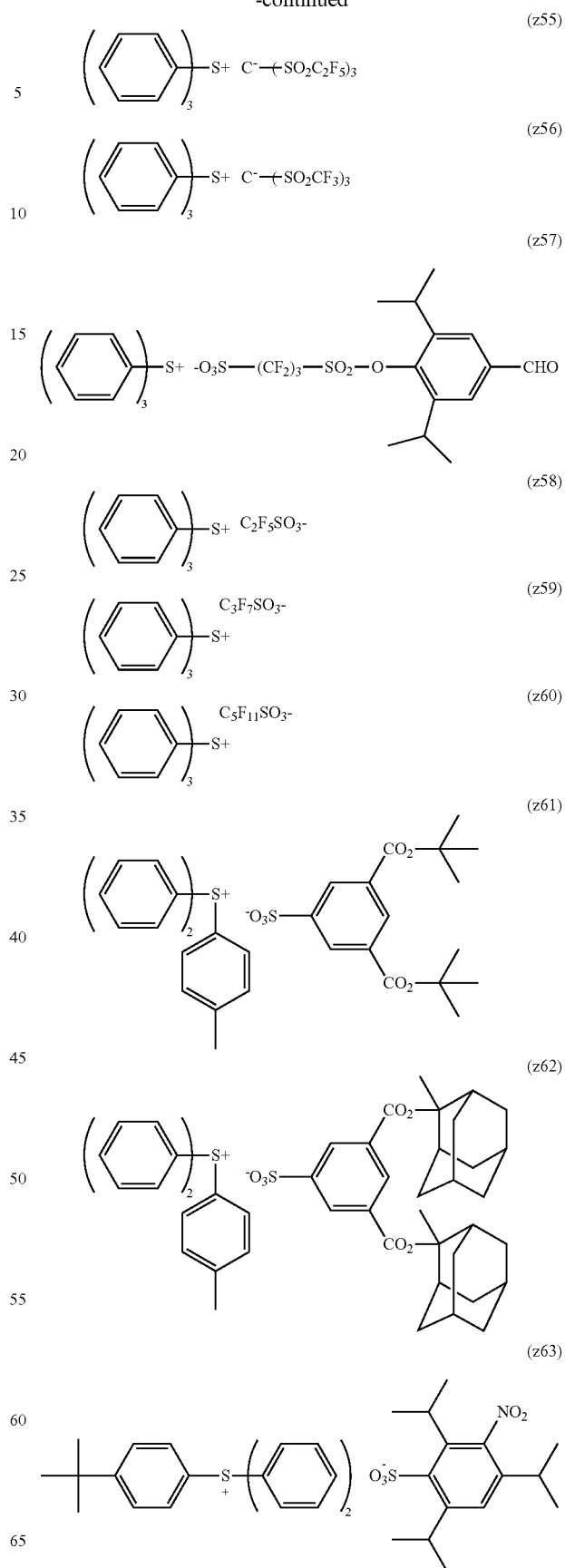


141

-continued

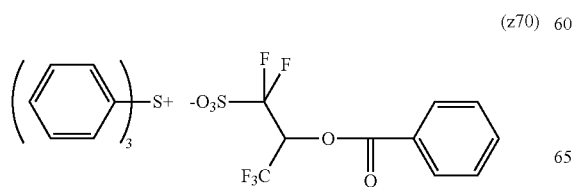
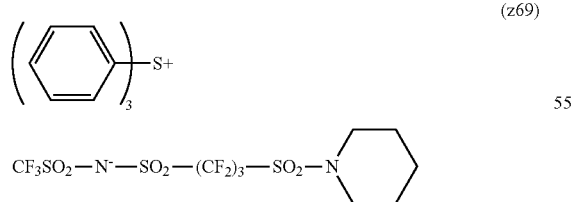
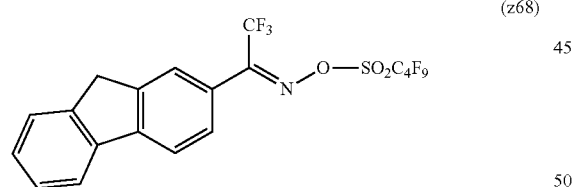
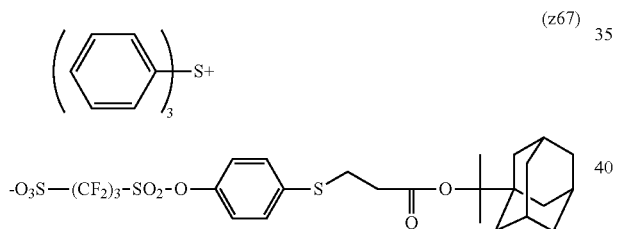
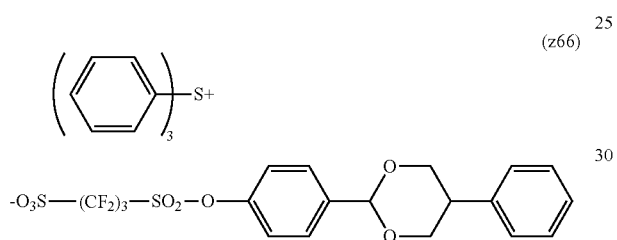
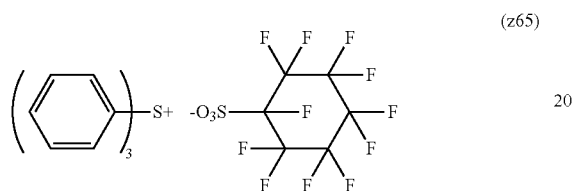
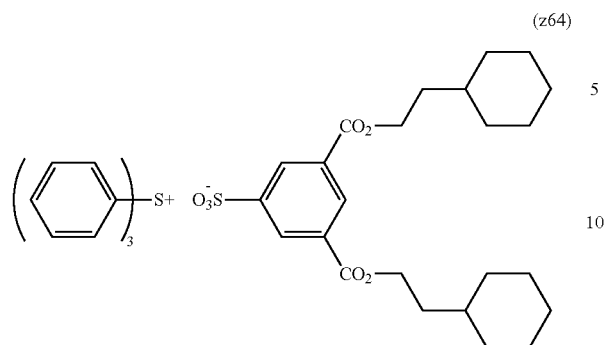
**142**

-continued

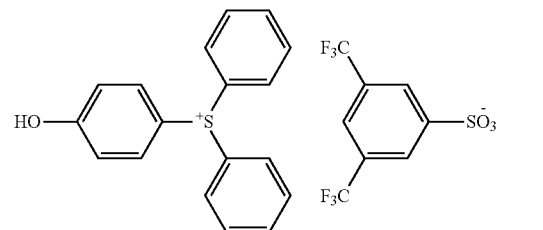
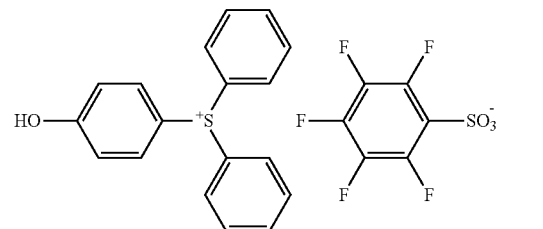
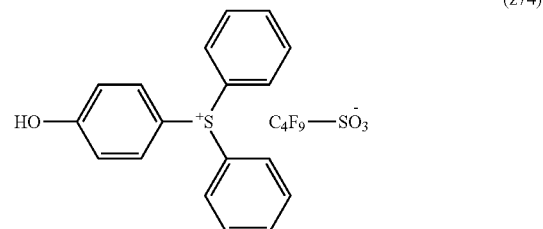
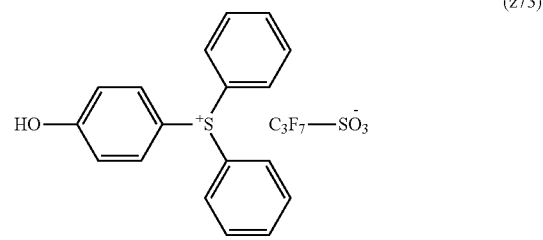
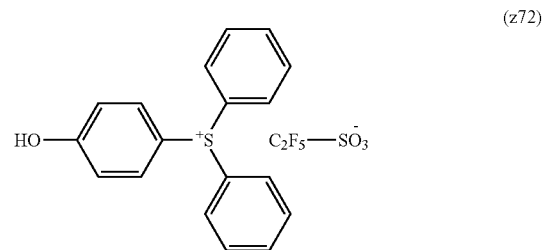
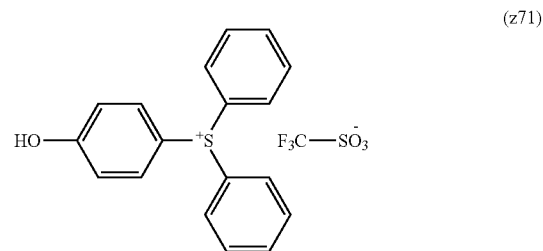


143

-continued

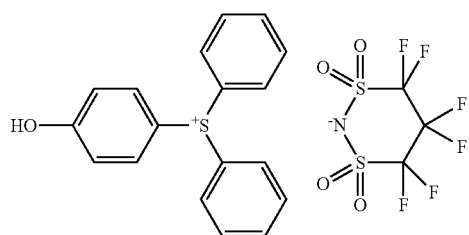
**144**

-continued



145

-continued

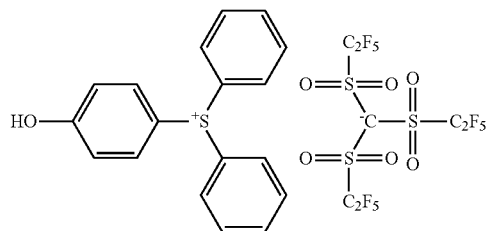


(z77)

5

10

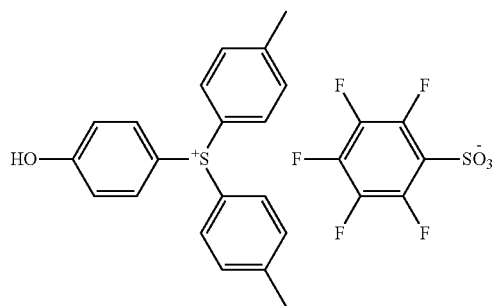
(z78)



(z79)

15

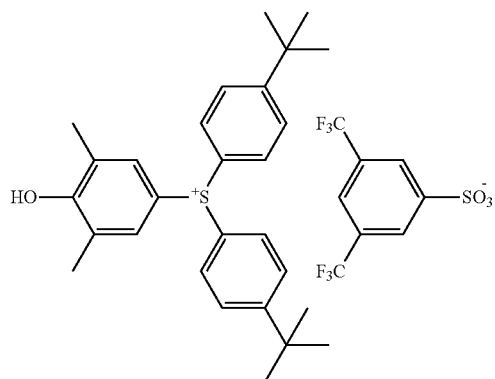
20



(z80)

25

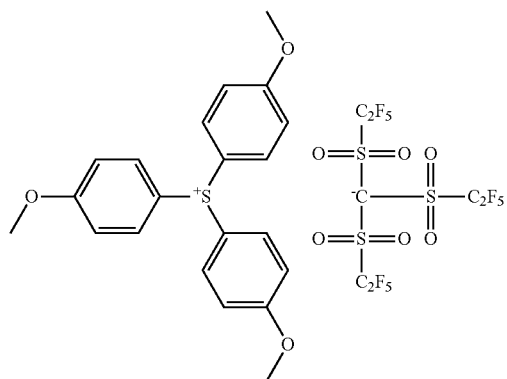
30



(z81)

40

45



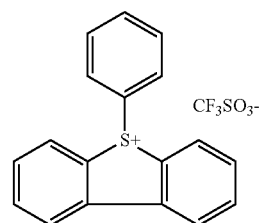
55

60

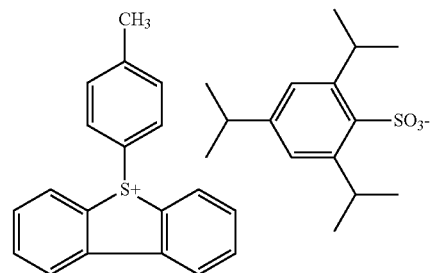
65

146

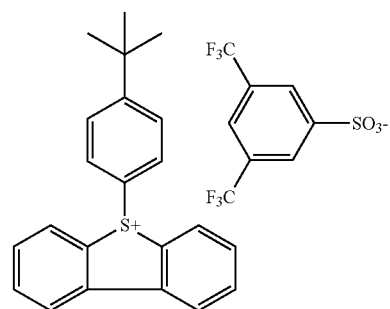
-continued



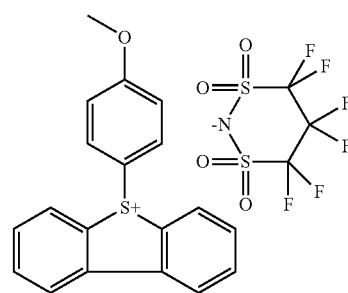
(z82)



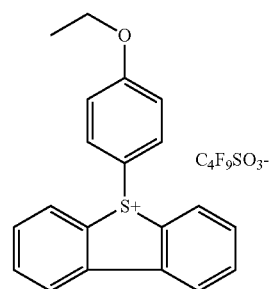
(z83)



(z84)



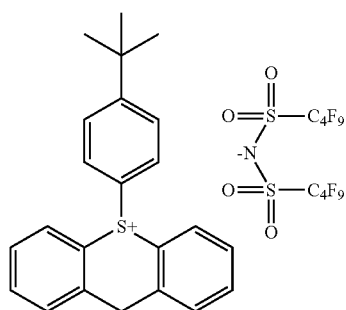
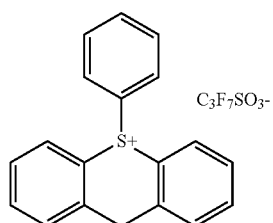
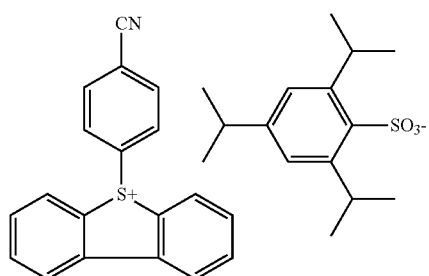
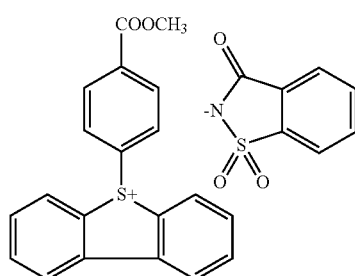
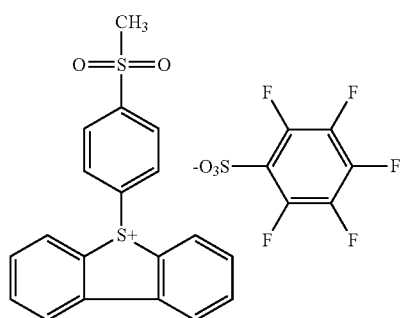
(z85)



(z86)

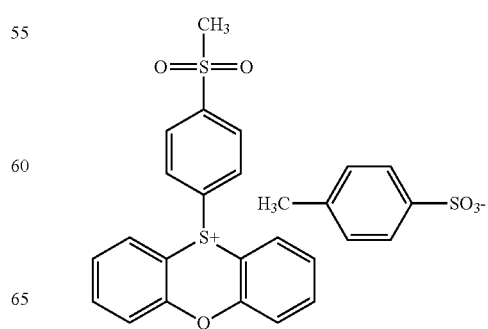
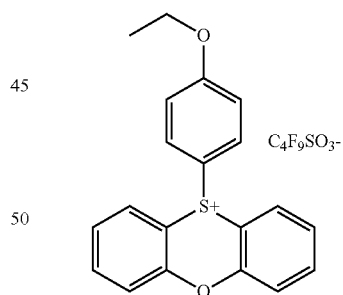
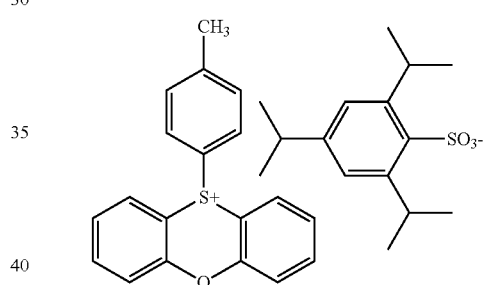
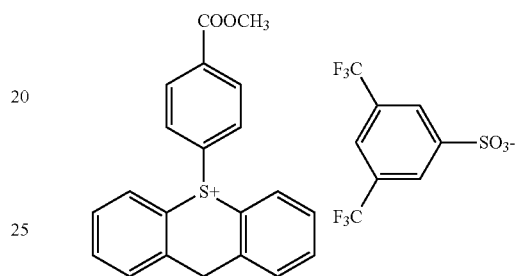
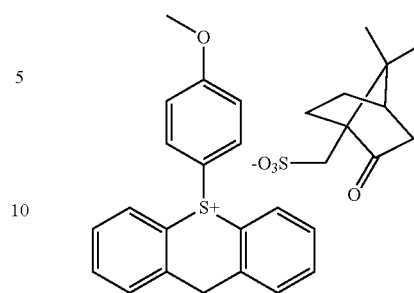
147

-continued



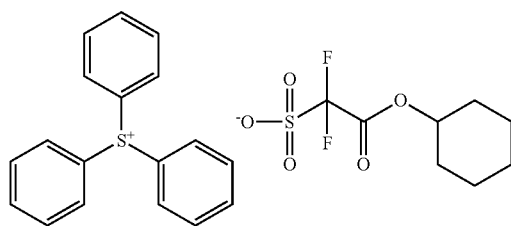
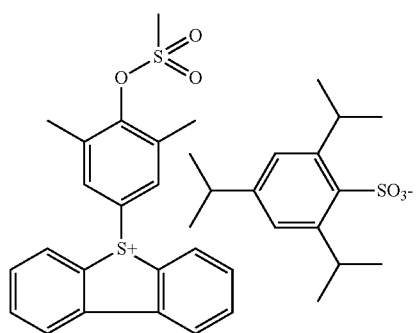
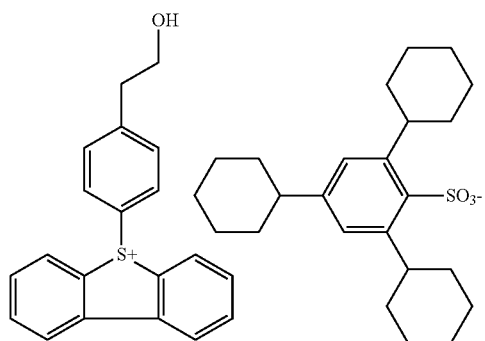
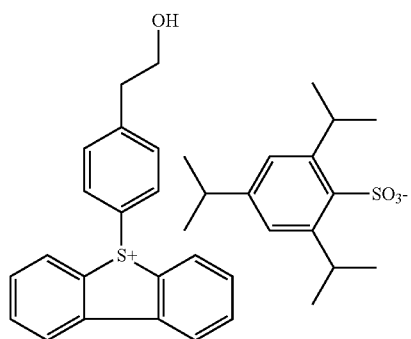
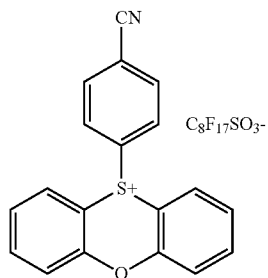
148

-continued

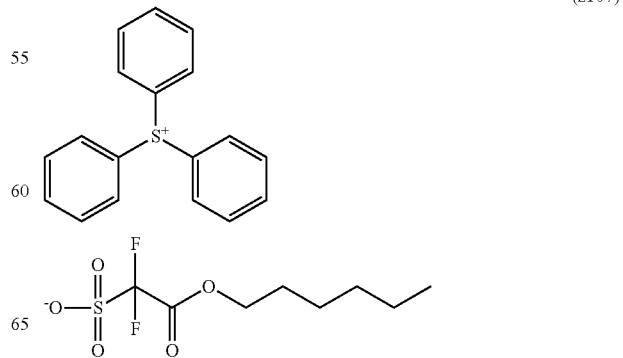
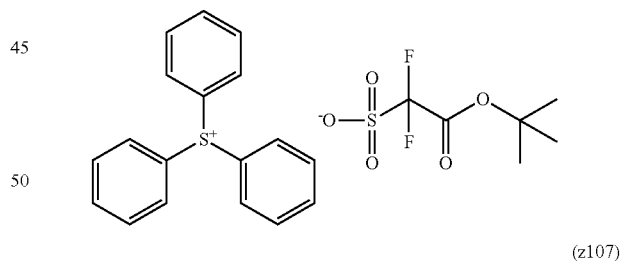
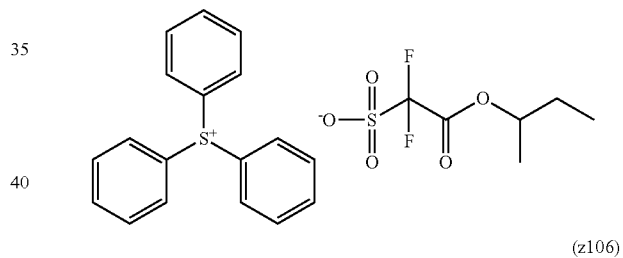
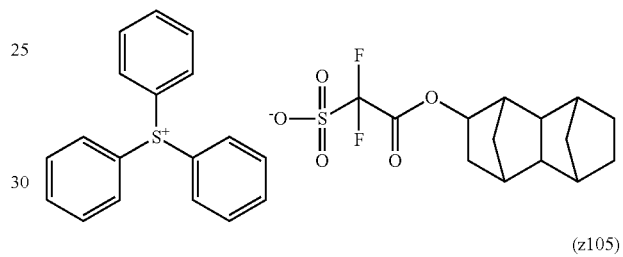
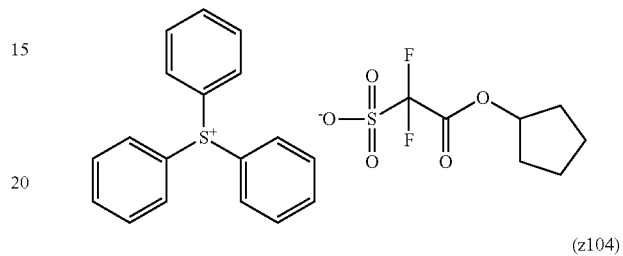
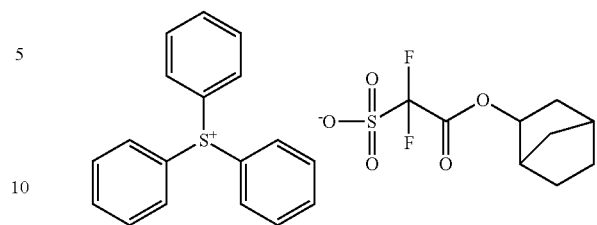


149

-continued

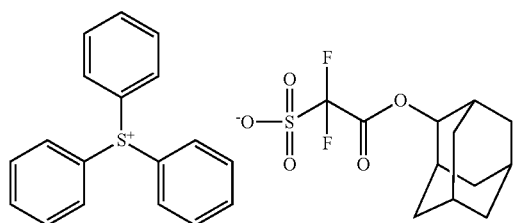
**150**

-continued

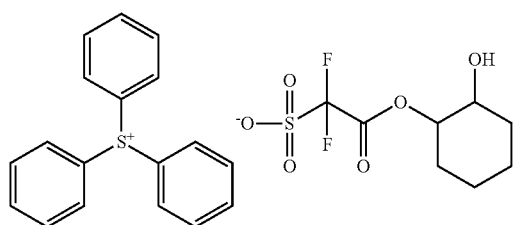


151

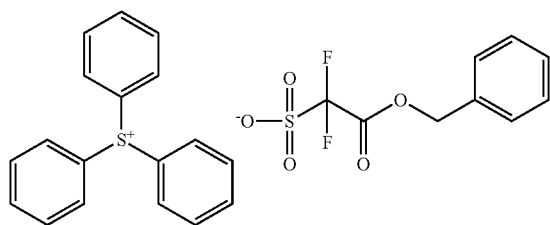
-continued



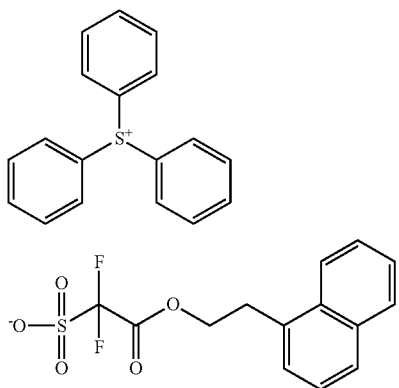
5



15

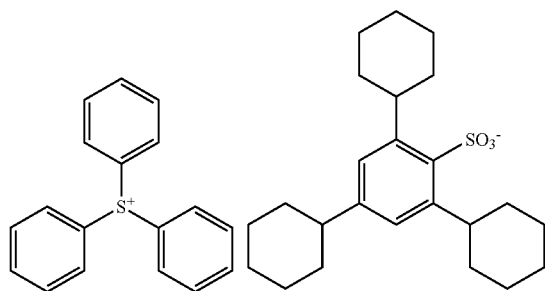


25



(z111)

40



(z112)

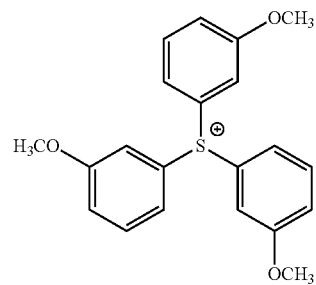
55

60

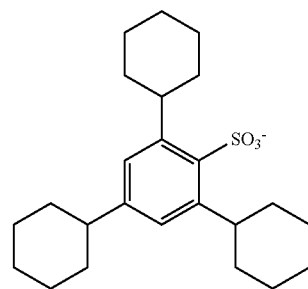
65

152

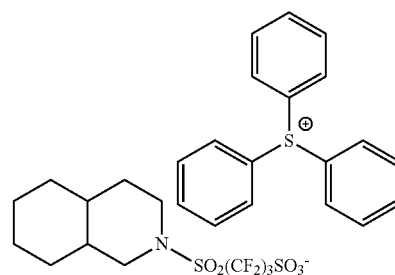
-continued



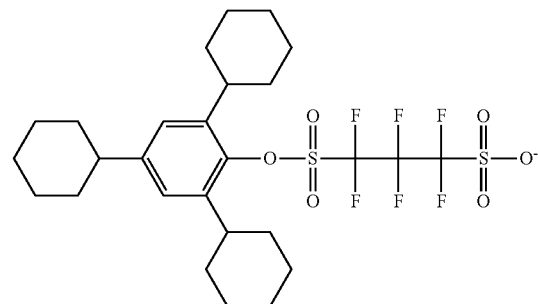
(z113)



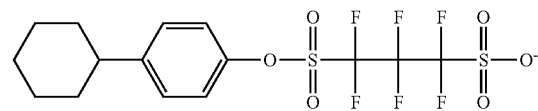
(z114)



(z115)

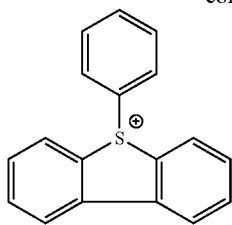


(z116)

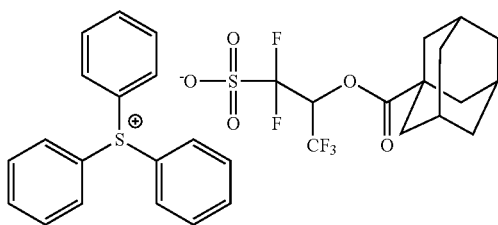


153

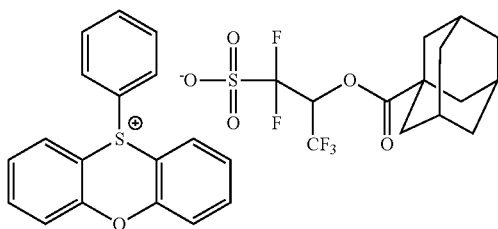
-continued



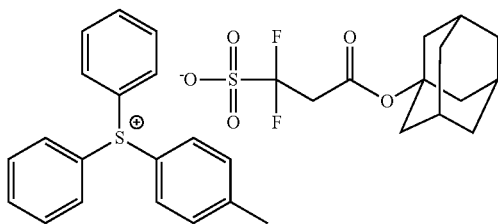
(z117)



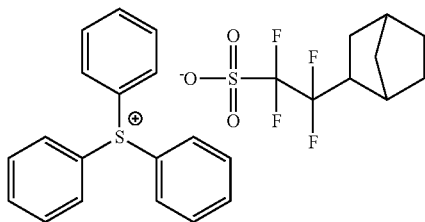
(z118)



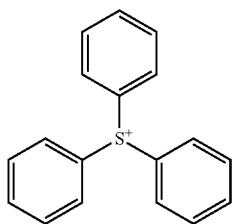
(z119)



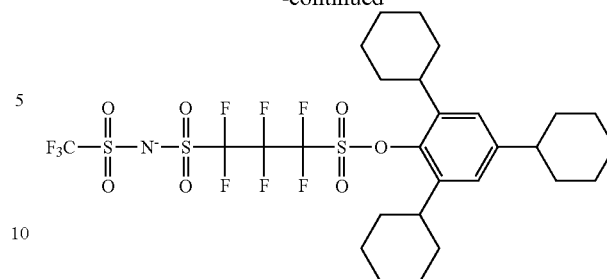
(z120)



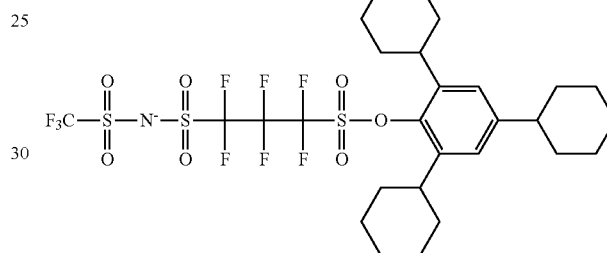
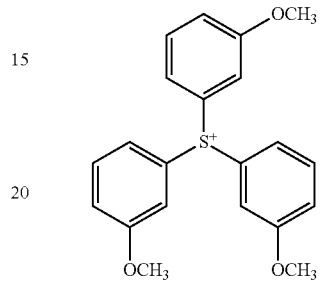
(z121)

**154**

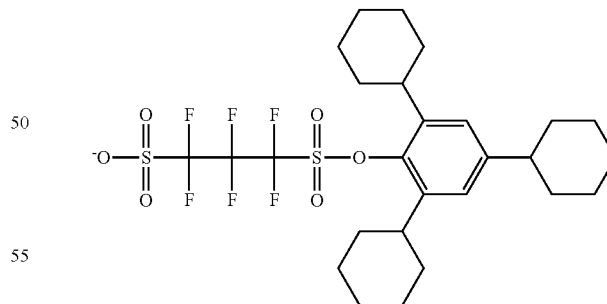
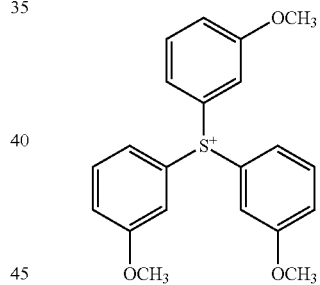
-continued



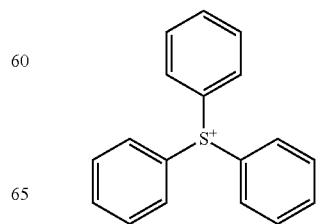
(z122)



(z123)

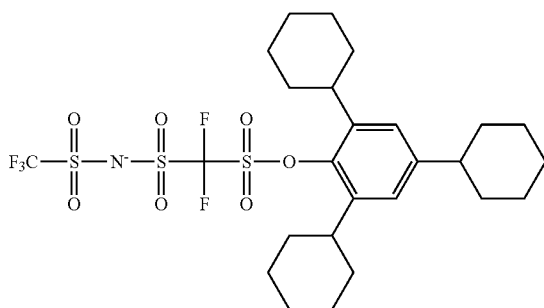
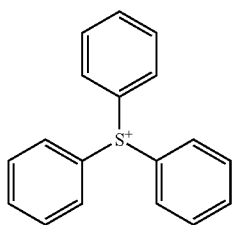
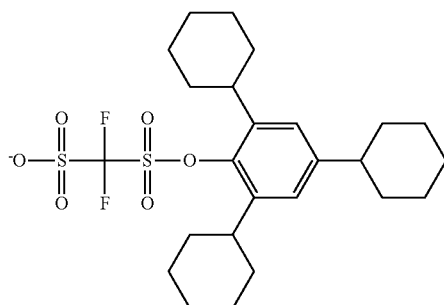
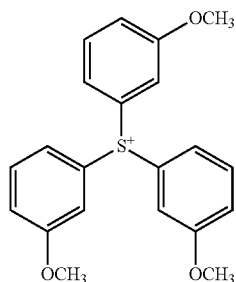
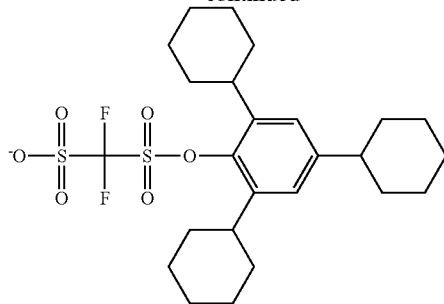


(z124)



155

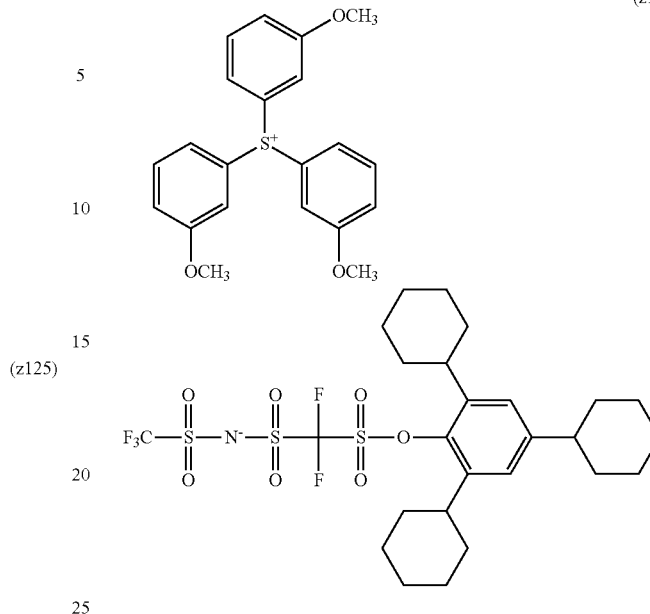
-continued



156

-continued

(z127)



One kind of acid generator may be used alone, or two or more kinds may be used in combination.

The content of the acid generator in the composition is 21% by mass to 70% by mass based on all the solids content in the composition. When the content is less than 21% by mass, it becomes difficult to reveal high sensitivity and high LWR performance. When the content exceeds 70% by mass, it becomes difficult to reveal high resolution and high LWR performance.

The content of the acid generator in the composition is preferably 31% by mass to 60% by mass, and more preferably 31% by mass to 50% by mass based on all the solids content in the composition.

[3] Resist Solvent (C) (Coating Solvent)

The solvents usable in preparing the composition are not especially restricted so long as they are capable of dissolving each component, for example, alkylene glycol monoalkyl ether carboxylate (propylene glycol monomethyl ether acetate (also known as PGMEA, 1-methoxy-2-acetoxyp propane), alkylene glycol monoalkyl ether (propylene glycol monomethyl ether (PGME, 1-methoxy-2-propanol), etc.), alkyl lactate (ethyl lactate, methyl lactate, etc.), cyclic lactone (γ -butyrolactone, etc., preferably having 4 to 10 carbon atoms), chain or cyclic ketone (2-heptanone, cyclohexanone, etc., preferably having 4 to 10 carbon atoms), alkylene carbonate (ethylene carbonate, propylene carbonate, etc.), alkyl carboxylate (alkyl acetate such as butyl acetate is preferred), and alkyl alkoxyacetate (ethyl ethoxypropionate) are exemplified. As other usable solvents, the solvents disclosed in U.S. Patent Application 2008/0248425A1, paragraphs from [0244] downward are exemplified.

Of the above solvents, alkylene glycol monoalkyl ether carboxylate and alkylene glycol monoalkyl ether are preferred.

One kind of these solvents may be used alone, or two or more kinds may be mixed. When two or more kinds are mixed, it is preferred to mix a solvent having a hydroxyl group and a solvent not having a hydroxyl group. The mass ratio of the solvent having a hydroxyl group and the solvent not having a hydroxyl group is 1/99 to 99/1, preferably 10/90 to 90/10, and more preferably 20/80 to 60/40.

157

As the solvent having a hydroxyl group, alkylene glycol monoalkyl ether is preferred, and as the solvent not having a hydroxyl group, alkylene glycol monoalkyl ether carboxylate is preferred.

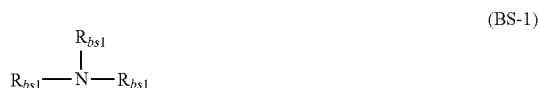
[4] Basic Compounds

It is preferred that the electron beam sensitive or extreme ultraviolet radiation-sensitive resin composition in the invention contains a basic compound.

The basic compound is preferably a nitrogen-containing organic basic compound.

Usable compounds are not especially limited and, for example, compounds classified into the following (1) to (4) are preferably used.

(1) Compound Represented by the Following Formula (BS-1)



In formula (BS-1), each of R_{bs1} independently represents any of a hydrogen atom, an alkyl group (straight chain or branched), a cycloalkyl group (monocyclic or polycyclic), an aryl group and an aralkyl group. However, not all R_{bs1} represent a hydrogen atom.

The carbon atom number of the alkyl group represented by R_{bs1} is not especially restricted and is generally 1 to 20, and preferably 1 to 12.

The carbon atom number of the cycloalkyl group represented by R_{bs1} is not especially restricted and is generally 3 to 20, and preferably 5 to 15.

The carbon atom number of the aryl group represented by R_{bs1} is not especially restricted and is generally 6 to 20, and preferably 6 to 10. Specifically a phenyl group and a naphthyl group are exemplified.

The carbon atom number of the aralkyl group represented by R_{bs1} is not especially restricted and is generally 7 to 20, and preferably 7 to 11. Specifically a benzyl group is exemplified.

158

The hydrogen atom of each of the alkyl group, cycloalkyl group, aryl group or aralkyl group represented by R_{bs1} may be substituted with a substituent. As the substituents, an alkyl group, a cycloalkyl group, an aryl group, an aralkyl group, a hydroxyl group, a carboxyl group, an alkoxy group, an aryloxy group, an alkylcarbonyloxy group and an alkyloxycarbonyl group are exemplified.

It is preferred that, in the compound represented by formula (BS-1), one alone of three R_{bs1} represents a hydrogen atom, or not all R_{bs1} represent a hydrogen atom.

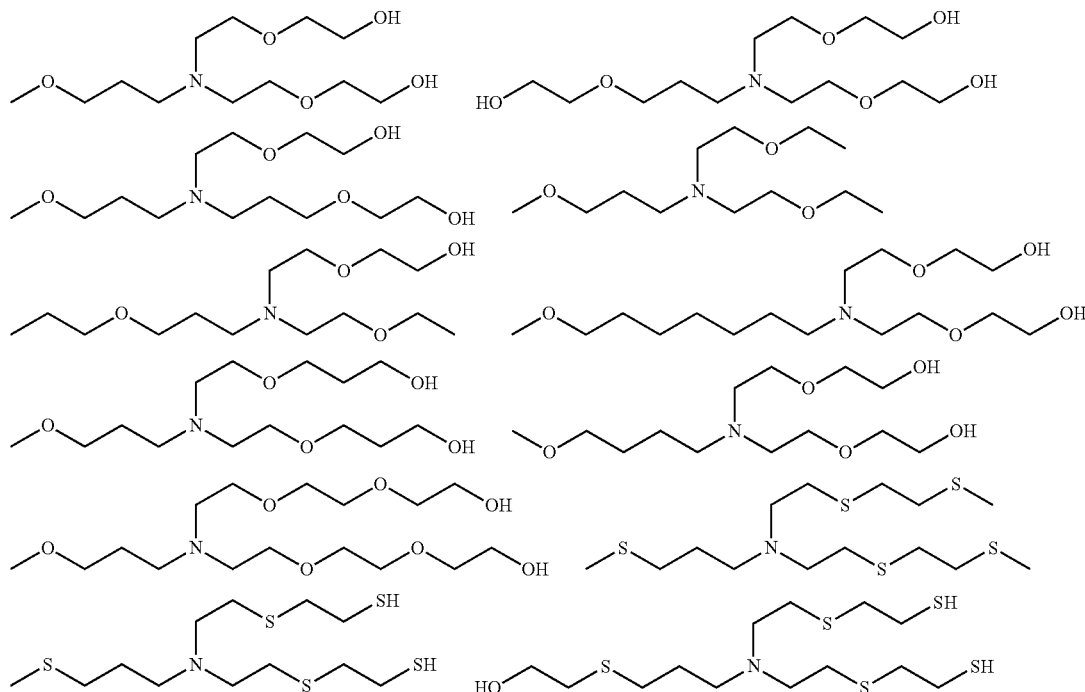
As the specific examples of the compound represented by formula (BS-1), tri-n-butylamine, tri-n-pentylamine, tri-n-octylamine, tri-n-decylamine, triisodecylamine, dicyclohexylmethylamine, tetradecylamine, pentadecylamine, hexadecylamine, octadecylamine, didecylamine, methyloctadecylamine, dimethylundecylamine, N,N-dimethyldodecylamine, methyldioctadecylamine, N,N-dibutylaniline, and N,N-dihexylaniline are exemplified.

Further, in formula (BS-1), a compound in which at least one R_{bs1} is an alkyl group substituted with a hydroxyl group is exemplified as a preferred embodiment. As the specific compounds, triethanolamine and N,N-dihydroxyethylaniline are exemplified.

Further, the alkyl group represented by R_{bs1} may have an oxygen atom in the alkyl chain to form an oxyalkylene chain. As the oxyalkylene chain, $-\text{CH}_2\text{CH}_2\text{O}-$ is preferred. As the specific examples, tris(methoxyethoxyethyl)amine and the compounds disclosed in U.S. Pat. No. 6,040,112, column 3, line 60 and after, are exemplified.

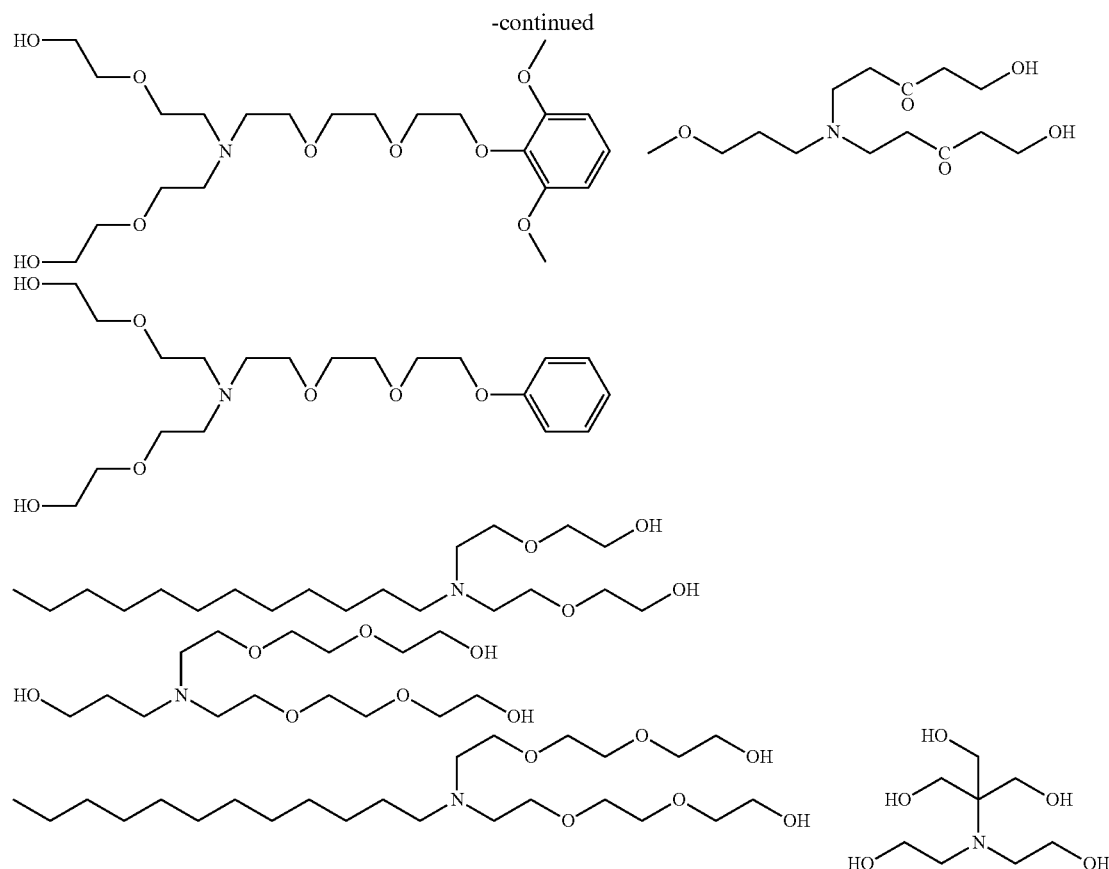
Further, as a preferred basic compound represented by formula (BS-1), a compound having an alkyl group in which at least one R is substituted with a hydroxyl group is exemplified. Specifically, for example, triethanolamine and N,N-dihydroxyethylaniline are exemplified.

As the basic compounds represented by formula (BS-1), for example, the following compounds are exemplified.



159

160



35

(2) Compound Having a Nitrogen-Containing Heterocyclic Structure

As the heterocyclic structure, the compound may not have an aromatic property. Further, a plurality of nitrogen atoms may be contained, and hetero atoms other than a nitrogen atom may be contained. Specifically, a compound having an imidazole structure, (2-phenylbenzimidazole, 2,4,5-triphenylimidazole), a compound having a piperidine structure (N-hydroxyethylpiperidine, bis(1,2,2,6,6-pentamethyl-4-piperidyl)sebacate), a compound having a pyridine structure (4-dimethylamino-pyridine), and a compound having an antipyrine structure (antipyrine, hydroxyl-antipyrine) are exemplified.

A compound having two or more cyclic structures is also preferably used. Specifically, 1,5-diazabicyclo[4.3.0]non-5-ene, 1,8-diazabicyclo[5.4.0]undeca-7-ene are exemplified.

(3) Amine Compound Having a Phenoxy Group

An amine compound having a phenoxy group is a compound having a phenoxy group at the terminal on the opposite side to the nitrogen atom of the alkyl group of an amine compound. The phenoxy group may have a substituent, e.g., an alkyl group, an alkoxy group, a halogen atom, a cyano group, a nitro group, a carboxyl group, a carboxylic acid ester group, a sulfonic acid ester group, an aryl group, an aralkyl group, an acyloxy group or an aryloxy group.

More preferably, the compound is a compound having at least one oxyalkylene chain between the phenoxy group and the nitrogen atom. The number of oxyalkylene chains in one molecule is preferably 3 to 9, and more preferably 4 to 6. Of oxyalkylene chains, $-\text{CH}_2\text{CH}_2\text{O}-$ is preferred.

As the specific examples, 2-[2-{2-(2,2-dimethoxyphenoxyethoxy)ethyl}-bis-(2-methoxyethyl)]amine, and Com-

pounds (C1-1) to (C3-3) disclosed in U.S. Patent Application 2007/0224539A1, paragraph [0066] are exemplified.

(4) Ammonium Salt

Ammonium salts are also arbitrarily used. Preferred compound is hydroxide or carboxylate. More specifically, tetraalkylammonium hydroxide represented by tetrabutylammonium hydroxide is preferred. Besides the above, ammonium salts deriving from the amines in the above (1) to (3) can be used.

(5) Guanidine Compound

The composition according to the invention may further contain a guanidine compound having a structure represented by the following formula.



Since the positive charge of conjugated acid is stably distributed by three nitrogen atoms, the guanidine compound shows strong basicity.

As the basicity of guanidine compound (A) of the invention, pKa of conjugated acid is preferably 6.0 or more, when pKa is 7.0 to 20.0, neutral reactivity with an acid is high and excellent roughness characteristics are obtained and so preferred, and more preferably 8.0 to 16.0.

Due to such strong basicity, distribution of acid is restrained and an excellent pattern form can be obtained.

Incidentally, "pKa" here means pKa in an aqueous solution, which is, for example, described in Kagaku Binran (II)

65

161

(Chemistry Handbook) (Revised Fourth Edition (1993), compiled by The Chemical Society of Japan, published by Maruzen), which shows that the lower the value, the higher is the acid strength. Specifically, pKa in an aqueous solution can be actually measured by the measurement of acid dissociation constant at 25° C. with infinite dilution aqueous solution. Further, the value based on Hammett's substitution constant and data base of known documents can be found by computation by the following software package 1. All the pKa values described in the present specification are the values found by computation by the software package.

Software package 1: Advanced Chemistry Development (ACD/Labs) Software V8.14 for Solaris (1994-2007 ACD/Labs)

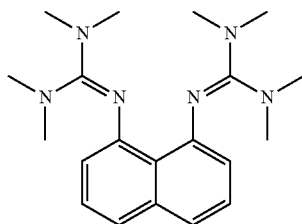
In the invention, log P is a logarithmic value of n-octanol/water distribution coefficient (P), which is an effective parameter capable of characterizing a hydrophilic property and a hydrophobic property of a wide range of compounds. Distribution coefficient can be generally found by computation not by experiment. In the invention, log P means a value computed by CS Chem Draw Ultra Ver. 8.0 software package (Crippen's fragmentation method).

log P of guanidine compound (A) is preferably 10 or less. When the value is 10 or less, guanidine compound (A) can be uniformly contained in a resist film.

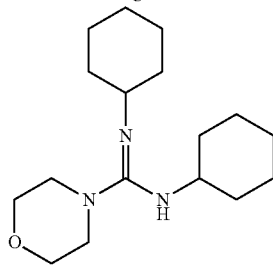
log P of guanidine compound (A) in the invention is preferably in the range of 2 to 10, more preferably in the range of 3 to 8, and still more preferably in the range of 4 to 8.

It is preferred that guanidine compound (A) in the invention does not have a nitrogen atom beside the guanidine structure.

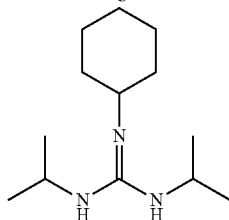
The specific examples of the guanidine compounds are shown below, but the invention is not restricted thereto.



Log P: 4.29



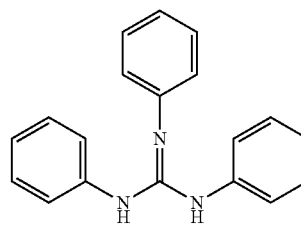
Log P: 3.32



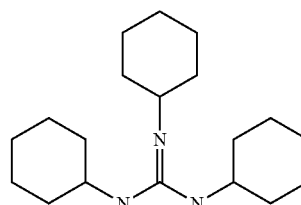
Log P: 3.1

162

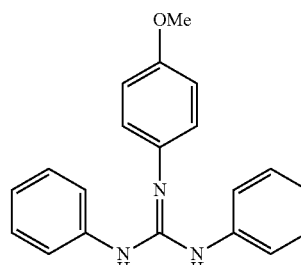
-continued



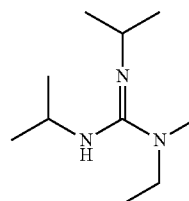
Log P: 5.24



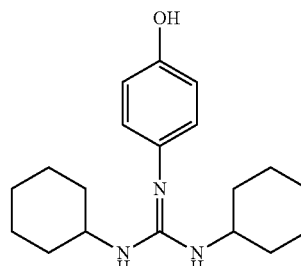
Log P: 4.89



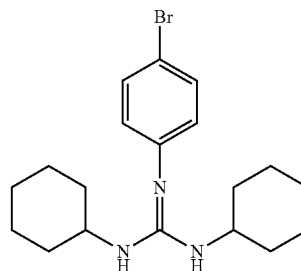
Log P: 5.11



Log P: 2.61



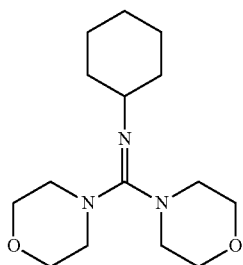
Log P: 4.61



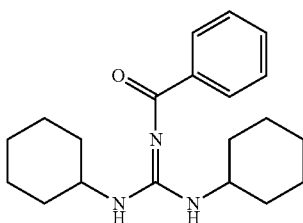
Log P: 5.83

163

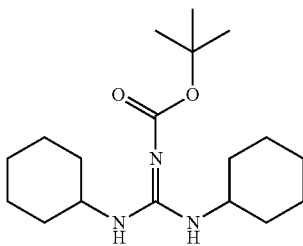
-continued



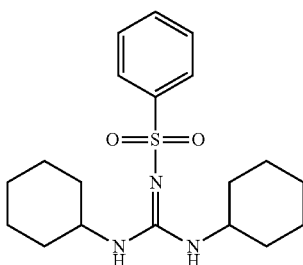
Log P: 1.75



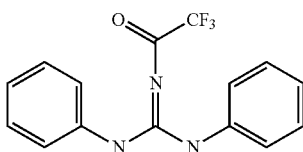
Log P: 4.95



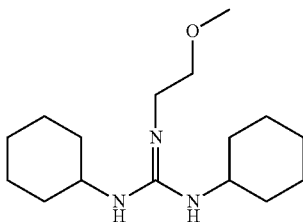
Log P: 4.51



Log P: 4.55



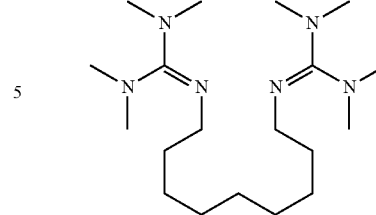
Log P: 4.43



Log P: 3.18

164

-continued



Log P: 4.4

As other basic compounds, the compounds disclosed in JP-A-2011-85926, the compounds synthesized in JP-A-2002-363146, and the compounds disclosed in JP-A-2007-298569, paragraph [0108] can also be used.

The composition according to the invention may contain, as a basic compound, a low molecular weight compound having a nitrogen atom and a group capable of leaving by the action of an acid (hereinafter also referred to as "low molecular weight compound (D)" or "compound (D)").

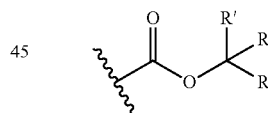
The group capable of leaving by the action of an acid is not especially limited, but an acetal group, a carbonate group, a carbamate group, a tertiary ester group, a tertiary hydroxyl group and a hemiaminal ether group are preferred, and a carbamate group and a hemiaminal ether group are especially preferred.

The molecular weight of compound (D) is preferably 100 to 1,000, more preferably 100 to 700, and especially preferably 100 to 500.

As compound (D), amine derivatives having a group capable of leaving by the action of an acid on a nitrogen atom are preferred.

Compound (D) may have a carbamate group having a protective group on a nitrogen atom. The protective group constituting the carbamate group can be, for example, represented by the following formula (d-1).

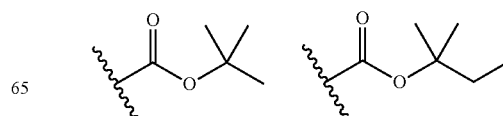
(d-1)



In formula (d-1), each R' independently represents a hydrogen atom, a straight chain or branched alkyl group, a cycloalkyl group, an aryl group, an aralkyl group or an alkoxyalkyl group. R' may be bonded to each other to form a ring.

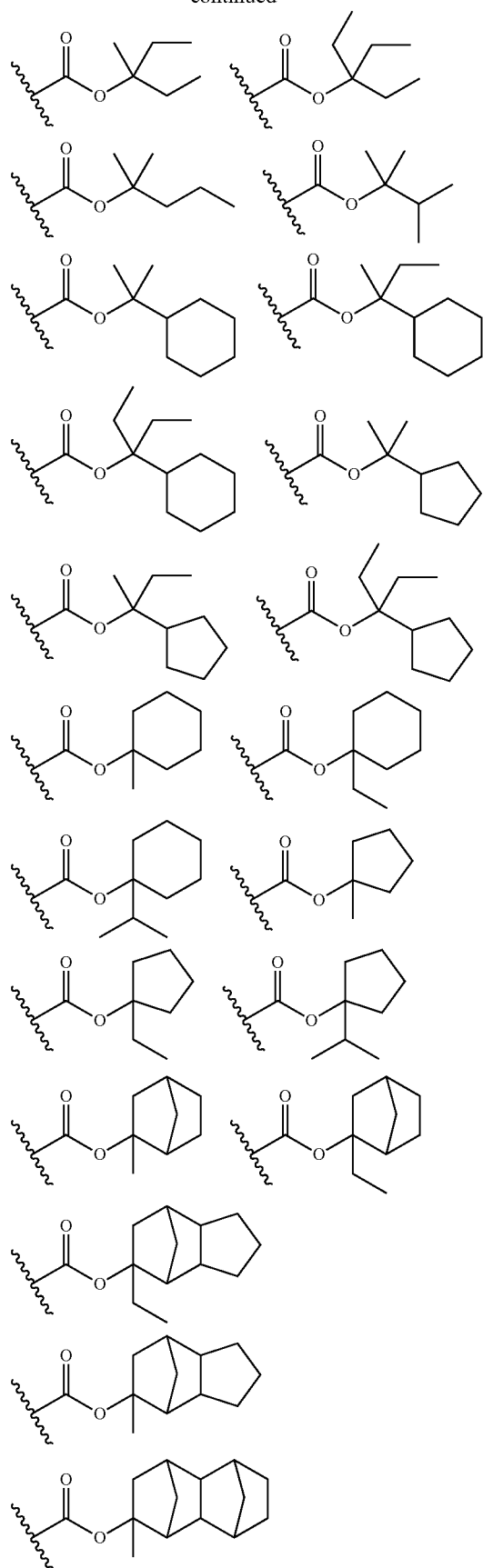
R' preferably represents a straight chain or branched alkyl group, a cycloalkyl group or an aryl group, and more preferably a straight chain or branched alkyl group or a cycloalkyl group.

The specific examples of such groups are shown below.

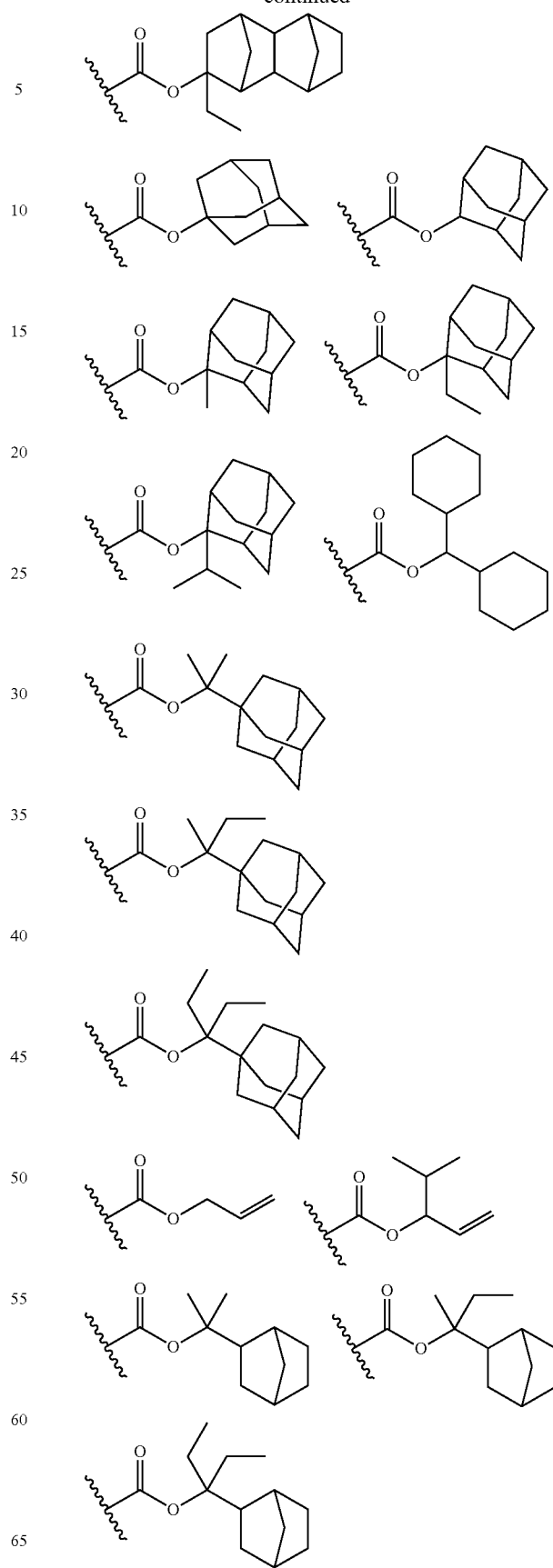


165

-continued

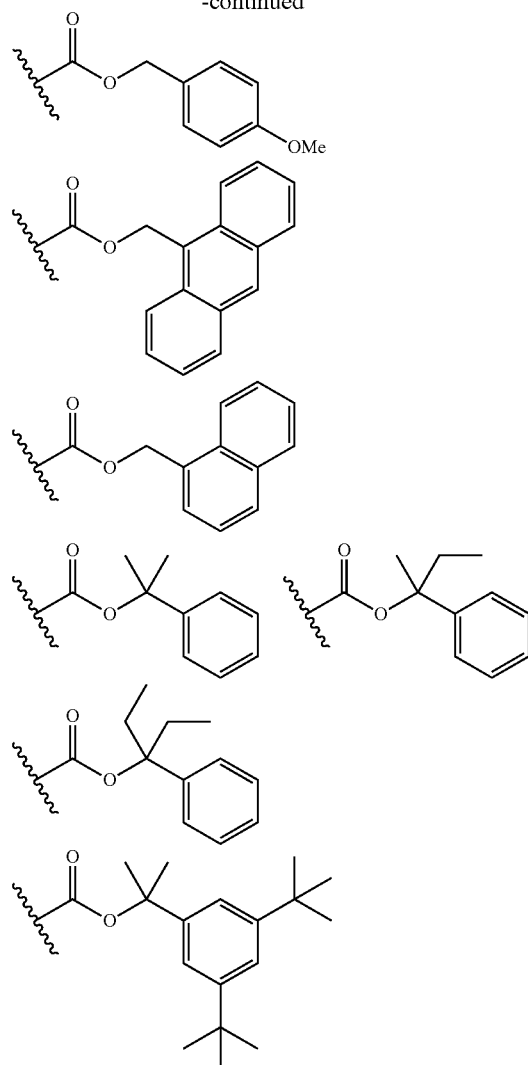
**166**

-continued



167

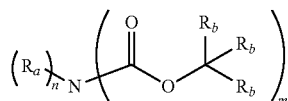
-continued



Compound (D) can also be constituted by arbitrarily combining the above described various basic compounds with the structure represented by formula (d-1).

Compound (D) is especially preferably a compound having the structure represented by the following formula (F).

So long as compound (D) is a low molecular weight compound having a group capable of leaving by the action of an acid, compound (D) may be a compound corresponding to the above various basic compounds.



In formula (F), Ra represents a hydrogen atom, an alkyl group, a cycloalkyl group, an aryl group, or an aralkyl group. When n is 2, two Ra's may be the same with or different from each other, and two Ra's may be bonded to each other to form a divalent heterocyclic hydrocarbon group (preferably having 20 or less carbon atoms) or derivatives thereof.

Each Rb independently represents a hydrogen atom, an alkyl group, a cycloalkyl group, an aryl group, an aralkyl

168

group or an alkoxyalkyl group, provided that when one or more Rb in $-\text{C}(\text{Rb})(\text{Rb})(\text{Rb})$ are hydrogen atoms, at least one of the remaining Rb is a cyclopropyl group, a 1-alkoxyalkyl group or an aryl group.

At least two Rb's may be bonded to form an alicyclic hydrocarbon group, an aromatic hydrocarbon group, a heterocyclic hydrocarbon group or derivatives thereof.

n represents an integer of 0 to 2, m represents an integer of 1 to 3, and $n+m=3$.

In formula (F), each of the alkyl group, cycloalkyl group, aryl group and aralkyl group represented by Ra and Rb may be substituted with a functional group such as hydroxyl group, cyano group, amino group, pyrrolidino group, piperidino group, morpholino group and oxo group, an alkoxy group, or a halogen atom. The alkoxyalkyl group represented by Rb may be substituted in the same manner.

As the alkyl group, cycloalkyl group, aryl group, and aralkyl group (these alkyl group, cycloalkyl group, aryl group, and aralkyl group may be substituted with the above functional group, alkoxy group, or halogen atom) represented by Ra and/or Rb, there are exemplified, for example:

groups deriving from straight chain or branched alkane such as methane, ethane, propane, butane, pentane, hexane, heptanes, octane, nonane, decane, undecane, dodecane, etc., groups obtained by substituting these groups deriving from alkane with, for example, one kind or more or one group or more of a cycloalkyl group such as a cyclobutyl group, a cyclopentyl group, or a cyclohexyl group,

groups deriving from cycloalkane such as cyclobutane, cyclopentane, cyclohexane, cycloheptane, cyclooctane, norbornane, adamantane, noradamantane, etc., groups obtained by substituting these groups deriving from cycloalkane with, for example, one kind or more or one group or more of a straight chain or branched alkyl group such as a methyl group, an ethyl group, an n-propyl group, an i-propyl group, an n-butyl group, a 2-methylpropyl group, a 1-methylpropyl group, or a t-butyl group,

groups deriving from an aromatic compound such as benzene, naphthalene, anthracene, etc., groups obtained by substituting these groups deriving from aromatic compound with, for example, one kind or more or one group or more of a straight chain or branched alkyl group such as a methyl group, an ethyl group, an n-propyl group, an i-propyl group, an n-butyl group, a 2-methylpropyl group, a 1-methylpropyl group, or a t-butyl group,

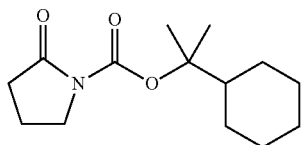
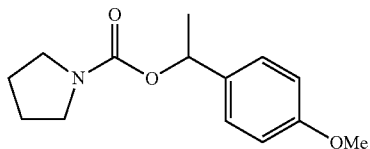
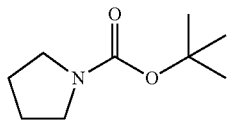
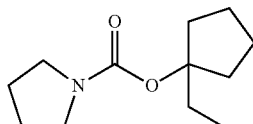
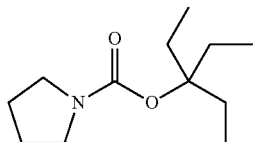
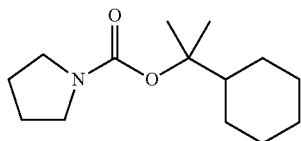
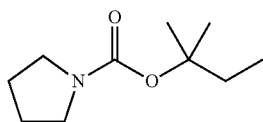
groups deriving from a heterocyclic compound such as pyrrolidine, piperidine, morpholine, tetrahydrofuran, tetrahydropyran, indole, indoline, quinoline, perhydroquinoline, indazole, benzimidazole, etc., groups obtained by substituting these groups deriving from heterocyclic compound with one kind or more or one group or more of a straight chain or branched alkyl group or a group deriving from an aromatic compound, groups obtained by substituting a group deriving from straight chain or branched alkane and a group deriving from cycloalkane with one kind or more or one group or more of a group deriving from an aromatic compound such as a phenyl group, a naphthyl group, anthracenyl, etc., or groups obtained by substituting the above substituents with a functional group such as a hydroxyl group, a cyano group, an amino group, a pyrrolidino group, a piperidino group, a morpholino group, or an oxiso group.

Examples of the divalent heterocyclic hydrocarbon group (preferably having a carbon number of 1 to 20) formed by combining Ra with each other or a derivative thereof include a group derived from a heterocyclic compound such as pyrrolidine, piperidine, morpholine, 1,4,5,6-tetrahydropyrimidine, 1,2,3,4-tetrahydroquinoline, 1,2,3,6-tetrahydropyri-

169

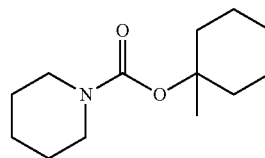
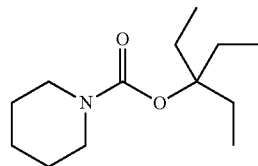
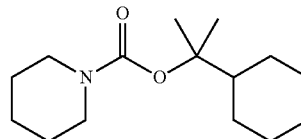
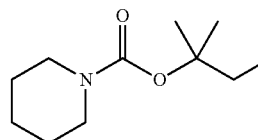
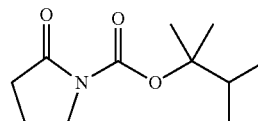
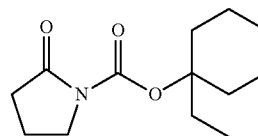
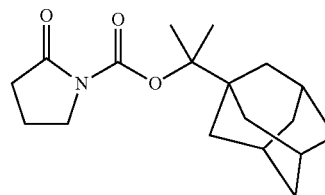
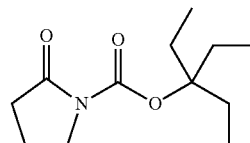
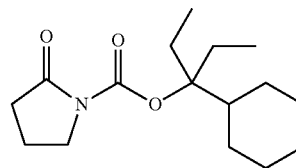
dine, homopiperazine, 4-azabenzimidazole, benzotriazole, 5-azabenzotriazole, 1H-1,2,3-triazole, 1,4,7-triazacyclononane, tetrazole, 7-azaindole, indazole, benzimidazole, imidazo[1,2-a]pyridine, (1S,4S)-(+)-2,5-diazabicyclo[2.2.1]heptane, 1,5,7-triazabicyclo[4.4.0]dec-5-ene, indole, indoline, 1,2,3,4-tetrahydroquinoxaline, perhydroquinoline and 1,5,9-triazacyclododecane, and a group where the group derived from such a heterocyclic compound is substituted with one or more kinds of or one or more groups of linear or branched alkane-derived groups, cycloalkane-derived groups, aromatic compound-derived groups, heterocyclic compound-derived groups and functional groups such as hydroxyl group, cyano group, amino group, pyrrolidino group, piperidino group, morpholino group and oxo group.

The specific examples of especially preferred compound (D) in the invention are shown below, but the invention is not restricted thereto.



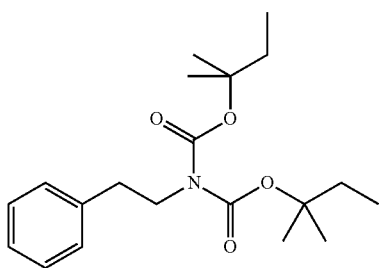
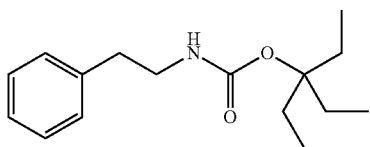
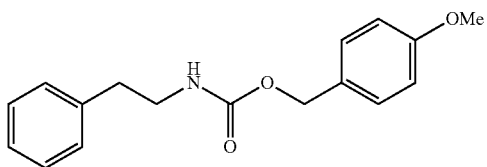
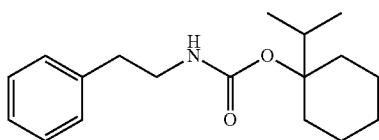
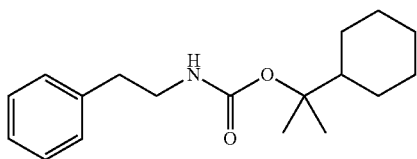
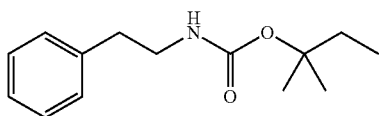
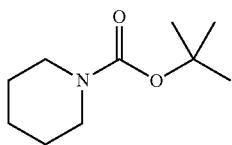
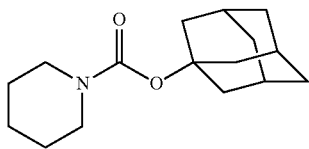
170

-continued



171

-continued

**172**

-continued

(D-17)

5

(D-18)

15

(D-19) 20

25

(D-20)

30

(D-21) 35

(D-22)

45

(D-23)

55

(D-24)

60

65

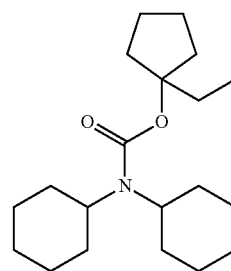
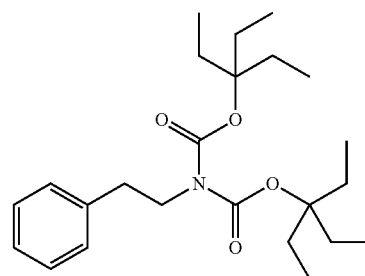
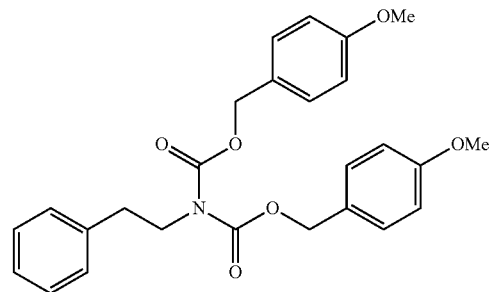
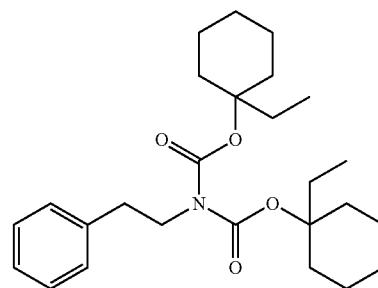
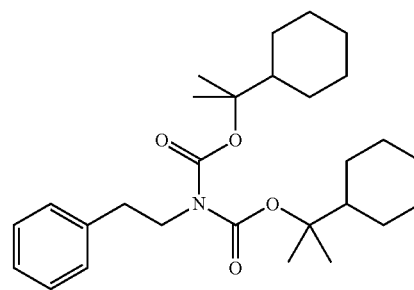
(D-25)

(D-26)

(D-27)

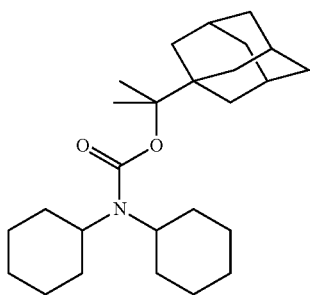
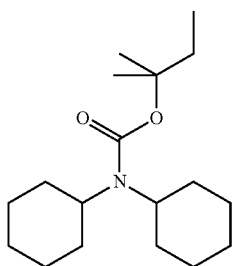
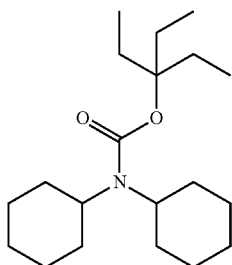
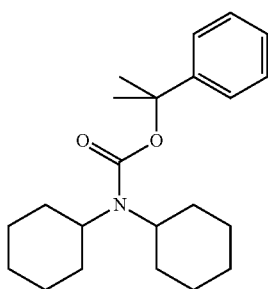
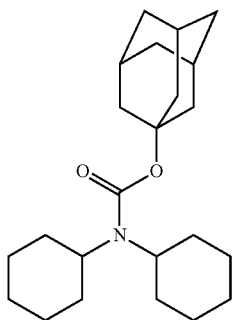
(D-28)

(D-29)

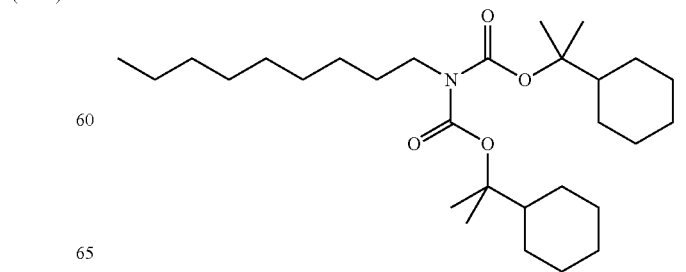
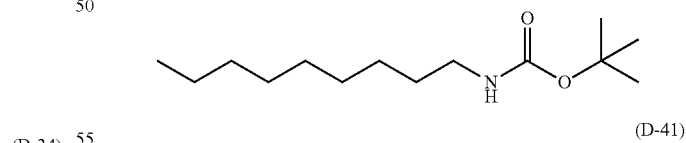
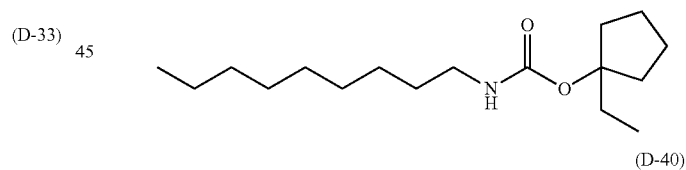
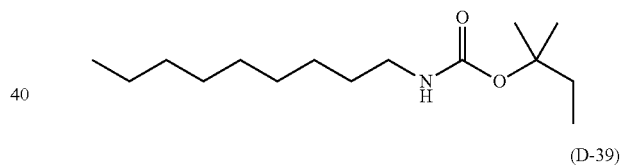
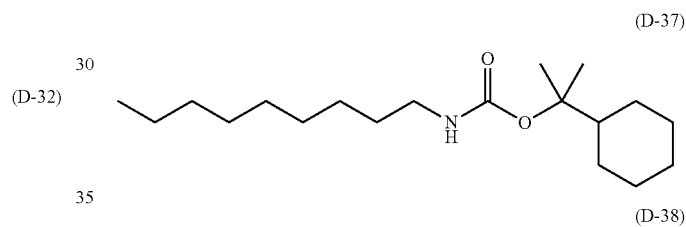
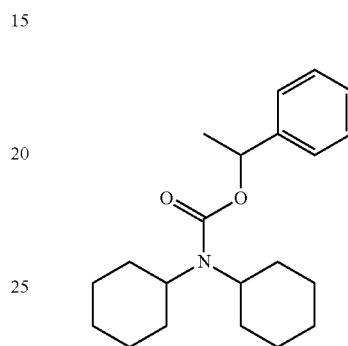
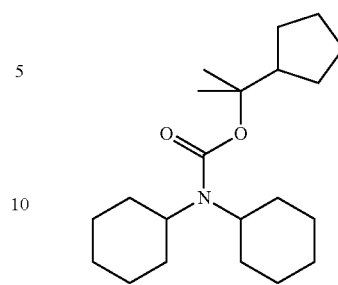


173

-continued

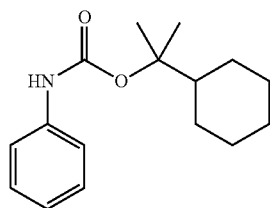
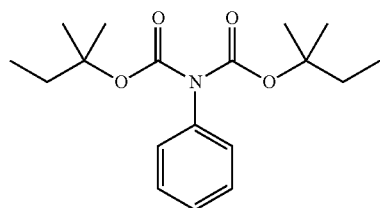
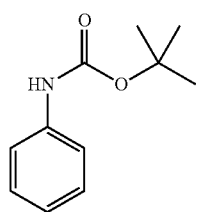
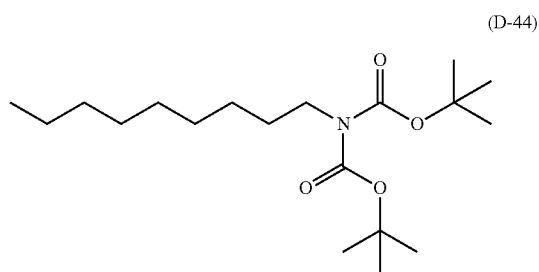
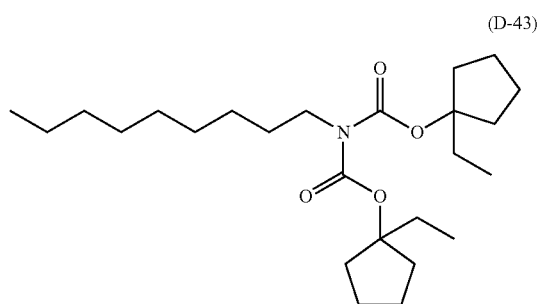
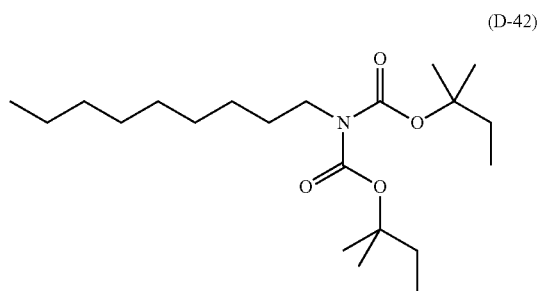
**174**

-continued

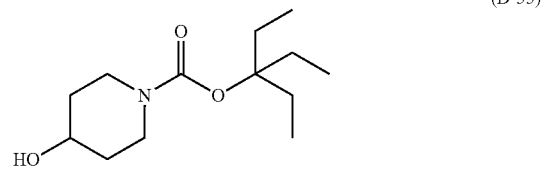
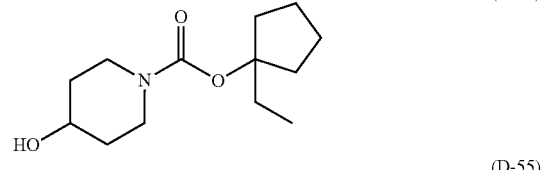
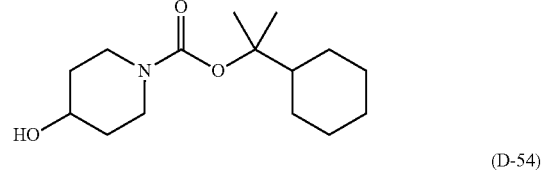
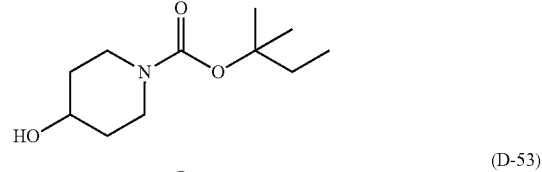
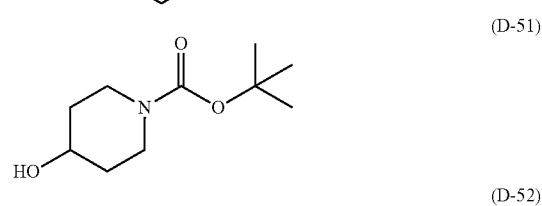
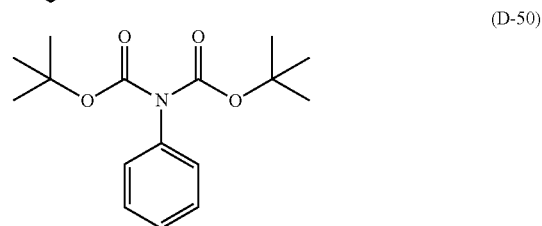
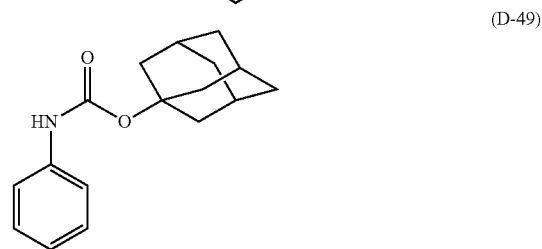
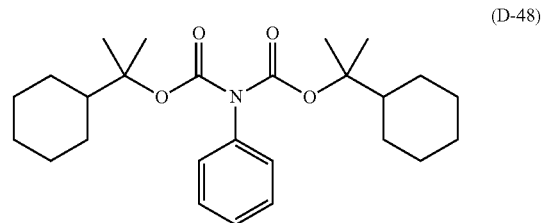


175

-continued

**176**

-continued



The compound represented by formula (A) can be easily synthesized from commercially available amine according to the method described in Protective Groups in Organic Synthesis, Fourth Edition. As the most ordinary method, there is a method of obtaining the compound by acting dicarbonate

177

ester or haloformate ester to commercially available amine. In the formula, X represents a halogen atom. The definition and specific examples of Ra and Rb are the same with those described in the above formula (F).

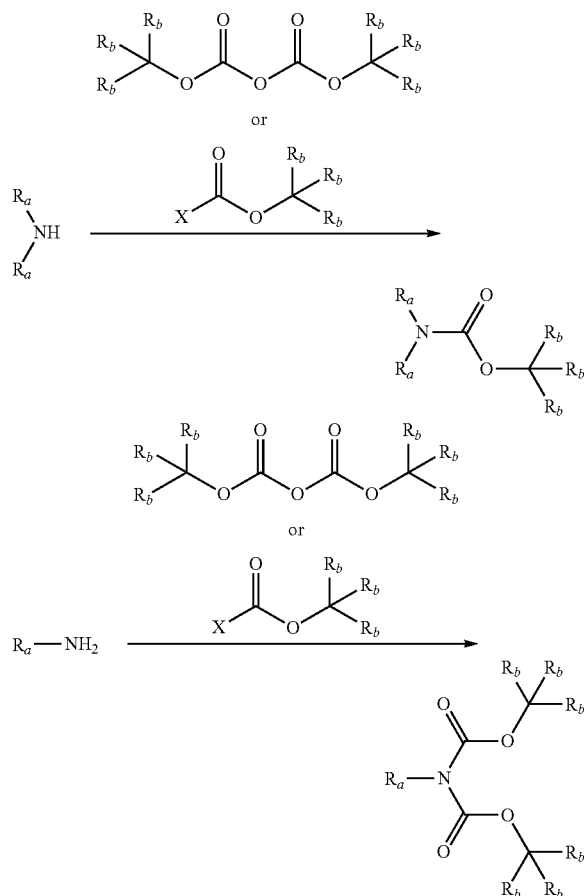


Photo-decomposable basic compounds (compounds which show basic properties by the work of basic nitrogen atoms as a base at the beginning, but decomposed upon irradiation with actinic ray or radiation and generate amphoteric ion compounds having basic nitrogen atoms and organic acid sites, and basic properties diminish or vanish by the neutralization of them in the molecule, for example, onium salts disclosed in Japanese Patent No. 3577743, JP-A-2001-215689, JP-A-2001-166476, and JP-A-2008-102383), and photo-base generating agents (for example, compounds disclosed in JP-A-2010-243773) are also arbitrarily used.

One kind of basic compound (containing compound (D)) is used alone, or two or more kinds are used in combination.

The use amount of basic compound is generally 0.001% by mass to 10% by mass on the basis of the solids content of the composition, and preferably 0.01% by mass to 5% by mass.

The molar ratio of acid generator/basic compound is preferably 2.5 to 300. That is, the molar ratio is preferably 2.5 or more from the point of sensitivity and resolution, and preferably 300 or less from the point of inhibition of lowering of resolution due to thickening of the pattern during the time after exposure to heating treatment. The molar ratio is more preferably 5.0 to 200, and still more preferably 7.0 to 150.

[5] Surfactant

The composition according to the invention may further contain surfactants. By containing surfactants, it becomes

178

possible to form a pattern showing high sensitivity, good resolution and little in defects of adhesion and development when an exposure light source of the wavelength of 250 nm or less, particularly 220 nm or less, is used.

It is especially preferred to use fluorine and/or silicon surfactants.

As fluorine and/or silicon surfactants, the surfactants disclosed in U.S. Patent Application No. 2008/0248425, paragraph [0276] are exemplified. Further, Eftop EF301 and EF303 (manufactured by Shin-Akita Kasei Co., Ltd.), Fluorad FC 430, 431 and 4430 (manufactured by Sumitomo 3M Limited), Megafac F171, F173, F176, F189, F113, F110, F177, F120, and R08 (manufactured by DIC Corporation), Sarfron S-382, SC 101, 102, 103, 104, 105 and 106 (manufactured by ASAHI GLASS CO., LTD.), Troy Sol S-366 (manufactured by Troy Chemical Co., Ltd.), GF-300 and GF-150 (manufactured by TOAGOSEI CO., LTD.), Sarfron S-393 (manufactured by SEIMI CHEMICAL CO., LTD.), Eftop EF121, EF122A, EF122B, RF122C, EF125M, EF135M, EF351, EF352, EF801, EF802, and EF601 (manufactured by JEMCO INC.), PF636, PF656, PF6320 and PF6520 (manufactured by OMNOVA), and FTX-204G, 208G, 218G, 230G, 204D, 208D, 212D, 218D, and 222D (manufactured by NEOS) may be used. Further, polysiloxane polymer KP-341 (manufactured by Shin-Etsu Chemical Co., Ltd.) can also be used as a silicon surfactant.

In addition to these known surfactants as exemplified above, surfactants may also be synthesized with fluoro-aliphatic compounds manufactured by a telomerization method (also called a telomer method) or an oligomerization method (also called an oligomer method). Specifically, polymers having fluoro-aliphatic groups derived from the fluoro-aliphatic compounds may be used as surfactants. The fluoro-aliphatic compound can be synthesized by the method disclosed in JP-A-2002-90991.

As polymers having fluoro-aliphatic groups, copolymers of monomers having fluoro-aliphatic groups and (poly(oxyalkylene)) acrylate or methacrylate and/or (poly(oxyalkylene)) methacrylate are preferred, and they may be distributed at random or may be block copolymerized.

As the poly(oxyalkylene) groups, a poly(oxyethylene) group, a poly(oxypropylene) group, and a poly(oxybutylene) group are exemplified. Further, the polymers may be units having alkyls different in chain length in the same chain length, such as a block combination of poly(oxyethylene and oxypropylene and oxyethylene), and a block combination of poly(oxyethylene and oxypropylene).

In addition, copolymers of monomers having fluoro-aliphatic groups and poly(oxyalkylene) acrylate or methacrylate may be terpolymers or higher polymers obtained by copolymerization of monomers having different two or more kinds of fluoro-aliphatic groups or different two or more kinds of poly(oxyalkylene) acrylates or methacrylates at the same time.

For example, as commercially available surfactants, Megafac F178, F470, F473, F475, F476 and F472 (manufactured by DIC Corporation) can be exemplified. Further, copolymers of acrylate or methacrylate having a C₆F₁₃ group and poly(oxyalkylene) acrylate or methacrylate, copolymers of acrylate or methacrylate having a C₆F₁₃ group, poly(oxyethylene) acrylate or methacrylate, and poly(oxypropylene) acrylate or methacrylate, copolymers of acrylate or methacrylate having a C₈F₁₇ group and poly(oxyalkylene) acrylate or methacrylate, and copolymers of acrylate or methacrylate having a C₈F₁₇ group, poly(oxyethylene) acrylate or methacrylate, and poly(oxypropylene) acrylate or methacrylate are exemplified.

179

Fluorine and/or silicon surfactants other than those disclosed in U.S. Patent Application 2008/0248425, paragraph [0280] may be used.

These surfactants may be used by one kind alone, or two or more kinds of surfactants may be used in combination.

When the composition according to the invention contains surfactants, the content is preferably 0% by mass to 2% by mass, more preferably 0.0001% by mass to 2% by mass, and still more preferably 0.0005% by mass to 1% by mass based on all the solid contents in the composition.

[6] Other Additives

Other than the above-described components, the composition of the invention can arbitrarily contain a carboxylic acid, a carboxylic acid onium salt, dissolution inhibiting compounds having a molecular weight of 3,000 or less as described in Proceeding of SPIE, 2724, 355 (1996), etc., a dye, a plasticizer, a photo-sensitizer, a photo-absorber, and an antioxidant.

In particular, a carboxylic acid is preferably used for the improvement of performances. As the carboxylic acid, aromatic carboxylic acids such as a benzoic acid and naphthoic acid are preferred.

The content of the carboxylic acid is preferably 0.01% by mass to 10% by mass in all the solid content concentration of the composition, more preferably 0.01% by mass to 5% by mass, and still more preferably 0.01% by mass to 3% by mass.

From the standpoint of enhancing the resolution, the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition for use in the present invention is preferably used in a film thickness of 10 to 250 nm, more preferably from 20 to 200 nm, even more preferably from 30 to 100 nm. Such a film thickness can be obtained by setting the solid content concentration in the composition to an appropriate range, thereby imparting an appropriate viscosity and enhancing the coatability and film-forming property.

The entire solid content concentration in the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition for use in the present invention is usually from 1.0 to 10 mass %, preferably from 2.0 to 5.7 mass %, more preferably from 2.0 to 5.3 mass %. By setting the solid content concentration to the range above, the resist solution can be uniformly applied on a substrate and furthermore, a resist pattern with excellent performance in terms of line width roughness can be formed. The reason therefor is not clearly known, but it is considered that thanks to a solid content concentration of 10 mass % or less, preferably 5.7 mass % or less, aggregation of materials, particularly, a photoacid generator, in the resist solution is suppressed, as a result, a uniform resist film can be formed.

The solid content concentration is a weight percentage of the weight of other resist components excluding the solvent, based on the total weight of the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition.

The electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition for use in the present invention is used by dissolving the components above in a predetermined organic solvent, preferably in the above-described mixed solvent, filtering the solution, and applying it on a predetermined support (substrate). The filter used for filtration is preferably a polytetrafluoroethylene-, polyethylene- or nylon-made filter having a pore size of 0.1 μm or less, more preferably 0.05 μm or less, still more preferably 0.03 μm or less. In the filtration through a filter, as described, for example, in JP-A-2002-62667, circulating filtration may be performed, or the filtration may be performed by connecting a plurality of kinds of filters in series or in parallel. Also, the composition may be filtered a plurality of times. Furthermore,

180

a deaeration treatment or the like may be applied to the composition before or after filtration through a filter.

[Uses]

The pattern-forming method of the invention is preferably used in the formation of semiconductor fine circuit such as the manufacture of super LSI and high capacity microchips. At the time of forming a semiconductor fine circuit, a resist film formed with a pattern is subjected to circuit formation and etching, and then the residual resist film part is finally removed with a solvent, and so the resist film resulting from the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition of the invention does not remain on the final product such as microchips unlike what is called a permanent resist for use in a print substrate and the like.

The invention also relates to a manufacturing method of an electronic device containing the above described pattern-forming method and also relates to an electronic device manufactured according to the manufacturing method.

The electronic device of the invention is preferably mounted on electric and electronic apparatus (domestic electric apparatus, OA and peripheral devices of broadcasting media, optical apparatus, and communication devices).

EXAMPLE

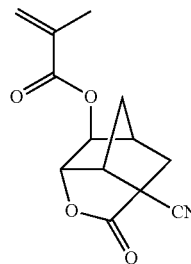
The invention will be further specifically explained with reference to examples but the invention is not restricted to these examples.

Synthesis Example 1

Synthesis of Resin (A1-1-1)

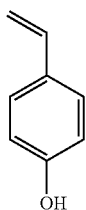
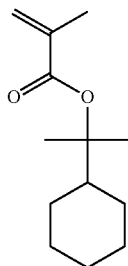
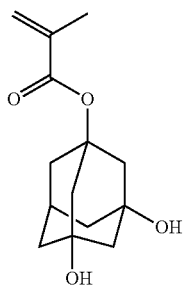
Under nitrogen flow, 20 g of cyclohexanone is put in a three-necked flask and heated at 80° C. (solvent 1). M-1, M-2, M-3 and M-4 shown below are dissolved in the cyclohexanone at a molar rate of 40/10/40/10 to prepare a 22% by mass monomer solution (200 g). Further, a solution obtained by adding 6 mol % of initiator V-601 (manufactured by Wako Pure Chemical Industries) to monomer and dissolving is dripped into solvent 1 over 6 hours. After termination of dripping, the reaction solution is further reacted at 80° C. for 2 hours. The reaction solution is allowed to be cooled, and then poured into a mixed solution comprising 1,400 ml of hexane and 600 ml of ethyl acetate. The powder precipitated is collected by filtration and dried to obtain 37 g of resin (A1-1-1). From GPC of the obtained resin (A1-1-1), weight average molecular weight (Mw: polystyrene-equivalent) is 10,000, and polydispersity (Mw/Mn) is 1.60.

M-1

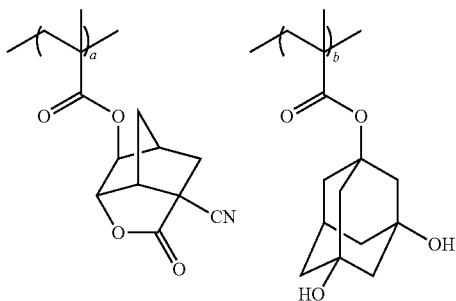


181

-continued



Resins (A1-1-2), (A1-2) to (A1-21) are synthesized in the similar method. The polymer structure, weight average molecular weight (Mw) and polydispersity (Mw/Mn) of each of the synthesized polymers are shown below. The compositional ratio of each repeating unit of the structures of the following polymers is shown in a molar ratio.

**182**

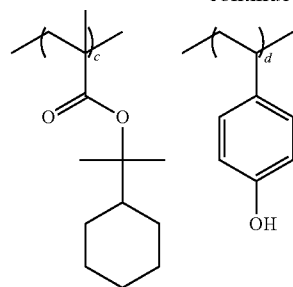
-continued

M-2

5

10

15



(A1-1-1)

a/b/c/d = 40/10/40/10

MW = 10000, Mw/Mn = 1.60

(A1-1-2)

a/b/c/d = 40/10/46/4

MW = 11000, Mw/Mn = 1.60

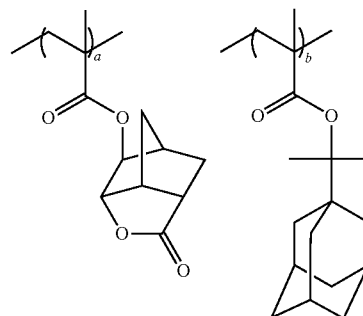
M-3

25

30

35

(A1-2)

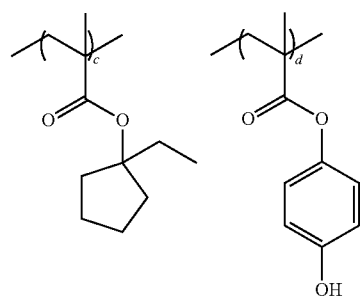


M-4

40

45

50



a/b/c/d = 40/10/47/3

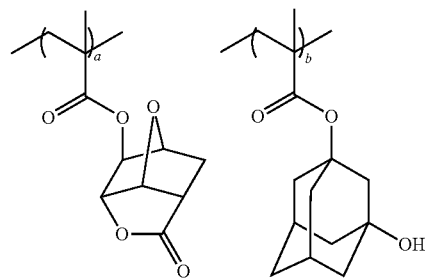
MW = 11000, Mw/Mn = 1.85

55

60

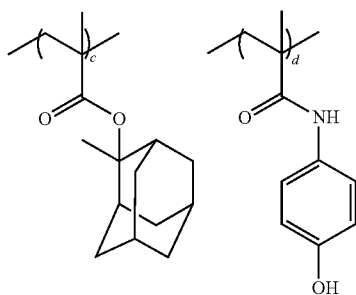
65

(A1-3)



183

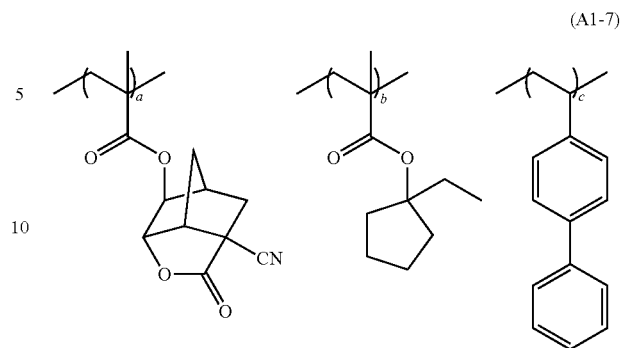
-continued



a/b/c/d = 40/12/45/3
MW = 8000, Mw/Mn = 1.65

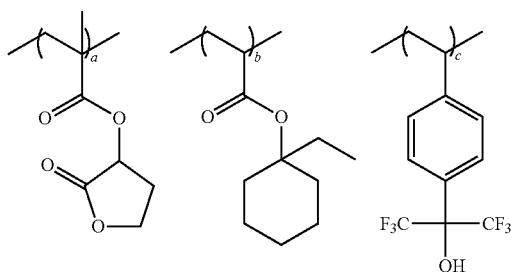
184

-continued



a/b/c = 40/40/20
MW = 7000, Mw/Mn = 1.65

(A1-4)



a/b/c = 46/50/4
MW = 26000, Mw/Mn = 1.85

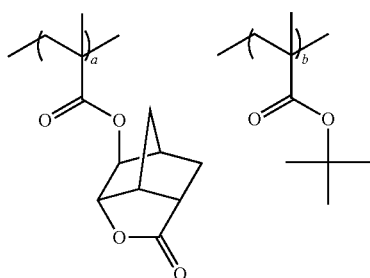
20

25

30

35

(A1-5)



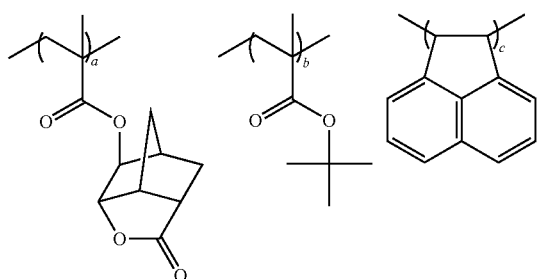
a/b = 60/40
MW = 5500, Mw/Mn = 1.40

40

45

50

(A1-6)



a/b/c = 40/45/15
MW = 7500, Mw/Mn = 1.50

55

60

65

70

75

80

85

90

95

100

105

110

115

120

125

130

135

140

145

150

155

160

165

170

175

180

185

190

195

200

205

210

215

220

225

230

235

240

245

250

255

260

265

270

275

280

285

290

295

300

305

310

315

320

325

330

335

340

345

350

355

360

365

370

375

380

385

390

395

400

405

410

415

420

425

430

435

440

445

450

455

460

465

470

475

480

485

490

495

500

505

510

515

520

525

530

535

540

545

550

555

560

565

570

575

580

585

590

595

600

605

610

615

620

625

630

635

640

645

650

655

660

665

670

675

680

685

690

695

700

705

710

715

720

725

730

735

740

745

750

755

760

765

770

775

780

785

790

795

800

805

810

815

820

825

830

835

840

845

850

855

860

865

870

875

880

885

890

895

900

905

910

915

920

925

930

935

940

945

950

955

960

965

970

975

980

985

990

995

1000

1005

1010

1015

1020

1025

1030

1035

1040

1045

1050

1055

1060

1065

1070

1075

1080

1085

1090

1095

1100

1105

1110

1115

1120

1125

1130

1135

1140

1145

1150

1155

1160

1165

1170

1175

1180

1185

1190

1195

1200

1205

1210

1215

1220

1225

1230

1235

1240

1245

1250

1255

1260

1265

1270

1275

1280

1285

1290

1295

1300

1305

1310

1315

1320

1325

1330

1335

1340

1345

1350

1355

1360

1365

1370

1375

1380

1385

1390

1395

1400

1405

1410

1415

1420

1425

1430

1435

1440

1445

1450

1455

1460

1465

1470

1475

1480

1485

1490

1495

1500

1505

1510

1515

1520

1525

1530

1535

1540

1545

1550

1555

1560

1565

1570

1575

1580

1585

1590

1595

1600

1605

1610

1615

1620

1625

1630

1635

1640

1645

1650

1655

1660

1665

1670

1675

1680

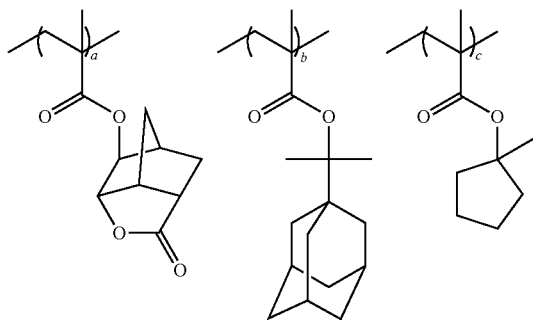
1685

1690

185

-continued

(A1-10)



a/b/c = 40/40/20
MW = 11000,
Mw/Mn = 1.60

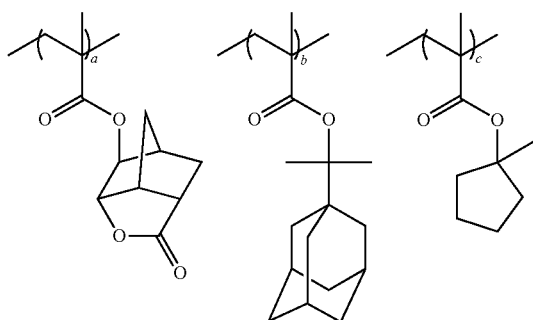
5

10

15

20

(A1-11)



a/b/c = 35/35/20/10
MW = 21000, Mw/Mn = 1.60

25

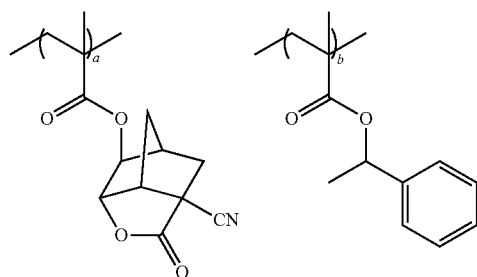
30

35

40

45

(A1-12)



a/b = 60/40
MW = 6500, Mw/Mn = 1.50

50

55

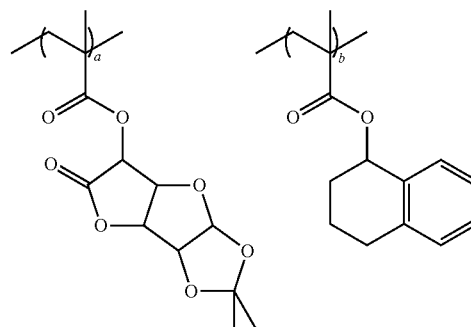
60

65

186

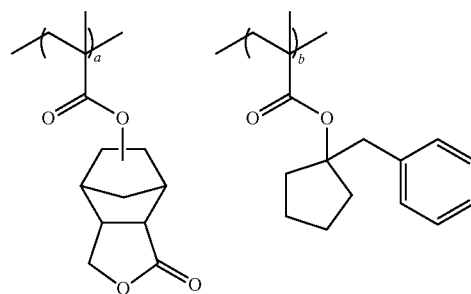
-continued

(A1-13)



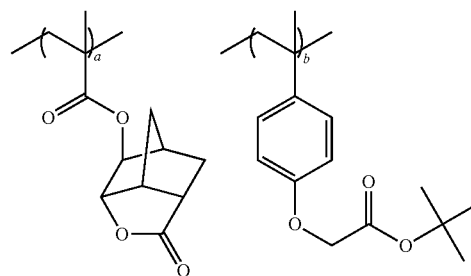
a/b = 50/50
MW = 28500, Mw/Mn = 1.55

(A1-14)



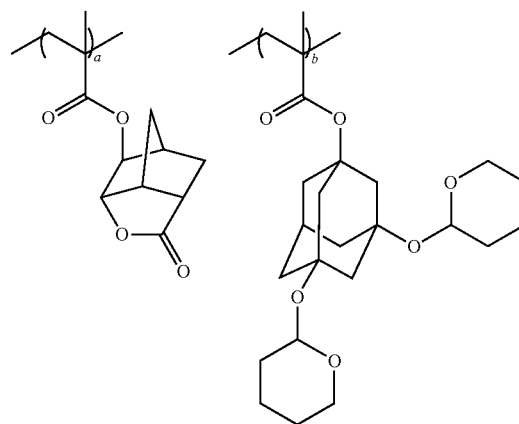
a/b = 70/30
MW = 8000, Mw/Mn = 1.85

(A1-15)



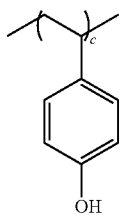
a/b = 60/40
MW = 7000, Mw/Mn = 1.65

(A1-16)

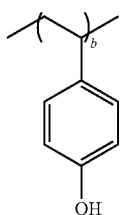
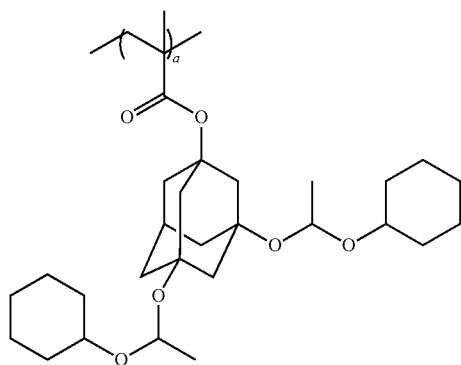


187

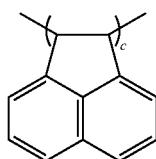
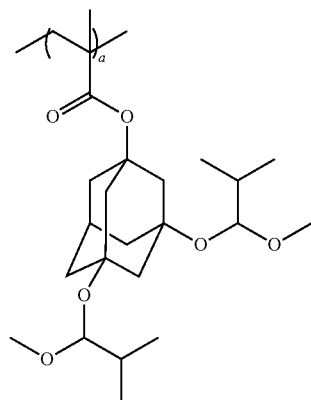
-continued



$a/b/c = 10/60/30$
MW = 10000, Mw/Mn = 1.45



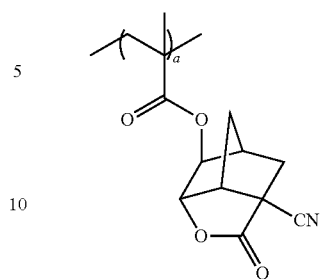
$a/b = 70/30$
MW = 13000, Mw/Mn = 1.55



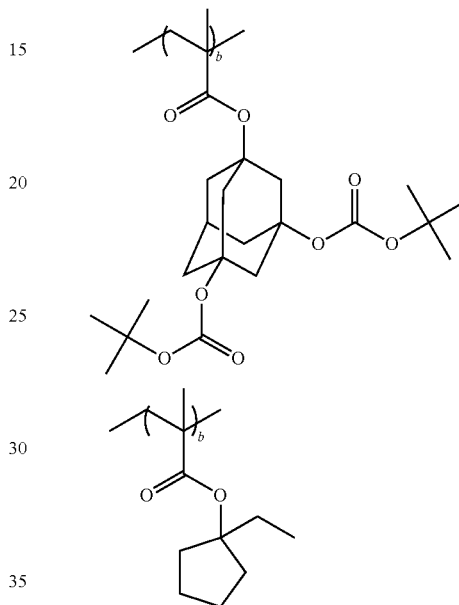
$a/b/c = 60/20/20$
MW = 18000, Mw/Mn = 1.75

188

-continued

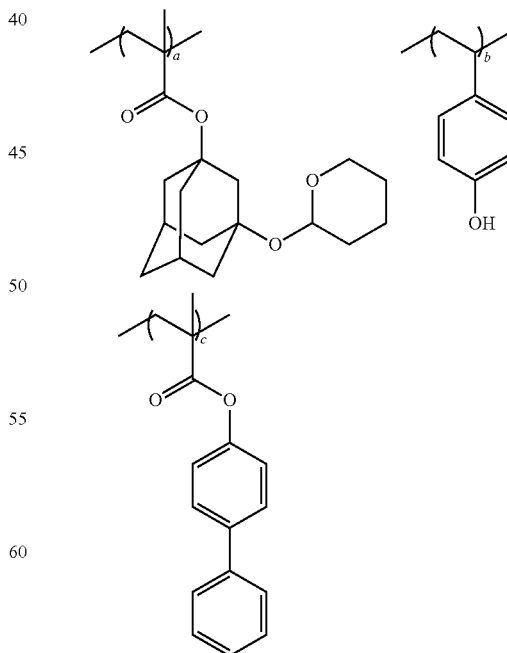


(A1-17)



$a/b/c = 30/50/20$
MW = 11000, Mw/Mn = 1.65

(A1-18)



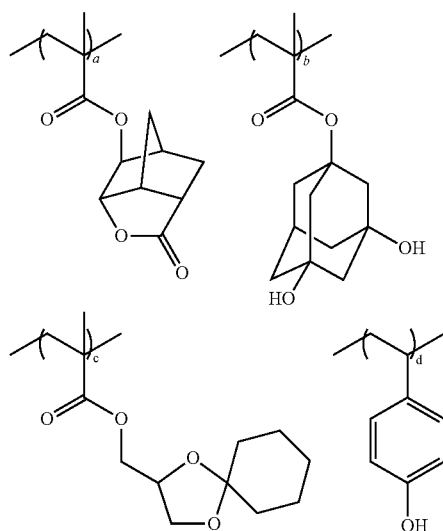
$a/b/c = 60/20/20$
MW = 8000, Mw/Mn = 1.6

(A1-19)

(A1-20)

189

-continued



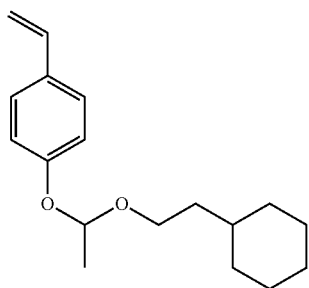
a/b/c/d = 10/20/60/10
MW = 13000, Mw/Mn = 1.65

Synthesis Example 2

Synthesis of Resin (A2-1)

Under nitrogen flow, 4.66 parts by mass of 1-methoxy-2-propanol is heated at 80° C. A mixed solution comprising 5.05 parts by mass of 4-hydroxystyrene, 4.95 parts by mass of monomer (M-5) (the molar ratio of 4-hydroxystyrene and monomer (M-5) is 7/3), 18.6 parts by mass of 1-methoxy-2-propanol, and 1.36 parts by mass of dimethyl-2,2'-azobisisobutyrate (V-601, manufactured by Wako Pure Chemical Industries) is dripped into the above liquid over two hours while stirring the liquid. After termination of dripping, the reaction solution is stirred at 80° C. for further 4 hours. The reaction solution is allowed to be cooled, and then the reaction product is reprecipitated with a large amount of hexane/ethyl acetate and vacuum dried to obtain 5.9 parts by mass of resin (A2-1) of the invention.

From GPC, weight average molecular weight (Mw: polystyrene-equivalent) of resin (A2-1) is Mw=15,100, and polydispersity (Mw/Mn) is 1.40.



Resins (A2-2) to (A2-4) are synthesized in the similar method. The polymer structure, weight average molecular weight (Mw) and polydispersity (Mw/Mn) of each of the synthesized polymers are shown below. The compositional

190

ratio of each repeating unit of the structures of the following polymers is shown in a molar ratio.

(A1-21)

5

(A2-1)

10

15

20

a/b = 70/30
MW = 15100, Mw/Mn = 1.40

25

(A2-2)

30

35

a/b = 40/60
MW = 9000, Mw/Mn = 1.25

40

(A2-3)

45

50

M-5

a/b/c = 40/45/15
MW = 8000, Mw/Mn = 1.35

55

(A2-4)

60

a/b = 70/30
MW = 4800, Mw/Mn = 1.15

Electron Beam (EB) Exposure

(1) Preparation of Coating Solution of Electron Beam-Sensitive or Extreme Ultraviolet Radiation-Sensitive Resin Compositions and Coating

The solution of the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition (resist composition) is obtained by precisely filtering the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition having the composition shown in Table 1 through a membrane filter having a pore size of 0.1 μm .

The solution of the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition is applied on a 6-inch Si wafer having been subjected to hexamethyldisilazane (HMDS) treatment in advance with a spin coater Mark 8 (manufactured by Tokyo Electron Limited), dried on a hot plate at 100° C. for 60 seconds, and a resist film having a thickness of 50 nm is obtained.

(2) EB Exposure and Development

Pattern irradiation is performed on the wafer coated with the resist film obtained in the above (1) with an electron beam drawing apparatus (HL750, accelerating voltage: 50 KeV, manufactured by Hitachi Ltd.). At this time, drawing is performed such that line and space of 1/1 is formed. After electron beam drawing, the wafer is heated at 110° C. for 60 seconds on a hot plate. After that, the wafer is puddled with the organic developer shown in the following table and developed for 30 seconds, and then rinsed by using the rinsing solution shown in the table below. Subsequently, the wafer is revolved at 4,000 rpm for 30 seconds and then heated at 90° C. for 60 seconds, to thereby obtain a resist pattern of line and space pattern of 1/1 having a line width of 50 nm.

Electron Beam (EB) Exposure

An electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition is prepared and a pattern is formed in the same manner as in Example 1 except that the constitution is changed as shown in the table below, and development is performed with an alkali aqueous solution (TMAH, a 2.38% by mass tetramethylammonium hydroxide aqueous solution) in place of the organic developer and water is used as the rinsing solution.

(3) Evaluation of Resist Pattern

Sensitivity, resolution and LWR of the obtained resist pattern are evaluated with a scanning electron microscope (S-9220, manufactured by Hitachi Limited) by the following methods. The results obtained are shown in the table below.

(3-1) Sensitivity

Energy of irradiation at the time of resolving a 1/1 line and space pattern having a line width of 50 nm is taken as sensitivity (Eop). The smaller the value, the better is the performance. However, since in Comparative Examples 5 and 6, 1/1 line and space pattern having a line width of 50 nm cannot be resolved, energy of irradiation at the time of resolving a 1/1 line and space pattern having a line width of 100 nm is taken as sensitivity (Eop).

(3-2) Resolution

In the above Eop, the smallest line width of the separated 1/1 line and space pattern is taken as resolution. The smaller the value, the better is the performance.

(3-3) Line Width Roughness (LWR)

Concerning line width roughness, in the above Eop, line width is measured at arbitrary 50 points of 0.5 μm in the longitudinal direction of a line and space pattern having a line width of 50 nm (however, a 1/1 line and space pattern having a line width of 100 nm in Comparative Examples 5 and 6), and standard deviation is obtained, from which 3 σ is computed. The smaller the value, the better is the performance.

TABLE 1

EB Exposure										
Example No.	Resin (A)	Acid Generator (B)	Solvent (mass ratio) (40 g)	Basic Compound	Surfactant (5 mg)	Developer (mass ratio)	Rinsing Solution	Sensitivity ($\mu\text{C}/\text{cm}^2$)	Resolution (nm)	LWR (nm)
Example 1	A1-1-1 (0.679 g)	z45 (0.310 g)	S-1/S-2 (80/20)	D-3 (6 mg)	W-1	S-5	S-8	12.0	35.5	4.8
Example 2	A1-1-2 (0.679 g)	z45 (0.310 g)	S-1/S-2 (80/20)	D-3 (6 mg)	W-1	S-5	S-8	13.5	33.5	4.4
Example 3	A1-2 (0.685 g)	z117 (0.310 g)	S-1	D-1 (5 mg)	Nothing	S-5	S-8	12.8	32.5	4.1
Example 4	A1-3 (0.737 g)	z119 (0.250 g)	S-1/S-2 (40/60)	D-1 (8 mg)	W-2	S-5	S-10	13.0	32.5	4.2
Example 5	A1-4 (0.780 g)	z120 (0.210 g)	S-1	D-4 (5 mg)	W-3	S-5	S-12	13.3	33.0	4.3
Example 6	A1-5 (0.781 g)	z114 (0.210 g)	S-1/S-2 (80/20)	D-3 (4 mg)	W-1	S-5	S-8	14.3	32.0	4.5
Example 7	A1-5 (0.681 g)	z114 (0.310 g)	S-1/S-2 (80/20)	D-3 (4 mg)	W-1	S-5	S-8	13.2	31.5	4.1
Example 8	A1-5 (0.591 g)	z114 (0.400 g)	S-1/S-2 (80/20)	D-3 (4 mg)	W-1	S-5	S-8	12.8	31.5	3.9
Example 9	A1-5 (0.491 g)	z114 (0.500 g)	S-1/S-2 (80/20)	D-3 (4 mg)	W-1	S-5	S-8	12.6	31.5	3.6
Example 10	A1-6 (0.592 g)	z115 (0.400 g)	S-1/S-4 (80/20)	D-1 (3 mg)	W-4	S-7	S-9	12.9	31.0	3.9
Example 11	A1-7 (0.583 g)	z69 (0.310 g)	S-3	D-1 (2 mg)	W-2	S-5/S-6 (80/20)	S-11	12.8	32.0	4.1
Example 12	A1-5 (0.100 g)									
	A1-8 (0.590 g)	z116 (0.300 g)	S-1	D-3 (5 mg)	W-1	S-13	S-10	12.7	31.5	3.9
		z115 (0.100 g)								

TABLE 1-continued

EB Exposure										
Example No.	Resin (A)	Acid Generator (B)	Solvent (mass ratio) (40 g)	Basic Compound	Surfactant (5 mg)	Developer (mass ratio)	Rinsing Solution	Sensitivity ($\mu\text{C}/\text{cm}^2$)	Resolution (nm)	LWR (nm)
Example 13	A1-9 (0.743 g)	z18 (0.250 g)	S-1/S-2 (70/30)	D-4 (2 mg)	W-2	S-14	S-8	12.8	31.5	3.8
Example 14	A1-10 (0.782 g)	z108 (0.210 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	14.4	31.0	4.4
Example 15	A1-10 (0.682 g)	z108 (0.310 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	13.3	31.0	4.0
Example 16	A1-10 (0.592 g)	z108 (0.400 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	12.7	31.0	3.8
Example 17	A1-10 (0.392 g)	z108 (0.600 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	12.4	31.5	3.6
Example 18	A1-11 (0.679 g)	z45 (0.310 g)	S-1	D-2 (6 mg)	W-3	S-6	S-12	13.0	30.5	3.9
Example 19	A1-12 (0.642 g)	z45 (0.350 g)	S-1/S-4 (80/20)	D-1 (3 mg)	W-4	S-5	S-11	13.2	31.0	3.9
Example 20	A1-13 (0.745 g)	z39 (0.250 g)	S-1/S-4 (70/30)	D-3 (5 mg)	Nothing	S-5	S-8	13.5	31.5	4.0
Example 21	A1-14 (0.639 g)	z19 (0.350 g)	S-1	D-4 (6 mg)	W-2	S-6	S-10	13.7	31.5	3.8
Example 22	A1-15 (0.681 g)	z2 (0.310 g)	S-1	D-3 (4 mg)	W-1	S-7	S-8	13.6	32.5	3.8
Example 23	A2-1 (0.733 g)	z4 (0.150 g)	S-1	D-1 (12 mg)	W-1	S-5	S-8	13.4	38.0	4.9
Example 24	A2-2 (0.670 g)	z10 (0.100 g)	S-1	D-1 (20 mg)	Nothing	S-7	S-10	13.0	37.0	4.7
Example 25	A2-3 (0.775 g)	z99 (0.310 g)	S-1	D-1 (10 mg)	W-1	S-5	S-8	13.9	35.5	4.5
Example 26	A2-3 (0.675 g)	z118 (0.210 g)	S-1/S-2 (80/20)	D-1 (10 mg)	W-1	S-5	S-8	13.2	35.0	4.1
Example 27	A2-3 (0.585 g)	z118 (0.310 g)	S-1/S-2 (80/20)	D-1 (10 mg)	W-1	S-5	S-8	12.7	35.0	3.9
Example 28	A2-4 (0.677 g)	z113 (0.400 g)	S-1	D-2 (8 mg)	W-4	S-6	S-10	13.2	36.5	4.8
Example 29	A1-16 (0.682 g)	z123 (0.310 g)	S-1/S-2 (80/20)	D-8 (3 mg)	W-1	S-5	S-8	13.5	31.0	3.9
Example 30	A1-17 (0.681 g)	z121 (0.310 g)	S-1/S-2 (80/20)	D-7 (4 mg)	W-1	S-5	S-8	13.8	32.0	4.0
Example 31	A1-18 (0.731 g)	z117 (0.260 g)	S-1/S-2 (60/40)	D-5 (4 mg)	W-2	S-5	S-10	14.6	33.0	4.5
Example 32	A1-19 (0.681 g)	z122 (0.310 g)	S-1	D-6 (5 mg)	W-3	S-6	S-8	14.8	34.0	4.6
Example 33	A1-20 (0.581 g)	z112 (0.410 g)	S-1/S-2 (80/20)	D-9 (4 mg)	W-4	S-5	S-8	14.2	33.0	4.6
Example 34	A1-21 (0.682 g)	z126 (0.310 g)	S-3	D-8 (3 mg)	W-1	S-7	S-12	14.5	34.0	4.7
Comparative Example 1	A1-10 (0.892 g)	z108 (0.100 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	19.5	33.5	5.3
Comparative Example 2	A1-10 (0.842 g)	z108 (0.150 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	17.4	33.0	4.9
Comparative Example 3	A1-12 (0.892 g)	z45 (0.100 g)	S-1/S-4 (80/20)	D-1 (3 mg)	W-4	S-5	S-8	16.4	33.0	4.7
Comparative Example 4	A2-3 (0.885 g)	z118 (0.100 g)	S-1/S-2 (80/20)	D-1 (10 mg)	W-1	S-5	S-8	15.5	37.0	5.0
Comparative Example 5	A1-5 (0.591 g)	z114 (0.400 g)	S-1/S-2 (80/20)	D-3 (4 mg)	W-1	TMAH (positive development)	Water	50.4	75.0	6.2
Comparative Example 6	A1-10 (0.592 g)	z108 (0.400 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	TMAH (positive development)	Water	58.7	81.0	6.0

195

The abbreviations in the tables show the compounds of the above specific examples and the following compounds.

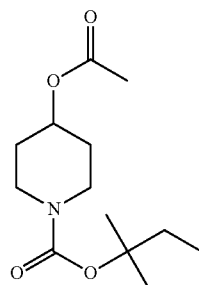
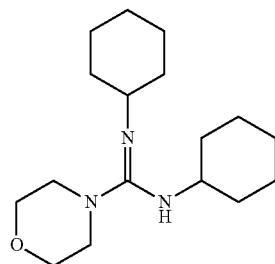
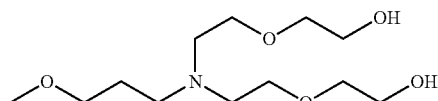
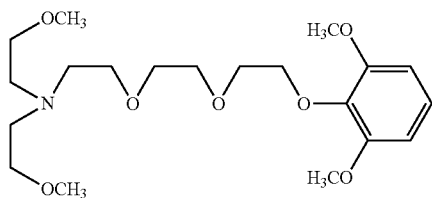
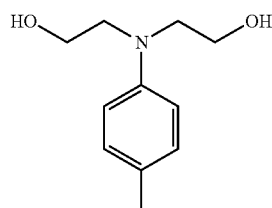
<Basic Compound>

D-1: Tetra-(n-butyl)ammonium hydroxide

D-2: 1,8-Diazabicyclo[5.4.0]-7-undecene

D-3: 2,4,5-Triphenylimidazole

D-4: Tridecylamine



<Surfactant>

W-1: Megafac F176 (fluorine surfactant, manufactured by DIC Corporation)

W-2: Megafac R08 (fluorine/silicon surfactant, manufactured by DIC Corporation)

W-3: Polysiloxane polymer KP-341 (silicon surfactant, manufactured by Shin-Etsu Chemical Co., Ltd.)

W-4: PF6320 (fluorine surfactant, manufactured by OMNOVA)

<Coating Solvent>

S-1: Propylene glycol monomethyl ether acetate (PGMEA)

S-2: Propylene glycol monomethyl ether (PGME)

196

S-3: Tetrahydrofuran

S-4: Cyclohexanone

<Developer, Rinsing Solution>

S-5: Butyl acetate

5 S-6: Pentyl acetate

S-7: Anisole

S-8: 1-Hexanol

S-9: 4-Methyl-2-pentanol

S-10: Decane

D-5 10 S-11: Octane

S-12: Ethylbenzene

S-13: Propylene glycol monomethyl ether acetate (PGMEA)

S-14: Ethoxybenzene

15 TMAH: Tetramethylammonium hydroxide 2.38% by mass aqueous solution

As can be seen from the above tables, Examples 1 to 34 can satisfy high sensitivity, high resolution, and high line width roughness (LWR) performance at the same time in on an extremely high level.

D-6

20 In particular, as can be seen from the comparison of Examples 8, 16 and Comparative Examples 5, 6, wherein positive development is performed with the same resist composition as in Examples 8, 16 and by alkali developer, by using the pattern forming method of the invention with the organic developer, patterns of high resolution, high sensitivity and high LWR can be formed. As described above, this is presumed for the reason that capillary force applied to the side wall of the pattern is reduced when the organic developer is used, as compared with the case of using an alkali developer, as a result pattern collapse can be prevented.

D-7

30 Further, Comparative Examples 1 to 4 where the content of the acid generator is less than 21% by mass to all the solid contents of the composition cannot reach the level of the examples of the invention concerning sensitivity and LWR. This is probably for the reason that Comparative Examples 1 to 4 are low in the amounts of the acid generators, and so the generated acids are too poor to satisfy high level where the examples of the invention can achieve.

D-8

40 Incidentally, in the case where a rinsing step is not carried out, excellent effects similar to those in the above examples can be obtained.

D-9

Examples 101 to 134 and Comparative Examples 101 to 104

45

Extreme Ultraviolet Radiation (EUV) Exposure

(4) Preparation of Coating Solution of Electron Beam-Sensitive or Extreme Ultraviolet Radiation-Sensitive Resin Compositions and Coating

50 The solution of the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition (resist composition) is obtained by precisely filtering the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition having the composition shown in table below through a membrane filter having a pore size of 0.05 μm .

55 The solution of the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition is applied on a 6-inch Si wafer having been subjected to hexamethyldisilazane (HMDS) treatment in advance with a spin coater Mark 8 (manufactured by Tokyo Electron Limited), dried on a hot plate at 100° C. for 60 seconds, and a resist film having a thickness of 50 nm is obtained.

(5) EUV Exposure and Development

65 Pattern irradiation is performed on the wafer coated with the resist film obtained in the above (4) with an EUV exposure apparatus (Micro Exposure Tool, NA 0.3, Quadrupole, outer

sigma 0.68, inner sigma 0.36, manufactured by Exitech) through an exposure mask (line/space: 1/1). After irradiation, the wafer is heated at 110° C. for 60 seconds on a hot plate. After that, the wafer is puddled with the organic developer shown in the following table and developed for 30 seconds, and then rinsed by using the rinsing solution shown in the table below. Subsequently, the wafer is revolved at 4,000 rpm for 30 seconds and then heated at 90° C. for 60 seconds, to thereby obtain a resist pattern of line and space pattern of 1/1 having a line width of 50 nm.

Comparative Examples 105 and 106

Extreme Ultraviolet Radiation (EUV) Exposure

An electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition is prepared and a pattern is formed in the same manner as in Example 101 except that the constitution is changed as shown in the table below, and development is performed with an alkali aqueous solution (TMAH, a 2.38% by mass tetramethyammonium hydroxide aqueous solution) in place of the organic developer and water is used as the rinsing solution.

(6) Evaluation of Resist Pattern

Sensitivity, resolution and LWR of the obtained resist pattern are evaluated with a scanning electron microscope (S-9380II, manufactured by Hitachi Limited) by the following methods. The results obtained are shown in the table below.

(6-1) Sensitivity

Energy of irradiation at the time of resolving a 1/1 line and space pattern having a line width of 50 nm is taken as sensitivity (Eop). The smaller the value, the better is the performance.

(6-2) Resolution

In the above Eop, the smallest line width of the separated 1/1 line and space pattern is taken as resolution. The smaller the value, the better is the performance.

(6-3) Line Width Roughness (LWR)

Concerning line width roughness, in the above Eop, line width is measured at arbitrary 50 points of 0.5 μm in the longitudinal direction of a line and space pattern having a line width of 50 nm and standard deviation is obtained, from which 3 σ is computed. The smaller the value, the better is the performance.

TABLE 2

EUV Exposure										
Example No.	Resin (A)	Acid Generator (B)	Solvent (mass ratio) (40 g)	Basic Compound	Surfactant (5 mg)	Developer (mass ratio)	Rinsing Solution	Sensitivity (mJ/cm ²)	Resolution (nm)	LWR (nm)
Example 101	A1-1-1 (0.679 g)	z45 (0.310 g)	S-1/S-2 (80/20)	D-3 (6 mg)	W-1	S-5	S-8	3.9	25.5	5.7
Example 102	A1-1-2 (0.679 g)	z45 (0.310 g)	S-1/S-2 (80/20)	D-3 (6 mg)	W-1	S-5	S-8	3.8	24.5	5.4
Example 103	A1-2 (0.685 g)	z117 (0.310 g)	S-1	D-1 (5 mg)	Nothing	S-5	S-8	3.7	24.0	5.3
Example 104	A1-3 (0.737 g)	z119 (0.250 g)	S-1/S-2 (40/60)	D-1 (8 mg)	W-2	S-5	S-10	3.9	24.5	5.5
Example 105	A1-4 (0.780 g)	z120 (0.210 g)	S-1	D-4 (5 mg)	W-3	S-5	S-12	3.8	25.0	5.5
Example 106	A1-5 (0.781 g)	z114 (0.210 g)	S-1/S-2 (80/20)	D-3 (4 mg)	W-1	S-5	S-8	3.7	24.0	5.3
Example 107	A1-5 (0.681 g)	z114 (0.310 g)	S-1/S-2 (80/20)	D-3 (4 mg)	W-1	S-5	S-8	3.5	23.0	4.9
Example 108	A1-5 (0.591 g)	z114 (0.400 g)	S-1/S-2 (80/20)	D-3 (4 mg)	W-1	S-5	S-8	3.3	22.5	4.5
Example 109	A1-5 (0.491 g)	z114 (0.500 g)	S-1/S-2 (80/20)	D-3 (4 mg)	W-1	S-5	S-8	3.2	22.5	4.3
Example 110	A1-6 (0.592 g)	z115 (0.400 g)	S-1/S-4 (80/20)	D-1 (3 mg)	W-4	S-7	S-9	3.2	22.0	4.2
Example 111	A1-7 (0.583 g)	z69 (0.310 g)	S-3	D-1 (2 mg)	W-2	S-5/S-6 (80/20)	S-11	3.3	22.0	4.2
Example 112	A1-8 (0.590 g)	z116 (0.300 g)	S-1	D-3 (5 mg)	W-1	S-13	S-10	3.3	22.5	4.3
Example 113	A1-9 (0.743 g)	z115 (0.100 g)	S-1	D-3 (5 mg)	W-1	S-13	S-10	3.3	22.5	4.3
Example 113	A1-9 (0.743 g)	z18 (0.250 g)	S-1/S-2 (70/30)	D-4 (2 mg)	W-2	S-14	S-8	3.4	22.0	4.1
Example 114	A1-10 (0.782 g)	z108 (0.210 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	3.9	25.0	5.4
Example 115	A1-10 (0.682 g)	z108 (0.310 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	3.6	24.0	5.0
Example 116	A1-10 (0.592 g)	z108 (0.400 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	3.4	23.5	4.6
Example 117	A1-10 (0.392 g)	z108 (0.600 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	3.3	24.0	4.5
Example 118	A1-11 (0.679 g)	z45 (0.310 g)	S-1	D-2 (6 mg)	W-3	S-6	S-12	3.5	23.0	4.3
Example 119	A1-12 (0.642 g)	z45 (0.350 g)	S-1/S-4 (80/20)	D-1 (3 mg)	W-4	S-5	S-8	3.5	23.0	4.0
Example 120	A1-13 (0.745 g)	z39 (0.250 g)	S-1/S-4 (70/30)	D-3 (5 mg)	Nothing	S-5	S-11	3.8	23.5	4.2

TABLE 2-continued

EUV Exposure										
Example No.	Resin (A)	Acid Generator (B)	Solvent (mass ratio) (40 g)	Basic Compound	Surfactant (5 mg)	Developer (mass ratio)	Rinsing Solution	Sensitivity (mJ/cm ²)	Resolution (nm)	LWR (nm)
Example 121	A1-14 (0.639 g)	z19 (0.350 g)	S-1	D-4 (6 mg)	W-2	S-6	S-10	3.9	24.0	4.2
Example 122	A1-15 (0.681 g)	z2 (0.310 g)	S-1	D-3 (4 mg)	W-1	S-7	S-8	3.8	24.0	4.3
Example 123	A2-1 (0.733 g)	z4 (0.150 g)	S-1	D-1 (12 mg)	W-1	S-5	S-8	1.7	26.0	5.8
Example 124	A2-2 (0.670 g)	z10 (0.100 g)	S-1	D-1 (20 mg)	Nothing	S-7	S-10	1.9	25.5	5.6
Example 125	A2-3 (0.775 g)	z99 (0.310 g)	S-1	D-1 (10 mg)	W-1	S-5	S-8	2.5	26.0	5.5
Example 126	A2-3 (0.675 g)	z118 (0.310 g)	S-1/S-2 (80/20)	D-1 (10 mg)	W-1	S-5	S-8	2.3	25.0	5.1
Example 127	A2-3 (0.585 g)	z118 (0.400 g)	S-1/S-2 (80/20)	D-1 (10 mg)	W-1	S-5	S-8	1.9	25.0	4.9
Example 128	A2-4 (0.677 g)	z113 (0.310 g)	S-1	D-2 (8 mg)	W-4	S-6	S-10	1.7	25.5	5.6
Example 129	A1-16 (0.682 g)	z123 (0.310 g)	S-1/S-2 (80/20)	D-8 (3 mg)	W-1	S-5	S-8	3.6	23.0	4.4
Example 130	A1-17 (0.681 g)	z121 (0.310 g)	S-1/S-2 (80/20)	D-7 (4 mg)	W-1	S-5	S-8	3.7	24.0	4.5
Example 131	A1-18 (0.731 g)	z117 (0.260 g)	S-1/S-2 (60/40)	D-5 (4 mg)	W-2	S-5	S-10	4.0	25.0	5.0
Example 132	A1-19 (0.681 g)	z122 (0.310 g)	S-1	D-6 (5 mg)	W-3	S-6	S-8	4.0	26.0	4.9
Example 133	A1-20 (0.581 g)	z112 (0.410 g)	S-1/S-2 (80/20)	D-9 (4 mg)	W-4	S-5	S-8	3.8	25.0	4.7
Example 134	A1-21 (0.682 g)	z126 (0.310 g)	S-3	D-8 (3 mg)	W-1	S-7	S-12	3.9	26.0	5.0
Comparative Example 101	A1-10 (0.892 g)	z108 (0.100 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	4.7	26.0	6.2
Comparative Example 102	A1-10 (0.842 g)	z108 (0.150 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	S-5	S-8	4.5	25.5	5.9
Comparative Example 103	A1-12 (0.892 g)	z45 (0.100 g)	S-1/S-4 (80/20)	D-1 (3 mg)	W-4	S-5	S-8	4.4	24.0	5.0
Comparative Example 104	A2-3 (0.885 g)	z118 (0.100 g)	S-1/S-2 (80/20)	D-1 (10 mg)	W-1	S-5	S-8	2.9	27.0	6.1
Comparative Example 105	A1-5 (0.591 g)	z114 (0.400 g)	S-1/S-2 (80/20)	D-3 (4 mg)	W-1	TMAH (positive development)	Water	23.5	45.0	6.5
Comparative Example 106	A1-10 (0.592 g)	z108 (0.400 g)	S-1/S-2 (60/40)	D-3 (3 mg)	W-1	TMAH (positive development)	Water	25.2	46.0	6.5

As can be seen from the above tables, Examples 101 to 134 can satisfy high sensitivity, high resolution, and high line width roughness (LWR) performance at the same time in on an extremely high level.

In particular, as can be seen from the comparison of Examples 108, 116 and Comparative Examples 105, 106, wherein positive development is performed with the same resist composition as in Examples 108, 116 and by alkali developer, by using the pattern forming method of the invention with the organic developer, patterns of high resolution, high sensitivity and high LWR can be formed also in EUV exposure. As described above, this is presumed for the reason that capillary force applied to the side wall of the pattern is reduced when the organic developer is used, as compared with the case of using an alkali developer, and so pattern collapse can be prevented.

Further, Comparative Examples 101 to 104 where the content of the acid generator is less than 21% by mass to all the solid contents of the composition cannot reach the level of the examples of the invention concerning sensitivity and LWR. This is probably for the reason that Comparative Examples 1 to 4 are low in the amounts of the acid generators, and so the

generated acids are too poor to satisfy high level where the examples of the invention can achieve.

Further, as can be understood from the results of evaluations of Examples 111 and 113, when the resin contains the repeating unit having a plurality of aromatic rings, resolution and LWR performance are more excellent. This is thought for the reason that the aromatic rings absorb out-of-band light (leaking light occurring in the ultraviolet region), and the evil due to out-of-band light (surface pattern chapping and the like) is prevented furthermore.

Incidentally, in the case where a rinsing step is not carried out, excellent effects similar to those in the above examples can be obtained.

INDUSTRIAL APPLICABILITY

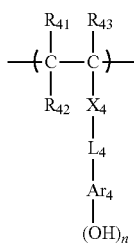
According to the invention, a pattern-forming method capable of satisfying high sensitivity, high resolution (high resolving power, etc.), and high line width roughness (LWR) performance on an extremely higher order at the same time; an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition; a resist film; a manufacturing method of an electronic device using them; and an electronic device can be provided.

201

This application is based on Japanese patent application No. JP 2011-202044 filed on Sep. 15, 2011 and U.S. Provisional Application No. 61/535,024 filed on Sep. 15, 2011, the entire contents of which are hereby incorporated by reference, the same as if set forth at length.

The invention claimed is:

1. A pattern-forming method, comprising in this order:
 - step (1) of forming a film with an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition that contains (A) a resin having an acid-decomposable repeating unit and capable of decreasing a solubility of the resin (A) in a developer containing an organic solvent by an action of an acid, (B) a compound capable of generating an acid upon irradiation with an electron beam or extreme ultraviolet radiation and (C) a solvent;
 - step (2) of exposing the film with an electron beam or extreme ultraviolet radiation; and
 - step (3) of forming a negative pattern by development of the film with a developer containing an organic solvent after the exposing of the film,
 wherein a content of the compound (B) is 21% by mass to 70% by mass on the basis of all solids content of the composition, and
 wherein a content of a repeating unit represented by the following formula (I) to all repeating units in the resin (A) is 4 mol % or less:



wherein each of R_{41} , R_{42} and R_{43} independently represents a hydrogen atom, an alkyl group, a halogen atom, a cyano group or an alkoxy carbonyl group, and R_{42} may be bonded to Ar_4 to form a ring, and in this case, R_{42} represents a single bond or an alkylene group;
 X_4 represents a single bond, ---COO--- or $\text{---CONR}_{64}\text{---}$, and R_{64} represents a hydrogen atom or an alkyl group;
 L_4 represents a single bond or an alkylene group;
 Ar_4 represents an (n+1)-valent aromatic ring group, and when Ar_4 forms a ring together with R_{42} , Ar_4 represents an (n+2)-valent aromatic ring group; and
 n represents an integer of 1 to 4.

2. The pattern-forming method according to claim 1, wherein the content of the compound (B) is 31% by mass to 60% by mass on the basis of all solids content of the composition.
3. The pattern-forming method according to claim 1, wherein the resin (A) further has a repeating unit having a polar group.
4. The pattern-forming method according to claim 3, wherein the polar group is selected from the group consisting of a hydroxyl group, a cyano group, a lactone group, a carboxylic acid group, a sulfonic acid group, an amido group, a sulfonamido group, an ammonium group, a sulfonium group and a group obtained by combining two or more of the above groups.

202

5. The pattern-forming method according to claim 1, wherein the resin (A) further has a repeating unit having an acid group.

6. The pattern-forming method according to claim 5, wherein the acid group is a phenolic hydroxyl group, a carboxylic acid group, a sulfonic acid group, a fluorinated alcohol group, a sulfonamido group, a sulfonylimido group, an (alkylsulfonyl)(alkylcarbonyl)methylene group, an (alkylsulfonyl)(alkylcarbonyl)imido group, a bis(alkylcarbonyl)methylene group, a bis(alkylcarbonyl)imido group, a bis(alkylsulfonyl)methylene group, a bis(alkylsulfonyl)imido group, a tris(alkylcarbonyl)methylene group or a tris(alkylsulfonyl)methylene group.

7. The pattern-forming method according to claim 1, which is a method for forming a semiconductor fine circuit.

8. An electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition, which is used for the pattern-forming method according to claim 1.

9. A resist film, which is formed with the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition according to claim 8.

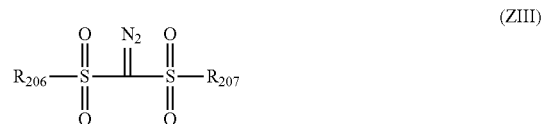
10. A manufacturing method of an electronic device, comprising:

the pattern-forming method according to claim 1.

11. An electronic device, which is manufactured by the manufacturing method of an electronic device according to claim 10.

12. The pattern-forming method according to claim 1, further comprising, between steps (2) and (3), a step of baking the exposed film.

13. The pattern-forming method according to claim 1, wherein the compound (B) is a compound selected from the following formulae (ZI) to (ZIII):



wherein, in formula (ZI) each of R_{201} , R_{202} and R_{203} independently represents an organic group, in formulae (ZII) and (ZIII) each of R_{204} to R_{207} independently represents an aryl group, an alkyl group or a cycloalkyl group, Z^- represents a non-nucleophilic group, and two of R_{201} , R_{202} and R_{203} are not bonded to form a cyclic structure.

14. A pattern-forming method, comprising in this order:
 - step (1) of forming a film with an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition that contains (A) a resin having an acid-decomposable repeating unit and capable of decreasing a solubility of the resin (A) in a developer containing an organic solvent by an action of an acid, (B) a compound capable of generating an acid upon irradiation with an electron beam or extreme ultraviolet radiation and (C) a solvent;
 - step (2) of exposing the film with an electron beam or extreme ultraviolet radiation; and

203

step (3) of forming a negative pattern by development of the film with a developer containing an organic solvent after the exposing of the film,

wherein a content of the compound (B) is 31% by mass to 60% by mass on the basis of all solids content of the composition.

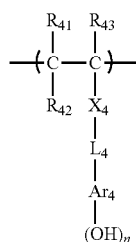
15. The pattern-forming method according to claim 14, wherein the resin (A) further has a repeating unit having a polar group.

16. The pattern-forming method according to claim 15, wherein the polar group is selected from the group consisting of a hydroxyl group, a cyano group, a lactone group, a carboxylic acid group, a sulfonic acid group, an amido group, a sulfonamido group, an ammonium group, a sulfonium group and a group obtained by combining two or more of the above groups.

17. The pattern-forming method according to claim 14, wherein the resin (A) further has a repeating unit having an acid group.

18. The pattern-forming method according to claim 17, wherein the acid group is a phenolic hydroxyl group, a carboxylic acid group, a sulfonic acid group, a fluorinated alcohol group, a sulfonamido group, a sulfonylimido group, an (alkylsulfonyl)(alkylcarbonyl)methylene group, an (alkylsulfonyl)(alkylcarbonyl)imido group, a bis(alkylcarbonyl)methylene group, a bis(alkylcarbonyl)imido group, a bis(alkylsulfonyl)methylene group, a bis(alkylsulfonyl)imido group, a tris-(alkylcarbonyl)methylene group or a tris(alkylsulfonyl)methylene group.

19. The pattern-forming method according to claim 14, wherein a content of a repeating unit represented by the following formula (I) to all repeating units in the resin (A) is 4 mol % or less:



wherein each of R_{41} , R_{42} and R_{43} independently represents a hydrogen atom, an alkyl group, a halogen atom, a cyano group or an alkoxy carbonyl group, and R_{42} may be bonded to Ar_4 to form a ring, and in this case, R_{42} represents a single bond or an alkylene group;

X_4 represents a single bond, $-COO-$ or $-CONR_{64}-$, and R_{64} represents a hydrogen atom or an alkyl group;

L_4 represents a single bond or an alkylene group;

Ar_4 represents an (n+1)-valent aromatic ring group, and when Ar_4 forms a ring together with R_{42} , Ar_4 represents an (n+2)-valent aromatic ring group; and n represents an integer of 1 to 4.

20. The pattern-forming method according to claim 14, which is a method for forming a semiconductor fine circuit.

21. An electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition, which is used for the pattern-forming method according to claim 14.

22. A resist film, which is formed with the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition according to claim 21.

204

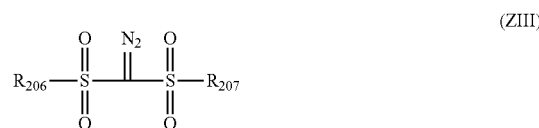
23. A manufacturing method of an electronic device, comprising:

the pattern-forming method according to claim 14.

24. An electronic device, which is manufactured by the manufacturing method of an electronic device according to claim 23.

25. The pattern-forming method according to claim 14, further comprising, between steps (2) and (3), a step of baking the exposed film.

26. The pattern-forming method according to claim 14, wherein the compound (B) is a compound selected from the following formulae (ZI) to (ZIII):



wherein, in formula (ZI) each of R_{201} , R_{202} and R_{203} independently represents an organic group, in formulae (ZII) and (ZIII) each of R_{204} to R_{207} independently represents an aryl group, an alkyl group or a cycloalkyl group, Z^- represents a non-nucleophilic group, and two of R_{201} , R_{202} and R_{203} are not bonded to form a cyclic structure.

27. A pattern-forming method, comprising in this order:

step (1) of forming a film with an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition that contains (A) a resin having an acid-decomposable repeating unit and capable of decreasing a solubility of the resin (A) in a developer containing an organic solvent by an action of an acid, (B) a compound capable of generating an acid upon irradiation with an electron beam or extreme ultraviolet radiation and (C) a solvent;

step (2) of exposing the film with an electron beam or extreme ultraviolet radiation; and

step (3) of forming a negative pattern by development of the film with a developer containing an organic solvent after the exposing of the film,

wherein a content of the compound (B) is 21% by mass to 70% by mass on the basis of all solids content of the composition, and

wherein resin (A) contains a repeating group represented by formula (I):



205

wherein each of R_{41} , R_{42} and R_{43} independently represents a hydrogen atom, an alkyl group, a halogen atom, a cyano group or an alkoxy carbonyl group, and R_{42} may be bonded to Ar_4 to form a ring, and in this case, R_{42} represents a single bond or an alkylene group;

X_4 represents $-COO-$ or $-CONR_{64}-$, and R_{64} represents a hydrogen atom or an alkyl group;

L_4 represents a single bond or an alkylene group;

Ar_4 represents an $(n+1)$ -valent aromatic ring group, and when Ar_4 forms a ring together with R_{42} , Ar_4 represents an $(n+2)$ -valent aromatic ring group; and n represents an integer of 1 to 4.

28. The pattern-forming method according to claim 27, wherein the content of the compound (B) is 31% by mass to 60% by mass on the basis of all solids content of the composition.

29. The pattern-forming method according to claim 27, wherein the resin (A) further has a repeating unit having a polar group.

30. The pattern-forming method according to claim 29, wherein the polar group is selected from the group consisting of a hydroxyl group, a cyano group, a lactone group, a carboxylic acid group, a sulfonic acid group, an amido group, a sulfonamido group, an ammonium group, a sulfonium group and a group obtained by combining two or more of the above groups.

31. The pattern-forming method according to claim 27, wherein the resin (A) further has a repeating unit having an acid group.

32. The pattern-forming method according to claim 28, wherein the acid group is a phenolic hydroxyl group, a carboxylic acid group, a sulfonic acid group, a fluorinated alcohol group, a sulfonamido group, a sulfonylimido group, an (alkylsulfonyl)(alkylcarbonyl)methylene group, an (alkylsulfonyl)(alkylcarbonyl)imido group, a bis(alkylcarbonyl)methylene group, a bis(alkylcarbonyl)imido group, a bis(alkylsulfonyl)methylene group, a bis(alkylsulfonyl)imido group, a tris(alkylcarbonyl)methylene group or a tris(alkylsulfonyl)methylene group.

33. The pattern-forming method according to claim 27, which is a method for forming a semiconductor fine circuit.

34. An electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition, which is used for the pattern-forming method according to claim 27.

35. A resist film, which is formed with the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition according to claim 34.

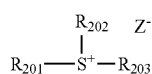
36. A manufacturing method of an electronic device, comprising:

the pattern-forming method according to claim 27.

37. An electronic device, which is manufactured by the manufacturing method of an electronic device according to claim 36.

38. The pattern-forming method according to claim 27, further comprising, between steps (2) and (3), a step of baking the exposed film.

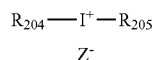
39. The pattern-forming method according to claim 27, wherein the compound (B) is a compound selected from the following formulae (ZI) to (ZIII):



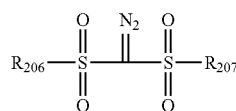
(ZI)

206

-continued



(ZII)



(ZIII)

wherein, in formula (ZI) each of R_{201} , R_{202} and R_{203} independently represents an organic group, in formulae (ZII) and (ZIII) each of R_{204} to R_{207} independently represents an aryl group, an alkyl group or a cycloalkyl group, Z^- represents a non-nucleophilic group, and two of R_{201} , R_{202} and R_{203} are not bonded to form a cyclic structure.

40. The pattern-forming method according to claim 27, wherein a content of a repeating unit represented by the following formula (I) to all repeating units in the resin (A) is 4 mol % or less.

41. A pattern-forming method, comprising in this order:

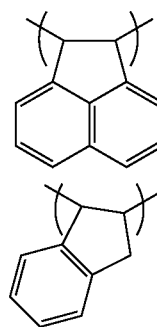
step (1) of forming a film with an electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition that contains (A) a resin having an acid-decomposable repeating unit and capable of decreasing a solubility of the resin (A) in a developer containing an organic solvent by an action of an acid, (B) a compound capable of generating an acid upon irradiation with an electron beam or extreme ultraviolet radiation and (C) a solvent;

step (2) of exposing the film with an electron beam or extreme ultraviolet radiation; and

step (3) of forming a negative pattern by development of the film with a developer containing an organic solvent after the exposing of the film,

wherein a content of the compound (B) is 21% by mass to 70% by mass on the basis of all solids content of the composition, and

wherein the resin (A) contains at least one of the following repeating units:



42. The pattern-forming method according to claim 41, wherein the content of the compound (B) is 31% by mass to 60% by mass on the basis of all solids content of the composition.

43. The pattern-forming method according to claim 41, wherein the resin (A) further has a repeating unit having a polar group.

44. The pattern-forming method according to claim 43, wherein the polar group is selected from the group consisting of a hydroxyl group, a cyano group, a lactone group,

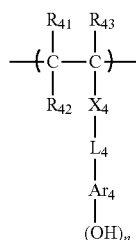
207

a carboxylic acid group, a sulfonic acid group, an amido group, a sulfonamido group, an ammonium group, a sulfonium group and a group obtained by combining two or more of the above groups.

45. The pattern-forming method according to claim 41, wherein the resin (A) further has a repeating unit having an acid group.

46. The pattern-forming method according to claim 45, wherein the acid group is a phenolic hydroxyl group, a carboxylic acid group, a sulfonic acid group, a fluorinated alcohol group, a sulfonamido group, a sulfonylimido group, an (alkylsulfonyl)(alkylcarbonyl)methylene group, an (alkylsulfonyl)(alkylcarbonyl)imido group, a bis(alkylcarbonyl)methylene group, a bis(alkylcarbonyl)imido group, a bis(alkylsulfonyl)methylene group, a bis(alkylsulfonyl)imido group, a tris-(alkylcarbonyl)methylene group or a tris(alkylsulfonyl)methylene group.

47. The pattern-forming method according to claim 41, wherein a content of a repeating unit represented by the following formula (I) to all repeating units in the resin (A) is 4 mol % or less:



wherein each of R_{41} , R_{42} and R_{43} independently represents a hydrogen atom, an alkyl group, a halogen atom, a cyano group or an alkoxy carbonyl group, and R_{42} may be bonded to Ar_4 to form a ring, and in this case, R_{42} represents a single bond or an alkylene group;

X_4 represents a single bond, ---COO--- or $\text{---CONR}_{64}\text{---}$, and R_{64} represents a hydrogen atom or an alkyl group;

L_4 represents a single bond or an alkylene group;

Ar_4 represents an (n+1)-valent aromatic ring group, and when Ar_4 forms a ring together with R_{42} , Ar_4 represents an (n+2)-valent aromatic ring group; and

n represents an integer of 1 to 4.

(I) 25

30

35

40

45

208

48. The pattern-forming method according to claim 41, which is a method for forming a semiconductor fine circuit.

49. An electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition, which is used for the pattern-forming method according to claim 41.

50. A resist film, which is formed with the electron beam-sensitive or extreme ultraviolet radiation-sensitive resin composition according to claim 49.

51. A manufacturing method of an electronic device, comprising:

the pattern-forming method according to claim 41.

52. An electronic device, which is manufactured by the manufacturing method of an electronic device according to claim 51.

53. The pattern-forming method according to claim 41, further comprising, between steps (2) and (3), a step of baking the exposed film.

54. The pattern-forming method according to claim 41, wherein the compound (B) is a compound selected from the following formulae (ZI) to (ZIII):



wherein, in formula (ZI) each of R_{201} , R_{202} and R_{203} independently represents an organic group, in formulae (ZII) and (ZIII) each of R_{204} to R_{207} independently represents an aryl group, an alkyl group or a cycloalkyl group, Z^- represents a non-nucleophilic group, and two of R_{201} , R_{202} and R_{203} are not bonded to form a cyclic structure.

* * * * *